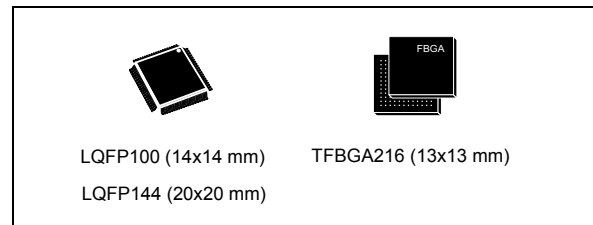


## Arm<sup>®</sup>-based Cortex<sup>®</sup>-M7 32b MCU+FPU, 462DMIPS, 64KB Flash/ 320+16+ 4KB RAM, USB OTG HS/FS, 25 com IF, cam, LCD

Datasheet - production data

### Features

- Core: Arm<sup>®</sup> 32-bit Cortex<sup>®</sup>-M7 CPU with FPU, adaptive real-time accelerator (ART Accelerator™) and L1-cache: 4-Kbyte data cache and 4-Kbyte instruction cache, allowing 0-wait state execution from embedded Flash memory and external memories, frequency up to 216 MHz, MPU, 462 DMIPS/2.14 DMIPS/MHz (Dhrystone 2.1), and DSP instructions.
- Memories
  - 64 Kbytes of Flash memory
  - 1024 bytes of OTP memory
  - SRAM: 320 Kbytes (including 64 Kbytes of data TCM RAM for critical real-time data) + 16 Kbytes of instruction TCM RAM (for critical real-time routines) + 4 Kbytes of backup SRAM (available in the lowest power modes)
  - Flexible external memory controller with up to 32-bit data bus: SRAM, PSRAM, SDRAM/LPSSDR SDRAM, NOR/NAND memories
- Dual mode Quad-SPI
- LCD parallel interface, 8080/6800 modes
- LCD-TFT controller up to XGA resolution with dedicated Chrom-ART Accelerator™ for enhanced graphic content creation (DMA2D)
- Clock, reset and supply management
  - 1.7 V to 3.6 V application supply and I/Os
  - POR, PDR, PVD and BOR
  - Dedicated USB power
  - 4-to-26 MHz crystal oscillator
  - Internal 16 MHz factory-trimmed RC (1% accuracy)
  - 32 kHz oscillator for RTC with calibration
  - Internal 32 kHz RC with calibration
- Low-power
  - Sleep, Stop and Standby modes



- V<sub>BAT</sub> supply for RTC, 32×32-bit backup registers + 4 Kbytes of backup SRAM
- 3×12-bit, 2.4 MSPS ADC: up to 24 channels and 7.2 MSPS in triple interleaved mode
- 2×12-bit D/A converters
- Up to 18 timers: up to thirteen 16-bit (1x low-power 16-bit timer available in Stop mode) and two 32-bit timers, each with up to 4 IC/OC/PWM or pulse counter and quadrature (incremental) encoder input. All 15 timers running up to 216 MHz. 2x watchdogs, SysTick timer
- General-purpose DMA: 16-stream DMA controller with FIFOs and burst support
- Debug mode
  - SWD & JTAG interfaces
  - Cortex<sup>®</sup>-M7 Trace Macrocell™
- Up to 168 I/O ports with interrupt capability
  - Up to 164 fast I/Os up to 108 MHz
  - Up to 166 5 V-tolerant I/Os
- Up to 25 communication interfaces
  - Up to 4× I<sup>2</sup>C interfaces (SMBus/PMBus)
  - Up to 4 USARTs/4 UARTs (27 Mbit/s, ISO7816 interface, LIN, IrDA, modem control)
  - Up to 6 SPIs (up to 50 Mbit/s), 3 with muxed simplex I<sup>2</sup>S for audio class accuracy via internal audio PLL or external clock
  - 2 x SAs (serial audio interface)
  - 2 × CANs (2.0B active) and SDMMC interface

- SPDIFRX interface
- HDMI-CEC
- Advanced connectivity
  - USB 2.0 full-speed device/host/OTG controller with on-chip PHY
  - USB 2.0 high-speed/full-speed device/host/OTG controller with dedicated DMA, on-chip full-speed PHY and ULPI
  - 10/100 Ethernet MAC with dedicated DMA: supports IEEE 1588v2 hardware, MII/RMII
- 8- to 14-bit parallel camera interface up to 54 Mbyte/s
- Cryptographic acceleration: hardware acceleration for AES 128, 192, 256, triple DES, HASH (MD5, SHA-1, SHA-2), and HMAC
- True random number generator
- CRC calculation unit
- RTC: subsecond accuracy, hardware calendar
- 96-bit unique ID

**Table 1. Device summary**

Reference	Part number
STM32F750x8	STM32F750V8, STM32F750Z8, STM32F750N8

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# 1 Introduction

This datasheet provides the ordering information and mechanical device characteristics of the STM32F750x8 microcontrollers.

This document should be read in conjunction with the *STM32F75xxx and STM32F74xxx advanced Arm<sup>®</sup>-based 32-bit MCUs* reference manual (RM0385). The reference manual is available from the STMicroelectronics website [www.st.com](http://www.st.com).

For information on the Arm<sup>®(a)</sup> Cortex<sup>®</sup>-M7 core, refer to the Cortex<sup>®</sup>-M7 technical reference manual available from the <http://www.arm.com> website.



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## 2 Description

The STM32F750x8 devices are based on the high-performance Arm® Cortex®-M7 32-bit RISC core operating at up to 216 MHz frequency. The Cortex®-M7 core features a single floating point unit (SFPU) precision which supports all Arm® single-precision data-processing instructions and data types. It also implements a full set of DSP instructions and a memory protection unit (MPU) which enhances the application security.

The STM32F750x8 devices incorporate high-speed embedded memories with a Flash memory of 64 Kbytes, 320 Kbytes of SRAM (including 64 Kbytes of Data TCM RAM for critical real-time data), 16 Kbytes of instruction TCM RAM (for critical real-time routines), 4 Kbytes of backup SRAM available in the lowest power modes, and an extensive range of enhanced I/Os and peripherals connected to two APB buses, two AHB buses, a 32-bit multi-AHB bus matrix and a multi layer AXI interconnect supporting internal and external memories access.

All the devices offer three 12-bit ADCs, two DACs, a low-power RTC, thirteen general-purpose 16-bit timers including two PWM timers for motor control and one low-power timer available in Stop mode, two general-purpose 32-bit timers, a true random number generator (RNG), and a cryptographic acceleration cell. They also feature standard and advanced communication interfaces.

- Up to four I<sup>2</sup>Cs
- Six SPIs, three I<sup>2</sup>Ss in duplex mode. To achieve the audio class accuracy, the I<sup>2</sup>S peripherals can be clocked via a dedicated internal audio PLL or via an external clock to allow synchronization.
- Four USARTs plus four UARTs
- An USB OTG full-speed and a USB OTG high-speed with full-speed capability (with the ULPI),
- Two CANs
- Two SAI serial audio interfaces
- An SDMMC host interface
- Ethernet and camera interfaces
- LCD-TFT display controller
- Chrom-ART Accelerator™
- SPDIFRX interface
- HDMI-CEC

Advanced peripherals include an SDMMC interface, a flexible memory control (FMC) interface, a Quad-SPI Flash memory interface, a camera interface for CMOS sensors and a cryptographic acceleration cell.

The STM32F750x8 devices operate in the –40 to +105 °C temperature range from a 1.7 to 3.6 V power supply. A dedicated supply input for USB (OTG\_FS and OTG\_HS) is available on all the packages except LQFP100 for a greater power supply choice.

The supply voltage can drop to 1.7 V with the use of an external power supply supervisor. A comprehensive set of power-saving mode allows the design of low-power applications.

The STM32F750x8 devices offer devices in 3 packages ranging from 100 pins to 216 pins. The set of included peripherals changes with the device chosen.

These features make the STM32F750x8 microcontrollers suitable for a wide range of applications.

- Motor drive and application control,
- Medical equipment,
- Industrial applications: PLC, inverters, circuit breakers,
- Printers, and scanners,
- Alarm systems, video intercom, and HVAC,
- Home audio appliances,
- Mobile applications, Internet of Things,
- Wearable devices: smartwatches.

**Table 2. STM32F750x8 features and peripheral counts**

Peripherals		STM32F750V8	STM32F750Z8	STM32F750N8
Flash memory in Kbytes		64		
SRAM in Kbytes	System	320(240+16+64)		
	Instruction	16		
	Backup	4		
FMC memory controller		Yes <sup>(1)</sup>		
Ethernet		Yes		
Timers	General-purpose	10		
	Advanced-control	2		
	Basic	2		
	Low-power	1		
Random number generator		Yes		
Communication interfaces	SPI / I <sup>2</sup> S	4/3 (simplex) <sup>(2)</sup>	6/3 (simplex) <sup>(2)</sup>	
	I <sup>2</sup> C	4		
	USART/UART	4/4		
	USB OTG FS	Yes		
	USB OTG HS	Yes		
	CAN	2		
	SAI	2		
	SPDIFRX	4 inputs		
	SDMMC	Yes		
Camera interface		Yes		
LCD-TFT		Yes		
Chrom-ART Accelerator™ (DMA2D)		Yes		
Cryptography		Yes		
GPIOs		82	114	168

Table 2. STM32F750x8 features and peripheral counts (continued)

Peripherals	STM32F750V8	STM32F750Z8	STM32F750N8
12-bit ADC	3		
Number of channels	16	24	
12-bit DAC	Yes		
Number of channels	2		
Maximum CPU frequency	216 MHz <sup>(3)</sup>		
Operating voltage	1.7 to 3.6 V <sup>(4)</sup>		
Operating temperatures	Ambient temperatures: -40 to +85 °C / -40 to +105 °C		
	Junction temperature: -40 to + 125 °C		
Package	LQFP100	LQFP144	TFBGA216

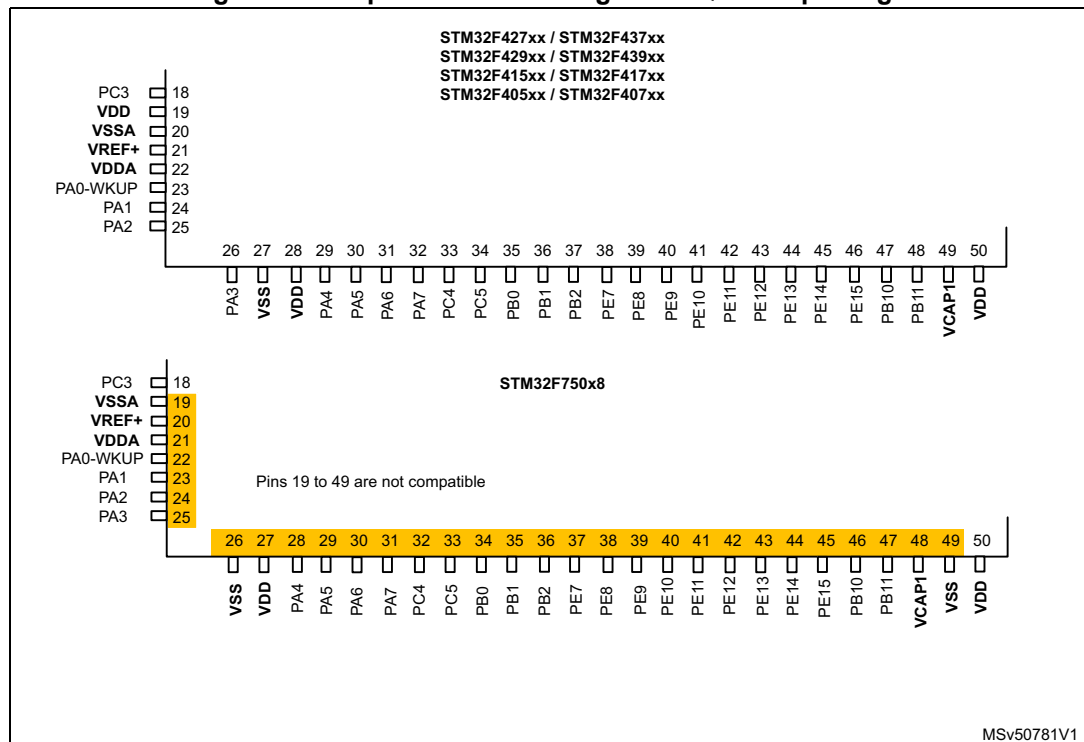
1. For the LQFP100 package, only FMC Bank1 is available. Bank1 can only support a multiplexed NOR/PSRAM memory using the NE1 Chip Select.
2. The SPI1, SPI2 and SPI3 interfaces give the flexibility to work in an exclusive way in either the SPI mode or the I2S audio mode.
3. 216 MHz maximum frequency for -40°C to + 85°C ambient temperature range (200 MHz maximum frequency for -40°C to + 105°C ambient temperature range).
4.  $V_{DD}/V_{DDA}$  minimum value of 1.7 V is obtained when the internal reset is OFF (refer to [Section 3.17.2: Internal reset OFF](#)).

## 2.1 Full compatibility throughout the family

The STM32F750x8 devices are fully pin-to-pin, compatible with the STM32F4xxxx devices, allowing the user to try different peripherals, and reaching higher performances (higher frequency) for a greater degree of freedom during the development cycle.

Figure 1 give compatible board designs between the STM32F4xx families.

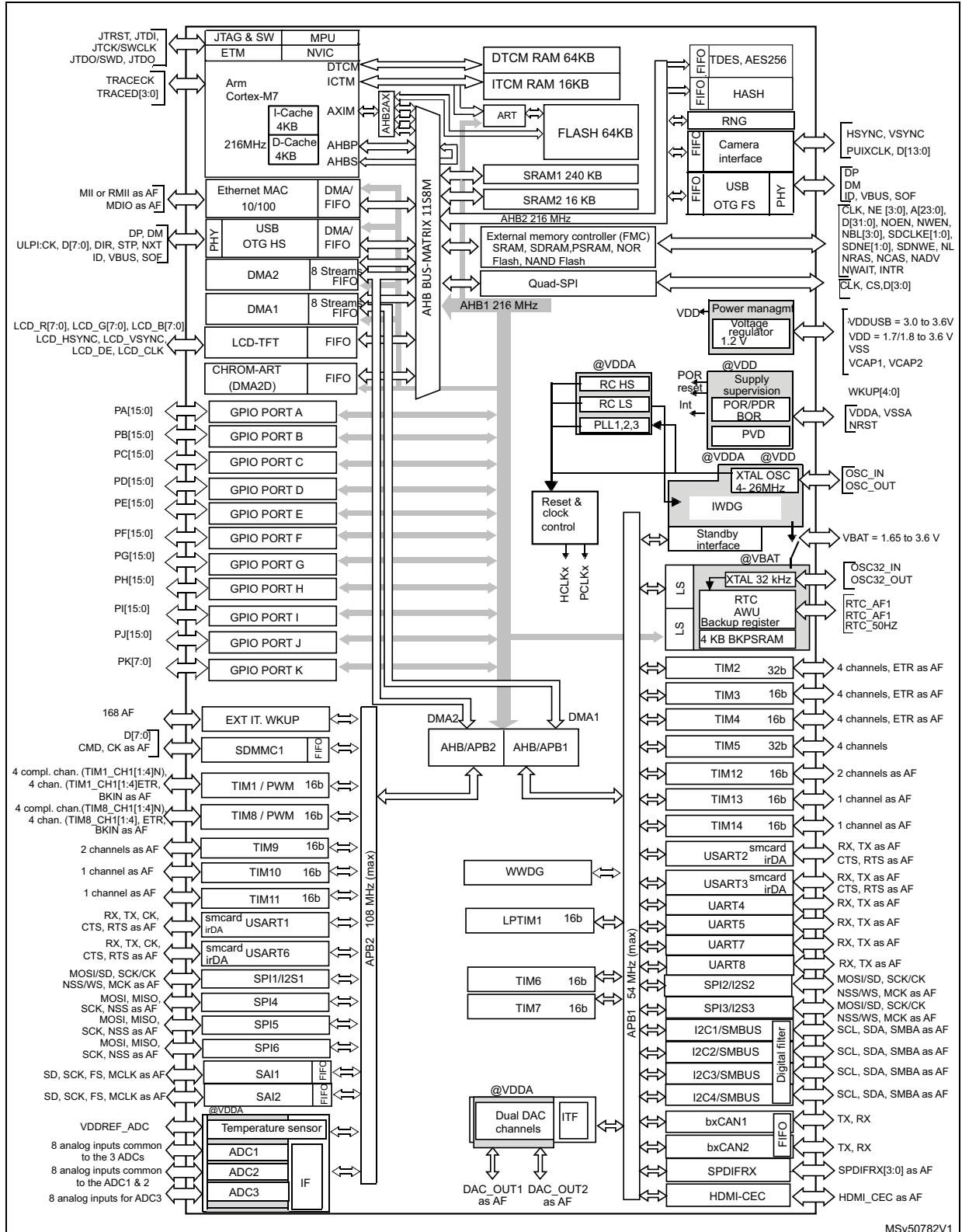
Figure 1. Compatible board design for LQFP100 package



The STM32F750x8 LQFP144 and TFBGA216 packages are fully pin to pin compatible with STM32F4xxxx devices.



Figure 2. STM32F750x8 block diagram



1. The timers connected to APB2 are clocked from TIMxCLK up to 216 MHz, while the timers connected to APB1 are clocked from TIMxCLK either up to 108 MHz or 216 MHz depending on TIMPRE bit configuration in the RCC\_DCKCFGR register.

## 3 Functional overview

### 3.1 Arm<sup>®</sup> Cortex<sup>®</sup>-M7 with FPU

The Arm<sup>®</sup> Cortex<sup>®</sup>-M7 with FPU processor is the latest generation of Arm processors for embedded systems. It was developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and a low-power consumption, while delivering an outstanding computational performance and low interrupt latency.

The Cortex<sup>®</sup>-M7 processor is a highly efficient high-performance featuring:

- Six-stage dual-issue pipeline
- Dynamic branch prediction
- Harvard caches (4 Kbytes of I-cache and 4 Kbytes of D-cache)
- 64-bit AXI4 interface
- 64-bit ITCM interface
- 2x32-bit DTCM interfaces

The processor supports the following memory interfaces:

- Tightly Coupled Memory (TCM) interface.
- Harvard instruction and data caches and AXI master (AXIM) interface.
- Dedicated low-latency AHB-Lite peripheral (AHBP) interface.

The processor supports a set of DSP instructions which allow efficient signal processing and complex algorithm execution.

Its single precision FPU (floating point unit) speeds up the software development by using metalanguage development tools, while avoiding saturation.

*Figure 2* shows the general block diagram of the STM32F750x8 devices.

*Note:* Cortex<sup>®</sup>-M7 with FPU core is binary compatible with the Cortex<sup>®</sup>-M4 core.

### 3.2 Memory protection unit

The memory protection unit (MPU) is used to manage the CPU accesses to memory to prevent one task to accidentally corrupt the memory or resources used by any other active task. This memory area is organized into up to 8 protected areas that can in turn be divided up into 8 subareas. The protection area sizes are between 32 bytes and the whole 4 gigabytes of addressable memory.

The MPU is especially helpful for applications where some critical or certified code has to be protected against the misbehavior of other tasks. It is usually managed by an RTOS (real-time operating system). If a program accesses a memory location that is prohibited by the MPU, the RTOS can detect it and take action. In an RTOS environment, the kernel can dynamically update the MPU area setting, based on the process to be executed.

The MPU is optional and can be bypassed for applications that do not need it.

### 3.3 Embedded Flash memory

The STM32F750x8 devices embed a Flash memory of 64 Kbytes available for storing programs and data.

### 3.4 CRC (cyclic redundancy check) calculation unit

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code using a configurable generator polynomial value and size.

Among other applications, CRC-based techniques are used to verify the data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a mean of verifying the Flash memory integrity. The CRC calculation unit helps to compute a signature of the software during runtime, to be compared with a reference signature generated at link-time and stored at a given memory location.

### 3.5 Embedded SRAM

All the devices features:

- System SRAM up to 320 Kbytes:
  - SRAM1 on AHB bus Matrix: 240 Kbytes
  - SRAM2 on AHB bus Matrix: 16 Kbytes
  - DTCM-RAM on TCM interface (Tightly Coupled Memory interface): 64 Kbytes for critical real-time data.
- Instruction RAM (ITCM-RAM) 16 Kbytes:
  - It is mapped on TCM interface and reserved only for CPU Execution/Instruction useful for critical real-time routines.

The Data TCM RAM is accessible by the GP-DMA's and peripherals DMA's through specific AHB slave of the CPU. The TCM RAM instruction is reserved only for CPU. It is accessed at CPU clock speed with 0-wait states.

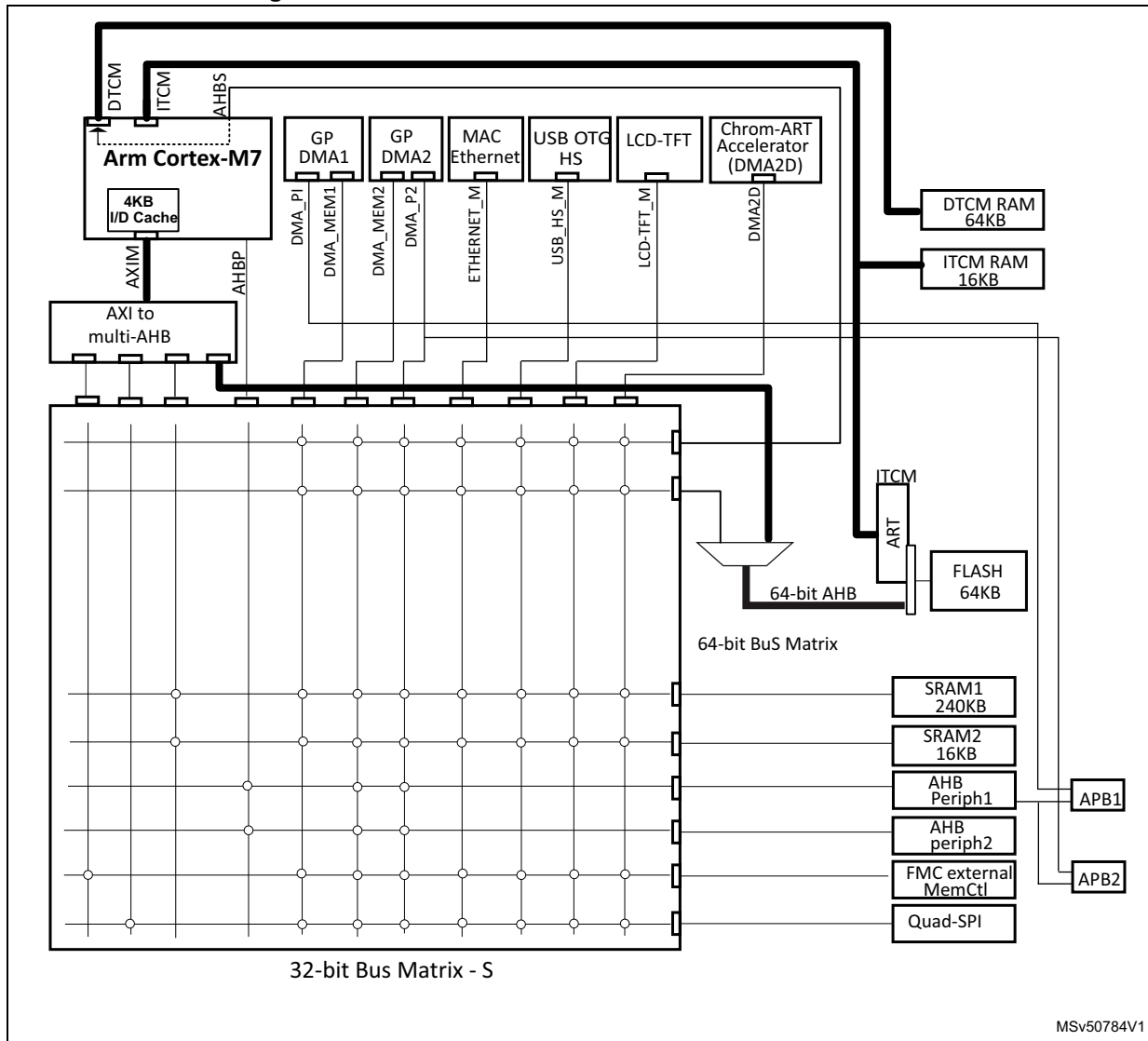
- 4 Kbytes of backup SRAM
  - This area is accessible only from the CPU. Its content is protected against possible unwanted write accesses, and is retained in Standby or VBAT mode.

### 3.6 AXI-AHB bus matrix

The STM32F750x8 system architecture is based on 2 sub-systems:

- An AXI to multi AHB bridge converting AXI4 protocol to AHB-Lite protocol:
  - 3x AXI to 32-bit AHB bridges connected to AHB bus matrix
  - 1x AXI to 64-bit AHB bridge connected to the embedded flash
- A multi-AHB Bus-Matrix:
  - The 32-bit multi-AHB bus matrix interconnects all the masters (CPU, DMA's, Ethernet, USB HS, LCD-TFT, and DMA2D) and the slaves (Flash memory, RAM, FMC, Quad-SPI, AHB and APB peripherals) and ensures a seamless and an efficient operation even when several high-speed peripherals work simultaneously.

Figure 3. STM32F750x8 AXI-AHB bus matrix architecture



1. The above figure has large wires for 64-bits bus and thin wires for 32-bits bus.

### 3.7 DMA controller (DMA)

The devices feature two general-purpose dual-port DMAs (DMA1 and DMA2) with 8 streams each. They are able to manage memory-to-memory, peripheral-to-memory and memory-to-peripheral transfers. They feature dedicated FIFOs for APB/AHB peripherals, support burst transfer and are designed to provide the maximum peripheral bandwidth (AHB/APB).

The two DMA controllers support circular buffer management, so that no specific code is needed when the controller reaches the end of the buffer. The two DMA controllers also have a double buffering feature, which automates the use and switching of two memory buffers without requiring any special code.

Each stream is connected to dedicated hardware DMA requests, with support for software trigger on each stream. Configuration is made by software and transfer sizes between source and destination are independent.

The DMA can be used with the main peripherals:

- SPI and I<sup>2</sup>S
- I<sup>2</sup>C
- USART
- General-purpose, basic and advanced-control timers TIMx
- DAC
- SDMMC
- Cryptographic acceleration
- Camera interface (DCMI)
- ADC
- SAI
- SPDIFRX
- Quad-SPI
- HDMI-CEC

### **3.8 Flexible memory controller (FMC)**

The Flexible memory controller (FMC) includes three memory controllers:

- The NOR/PSRAM memory controller
- The NAND/memory controller
- The Synchronous DRAM (SDRAM/Mobile LPDDR SDRAM) controller

The main features of the FMC controller are the following:

- Interface with static-memory mapped devices including:
  - Static random access memory (SRAM)
  - NOR Flash memory/OneNAND Flash memory
  - PSRAM (4 memory banks)
  - NAND Flash memory with ECC hardware to check up to 8 Kbytes of data
- Interface with synchronous DRAM (SDRAM/Mobile LPDDR SDRAM) memories
- 8-,16-,32-bit data bus width
- Independent Chip Select control for each memory bank
- Independent configuration for each memory bank
- Write FIFO
- Read FIFO for SDRAM controller
- The Maximum FMC\_CLK/FMC\_SDCLK frequency for synchronous accesses is HCLK/2.

#### **LCD parallel interface**

The FMC can be configured to interface seamlessly with most graphic LCD controllers. It supports the Intel 8080 and Motorola 6800 modes, and is flexible enough to adapt to

specific LCD interfaces. This LCD parallel interface capability makes it easy to build cost-effective graphic applications using LCD modules with embedded controllers or high performance solutions using external controllers with dedicated acceleration.

### 3.9 Quad-SPI memory interface (QUADSPI)

All devices embed a Quad-SPI memory interface, which is a specialized communication interface targeting Single, Dual or Quad-SPI Flash memories. It can work in:

- Direct mode through registers.
- External flash status register polling mode.
- Memory mapped mode.

Up to 256 Mbytes external flash are memory mapped, supporting 8, 16 and 32-bit access. Code execution is supported.

The opcode and the frame format are fully programmable. Communication can be either in Single Data Rate or Dual Data Rate.

### 3.10 LCD-TFT controller

The LCD-TFT display controller provides a 24-bit parallel digital RGB (Red, Green, Blue) and delivers all signals to interface directly to a broad range of LCD and TFT panels up to XGA (1024x768) resolution with the following features:

- 2 displays layers with dedicated FIFO (64x32-bit)
- Color Look-Up table (CLUT) up to 256 colors (256x24-bit) per layer
- Up to 8 Input color formats selectable per layer
- Flexible blending between two layers using alpha value (per pixel or constant)
- Flexible programmable parameters for each layer
- Color keying (transparency color)
- Up to 4 programmable interrupt events.

### 3.11 Chrom-ART Accelerator™ (DMA2D)

The Chrom-Art Accelerator™ (DMA2D) is a graphic accelerator which offers advanced bit blitting, row data copy and pixel format conversion. It supports the following functions:

- Rectangle filling with a fixed color
- Rectangle copy
- Rectangle copy with pixel format conversion
- Rectangle composition with blending and pixel format conversion.

Various image format coding are supported, from indirect 4bpp color mode up to 32bpp direct color. It embeds dedicated memory to store color lookup tables.

An interrupt can be generated when an operation is complete or at a programmed watermark.

All the operations are fully automatized and are running independently from the CPU or the DMAs.

### 3.12 Nested vectored interrupt controller (NVIC)

The devices embed a nested vectored interrupt controller able to manage 16 priority levels, and handle up to 97 maskable interrupt channels plus the 16 interrupt lines of the Cortex<sup>®</sup>-M7 with FPU core.

- Closely coupled NVIC gives low-latency interrupt processing
- Interrupt entry vector table address passed directly to the core
- Allows early processing of interrupts
- Processing of late arriving, higher-priority interrupts
- Support tail chaining
- Processor state automatically saved
- Interrupt entry restored on interrupt exit with no instruction overhead

This hardware block provides flexible interrupt management features with minimum interrupt latency.

### 3.13 External interrupt/event controller (EXTI)

The external interrupt/event controller consists of 24 edge-detector lines used to generate interrupt/event requests. Each line can be independently configured to select the trigger event (rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The EXTI can detect an external line with a pulse width shorter than the Internal APB2 clock period. Up to 168 GPIOs can be connected to the 16 external interrupt lines.

### 3.14 Clocks and startup

On reset the 16 MHz internal HSI RC oscillator is selected as the default CPU clock. The 16 MHz internal RC oscillator is factory-trimmed to offer 1% accuracy. The application can then select as system clock either the RC oscillator or an external 4-26 MHz clock source. This clock can be monitored for failure. If a failure is detected, the system automatically switches back to the internal RC oscillator and a software interrupt is generated (if enabled). This clock source is input to a PLL thus allowing to increase the frequency up to 216 MHz. Similarly, full interrupt management of the PLL clock entry is available when necessary (for example if an indirectly used external oscillator fails).

Several prescalers allow the configuration of the two AHB buses, the high-speed APB (APB2) and the low-speed APB (APB1) domains. The maximum frequency of the two AHB buses is 216 MHz while the maximum frequency of the high-speed APB domains is 108 MHz. The maximum allowed frequency of the low-speed APB domain is 54 MHz.

The devices embed two dedicated PLL (PLLI2S and PLLSAI) which allow to achieve audio class performance. In this case, the I<sup>2</sup>S and SAI master clock can generate all standard sampling frequencies from 8 kHz to 192 kHz.

### 3.15 Boot modes

At startup, the boot memory space is selected by the BOOT pin and BOOT\_ADDx option bytes, allowing to program any boot memory address from 0x0000 0000 to 0x3FFF FFFF which includes:

- All Flash address space mapped on ITCM or AXIM interface
- All RAM address space: ITCM, DTCM RAMs and SRAMs mapped on AXIM interface
- The System memory bootloader

The boot loader is located in system memory. It is used to reprogram the Flash memory through a serial interface.

### 3.16 Power supply schemes

- $V_{BAT}$  = 1.65 to 3.6 V: power supply for RTC, external clock 32 kHz oscillator and backup registers (through power switch) when  $V_{DD}$  is not present.
- $V_{DD}$  = 1.7 to 3.6 V external power supply for I/Os and the internal regulator (when enabled), provided externally through  $V_{DD}$  pins.
- $V_{SSA}$ ,  $V_{DDA}$  = 1.7 to 3.6 V: external analog power supplies for ADC, DAC, reset blocks, RCs and PLL.  $V_{DDA}$  and  $V_{SSA}$  must be connected to  $V_{DD}$  and  $V_{SS}$ , respectively.

*Note:*  $V_{DD}/V_{DDA}$  minimum value of 1.7 V is obtained when the internal reset is OFF (refer to [Section 3.17.2: Internal reset OFF](#)). Refer to [Table 3: Voltage regulator configuration mode versus device operating mode](#) to identify the packages supporting this option.

- $V_{DDUSB}$  can be connected either to  $V_{DD}$  or an external independent power supply (3.0 to 3.6V) for USB transceivers (refer to [Figure 4](#) and [Figure 5](#)). For example, when device is powered at 1.8V, an independent power supply 3.3V can be connected to  $V_{DDUSB}$ . When the  $V_{DDUSB}$  is connected to a separated power supply, it is independent from  $V_{DD}$  or  $V_{DDA}$  but it must be the last supply to be provided and the first to disappear. The following conditions  $V_{DDUSB}$  must be respected:
  - During power-on phase ( $V_{DD} < V_{DD\_MIN}$ ),  $V_{DDUSB}$  should be always lower than  $V_{DD}$
  - During power-down phase ( $V_{DD} < V_{DD\_MIN}$ ),  $V_{DDUSB}$  should be always lower than  $V_{DD}$
  - $V_{DDSUB}$  rising and falling time rate specifications must be respected (see [Table 19](#) and [Table 20](#))
  - In operating mode phase,  $V_{DDUSB}$  could be lower or higher than  $V_{DD}$ :
    - If USB (USB OTG\_HS/OTG\_FS) is used, the associated GPIOs powered by  $V_{DDUSB}$  are operating between  $V_{DDUSB\_MIN}$  and  $V_{DDUSB\_MAX}$ .
    - The  $V_{DDUSB}$  supply both USB transceiver (USB OTG\_HS and USB OTG\_FS). If only one USB transceiver is used in the application, the GPIOs associated to the other USB transceiver are still supplied by  $V_{DDUSB}$ .
    - If USB (USB OTG\_HS/OTG\_FS) is not used, the associated GPIOs powered by  $V_{DDUSB}$  are operating between  $V_{DD\_MIN}$  and  $V_{DD\_MAX}$ .



Figure 4.  $V_{DDUSB}$  connected to  $V_{DD}$  power supply

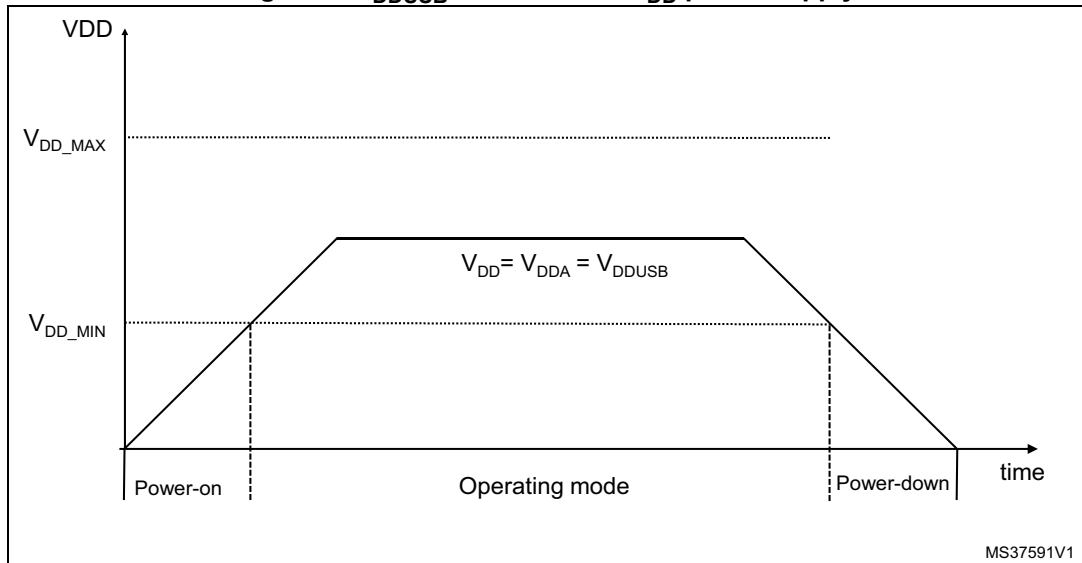
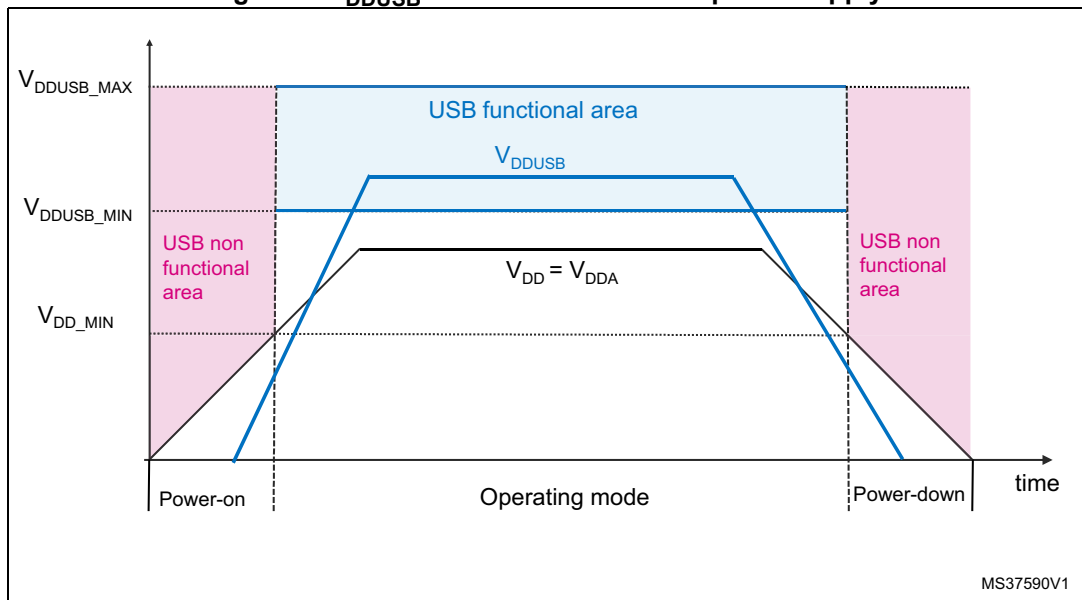


Figure 5.  $V_{DDUSB}$  connected to external power supply



### 3.17 Power supply supervisor

#### 3.17.1 Internal reset ON

On packages embedding the PDR\_ON pin, the power supply supervisor is enabled by holding PDR\_ON high. On the other packages, the power supply supervisor is always enabled.

The device has an integrated power-on reset (POR)/ power-down reset (PDR) circuitry coupled with a Brownout reset (BOR) circuitry. At power-on, POR/PDR is always active and ensures proper operation starting from 1.8 V. After the 1.8 V POR threshold level is

reached, the option byte loading process starts, either to confirm or modify default BOR thresholds, or to disable BOR permanently. Three BOR thresholds are available through option bytes. The device remains in reset mode when  $V_{DD}$  is below a specified threshold,  $V_{POR/PDR}$  or  $V_{BOR}$ , without the need for an external reset circuit.

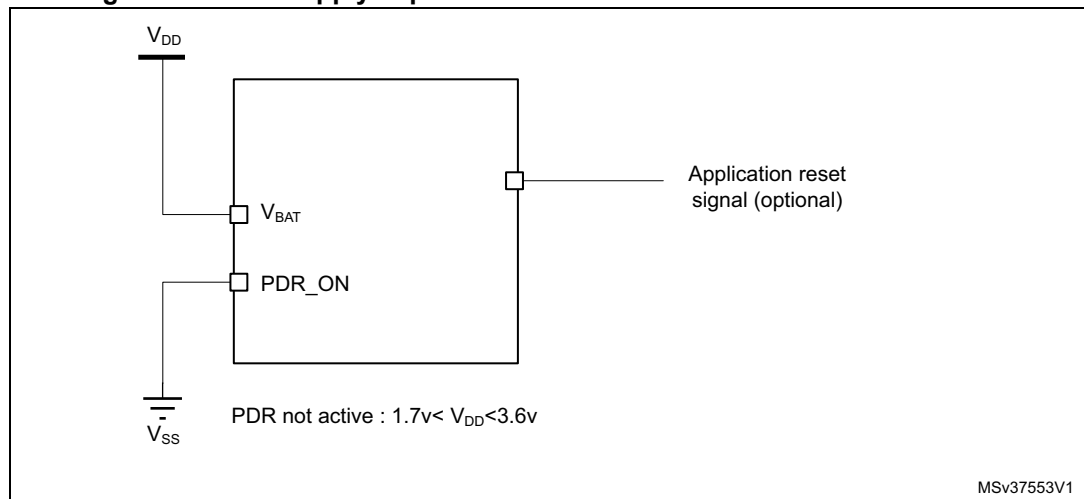
The device also features an embedded programmable voltage detector (PVD) that monitors the  $V_{DD}/V_{DDA}$  power supply and compares it to the  $V_{PVD}$  threshold. An interrupt can be generated when  $V_{DD}/V_{DDA}$  drops below the  $V_{PVD}$  threshold and/or when  $V_{DD}/V_{DDA}$  is higher than the  $V_{PVD}$  threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

### 3.17.2 Internal reset OFF

This feature is available only on packages featuring the PDR\_ON pin. The internal power-on reset (POR) / power-down reset (PDR) circuitry is disabled through the PDR\_ON pin.

An external power supply supervisor should monitor  $V_{DD}$  and should maintain the device in reset mode as long as  $V_{DD}$  is below a specified threshold. PDR\_ON should be connected to  $V_{SS}$ . Refer to [Figure 6: Power supply supervisor interconnection with internal reset OFF](#).

**Figure 6. Power supply supervisor interconnection with internal reset OFF**



The  $V_{DD}$  specified threshold, below which the device must be maintained under reset, is 1.7 V (see [Figure 7](#)).

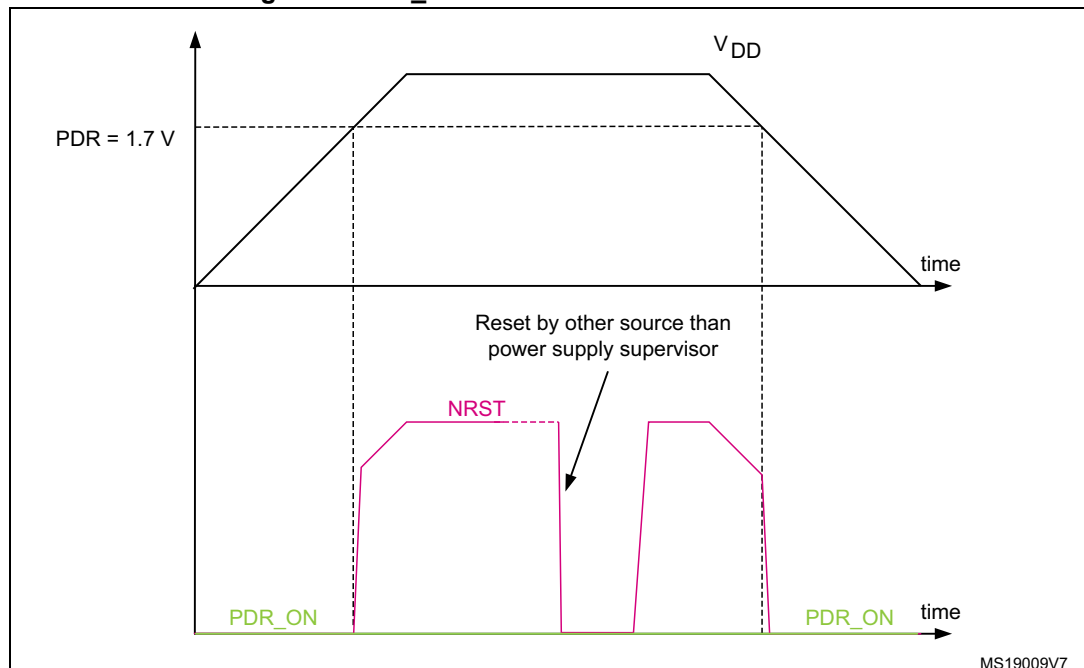
A comprehensive set of power-saving mode allows to design low-power applications.

When the internal reset is OFF, the following integrated features are no more supported:

- The integrated power-on reset (POR) / power-down reset (PDR) circuitry is disabled
- The brownout reset (BOR) circuitry must be disabled
- The embedded programmable voltage detector (PVD) is disabled
- $V_{BAT}$  functionality is no more available and  $V_{BAT}$  pin should be connected to  $V_{DD}$ .

All the packages, except for the LQFP100, allow to disable the internal reset through the PDR\_ON signal when connected to  $V_{SS}$ .

Figure 7. PDR\_ON control with internal reset OFF



### 3.18 Voltage regulator

The regulator has four operating modes:

- Regulator ON
  - Main regulator mode (MR)
  - Low-power regulator (LPR)
  - Power-down
- Regulator OFF

#### 3.18.1 Regulator ON

On packages embedding the BYPASS\_REG pin, the regulator is enabled by holding BYPASS\_REG low. On all other packages, the regulator is always enabled.

There are three power modes configured by software when the regulator is ON:

- MR mode used in Run/sleep modes or in Stop modes
  - In Run/Sleep mode
 

The MR mode is used either in the normal mode (default mode) or the over-drive mode (enabled by software). Different voltages scaling are provided to reach the best compromise between the maximum frequency and dynamic power

consumption. The over-drive mode allows operating at a higher frequency than the normal mode for a given voltage scaling.

- In Stop modes  
The MR can be configured in two ways during Stop mode:  
MR operates in normal mode (default mode of MR in Stop mode)  
MR operates in under-drive mode (reduced leakage mode).
- LPR is used in the Stop modes:  
The LP regulator mode is configured by software when entering Stop mode. Like the MR mode, the LPR can be configured in two ways during Stop mode:
  - LPR operates in normal mode (default mode when LPR is ON)
  - LPR operates in under-drive mode (reduced leakage mode).
- Power-down is used in Standby mode.  
The Power-down mode is activated only when entering in Standby mode. The regulator output is in high impedance and the kernel circuitry is powered down, inducing zero consumption. The contents of the registers and SRAM are lost.

Refer to [Table 3](#) for a summary of voltage regulator modes versus device operating modes.

Two external ceramic capacitors should be connected on V<sub>CAP\_1</sub> and V<sub>CAP\_2</sub> pin.

All packages have the regulator ON feature.

**Table 3. Voltage regulator configuration mode versus device operating mode<sup>(1)</sup>**

Voltage regulator configuration	Run mode	Sleep mode	Stop mode	Standby mode
Normal mode	MR	MR	MR or LPR	-
Over-drive mode <sup>(2)</sup>	MR	MR	-	-
Under-drive mode	-	-	MR or LPR	-
Power-down mode	-	-	-	Yes

1. '-' means that the corresponding configuration is not available.

2. The over-drive mode is not available when V<sub>DD</sub> = 1.7 to 2.1 V.

### 3.18.2 Regulator OFF

This feature is available only on packages featuring the BYPASS\_REG pin. The regulator is disabled by holding BYPASS\_REG high. The regulator OFF mode allows to supply externally a V<sub>12</sub> voltage source through V<sub>CAP\_1</sub> and V<sub>CAP\_2</sub> pins.

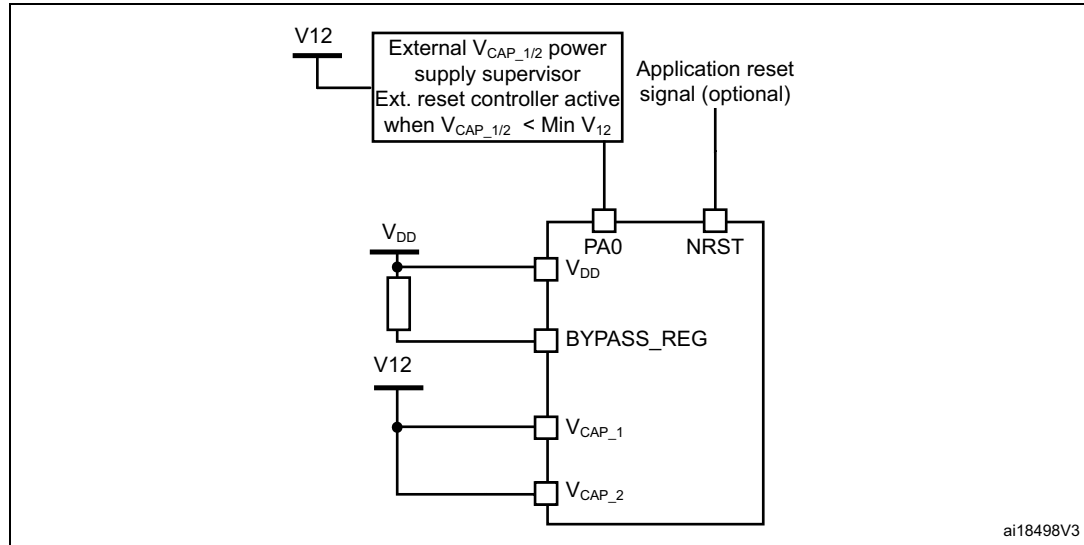
Since the internal voltage scaling is not managed internally, the external voltage value must be aligned with the targeted maximum frequency. The two 2.2 μF ceramic capacitors should be replaced by two 100 nF decoupling capacitors.

When the regulator is OFF, there is no more internal monitoring on V<sub>12</sub>. An external power supply supervisor should be used to monitor the V<sub>12</sub> of the logic power domain. PA0 pin should be used for this purpose, and act as power-on reset on V<sub>12</sub> power domain.

In regulator OFF mode, the following features are no more supported:

- PA0 cannot be used as a GPIO pin since it allows to reset a part of the  $V_{12}$  logic power domain which is not reset by the NRST pin.
- As long as PA0 is kept low, the debug mode cannot be used under power-on reset. As a consequence, PA0 and NRST pins must be managed separately if the debug connection under reset or pre-reset is required.
- The over-drive and under-drive modes are not available.
- The Standby mode is not available.

Figure 8. Regulator OFF

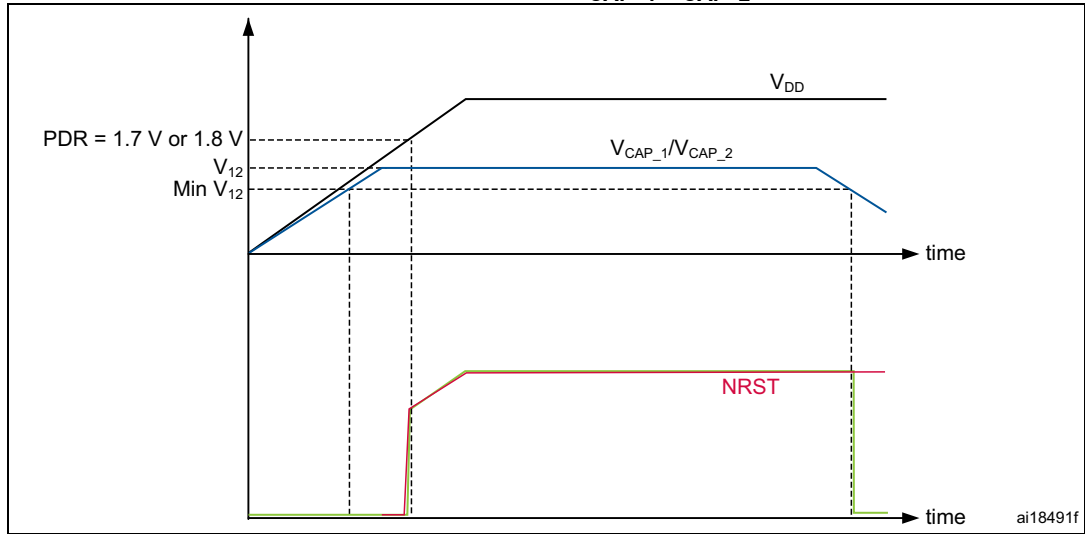


The following conditions must be respected:

- $V_{DD}$  should always be higher than  $V_{CAP\_1}$  and  $V_{CAP\_2}$  to avoid current injection between power domains.
- If the time for  $V_{CAP\_1}$  and  $V_{CAP\_2}$  to reach  $V_{12}$  minimum value is faster than the time for  $V_{DD}$  to reach 1.7 V, then PA0 should be kept low to cover both conditions: until  $V_{CAP\_1}$  and  $V_{CAP\_2}$  reach  $V_{12}$  minimum value and until  $V_{DD}$  reaches 1.7 V (see [Figure 9](#)).
- Otherwise, if the time for  $V_{CAP\_1}$  and  $V_{CAP\_2}$  to reach  $V_{12}$  minimum value is slower than the time for  $V_{DD}$  to reach 1.7 V, then PA0 could be asserted low externally (see [Figure 10](#)).
- If  $V_{CAP\_1}$  and  $V_{CAP\_2}$  go below  $V_{12}$  minimum value and  $V_{DD}$  is higher than 1.7 V, then a reset must be asserted on PA0 pin.

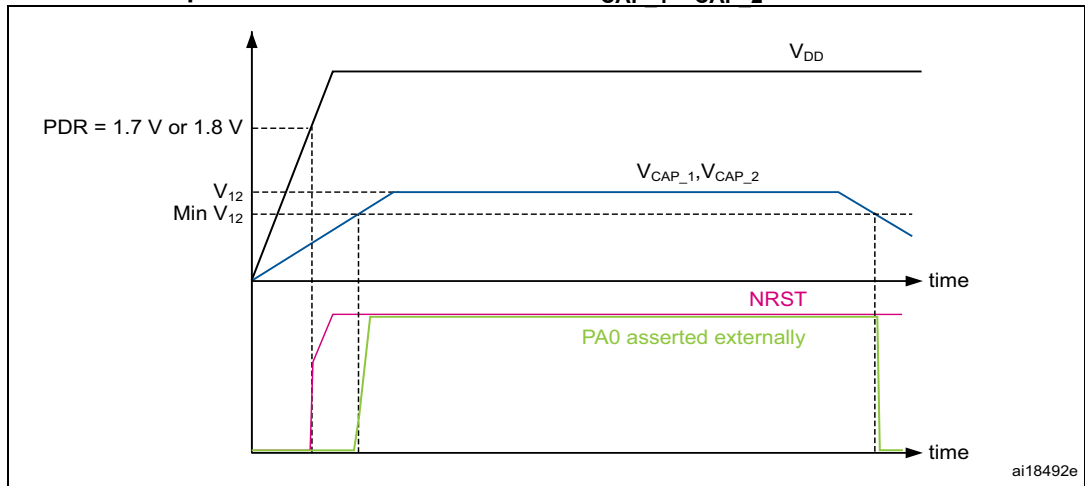
Note: The minimum value of  $V_{12}$  depends on the maximum frequency targeted in the application.

**Figure 9. Startup in regulator OFF: slow  $V_{DD}$  slope - power-down reset risen after  $V_{CAP\_1}/V_{CAP\_2}$  stabilization**



1. This figure is valid whatever the internal reset mode (ON or OFF).

**Figure 10. Startup in regulator OFF mode: fast  $V_{DD}$  slope - power-down reset risen before  $V_{CAP\_1}/V_{CAP\_2}$  stabilization**



1. This figure is valid whatever the internal reset mode (ON or OFF).

### 3.18.3 Regulator ON/OFF and internal reset ON/OFF availability

Table 4. Regulator ON/OFF and internal reset ON/OFF availability

Package	Regulator ON	Regulator OFF	Internal reset ON	Internal reset OFF
LQFP100	Yes	No	Yes	No
LQFP144			Yes PDR_ON set to V <sub>DD</sub>	Yes PDR_ON set to V <sub>SS</sub>
TFBGA216	Yes BYPASS_REG set to V <sub>SS</sub>	Yes BYPASS_REG set to V <sub>DD</sub>		

### 3.19 Real-time clock (RTC), backup SRAM and backup registers

The RTC is an independent BCD timer/counter. It supports the following features:

- Calendar with subsecond, seconds, minutes, hours (12 or 24 format), week day, date, month, year, in BCD (binary-coded decimal) format.
- Automatic correction for 28, 29 (leap year), 30, and 31 days of the month.
- Two programmable alarms.
- On-the-fly correction from 1 to 32767 RTC clock pulses. This can be used to synchronize it with a master clock.
- Reference clock detection: a more precise second source clock (50 or 60 Hz) can be used to enhance the calendar precision.
- Digital calibration circuit with 0.95 ppm resolution, to compensate for quartz crystal inaccuracy.
- Three anti-tamper detection pins with programmable filter.
- Timestamp feature which can be used to save the calendar content. This function can be triggered by an event on the timestamp pin, or by a tamper event, or by a switch to V<sub>BAT</sub> mode.
- 17-bit auto-reload wakeup timer (WUT) for periodic events with programmable resolution and period.

The RTC and the 32 backup registers are supplied through a switch that takes power either from the V<sub>DD</sub> supply when present or from the V<sub>BAT</sub> pin.

The backup registers are 32-bit registers used to store 128 bytes of user application data when V<sub>DD</sub> power is not present. They are not reset by a system or power reset, or when the device wakes up from Standby mode.

The RTC clock sources can be:

- A 32.768 kHz external crystal (LSE)
- An external resonator or oscillator(LSE)
- The internal low-power RC oscillator (LSI, with typical frequency of 32 kHz)
- The high-speed external clock (HSE) divided by 32.

The RTC is functional in V<sub>BAT</sub> mode and in all low-power modes when it is clocked by the LSE. When clocked by the LSI, the RTC is not functional in V<sub>BAT</sub> mode, but is functional in all low-power modes.

All RTC events (Alarm, WakeUp Timer, Timestamp or Tamper) can generate an interrupt and wakeup the device from the low-power modes.

### 3.20 Low-power modes

The devices support three low-power modes to achieve the best compromise between low-power consumption, short startup time and available wakeup sources:

- **Sleep mode**

In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.

- **Stop mode**

The Stop mode achieves the lowest power consumption while retaining the contents of SRAM and registers. All clocks in the 1.2 V domain are stopped, the PLL, the HSI RC and the HSE crystal oscillators are disabled.

The voltage regulator can be put either in main regulator mode (MR) or in low-power mode (LPR). Both modes can be configured as follows (see [Table 5: Voltage regulator modes in Stop mode](#)):

- Normal mode (default mode when MR or LPR is enabled)
- Under-drive mode.

The device can be woken up from the Stop mode by any of the EXTI line (the EXTI line source can be one of the 16 external lines, the PVD output, the RTC alarm / wakeup / tamper / time stamp events, the USB OTG FS/HS wakeup or the Ethernet wakeup and LPTIM1 asynchronous interrupt).

**Table 5. Voltage regulator modes in Stop mode**

Voltage regulator configuration	Main regulator (MR)	Low-power regulator (LPR)
Normal mode	MR ON	LPR ON
Under-drive mode	MR in under-drive mode	LPR in under-drive mode

- **Standby mode**

The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire 1.2 V domain is powered off. The PLL, the HSI RC and the HSE crystal oscillators are also switched off. After entering Standby mode, the SRAM and register contents are lost except for registers in the backup domain and the backup SRAM when selected.

The device exits the Standby mode when an external reset (NRST pin), an IWDG reset, a rising or falling edge on one of the 6 WKUP pins (PA0, PA2, PC1, PC13, PI8, PI11), or an RTC alarm / wakeup / tamper /time stamp event occurs.

The Standby mode is not supported when the embedded voltage regulator is bypassed and the 1.2 V domain is controlled by an external power.



### 3.21 $V_{BAT}$ operation

The  $V_{BAT}$  pin allows to power the device  $V_{BAT}$  domain from an external battery, an external supercapacitor, or from  $V_{DD}$  when no external battery and an external supercapacitor are present.

$V_{BAT}$  operation is activated when  $V_{DD}$  is not present.

The  $V_{BAT}$  pin supplies the RTC, the backup registers and the backup SRAM.

*Note:* When the microcontroller is supplied from  $V_{BAT}$ , external interrupts and RTC alarm/events do not exit it from  $V_{BAT}$  operation.

*When PDR\_ON pin is connected to  $V_{SS}$  (Internal Reset OFF), the  $V_{BAT}$  functionality is no more available and  $V_{BAT}$  pin should be connected to  $V_{DD}$ .*

### 3.22 Timers and watchdogs

The devices include two advanced-control timers, eight general-purpose timers, two basic timers and two watchdog timers.

All timer counters can be frozen in debug mode.

[Table 6](#) compares the features of the advanced-control, general-purpose and basic timers.

Table 6. Timer feature comparison

Timer type	Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/compare channels	Complementary output	Max interface clock (MHz)	Max timer clock (MHz) <sup>(1)</sup>
Advanced-control	TIM1, TIM8	16-bit	Up, Down, Up/down	Any integer between 1 and 65536	Yes	4	Yes	108	216
General purpose	TIM2, TIM5	32-bit	Up, Down, Up/down	Any integer between 1 and 65536	Yes	4	No	54	108/216
	TIM3, TIM4	16-bit	Up, Down, Up/down	Any integer between 1 and 65536	Yes	4	No	54	108/216
	TIM9	16-bit	Up	Any integer between 1 and 65536	No	2	No	108	216
	TIM10, TIM11	16-bit	Up	Any integer between 1 and 65536	No	1	No	108	216
	TIM12	16-bit	Up	Any integer between 1 and 65536	No	2	No	54	108/216
	TIM13, TIM14	16-bit	Up	Any integer between 1 and 65536	No	1	No	54	108/216
Basic	TIM6, TIM7	16-bit	Up	Any integer between 1 and 65536	Yes	0	No	54	108/216

1. The maximum timer clock is either 108 or 216 MHz depending on TIMPRE bit configuration in the RCC\_DCKCFGR register.

### 3.22.1 Advanced-control timers (TIM1, TIM8)

The advanced-control timers (TIM1, TIM8) can be seen as three-phase PWM generators multiplexed on 6 channels. They have complementary PWM outputs with programmable inserted dead times. They can also be considered as complete general-purpose timers. Their 4 independent channels can be used for:

- Input capture
- Output compare
- PWM generation (edge- or center-aligned modes)
- One-pulse mode output

If configured as standard 16-bit timers, they have the same features as the general-purpose TIMx timers. If configured as 16-bit PWM generators, they have full modulation capability (0-100%).

The advanced-control timer can work together with the TIMx timers via the Timer Link feature for synchronization or event chaining.

TIM1 and TIM8 support independent DMA request generation.

### 3.22.2 General-purpose timers (TIMx)

There are ten synchronizable general-purpose timers embedded in the STM32F74xxx devices (see [Table 6](#) for differences).

- **TIM2, TIM3, TIM4, TIM5**

The STM32F750x8 include 4 full-featured general-purpose timers: TIM2, TIM5, TIM3, and TIM4. The TIM2 and TIM5 timers are based on a 32-bit auto-reload up/downcounter and a 16-bit prescaler. The TIM3 and TIM4 timers are based on a 16-bit auto-reload up/downcounter and a 16-bit prescaler. They all feature 4 independent channels for input capture/output compare, PWM or one-pulse mode output. This gives up to 16 input capture/output compare/PWMs on the largest packages.

The TIM2, TIM3, TIM4, TIM5 general-purpose timers can work together, or with the other general-purpose timers and the advanced-control timers TIM1 and TIM8 via the Timer Link feature for synchronization or event chaining.

Any of these general-purpose timers can be used to generate PWM outputs.

TIM2, TIM3, TIM4, TIM5 all have independent DMA request generation. They are capable of handling quadrature (incremental) encoder signals and the digital outputs from 1 to 4 hall-effect sensors.

- **TIM9, TIM10, TIM11, TIM12, TIM13, and TIM14**

These timers are based on a 16-bit auto-reload upcounter and a 16-bit prescaler. TIM10, TIM11, TIM13, and TIM14 feature one independent channel, whereas TIM9 and TIM12 have two independent channels for input capture/output compare, PWM or one-pulse mode output. They can be synchronized with the TIM2, TIM3, TIM4, TIM5 full-featured general-purpose timers. They can also be used as simple time bases.

### 3.22.3 Basic timers TIM6 and TIM7

These timers are mainly used for DAC trigger and waveform generation. They can also be used as a generic 16-bit time base.

TIM6 and TIM7 support independent DMA request generation.

### 3.22.4 Low-power timer (LPTIM1)

The low-power timer has an independent clock and is running also in Stop mode if it is clocked by LSE, LSI or an external clock. It is able to wakeup the devices from Stop mode.

This low-power timer supports the following features:

- 16-bit up counter with 16-bit autoreload register
- 16-bit compare register
- Configurable output: pulse, PWM
- Continuous / one-shot mode
- Selectable software / hardware input trigger
- Selectable clock source:
  - Internal clock source: LSE, LSI, HSI or APB clock
  - External clock source over LPTIM input (working even with no internal clock source running, used by the Pulse Counter Application)
- Programmable digital glitch filter
- Encoder mode

### 3.22.5 Independent watchdog

The independent watchdog is based on a 12-bit downcounter and 8-bit prescaler. It is clocked from an independent 32 kHz internal RC and as it operates independently from the main clock, it can operate in Stop and Standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free-running timer for application timeout management. It is hardware- or software-configurable through the option bytes.

### 3.22.6 Window watchdog

The window watchdog is based on a 7-bit downcounter that can be set as free-running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early warning interrupt capability and the counter can be frozen in debug mode.

### 3.22.7 SysTick timer

This timer is dedicated to real-time operating systems, but could also be used as a standard downcounter. It features:

- A 24-bit downcounter
- Autoreload capability
- Maskable system interrupt generation when the counter reaches 0
- Programmable clock source.

### 3.23 Inter-integrated circuit interface (I<sup>2</sup>C)

The devices embed 4 I2C. Refer to [Table 7: I2C implementation](#) for the features implementation.

The I<sup>2</sup>C bus interface handles communication between the microcontroller and the serial I<sup>2</sup>C bus. It controls all I<sup>2</sup>C bus-specific sequencing, protocol, arbitration and timing.

The I2C peripheral supports:

- I<sup>2</sup>C-bus specification and user manual rev. 5 compatibility:
  - Slave and master modes, multimaster capability
  - Standard-mode (Sm), with a bitrate up to 100 kbit/s
  - Fast-mode (Fm), with a bitrate up to 400 kbit/s
  - 7-bit and 10-bit addressing mode, multiple 7-bit slave addresses
  - Programmable setup and hold times
  - Optional clock stretching
- System Management Bus (SMBus) specification rev 2.0 compatibility:
  - Hardware PEC (Packet Error Checking) generation and verification with ACK control
  - Address resolution protocol (ARP) support
  - SMBus alert
- Power System Management Protocol (PMBus™) specification rev 1.1 compatibility
- Independent clock: a choice of independent clock sources allowing the I2C communication speed to be independent from the PCLK reprogramming.
- Programmable analog and digital noise filters
- 1-byte buffer with DMA capability

**Table 7. I2C implementation**

I2C features <sup>(1)</sup>	I2C1	I2C2	I2C3	I2C4
Standard-mode (up to 100 kbit/s)	X	X	X	X
Fast-mode (up to 400 kbit/s)	X	X	X	X
Programmable analog and digital noise filters	X	X	X	X
SMBus/PMBus hardware support	X	X	X	X
Independent clock	X	X	X	X

1. X: supported

### 3.24 Universal synchronous/asynchronous receiver transmitters (USART)

The devices embed USART. Refer to [Table 8: USART implementation](#) for the features implementation.

The universal synchronous asynchronous receiver transmitter (USART) offers a flexible means of full-duplex data exchange with external equipment requiring an industry standard NRZ asynchronous serial data format.

The USART peripheral supports:

- Full-duplex asynchronous communications
- Configurable oversampling method by 16 or 8 to give flexibility between speed and clock tolerance
- Dual clock domain allowing convenient baud rate programming independent from the PCLK reprogramming
- A common programmable transmit and receive baud rate of up to 27 Mbit/s when USART clock source is system clock frequency (Max is 216 MHz) and oversampling by 8 is used.
- Auto baud rate detection
- Programmable data word length (7 or 8 or 9 bits) word length
- Programmable data order with MSB-first or LSB-first shifting
- Programmable parity (odd, even, no parity)
- Configurable stop bits (1 or 1.5 or 2 stop bits)
- Synchronous mode and clock output for synchronous communications
- Single-wire half-duplex communications
- Separate signal polarity control for transmission and reception
- Swappable Tx/Rx pin configuration
- Hardware flow control for modem and RS-485 transceiver
- Multiprocessor communications
- LIN master synchronous break send capability and LIN slave break detection capability
- IrDA SIR encoder decoder supporting 3/16 bit duration for normal mode
- Smartcard mode ( T=0 and T=1 asynchronous protocols for Smartcards as defined in the ISO/IEC 7816-3 standard )
- Support for Modbus communication

The table below summarizes the implementation of all U(S)ARTs instances

**Table 8. USART implementation**

features <sup>(1)</sup>	USART1/2/3/6	UART4/5/7/8
Data Length	7, 8 and 9 bits	
Hardware flow control for modem	X	X
Continuous communication using DMA	X	X
Multiprocessor communication	X	X
Synchronous mode	X	-

Table 8. USART implementation (continued)

features <sup>(1)</sup>	USART1/2/3/6	UART4/5/7/8
Smartcard mode	X	-
Single-wire half-duplex communication	X	X
IrDA SIR ENDEC block	X	X
LIN mode	X	X
Dual clock domain	X	X
Receiver timeout interrupt	X	X
Modbus communication	X	X
Auto baud rate detection	X	X
Driver Enable	X	X

1. X: supported.

### 3.25 Serial peripheral interface (SPI)/inter- integrated sound interfaces (I2S)

The devices feature up to six SPIs in slave and master modes in full-duplex and simplex communication modes. SPI1, SPI4, SPI5, and SPI6 can communicate at up to 50 Mbits/s, SPI2 and SPI3 can communicate at up to 25 Mbit/s. The 3-bit prescaler gives 8 master mode frequencies and the frame is configurable from 4 to 16 bits. The SPI interfaces support NSS pulse mode, TI mode and Hardware CRC calculation. All SPIs can be served by the DMA controller.

Three standard I<sup>2</sup>S interfaces (multiplexed with SPI1, SPI2 and SPI3) are available. They can be operated in master or slave mode, in simplex communication modes, and can be configured to operate with a 16-/32-bit resolution as an input or output channel. Audio sampling frequencies from 8 kHz up to 192 kHz are supported. When either or both of the I<sup>2</sup>S interfaces is/are configured in master mode, the master clock can be output to the external DAC/CODEC at 256 times the sampling frequency.

All I2Sx can be served by the DMA controller.

### 3.26 Serial audio interface (SAI)

The devices embed two serial audio interfaces.

The serial audio interface is based on two independent audio subblocks which can operate as transmitter or receiver with their FIFO. Many audio protocols are supported by each block: I2S standards, LSB or MSB-justified, PCM/DSP, TDM, AC'97 and SPDIF output, supporting audio sampling frequencies from 8 kHz up to 192 kHz. Both subblocks can be configured in master or in slave mode.

In master mode, the master clock can be output to the external DAC/CODEC at 256 times of the sampling frequency.

The two sub-blocks can be configured in synchronous mode when full-duplex mode is required.

SAI1 and SAI2 can be served by the DMA controller

### 3.27 SPDIFRX Receiver Interface (SPDIFRX)

The SPDIFRX peripheral, is designed to receive an S/PDIF flow compliant with IEC-60958 and IEC-61937. These standards support simple stereo streams up to high sample rate, and compressed multi-channel surround sound, such as those defined by Dolby or DTS (up to 5.1).

The main features of the SPDIFRX are the following:

- Up to 4 inputs available
- Automatic symbol rate detection
- Maximum symbol rate: 12.288 MHz
- Stereo stream from 32 to 192 kHz supported
- Supports Audio IEC-60958 and IEC-61937, consumer applications
- Parity bit management
- Communication using DMA for audio samples
- Communication using DMA for control and user channel information
- Interrupt capabilities

The SPDIFRX receiver provides all the necessary features to detect the symbol rate, and decode the incoming data stream. The user can select the wanted SPDIF input, and when a valid signal will be available, the SPDIFRX will re-sample the incoming signal, decode the manchester stream, recognize frames, sub-frames and blocks elements. It delivers to the CPU decoded data, and associated status flags.

The SPDIFRX also offers a signal named `spdif_frame_sync`, which toggles at the S/PDIF sub-frame rate that will be used to compute the exact sample rate for clock drift algorithms.

### 3.28 Audio PLL (PLLI2S)

The devices feature an additional dedicated PLL for audio I<sup>2</sup>S and SAI applications. It allows to achieve error-free I<sup>2</sup>S sampling clock accuracy without compromising on the CPU performance, while using USB peripherals.

The PLLI2S configuration can be modified to manage an I<sup>2</sup>S/SAI sample rate change without disabling the main PLL (PLL) used for CPU, USB and Ethernet interfaces.

The audio PLL can be programmed with very low error to obtain sampling rates ranging from 8 KHz to 192 KHz.

In addition to the audio PLL, a master clock input pin can be used to synchronize the I<sup>2</sup>S/SAI flow with an external PLL (or Codec output).



### 3.29 Audio and LCD PLL(PLLSAI)

An additional PLL dedicated to audio and LCD-TFT is used for SAI1 peripheral in case the PLLI2S is programmed to achieve another audio sampling frequency (49.152 MHz or 11.2896 MHz) and the audio application requires both sampling frequencies simultaneously.

The PLLSAI is also used to generate the LCD-TFT clock.

### 3.30 SD/SDIO/MMC card host interface (SDMMC)

An SDMMC host interface is available, that supports MultiMediaCard System Specification Version 4.2 in three different databus modes: 1-bit (default), 4-bit and 8-bit.

The interface allows data transfer at up to 50 MHz, and is compliant with the SD Memory card specification version 2.0.

The SDMMC card specification version 2.0 is also supported with two different databus modes: 1-bit (default) and 4-bit.

The current version supports only one SD/SDMMC/MMC4.2 card at any one time and a stack of MMC4.1 or previous.

The SDMMC can be served by the DMA controller

### 3.31 Ethernet MAC interface with dedicated DMA and IEEE 1588 support

The devices provide an IEEE-802.3-2002-compliant media access controller (MAC) for ethernet LAN communications through an industry-standard medium-independent interface (MII) or a reduced medium-independent interface (RMII). The microcontroller requires an external physical interface device (PHY) to connect to the physical LAN bus (twisted-pair, fiber, etc.). The PHY is connected to the device MII port using 17 signals for MII or 9 signals for RMII, and can be clocked using the 25 MHz (MII) from the microcontroller.

The devices include the following features:

- Support of 10 and 100 Mbit/s rates
- Dedicated DMA controller allowing high-speed transfers between the dedicated SRAM and the descriptors
- Tagged MAC frame support (VLAN support)
- Half-duplex (CSMA/CD) and full-duplex operation
- MAC control sublayer (control frames) support
- 32-bit CRC generation and removal
- Several address filtering modes for physical and multicast address (multicast and group addresses)
- 32-bit status code for each transmitted or received frame
- Internal FIFOs to buffer transmit and receive frames. The transmit FIFO and the receive FIFO are both 2 Kbytes.
- Supports hardware PTP (precision time protocol) in accordance with IEEE 1588 2008 (PTP V2) with the time stamp comparator connected to the TIM2 input
- Triggers interrupt when system time becomes greater than target time

### 3.32 Controller area network (bxCAN)

The two CANs are compliant with the 2.0A and B (active) specifications with a bitrate up to 1 Mbit/s. They can receive and transmit standard frames with 11-bit identifiers as well as extended frames with 29-bit identifiers. Each CAN has three transmit mailboxes, two receive FIFOs with 3 stages and 28 shared scalable filter banks (all of them can be used even if one CAN is used). 256 bytes of SRAM are allocated for each CAN.

### 3.33 Universal serial bus on-the-go full-speed (OTG\_FS)

The devices embed an USB OTG full-speed device/host/OTG peripheral with integrated transceivers. The USB OTG FS peripheral is compliant with the USB 2.0 specification and with the OTG 2.0 specification. It has software-configurable endpoint setting and supports suspend/resume. The USB OTG controller requires a dedicated 48 MHz clock that is generated by a PLL connected to the HSE oscillator.

The major features are:

- Combined Rx and Tx FIFO size of 1.28 Kbytes with dynamic FIFO sizing
- Support of the session request protocol (SRP) and host negotiation protocol (HNP)
- 1 bidirectional control endpoint + 5 IN endpoints + 5 OUT endpoints
- 12 host channels with periodic OUT support
- Software configurable to OTG1.3 and OTG2.0 modes of operation
- USB 2.0 LPM (Link Power Management) support
- Internal FS OTG PHY support
- HNP/SNP/IP inside (no need for any external resistor)

For OTG/Host modes, a power switch is needed in case bus-powered devices are connected

### 3.34 Universal serial bus on-the-go high-speed (OTG\_HS)

The devices embed a USB OTG high-speed (up to 480 Mb/s) device/host/OTG peripheral. The USB OTG HS supports both full-speed and high-speed operations. It integrates the transceivers for full-speed operation (12 MB/s) and features a UTMI low-pin interface (ULPI) for high-speed operation (480 MB/s). When using the USB OTG HS in HS mode, an external PHY device connected to the ULPI is required.

The USB OTG HS peripheral is compliant with the USB 2.0 specification and with the OTG 2.0 specification. It has software-configurable endpoint setting and supports suspend/resume. The USB OTG controller requires a dedicated 48 MHz clock that is generated by a PLL connected to the HSE oscillator.

The major features are:

- Combined Rx and Tx FIFO size of 4 Kbytes with dynamic FIFO sizing
- Support of the session request protocol (SRP) and host negotiation protocol (HNP)
- 8 bidirectional endpoints
- 16 host channels with periodic OUT support
- Software configurable to OTG1.3 and OTG2.0 modes of operation
- USB 2.0 LPM (Link Power Management) support
- Internal FS OTG PHY support
- External HS or HS OTG operation supporting ULPI in SDR mode. The OTG PHY is connected to the microcontroller ULPI port through 12 signals. It can be clocked using the 60 MHz output.
- Internal USB DMA
- HNP/SNP/IP inside (no need for any external resistor)
- for OTG/Host modes, a power switch is needed in case bus-powered devices are connected

### **3.35 High-definition multimedia interface (HDMI) - consumer electronics control (CEC)**

The devices embed a HDMI-CEC controller that provides hardware support for the Consumer Electronics Control (CEC) protocol (Supplement 1 to the HDMI standard).

This protocol provides high-level control functions between all audiovisual products in an environment. It is specified to operate at low speeds with minimum processing and memory overhead. It has a clock domain independent from the CPU clock, allowing the HDMI-CEC controller to wakeup the MCU from Stop mode on data reception.

### **3.36 Digital camera interface (DCMI)**

The devices embed a camera interface that can connect with camera modules and CMOS sensors through an 8-bit to 14-bit parallel interface, to receive video data. The camera interface can sustain a data transfer rate up to 54 Mbyte/s at 54 MHz. It features:

- Programmable polarity for the input pixel clock and synchronization signals
- Parallel data communication can be 8-, 10-, 12- or 14-bit
- Supports 8-bit progressive video monochrome or raw bayer format, YCbCr 4:2:2 progressive video, RGB 565 progressive video or compressed data (like JPEG)
- Supports continuous mode or snapshot (a single frame) mode
- Capability to automatically crop the image

### **3.37 Cryptographic acceleration**

The devices embed a cryptographic accelerator. This cryptographic accelerator provides a set of hardware acceleration for the advanced cryptographic algorithms usually needed to

provide confidentiality, authentication, data integrity and non repudiation when exchanging messages with a peer.

- These algorithms consists of:

Encryption/Decryption

- DES/TDES (data encryption standard/triple data encryption standard): ECB (electronic codebook) and CBC (cipher block chaining) chaining algorithms, 64-, 128- or 192-bit key
- AES (advanced encryption standard): ECB, CBC, GCM, CCM, and CTR (counter mode) chaining algorithms, 128, 192 or 256-bit key

Universal hash

- SHA-1 and SHA-2 (secure hash algorithms)
- MD5
- HMAC

The cryptographic accelerator supports DMA request generation.

### 3.38 Random number generator (RNG)

All devices embed an RNG that delivers 32-bit random numbers generated by an integrated analog circuit.

### 3.39 General-purpose input/outputs (GPIOs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain, with or without pull-up or pull-down), as input (floating, with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions. All GPIOs are high-current-capable and have speed selection to better manage internal noise, power consumption and electromagnetic emission.

The I/O configuration can be locked if needed by following a specific sequence in order to avoid spurious writing to the I/Os registers.

Fast I/O handling allowing maximum I/O toggling up to 108 MHz.

### 3.40 Analog-to-digital converters (ADCs)

Three 12-bit analog-to-digital converters are embedded and each ADC shares up to 16 external channels, performing conversions in the single-shot or scan mode. In scan mode, automatic conversion is performed on a selected group of analog inputs.

Additional logic functions embedded in the ADC interface allow:

- Simultaneous sample and hold
- Interleaved sample and hold

The ADC can be served by the DMA controller. An analog watchdog feature allows very precise monitoring of the converted voltage of one, some or all selected channels. An interrupt is generated when the converted voltage is outside the programmed thresholds.

To synchronize A/D conversion and timers, the ADCs could be triggered by any of TIM1, TIM2, TIM3, TIM4, TIM5, or TIM8 timer.

### 3.41 Temperature sensor

The temperature sensor has to generate a voltage that varies linearly with temperature. The conversion range is between 1.7 V and 3.6 V. The temperature sensor is internally connected to the same input channel as  $V_{BAT}$ , ADC1\_IN18, which is used to convert the sensor output voltage into a digital value. When the temperature sensor and  $V_{BAT}$  conversion are enabled at the same time, only  $V_{BAT}$  conversion is performed.

As the offset of the temperature sensor varies from chip to chip due to process variation, the internal temperature sensor is mainly suitable for applications that detect temperature changes instead of absolute temperatures. If an accurate temperature reading is needed, then an external temperature sensor part should be used.

### 3.42 Digital-to-analog converter (DAC)

The two 12-bit buffered DAC channels can be used to convert two digital signals into two analog voltage signal outputs.

This dual digital Interface supports the following features:

- two DAC converters: one for each output channel
- 8-bit or 12-bit monotonic output
- left or right data alignment in 12-bit mode
- synchronized update capability
- noise-wave generation
- triangular-wave generation
- dual DAC channel independent or simultaneous conversions
- DMA capability for each channel
- external triggers for conversion
- input voltage reference  $V_{REF+}$

Eight DAC trigger inputs are used in the device. The DAC channels are triggered through the timer update outputs that are also connected to different DMA streams.

### 3.43 Serial wire JTAG debug port (SWJ-DP)

The Arm SWJ-DP interface is embedded, and is a combined JTAG and serial wire debug port that enables either a serial wire debug or a JTAG probe to be connected to the target.

Debug is performed using 2 pins only instead of 5 required by the JTAG (JTAG pins could be re-use as GPIO with alternate function): the JTAG TMS and TCK pins are shared with SWDIO and SWCLK, respectively, and a specific sequence on the TMS pin is used to switch between JTAG-DP and SW-DP.

### 3.44 Embedded Trace Macrocell™

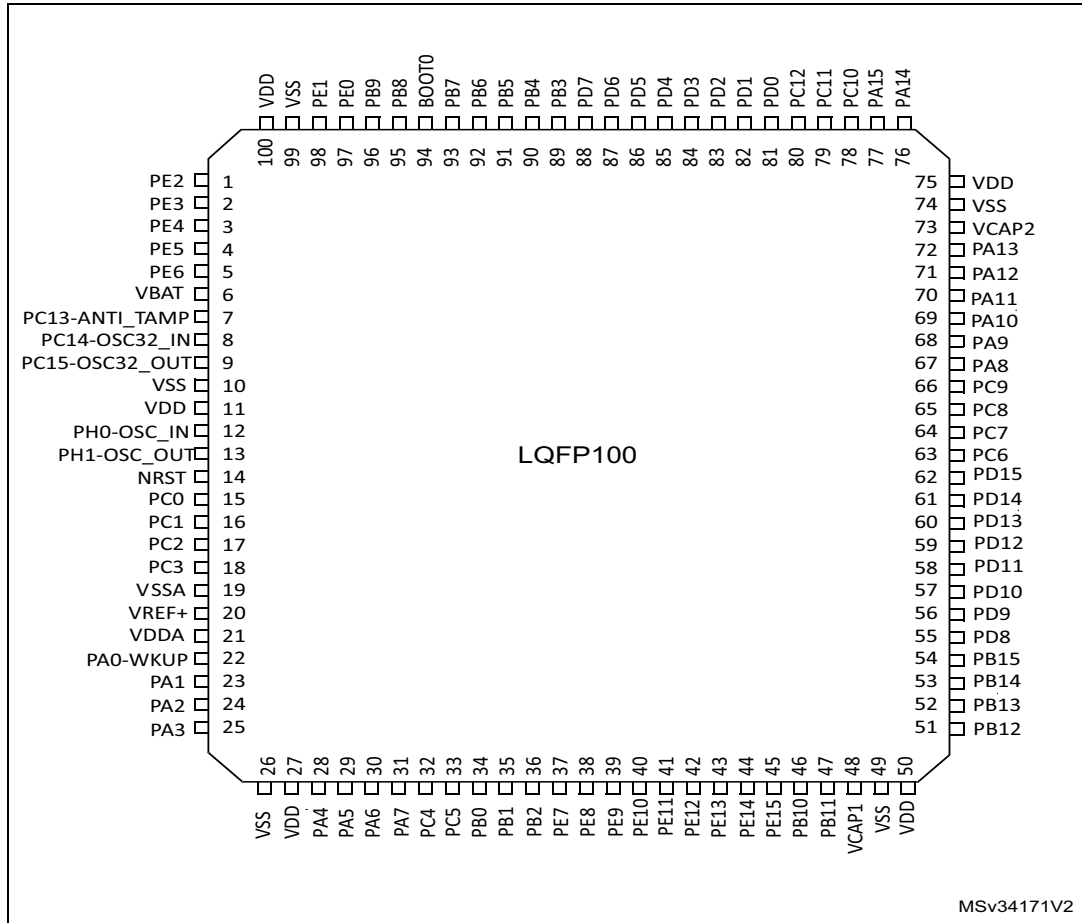
The Arm Embedded Trace Macrocell provides a greater visibility of the instruction and data flow inside the CPU core by streaming compressed data at a very high rate from the STM32F74xxx through a small number of ETM pins to an external hardware trace port analyzer (TPA) device. The TPA is connected to a host computer using USB, Ethernet, or

any other high-speed channel. Real-time instruction and data flow activity can be recorded and then formatted for display on the host computer that runs the debugger software. TPA hardware is commercially available from common development tool vendors.

The Embedded Trace Macrocell operates with third party debugger software tools.

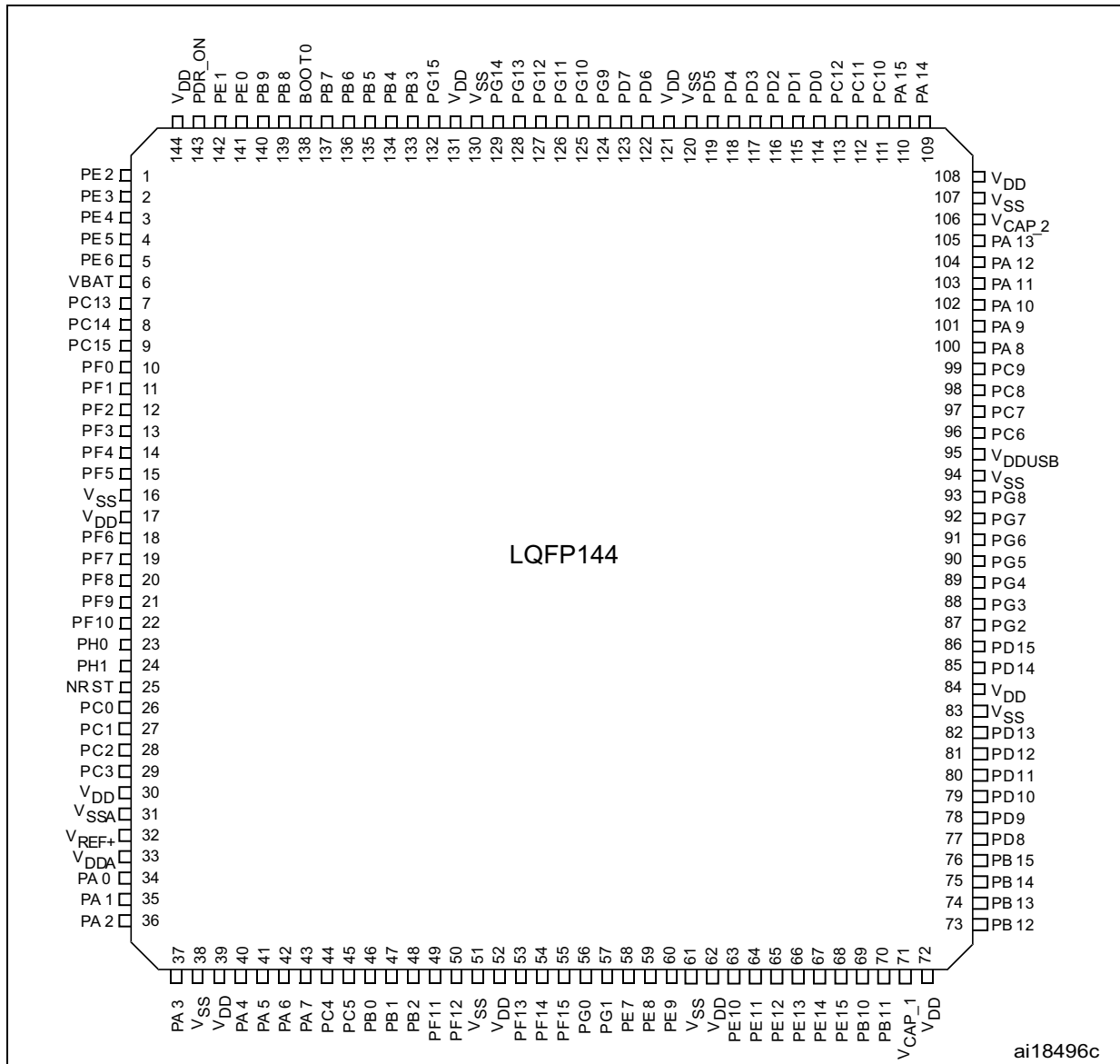
## 4 Pinouts and pin description

Figure 11. STM32F750V8 LQFP100 pinout



2. The above figure shows the package top view.

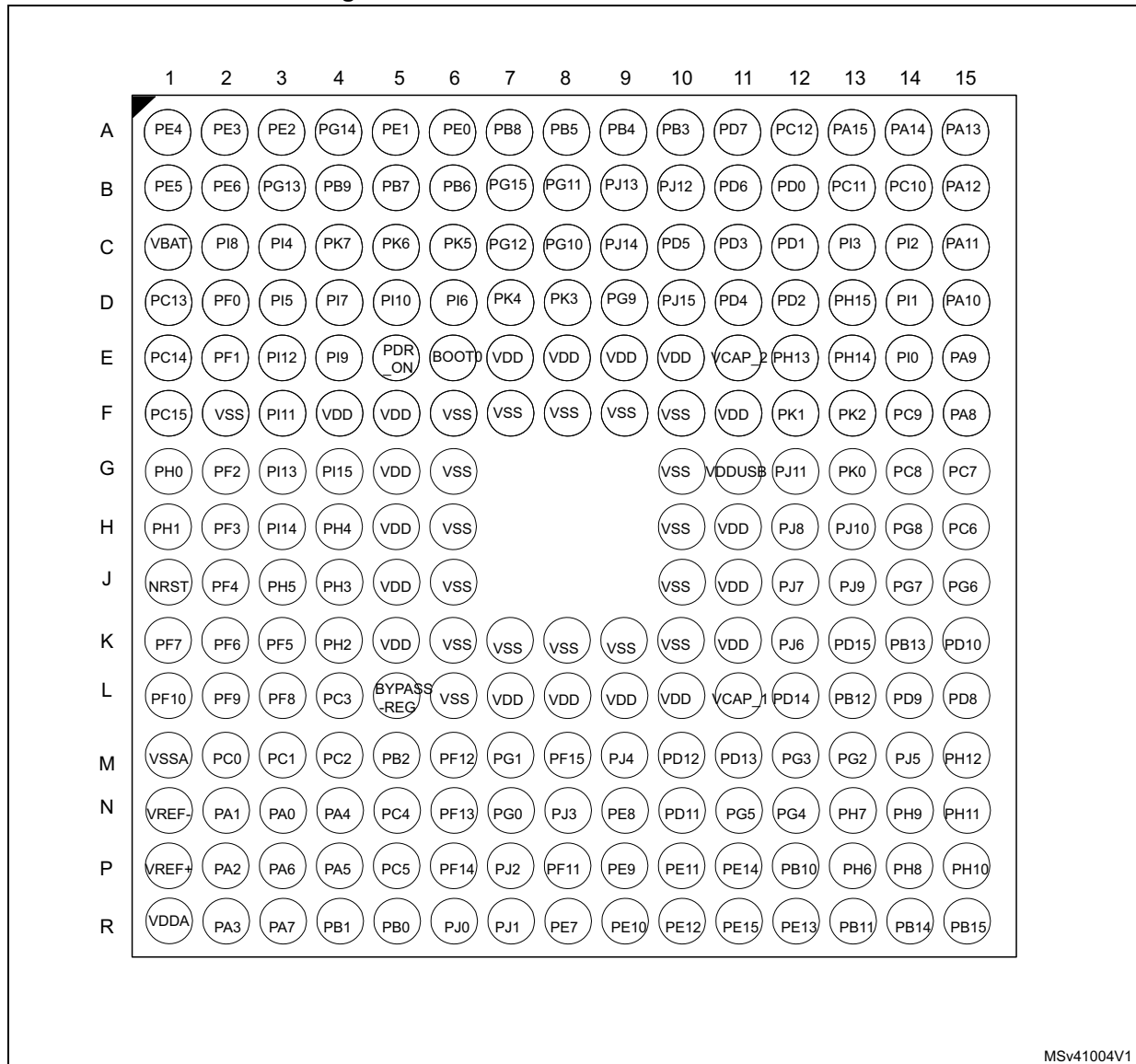
Figure 12. STM32F750Z8 LQFP144 pinout



1. The above figure shows the package top view.



Figure 13. STM32F750N8 TFBGA216 ballout



MSv41004V1

1. The above figure shows the package top view.

**Table 9. Legend/abbreviations used in the pinout table**

Name	Abbreviation	Definition
Pin name	Unless otherwise specified in brackets below the pin name, the pin function during and after reset is the same as the actual pin name	
Pin type	S	Supply pin
	I	Input only pin
	I/O	Input / output pin
I/O structure	FT	5 V tolerant I/O
	TTa	3.3 V tolerant I/O directly connected to ADC
	B	Dedicated BOOT pin
	RST	Bidirectional reset pin with weak pull-up resistor
Notes	Unless otherwise specified by a note, all I/Os are set as floating inputs during and after reset	
Alternate functions	Functions selected through GPIOx_AFR registers	
Additional functions	Functions directly selected/enabled through peripheral registers	

**Table 10. STM32F750x8 pin and ball definition**

Pin Number			Pin name (function after reset) <sup>(1)</sup>	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	TFBGA216						
1	1	A3	PE2	I/O	FT	-	TRACECLK, SPI4_SCK, SAI1_MCLK_A, QUADSPI_BK1_IO2, ETH_MII_TXD3, FMC_A23, EVENTOUT	-
2	2	A2	PE3	I/O	FT	-	TRACED0, SAI1_SD_B, FMC_A19, EVENTOUT	-
3	3	A1	PE4	I/O	FT	-	TRACED1, SPI4_NSS, SAI1_FS_A, FMC_A20, DCMI_D4, LCD_B0, EVENTOUT	-

Table 10. STM32F750x8 pin and ball definition (continued)

Pin Number			Pin name (function after reset) <sup>(1)</sup>	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	TFBGA216						
4	4	B1	PE5	I/O	FT	-	TRACED2, TIM9_CH1, SPI4_MISO, SAI1_SCK_A, FMC_A21, DCMI_D6, LCD_G0, EVENTOUT	-
5	5	B2	PE6	I/O	FT	-	TRACED3, TIM1_BKIN2, TIM9_CH2, SPI4_MOSI, SAI1_SD_A, SAI2_MCK_B, FMC_A22, DCMI_D7, LCD_G1, EVENTOUT	-
-	-	G6	VSS	S	-	-	-	-
-	-	F5	VDD	S	-	-	-	-
6	6	C1	VBAT	S	-	-	-	-
-	-	C2	PI8	I/O	FT	(2) (3)	EVENTOUT	RTC_TAMP2/ RTC_TS,WKUP5
7	7	D1	PC13	I/O	FT	(2) (3)	EVENTOUT	RTC_TAMP1/ RTC_TS/RTC_OUT ,WKUP4
8	8	E1	PC14- OSC32_IN(PC14)	I/O	FT	(2) (3)	EVENTOUT	OSC32_IN
9	9	F1	PC15- OSC32_OUT(PC 15)	I/O	FT	(2) (3)	EVENTOUT	OSC32_OUT
-	-	G5	VDD	S	-	-	-	-
-	-	E4	PI9	I/O	FT	-	CAN1_RX, FMC_D30, LCD_VSYNC, EVENTOUT	-
-	-	D5	PI10	I/O	FT	-	ETH_MII_RX_ER, FMC_D31, LCD_HSYNC, EVENTOUT	-
-	-	F3	PI11	I/O	FT	-	OTG_HS_ULPI_DIR, EVENTOUT	WKUP6
-	-	F2	VSS	S	-	-	-	-
-	-	F4	VDD	S	-	-	-	-
-	10	D2	PF0	I/O	FT	-	I2C2_SDA, FMC_A0, EVENTOUT	-

Table 10. STM32F750x8 pin and ball definition (continued)

Pin Number			Pin name (function after reset) <sup>(1)</sup>	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	TFBGA216						
-	11	E2	PF1	I/O	FT	-	I2C2_SCL, FMC_A1, EVENTOUT	-
-	12	G2	PF2	I/O	FT	-	I2C2_SMBA, FMC_A2, EVENTOUT	-
-	-	E3	PI12	I/O	FT	-	LCD_HSYNC, EVENTOUT	-
-	-	G3	PI13	I/O	FT	-	LCD_VSYNC, EVENTOUT	-
-	-	H3	PI14	I/O	FT	-	LCD_CLK, EVENTOUT	-
-	13	H2	PF3	I/O	FT	-	FMC_A3, EVENTOUT	ADC3_IN9
-	14	J2	PF4	I/O	FT	-	FMC_A4, EVENTOUT	ADC3_IN14
-	15	K3	PF5	I/O	FT	-	FMC_A5, EVENTOUT	ADC3_IN15
10	16	H6	VSS	S	-	-	-	-
11	17	H5	VDD	S	-	-	-	-
-	18	K2	PF6	I/O	FT	-	TIM10_CH1, SPI5_NSS, SAI1_SD_B, UART7_Rx, QUADSPI_BK1_IO3, EVENTOUT	ADC3_IN4
-	19	K1	PF7	I/O	FT	-	TIM11_CH1, SPI5_SCK, SAI1_MCLK_B, UART7_Tx, QUADSPI_BK1_IO2, EVENTOUT	ADC3_IN5
-	20	L3	PF8	I/O	FT	-	SPI5_MISO, SAI1_SCK_B, UART7_RTS, TIM13_CH1, QUADSPI_BK1_IO0, EVENTOUT	ADC3_IN6
-	21	L2	PF9	I/O	FT	-	SPI5_MOSI, SAI1_FS_B, UART7_CTS, TIM14_CH1, QUADSPI_BK1_IO1, EVENTOUT	ADC3_IN7
-	22	L1	PF10	I/O	FT	-	DCMI_D11, LCD_DE, EVENTOUT	ADC3_IN8
12	23	G1	PH0- OSC_IN(PH0)	I/O	FT	-	EVENTOUT	OSC_IN <sup>(4)</sup>

Table 10. STM32F750x8 pin and ball definition (continued)

Pin Number			Pin name (function after reset) <sup>(1)</sup>	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	TFBGA216						
13	24	H1	PH1- OSC_OUT(PH1)	I/O	FT	-	EVENTOUT	OSC_OUT <sup>(4)</sup>
14	25	J1	NRST	I/O	RS T	-	-	-
15	26	M2	PC0	I/O	FT	<sup>(4)</sup>	SAI2_FS_B, OTG_HS_ULPI_STP, FMC_SDNWE, LCD_R5, EVENTOUT	ADC123_IN10
16	27	M3	PC1	I/O	FT	<sup>(4)</sup>	TRACED0, SPI2_MOSI/I2S2_SD, SAI1_SD_A, ETH_MDC, EVENTOUT	ADC123_IN11, RTC_TAMP3, WKUP3
17	28	M4	PC2	I/O	FT	<sup>(4)</sup>	SPI2_MISO, OTG_HS_ULPI_DIR, ETH_MII_TXD2, FMC_SDNE0, EVENTOUT	ADC123_IN12
18	29	L4	PC3	I/O	FT	<sup>(4)</sup>	SPI2_MOSI/I2S2_SD, OTG_HS_ULPI_NXT, ETH_MII_TX_CLK, FMC_SDCKE0, EVENTOUT	ADC123_IN13
-	30	J5	VDD	S	-	-	-	-
-	-	J6	VSS	S	-	-	-	-
19	31	M1	VSSA	S	-	-	-	-
-	-	N1	VREF-	S	-	-	-	-
20	32	P1	VREF+	S	-	-	-	-
21	33	R1	VDDA	S	-	-	-	-
22	34	N3	PA0-WKUP(PA0)	I/O	FT	<sup>(5)</sup>	TIM2_CH1/TIM2_ETR, TIM5_CH1, TIM8_ETR, USART2_CTS, UART4_TX, SAI2_SD_B, ETH_MII_CRS, EVENTOUT	ADC123_IN0, WKUP1 <sup>(4)</sup>

Table 10. STM32F750x8 pin and ball definition (continued)

Pin Number			Pin name (function after reset) <sup>(1)</sup>	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	TFBGA216						
23	35	N2	PA1	I/O	FT	(4)	TIM2_CH2, TIM5_CH2, USART2_RTS, UART4_RX, QUADSPI_BK1_IO3, SAI2_MCK_B, ETH_MII_RX_CLK/ETH_RMII_REF_CLK , LCD_R2, EVENTOUT	ADC123_IN1
24	36	P2	PA2	I/O	FT	(4)	TIM2_CH3, TIM5_CH3, TIM9_CH1, USART2_TX, SAI2_SCK_B, ETH_MDIO, LCD_R1, EVENTOUT	ADC123_IN2, WKUP2
-	-	K4	PH2	I/O	FT		LPTIM1_IN2, QUADSPI_BK2_IO0, SAI2_SCK_B, ETH_MII_CRIS, FMC_SDCKE0, LCD_R0, EVENTOUT	-
-	-	J4	PH3	I/O	FT	-	QUADSPI_BK2_IO1, SAI2_MCK_B, ETH_MII_COL, FMC_SDNE0, LCD_R1, EVENTOUT	-
-	-	H4	PH4	I/O	FT	-	I2C2_SCL, OTG_HS_ULPI_NXT, EVENTOUT	-
-	-	J3	PH5	I/O	FT	-	I2C2_SDA, SPI5_NSS, FMC_SDNWE, EVENTOUT	-
25	37	R2	PA3	I/O	FT	(4)	TIM2_CH4, TIM5_CH4, TIM9_CH2, USART2_RX, OTG_HS_ULPI_D0, ETH_MII_COL, LCD_B5, EVENTOUT	ADC123_IN3
26	38	K6	VSS	S	-	-	-	-
-	-	L5	BYPASS_REG	I	FT	-	-	-
27	39	K5	VDD	S	-	-	-	-
28	40	N4	PA4	I/O	TTa	(4)	SPI1_NSS/I2S1_WS, SPI3_NSS/I2S3_WS, USART2_CK, OTG_HS_SOF, DCMI_HSYNC, LCD_VSYNC, EVENTOUT	ADC12_IN4, DAC_OUT1
29	41	P4	PA5	I/O	TTa	(4)	TIM2_CH1/TIM2_ETR, TIM8_CH1N, SPI1_SCK/I2S1_CK, OTG_HS_ULPI_CK, LCD_R4, EVENTOUT	ADC12_IN5, DAC_OUT2
30	42	P3	PA6	I/O	FT	(4)	TIM1_BKIN, TIM3_CH1, TIM8_BKIN, SPI1_MISO, TIM13_CH1, DCMI_PIXCLK, LCD_G2, EVENTOUT	ADC12_IN6

Table 10. STM32F750x8 pin and ball definition (continued)

Pin Number			Pin name (function after reset) <sup>(1)</sup>	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	TFBGA216						
31	43	R3	PA7	I/O	FT	(4)	TIM1_CH1N, TIM3_CH2, TIM8_CH1N, SPI1_MOSI/I2S1_SD, TIM14_CH1, ETH_MII_RX_DV/ETH_RMII_CRD_DV, FMC_SDNWE, EVENTOUT	ADC12_IN7
32	44	N5	PC4	I/O	FT	(4)	I2S1_MCK, SPDIFRX_IN2, ETH_MII_RXD0/ETH_RMII_RXD0, FMC_SDNE0, EVENTOUT	ADC12_IN14
33	45	P5	PC5	I/O	FT	(4)	SPDIFRX_IN3, ETH_MII_RXD1/ETH_RMII_RXD1, FMC_SDCKE0, EVENTOUT	ADC12_IN15
-	-	L7	VDD	S	-	-	-	-
-	-	L6	VSS	S	-	-	-	-
34	46	R5	PB0	I/O	FT	(4)	TIM1_CH2N, TIM3_CH3, TIM8_CH2N, UART4_CTS, LCD_R3, OTG_HS_ULPI_D1, ETH_MII_RXD2, EVENTOUT	ADC12_IN8
35	47	R4	PB1	I/O	FT	(4)	TIM1_CH3N, TIM3_CH4, TIM8_CH3N, LCD_R6, OTG_HS_ULPI_D2, ETH_MII_RXD3, EVENTOUT	ADC12_IN9
36	48	M5	PB2	I/O	FT	-	SAI1_SD_A, SPI3_MOSI/I2S3_SD, QUADSPI_CLK, EVENTOUT	-
-	-	G4	PI15	I/O	FT	-	LCD_R0, EVENTOUT	-
-	-	R6	PJ0	I/O	FT	-	LCD_R1, EVENTOUT	-
-	-	R7	PJ1	I/O	FT	-	LCD_R2, EVENTOUT	-
-	-	P7	PJ2	I/O	FT	-	LCD_R3, EVENTOUT	-
-	-	N8	PJ3	I/O	FT	-	LCD_R4, EVENTOUT	-
-	-	M9	PJ4	I/O	FT	-	LCD_R5, EVENTOUT	-
-	49	P8	PF11	I/O	FT	-	SPI5_MOSI, SAI2_SD_B, FMC_SDNRAS, DCMI_D12, EVENTOUT	-
-	50	M6	PF12	I/O	FT	-	FMC_A6, EVENTOUT	-
-	51	K7	VSS	S	-	-	-	-
-	52	L8	VDD	S	-	-	-	-
-	53	N6	PF13	I/O	FT	-	I2C4_SMBA, FMC_A7, EVENTOUT	-

Table 10. STM32F750x8 pin and ball definition (continued)

Pin Number			Pin name (function after reset) <sup>(1)</sup>	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	TFBGA216						
-	54	P6	PF14	I/O	FT	-	I2C4_SCL, FMC_A8, EVENTOUT	-
-	55	M8	PF15	I/O	FT	-	I2C4_SDA, FMC_A9, EVENTOUT	-
-	56	N7	PG0	I/O	FT	-	FMC_A10, EVENTOUT	-
-	57	M7	PG1	I/O	FT	-	FMC_A11, EVENTOUT	-
37	58	R8	PE7	I/O	FT	-	TIM1_ETR, UART7_Rx, QUADSPI_BK2_IO0, FMC_D4, EVENTOUT	-
38	59	N9	PE8	I/O	FT	-	TIM1_CH1N, UART7_Tx, QUADSPI_BK2_IO1, FMC_D5, EVENTOUT	-
39	60	P9	PE9	I/O	FT	-	TIM1_CH1, UART7_RTS, QUADSPI_BK2_IO2, FMC_D6, EVENTOUT	-
-	61	K8	VSS	S	-	-	-	-
-	62	L9	VDD	S	-	-	-	-
40	63	R9	PE10	I/O	FT	-	TIM1_CH2N, UART7_CTS, QUADSPI_BK2_IO3, FMC_D7, EVENTOUT	-
41	64	P10	PE11	I/O	FT	-	TIM1_CH2, SPI4_NSS, SAI2_SD_B, FMC_D8, LCD_G3, EVENTOUT	-
42	65	R10	PE12	I/O	FT	-	TIM1_CH3N, SPI4_SCK, SAI2_SCK_B, FMC_D9, LCD_B4, EVENTOUT	-
43	66	R12	PE13	I/O	FT	-	TIM1_CH3, SPI4_MISO, SAI2_FS_B, FMC_D10, LCD_DE, EVENTOUT	-
44	67	P11	PE14	I/O	FT	-	TIM1_CH4, SPI4_MOSI, SAI2_MCK_B, FMC_D11, LCD_CLK, EVENTOUT	-
45	68	R11	PE15	I/O	FT	-	TIM1_BKIN, FMC_D12, LCD_R7, EVENTOUT	-
46	69	P12	PB10	I/O	FT	-	TIM2_CH3, I2C2_SCL, SPI2_SCK/I2S2_CK, USART3_TX, OTG_HS_ULPI_D3, ETH_MII_RX_ER, LCD_G4, EVENTOUT	-



Table 10. STM32F750x8 pin and ball definition (continued)

Pin Number			Pin name (function after reset) <sup>(1)</sup>	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	TFBGA216						
47	70	R13	PB11	I/O	FT	-	TIM2_CH4, I2C2_SDA, USART3_RX, OTG_HS_ULPI_D4, ETH_MII_TX_EN/ETH_RMII_TX_EN, LCD_G5, EVENTOUT	-
48	71	L11	VCAP_1	S	-	-	-	-
49	-	K9	VSS	S	-	-	-	-
50	72	L10	VDD	S	-	-	-	-
-	-	M1 4	PJ5	I/O	FT	-	LCD_R6, EVENTOUT	-
-	-	P13	PH6	I/O	FT	-	I2C2_SMBA, SPI5_SCK, TIM12_CH1, ETH_MII_RXD2, FMC_SDNE1, DCMI_D8, EVENTOUT	-
-	-	N13	PH7	I/O	FT	-	I2C3_SCL, SPI5_MISO, ETH_MII_RXD3, FMC_SDCKE1, DCMI_D9, EVENTOUT	-
-	-	P14	PH8	I/O	FT	-	I2C3_SDA, FMC_D16, DCMI_HSYNC, LCD_R2, EVENTOUT	-
-	-	N14	PH9	I/O	FT	-	I2C3_SMBA, TIM12_CH2, FMC_D17, DCMI_D0, LCD_R3, EVENTOUT	-
-	-	P15	PH10	I/O	FT	-	TIM5_CH1, I2C4_SMBA, FMC_D18, DCMI_D1, LCD_R4, EVENTOUT	-
-	-	N15	PH11	I/O	FT	-	TIM5_CH2, I2C4_SCL, FMC_D19, DCMI_D2, LCD_R5, EVENTOUT	-
-	-	M1 5	PH12	I/O	FT	-	TIM5_CH3, I2C4_SDA, FMC_D20, DCMI_D3, LCD_R6, EVENTOUT	-
-	-	K10	VSS	S	-	-	-	-
-	-	K11	VDD	S	-	-	-	-
51	73	L13	PB12	I/O	FT	-	TIM1_BKIN, I2C2_SMBA, SPI2_NSS/I2S2_WS, USART3_CK, CAN2_RX, OTG_HS_ULPI_D5, ETH_MII_TXD0/ETH_RMII_TXD0, OTG_HS_ID, EVENTOUT	-

Table 10. STM32F750x8 pin and ball definition (continued)

Pin Number			Pin name (function after reset) <sup>(1)</sup>	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	TFBGA216						
52	74	K14	PB13	I/O	FT	-	TIM1_CH1N, SPI2_SCK/I2S2_CK, USART3_CTS, CAN2_TX, OTG_HS_ULPI_D6, ETH_MII_TXD1/ETH_RMII_TXD1, EVENTOUT	OTG_HS_VBUS
53	75	R14	PB14	I/O	FT	-	TIM1_CH2N, TIM8_CH2N, SPI2_MISO, USART3_RTS, TIM12_CH1, OTG_HS_DM, EVENTOUT	-
54	76	R15	PB15	I/O	FT	-	RTC_REFIN, TIM1_CH3N, TIM8_CH3N, SPI2_MOSI/I2S2_SD, TIM12_CH2, OTG_HS_DP, EVENTOUT	-
55	77	L15	PD8	I/O	FT	-	USART3_TX, SPDIFRX_IN11, FMC_D13, EVENTOUT	-
56	78	L14	PD9	I/O	FT	-	USART3_RX, FMC_D14, EVENTOUT	-
57	79	K15	PD10	I/O	FT	-	USART3_CK, FMC_D15, LCD_B3, EVENTOUT	-
58	80	N10	PD11	I/O	FT	-	I2C4_SMBA, USART3_CTS, QUADSPI_BK1_IO0, SAI2_SD_A, FMC_A16/FMC_CLE, EVENTOUT	-
59	81	M1 0	PD12	I/O	FT	-	TIM4_CH1, LPTIM1_IN1, I2C4_SCL, USART3_RTS, QUADSPI_BK1_IO1, SAI2_FS_A, FMC_A17/FMC_ALE, EVENTOUT	-
60	82	M11	PD13	I/O	FT	-	TIM4_CH2, LPTIM1_OUT, I2C4_SDA, QUADSPI_BK1_IO3, SAI2_SCK_A, FMC_A18, EVENTOUT	-
-	83	J10	VSS	S	-	-	-	-
-	84	J11	VDD	S	-	-	-	-
61	85	L12	PD14	I/O	FT	-	TIM4_CH3, UART8_CTS, FMC_D0, EVENTOUT	-
62	86	K13	PD15	I/O	FT	-	TIM4_CH4, UART8_RTS, FMC_D1, EVENTOUT	-
-	-	K12	PJ6	I/O	FT	-	LCD_R7, EVENTOUT	-
-	-	J12	PJ7	I/O	FT	-	LCD_G0, EVENTOUT	-

Table 10. STM32F750x8 pin and ball definition (continued)

Pin Number			Pin name (function after reset) <sup>(1)</sup>	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	TFBGA216						
-	-	H12	PJ8	I/O	FT	-	LCD_G1, EVENTOUT	-
-	-	J13	PJ9	I/O	FT	-	LCD_G2, EVENTOUT	-
-	-	H13	PJ10	I/O	FT	-	LCD_G3, EVENTOUT	-
-	-	G12	PJ11	I/O	FT	-	LCD_G4, EVENTOUT	-
-	-	H11	VDD	S	-	-	-	-
-	-	H10	VSS	S	-	-	-	-
-	-	G13	PK0	I/O	FT	-	LCD_G5, EVENTOUT	-
-	-	F12	PK1	I/O	FT	-	LCD_G6, EVENTOUT	-
-	-	F13	PK2	I/O	FT	-	LCD_G7, EVENTOUT	-
-	87	M1 3	PG2	I/O	FT	-	FMC_A12, EVENTOUT	-
-	88	M1 2	PG3	I/O	FT	-	FMC_A13, EVENTOUT	-
-	89	N12	PG4	I/O	FT	-	FMC_A14/FMC_BA0, EVENTOUT	-
-	90	N11	PG5	I/O	FT	-	FMC_A15/FMC_BA1, EVENTOUT	-
-	91	J15	PG6	I/O	FT	-	DCMI_D12, LCD_R7, EVENTOUT	-
-	92	J14	PG7	I/O	FT	-	USART6_CK, FMC_INT, DCMI_D13, LCD_CLK, EVENTOUT	-
-	93	H14	PG8	I/O	FT	-	SPI6_NSS, SPDIFRX_IN2, USART6_RTS, ETH_PPS_OUT, FMC_SDCLK, EVENTOUT	-
-	94	G10	VSS	S	-	-	-	-
-	95	G11	VDDUSB	S	-	-	-	-
63	96	H15	PC6	I/O	FT	-	TIM3_CH1, TIM8_CH1, I2S2_MCK, USART6_TX, SDMMC1_D6, DCMI_D0, LCD_HSYNC, EVENTOUT	-
64	97	G15	PC7	I/O	FT	-	TIM3_CH2, TIM8_CH2, I2S3_MCK, USART6_RX, SDMMC1_D7, DCMI_D1, LCD_G6, EVENTOUT	-
65	98	G14	PC8	I/O	FT	-	TRACED1, TIM3_CH3, TIM8_CH3, UART5_RTS, USART6_CK, SDMMC1_D0, DCMI_D2, EVENTOUT	-

Table 10. STM32F750x8 pin and ball definition (continued)

Pin Number			Pin name (function after reset) <sup>(1)</sup>	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	TFBGA216						
66	99	F14	PC9	I/O	FT	-	MCO2, TIM3_CH4, TIM8_CH4, I2C3_SDA, I2S_CKIN, UART5_CTS, QUADSPI_BK1_IO0, SDMMC1_D1, DCMI_D3, EVENTOUT	-
67	100	F15	PA8	I/O	FT	-	MCO1, TIM1_CH1, TIM8_BKIN2, I2C3_SCL, USART1_CK, OTG_FS_SOF, LCD_R6, EVENTOUT	-
68	101	E15	PA9	I/O	FT	-	TIM1_CH2, I2C3_SMBA, SPI2_SCK/I2S2_CK, USART1_TX, DCMI_D0, EVENTOUT	OTG_FS_VBUS
69	102	D15	PA10	I/O	FT	-	TIM1_CH3, USART1_RX, OTG_FS_ID, DCMI_D1, EVENTOUT	-
70	103	C15	PA11	I/O	FT	-	TIM1_CH4, USART1_CTS, CAN1_RX, OTG_FS_DM, LCD_R4, EVENTOUT	-
71	104	B15	PA12	I/O	FT	-	TIM1_ETR, USART1_RTS, SAI2_FS_B, CAN1_TX, OTG_FS_DP, LCD_R5, EVENTOUT	-
72	105	A15	PA13(JTMS- SWDIO)	I/O	FT	-	JTMS-SWDIO, EVENTOUT	-
73	106	E11	VCAP_2	S	-	-	-	-
74	107	F10	VSS	S	-	-	-	-
75	108	F11	VDD	S	-	-	-	-
-	-	E12	PH13	I/O	FT	-	TIM8_CH1N, CAN1_TX, FMC_D21, LCD_G2, EVENTOUT	-
-	-	E13	PH14	I/O	FT	-	TIM8_CH2N, FMC_D22, DCMI_D4, LCD_G3, EVENTOUT	-
-	-	D13	PH15	I/O	FT	-	TIM8_CH3N, FMC_D23, DCMI_D11, LCD_G4, EVENTOUT	-
-	-	E14	PI0	I/O	FT	-	TIM5_CH4, SPI2_NSS/I2S2_WS, FMC_D24, DCMI_D13, LCD_G5, EVENTOUT	-
-	-	D14	PI1	I/O	FT	-	TIM8_BKIN2, SPI2_SCK/I2S2_CK, FMC_D25, DCMI_D8, LCD_G6, EVENTOUT	-

Table 10. STM32F750x8 pin and ball definition (continued)

Pin Number			Pin name (function after reset) <sup>(1)</sup>	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	TFBGA216						
-	-	C14	PI2	I/O	FT	-	TIM8_CH4, SPI2_MISO, FMC_D26, DCMI_D9, LCD_G7, EVENTOUT	-
-	-	C13	PI3	I/O	FT	-	TIM8_ETR, SPI2_MOSI/I2S2_SD, FMC_D27, DCMI_D10, EVENTOUT	-
-	-	F9	VSS	S	-	-	-	-
-	-	E10	VDD	S	-	-	-	-
76	109	A14	PA14(JTCK- SWCLK)	I/O	FT	-	JTCK-SWCLK, EVENTOUT	-
77	110	A13	PA15(JTDI)	I/O	FT	-	JTDI, TIM2_CH1/TIM2_ETR, HDMI-CEC, SPI1_NSS/I2S1_WS, SPI3_NSS/I2S3_WS, UART4_RTS, EVENTOUT	-
78	111	B14	PC10	I/O	FT	-	SPI3_SCK/I2S3_CK, USART3_TX, UART4_TX, QUADSPI_BK1_IO1, SDMMC1_D2, DCMI_D8, LCD_R2, EVENTOUT	-
79	112	B13	PC11	I/O	FT	-	SPI3_MISO, USART3_RX, UART4_RX, QUADSPI_BK2_NCS, SDMMC1_D3, DCMI_D4, EVENTOUT	-
80	113	A12	PC12	I/O	FT	-	TRACED3, SPI3_MOSI/I2S3_SD, USART3_CK, UART5_TX, SDMMC1_CK, DCMI_D9, EVENTOUT	-
81	114	B12	PD0	I/O	FT	-	CAN1_RX, FMC_D2, EVENTOUT	-
82	115	C12	PD1	I/O	FT	-	CAN1_TX, FMC_D3, EVENTOUT	-
83	116	D12	PD2	I/O	FT	-	TRACED2, TIM3_ETR, UART5_RX, SDMMC1_CMD, DCMI_D11, EVENTOUT	-
84	117	C11	PD3	I/O	FT	-	SPI2_SCK/I2S2_CK, USART2_CTS, FMC_CLK, DCMI_D5, LCD_G7, EVENTOUT	-
85	118	D11	PD4	I/O	FT	-	USART2_RTS, FMC_NOE, EVENTOUT	-
86	119	C10	PD5	I/O	FT	-	USART2_TX, FMC_NWE, EVENTOUT	-
-	120	F8	VSS	S	-	-	-	-

Table 10. STM32F750x8 pin and ball definition (continued)

Pin Number			Pin name (function after reset) <sup>(1)</sup>	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	TFBGA216						
-	121	E9	VDD	S	-	-	-	-
87	122	B11	PD6	I/O	FT	-	SPI3_MOSI/I2S3_SD, SAI1_SD_A, USART2_RX, FMC_NWAIT, DCMI_D10, LCD_B2, EVENTOUT	-
88	123	A11	PD7	I/O	FT	-	USART2_CK, SPDIFRX_IN0, FMC_NE1, EVENTOUT	-
-	-	B10	PJ12	I/O	FT	-	LCD_B0, EVENTOUT	-
-	-	B9	PJ13	I/O	FT	-	LCD_B1, EVENTOUT	-
-	-	C9	PJ14	I/O	FT	-	LCD_B2, EVENTOUT	-
-	-	D10	PJ15	I/O	FT	-	LCD_B3, EVENTOUT	-
-	124	D9	PG9	I/O	FT	-	SPDIFRX_IN3, USART6_RX, QUADSPI_BK2_IO2, SAI2_FS_B, FMC_NE2/FMC_NCE, DCMI_VSYNC, EVENTOUT	-
-	125	C8	PG10	I/O	FT	-	LCD_G3, SAI2_SD_B, FMC_NE3, DCMI_D2, LCD_B2, EVENTOUT	-
-	126	B8	PG11	I/O	FT	-	SPDIFRX_IN0, ETH_MII_TX_EN/ETH_RMII_TX_EN, DCMI_D3, LCD_B3, EVENTOUT	-
-	127	C7	PG12	I/O	FT	-	LPTIM1_IN1, SPI6_MISO, SPDIFRX_IN1, USART6_RTS, LCD_B4, FMC_NE4, LCD_B1, EVENTOUT	-
-	128	B3	PG13	I/O	FT	-	TRACED0, LPTIM1_OUT, SPI6_SCK, USART6_CTS, ETH_MII_TXD0/ETH_RMII_TXD0, FMC_A24, LCD_R0, EVENTOUT	-

Table 10. STM32F750x8 pin and ball definition (continued)

Pin Number			Pin name (function after reset) <sup>(1)</sup>	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	TFBGA216						
-	129	A4	PG14	I/O	FT	-	TRACED1, LPTIM1_ETR, SPI6_MOSI, USART6_TX, QUADSPI_BK2_IO3, ETH_MII_TXD1/ETH_RMII_TXD1, FMC_A25, LCD_B0, EVENTOUT	-
-	130	F7	VSS	S	-	-	-	-
-	131	E8	VDD	S	-	-	-	-
-	-	D8	PK3	I/O	FT	-	LCD_B4, EVENTOUT	-
-	-	D7	PK4	I/O	FT	-	LCD_B5, EVENTOUT	-
-	-	C6	PK5	I/O	FT	-	LCD_B6, EVENTOUT	-
-	-	C5	PK6	I/O	FT	-	LCD_B7, EVENTOUT	-
-	-	C4	PK7	I/O	FT	-	LCD_DE, EVENTOUT	-
-	132	B7	PG15	I/O	FT	-	USART6_CTS, FMC_SDNCAS, DCMI_D13, EVENTOUT	-
89	133	A10	PB3(JTDO/TRAC ESWO)	I/O	FT	-	JTDO/TRACESWO, TIM2_CH2, SPI1_SCK/I2S1_CK, SPI3_SCK/I2S3_CK, EVENTOUT	-
90	134	A9	PB4(NJTRST)	I/O	FT	-	NJTRST, TIM3_CH1, SPI1_MISO, SPI3_MISO, SPI2_NSS/I2S2_WS, EVENTOUT	-
91	135	A8	PB5	I/O	FT	-	TIM3_CH2, I2C1_SMBA, SPI1_MOSI/I2S1_SD, SPI3_MOSI/I2S3_SD, CAN2_RX, OTG_HS_ULPI_D7, ETH_PPS_OUT, FMC_SDCKE1, DCMI_D10, EVENTOUT	-
92	136	B6	PB6	I/O	FT	-	TIM4_CH1, HDMI-CEC, I2C1_SCL, USART1_TX, CAN2_TX, QUADSPI_BK1_NCS, FMC_SDNE1, DCMI_D5, EVENTOUT	-

Table 10. STM32F750x8 pin and ball definition (continued)

Pin Number			Pin name (function after reset) <sup>(1)</sup>	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	TFBGA216						
93	137	B5	PB7	I/O	FT	-	TIM4_CH2, I2C1_SDA, USART1_RX, FMC_NL, DCM1_VSYNC, EVENTOUT	-
94	138	E6	BOOT	I	B	-	-	VPP
95	139	A7	PB8	I/O	FT	-	TIM4_CH3, TIM10_CH1, I2C1_SCL, CAN1_RX, ETH_MII_TXD3, SDMMC1_D4, DCM1_D6, LCD_B6, EVENTOUT	-
96	140	B4	PB9	I/O	FT	-	TIM4_CH4, TIM11_CH1, I2C1_SDA, SPI2_NSS/I2S2_WS, CAN1_TX, SDMMC1_D5, DCM1_D7, LCD_B7, EVENTOUT	-
97	141	A6	PE0	I/O	FT	-	TIM4_ETR, LPTIM1_ETR, UART8_Rx, SAI2_MCK_A, FMC_NBL0, DCM1_D2, EVENTOUT	-
98	142	A5	PE1	I/O	FT	-	LPTIM1_IN2, UART8_Tx, FMC_NBL1, DCM1_D3, EVENTOUT	-
99	-	F6	VSS	S	-	-	-	-
-	143	E5	PDR_ON	S	-	-	-	-
100	144	E7	VDD	S	-	-	-	-
-	-	C3	PI4	I/O	FT	-	TIM8_BKIN, SAI2_MCK_A, FMC_NBL2, DCM1_D5, LCD_B4, EVENTOUT	-
-	-	D3	PI5	I/O	FT	-	TIM8_CH1, SAI2_SCK_A, FMC_NBL3, DCM1_VSYNC, LCD_B5, EVENTOUT	-



**Table 10. STM32F750x8 pin and ball definition (continued)**

Pin Number			Pin name (function after reset) <sup>(1)</sup>	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	TFBGA216						
-	-	D6	PI6	I/O	FT	-	TIM8_CH2, SAI2_SD_A, FMC_D28, DCMI_D6, LCD_B6, EVENTOUT	-
-	-	D4	PI7	I/O	FT	-	TIM8_CH3, SAI2_FS_A, FMC_D29, DCMI_D7, LCD_B7, EVENTOUT	-

- Function availability depends on the chosen device.
- PC13, PC14, PC15 and PI8 are supplied through the power switch. Since the switch only sinks a limited amount of current (3 mA), the use of GPIOs PC13 to PC15 and PI8 in output mode is limited:
  - The speed should not exceed 2 MHz with a maximum load of 30 pF.
  - These I/Os must not be used as a current source (e.g. to drive an LED).
- Main function after the first backup domain power-up. Later on, it depends on the contents of the RTC registers even after reset (because these registers are not reset by the main reset). For details on how to manage these I/Os, refer to the RTC register description sections in the STM32F75xxx and STM32F74xxx reference manual.
- FT = 5 V tolerant except when in analog mode or oscillator mode (for PC14, PC15, PH0 and PH1).
- If the device is delivered in a TFBGA216 package, and the BYPASS\_REG pin is set to VDD (Regulator OFF/internal reset ON mode), then PA0 is used as an internal Reset (active low).

Table 11. FMC pin definition

Pin name	NOR/PSRAM/SRAM	NOR/PSRAM Mux	NAND16	SDRAM
PF0	A0	-	-	A0
PF1	A1	-	-	A1
PF2	A2	-	-	A2
PF3	A3	-	-	A3
PF4	A4	-	-	A4
PF5	A5	-	-	A5
PF12	A6	-	-	A6
PF13	A7	-	-	A7
PF14	A8	-	-	A8
PF15	A9	-	-	A9
PG0	A10	-	-	A10
PG1	A11	-	-	A11
PG2	A12	-	-	A12
PG3	A13	-	-	-
PG4	A14	-	-	BA0
PG5	A15	-	-	BA1
PD11	A16	A16	CLE	-
PD12	A17	A17	ALE	-
PD13	A18	A18	-	-
PE3	A19	A19	-	-
PE4	A20	A20	-	-
PE5	A21	A21	-	-
PE6	A22	A22	-	-
PE2	A23	A23	-	-
PG13	A24	A24	-	-
PG14	A25	A25	-	-
PD14	D0	DA0	D0	D0
PD15	D1	DA1	D1	D1
PD0	D2	DA2	D2	D2
PD1	D3	DA3	D3	D3
PE7	D4	DA4	D4	D4
PE8	D5	DA5	D5	D5
PE9	D6	DA6	D6	D6
PE10	D7	DA7	D7	D7

Table 11. FMC pin definition (continued)

Pin name	NOR/PSRAM/SRAM	NOR/PSRAM Mux	NAND16	SDRAM
PE11	D8	DA8	D8	D8
PE12	D9	DA9	D9	D9
PE13	D10	DA10	D10	D10
PE14	D11	DA11	D11	D11
PE15	D12	DA12	D12	D12
PD8	D13	DA13	D13	D13
PD9	D14	DA14	D14	D14
PD10	D15	DA15	D15	D15
PH8	D16	-	-	D16
PH9	D17	-	-	D17
PH10	D18	-	-	D18
PH11	D19	-	-	D19
PH12	D20	-	-	D20
PH13	D21	-	-	D21
PH14	D22	-	-	D22
PH15	D23	-	-	D23
PI0	D24	-	-	D24
PI1	D25	-	-	D25
PI2	D26	-	-	D26
PI3	D27	-	-	D27
PI6	D28	-	-	D28
PI7	D29	-	-	D29
PI9	D30	-	-	D30
PI10	D31	-	-	D31
PD7	NE1	NE1	-	-
PG9	NE2	NE2	NCE	-
PG10	NE3	NE3	-	-
PG11	-	-	-	-
PG12	NE4	NE4	-	-
PD3	CLK	CLK	-	-
PD4	NOE	NOE	NOE	-
PD5	NWE	NWE	NWE	-
PD6	NWAIT	NWAIT	NWAIT	-
PB7	NADV	NADV	-	-

Table 11. FMC pin definition (continued)

Pin name	NOR/PSRAM/SRAM	NOR/PSRAM Mux	NAND16	SDRAM
PF6	-	-	-	-
PF7	-	-	-	-
PF8	-	-	-	-
PF9	-	-	-	-
PF10	-	-	-	-
PG6	-	-	-	-
PG7	-	-	INT	-
PE0	NBL0	NBL0	-	NBL0
PE1	NBL1	NBL1	-	NBL1
PI4	NBL2	-	-	NBL2
PI5	NBL3	-	-	NBL3
PG8	-	-	-	SDCLK
PC0	-	-	-	SDNWE
PF11	-	-	-	SDNRAS
PG15	-	-	-	SDNCAS
PH2	-	-	-	SDCKE0
PH3	-	-	-	SDNE0
PH6	-	-	-	SDNE1
PH7	-	-	-	SDCKE1
PH5	-	-	-	SDNWE
PC2	-	-	-	SDNE0
PC3	-	-	-	SDCKE0
PB5	-	-	-	SDCKE1
PB6	-	-	-	SDNE1



Table 12. STM32F750x8 alternate function mapping

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/11/LPTIM1/CEC	I2C1/2/3/4/CEC	SPI1/2/3/4/5/6	SPI3/SAI1	SPI2/3/USART1/2/3/UART5/SPDIFRX	SAI2/USART6/UART4/5/7/8/SPDIFRX	CAN1/2/TIM12/13/14/QUADSPI/LCD	SAI2/QUADSPI/OTG1_FS	ETH_OTG	
Port A	PA0	-	TIM2_CH1/TIM2_ETR	TIM5_CH1	TIM8_ETR	-	-	-	USART2_CTS	UART4_TX	-	SAI2_SD_B	ETH_C	
	PA1	-	TIM2_CH2	TIM5_CH2	-	-	-	-	USART2_RTS	UART4_RX	QUADSPI_BK1_IO3	SAI2_MC_K_B	ETH_RX_ETH_I_RE_L	
	PA2	-	TIM2_CH3	TIM5_CH3	TIM9_CH1	-	-	-	USART2_TX	SAI2_SC_K_B	-	-	ETH_C	
	PA3	-	TIM2_CH4	TIM5_CH4	TIM9_CH2	-	-	-	USART2_RX	-	-	OTG_HS_ULPI_D0	ETH_C	
	PA4	-	-	-	-	-	-	SPI1_NSS/12S1_WS	SPI3_NSS/12S3_WS	USART2_CK	-	-	-	
	PA5	-	TIM2_CH1/TIM2_ETR	-	TIM8_CH1N	-	-	SPI1_SCK/12S1_CK	-	-	-	-	OTG_HS_ULPI_CK	-
	PA6	-	TIM1_BKIN	TIM3_CH1	TIM8_BK1N	-	-	SPI1_MISO	-	-	-	TIM13_CH1	-	-
	PA7	-	TIM1_CH1N	TIM3_CH2	TIM8_CH1N	-	-	SPI1_MOSI/12S1_SD	-	-	-	TIM14_CH1	-	ETH_RX_ETH_I_TH_F_CRS
	PA8	MCO1	TIM1_CH1	-	TIM8_BK1N2	I2C3_SCL	-	-	-	USART1_CK	-	-	OTG_FS_SOF	-
	PA9	-	TIM1_CH2	-	-	I2C3_SMBA	SPI2_SCK/12S2_CK	-	-	USART1_TX	-	-	-	-
	PA10	-	TIM1_CH3	-	-	-	-	-	-	USART1_RX	-	-	OTG_FS_ID	-
	PA11	-	TIM1_CH4	-	-	-	-	-	-	USART1_CTS	-	CAN1_RX	OTG_FS_DM	-

Table 12. STM32F750x8 alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/ 11/LPTIM 1/CEC	I2C1/2/3/ 4/CEC	SPI1/2/3/ 4/5/6	SPI3/ SAI1	SPI2/3/U SART1/2/ 3/UART5/ SPDIFRX	SAI2/US ART6/UA RT4/5/7/8 /SPDIFR X	CAN1/2/T IM12/13/ 14/QUAD SPI/LCD	SAI2/QU ADSPI/O TG2_HS/ OTG1_FS	ET OTG
Port A	PA12	-	TIM1_ET R	-	-	-	-	-	USART1 _RTS	SAI2_FS _B	CAN1_T X	OTG_FS_ DP	-
	PA13	JTMS- SWDIO	-	-	-	-	-	-	-	-	-	-	-
	PA14	JTCK- SWCLK	-	-	-	-	-	-	-	-	-	-	-
	PA15	JTDI	TIM2_C H1/TIM2 _ETR	-	-	HDMI- CEC	SPI1_NS S/12S1_ WS	SPI3_NS S/12S3_ WS	-	UART4_ RTS	-	-	-
Port B	PB0	-	TIM1_C H2N	TIM3_C H3	TIM8_CH 2N	-	-	-	-	UART4_ CTS	LCD_R3	OTG_HS_ ULPI_D1	ETH_ RX
	PB1	-	TIM1_C H3N	TIM3_C H4	TIM8_CH 3N	-	-	-	-	-	LCD_R6	OTG_HS_ ULPI_D2	ETH_ RX
	PB2	-	-	-	-	-	-	SAI1_SD _A	SPI3_MO S/12S3_ SD	-	QUADSP I_CLK	-	-
	PB3	JTDO/T RACES WO	TIM2_C H2	-	-	-	SPI1_SC K/12S1_ CK	SPI3_SC K/12S3_ CK	-	-	-	-	-
	PB4	NJTRST	-	TIM3_C H1	-	-	SPI1_MI SO	SPI3_MI SO	SPI2_NS S/12S2_ WS	-	-	-	-
	PB5	-	-	TIM3_C H2	-	I2C1_SM BA	SPI1_M OSI/12S1 _SD	SPI3_M OSI/12S3 _SD	-	-	CAN2_R X	OTG_HS_ ULPI_D7	ETH_ _O
	PB6	-	-	TIM4_C H1	HDMI- CEC	I2C1_SC L	-	-	USART1 _TX	-	CAN2_T X	QUADSPI _BK1_NC S	-
	PB7	-	-	TIM4_C H2	-	I2C1_SD A	-	-	USART1 _RX	-	-	-	-
	PB8	-	-	TIM4_C H3	TIM10_C H1	I2C1_SC L	-	-	-	-	CAN1_R X	-	ETH_ TX



**Table 12. STM32F750x8 alternate function mapping (continued)**

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/11/LPTIM1/CEC	I2C1/2/3/4/CEC	SPI1/2/3/4/5/6	SPI3/SAI1	SPI2/3/USART1/2/3/UART5/SPDIFRX	SAI2/USART6/UART4/5/7/8/SPDIFRX	CAN1/2/TIM12/13/14/QUADSPI/LCD	SAI2/QUADSPI/OTG1_FS	ETH_OTG
Port B	PB9	-	-	TIM4_CH4	TIM11_CH1	I2C1_SDA	SPI2_NSS/I2S2_WS	-	-	-	CAN1_TX	-	-
	PB10	-	TIM2_CH3	-	-	I2C2_SCL	SPI2_SCK/I2S2_CK	-	USART3_TX	-	-	OTG_HS_ULPI_D3	ETH_RX
	PB11	-	TIM2_CH4	-	-	I2C2_SDA	-	-	USART3_RX	-	-	OTG_HS_ULPI_D4	ETH_TX_ETH_FTH_FTH_TX
	PB12	-	TIM1_BKIN	-	-	I2C2_SMBA	SPI2_NSS/I2S2_WS	-	USART3_CK	-	CAN2_RX	OTG_HS_ULPI_D5	ETH_TXD_ETH_RN_ETH_XD
	PB13	-	TIM1_CH1N	-	-	-	SPI2_SCK/I2S2_CK	-	USART3_CTS	-	CAN2_TX	OTG_HS_ULPI_D6	ETH_TXD_ETH_RN_ETH_XD
	PB14	-	TIM1_CH2N	-	TIM8_CH2N	-	SPI2_MISO	-	USART3_RTS	-	TIM12_CH1	-	-
	PB15	RTC_REFIN	TIM1_CH3N	-	TIM8_CH3N	-	SPI2_MOSI/I2S2_SD	-	-	-	TIM12_CH2	-	-
Port C	PC0	-	-	-	-	-	-	-	-	SAI2_FS_B	-	OTG_HS_ULPI_STP	-
	PC1	TRACE_D0	-	-	-	-	SPI2_MOSI/I2S2_SD	SAI1_SDA	-	-	-	-	ETH_C
	PC2	-	-	-	-	-	SPI2_MISO	-	-	-	-	OTG_HS_ULPI_DIR	ETH_TX
	PC3	-	-	-	-	-	SPI2_MOSI/I2S2_SD	-	-	-	-	OTG_HS_ULPI_NXT	ETH_TX

Table 12. STM32F750x8 alternate function mapping (continued)

Port	AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	
	SYS	TIM1/2	TIM3/4/5	TIM8/9/10/ 11/LPTIM 1/CEC	I2C1/2/3/ 4/CEC	SPI1/2/3/ 4/5/6	SPI3/ SAI1	SPI2/3/U SART1/2/ 3/UART5/ SPDIFRX	SAI2/US ART6/UA RT4/5/7/8 /SPDIFR X	CAN1/2/T IM12/13/ 14/QUAD SPI/LCD	SAI2/QU ADSPI/O TG2_HS/ OTG1_FS	ETH OTG	
Port C	PC4	-	-	-	-	-	I2S1_M CK	-	-	SPDIFRX _IN2	-	-	ETH_ RXD H_R RX
	PC5	-	-	-	-	-	-	-	-	SPDIFRX _IN3	-	-	ETH_ RXD H_R RX
	PC6	-	-	TIM3_C H1	TIM8_CH 1	-	I2S2_M CK	-	-	USART6 _TX	-	-	-
	PC7	-	-	TIM3_C H2	TIM8_CH 2	-	-	I2S3_M CK	-	USART6 _RX	-	-	-
	PC8	TRACE D1	-	TIM3_C H3	TIM8_CH 3	-	-	-	UART5_ RTS	USART6 _CK	-	-	-
	PC9	MCO2	-	TIM3_C H4	TIM8_CH 4	I2C3_SD A	I2S_CK1 N	-	UART5_ CTS	-	QUADSP I_BK1_IO 0	-	-
	PC10	-	-	-	-	-	-	SPI3_SC K/I2S3_ CK	USART3 _TX	UART4_T X	QUADSP I_BK1_IO 1	-	-
	PC11	-	-	-	-	-	-	SPI3_MI SO	USART3 _RX	UART4_ RX	QUADSP I_BK2_N CS	-	-
	PC12	TRACE D3	-	-	-	-	-	SPI3_M OSI/I2S3 _SD	USART3 _CK	UART5_T X	-	-	-
	PC13	-	-	-	-	-	-	-	-	-	-	-	-
	PC14	-	-	-	-	-	-	-	-	-	-	-	-
	PC15	-	-	-	-	-	-	-	-	-	-	-	-





**Table 12. STM32F750x8 alternate function mapping (continued)**

Port	AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	
	SYS	TIM1/2	TIM3/4/5	TIM8/9/10/11/LPTIM1/CEC	I2C1/2/3/4/CEC	SPI1/2/3/4/5/6	SPI3/SAI1	SPI2/3/USART1/2/3/UART5/SPDIFRX	SAI2/USART6/UART4/5/7/8/SPDIFRX	CAN1/2/TIM12/13/14/QUADSPI/LCD	SAI2/QUADSPI/OTG1_FS	ETB/OTG2_FS	
Port D	PD0	-	-	-	-	-	-	-	-	-	CAN1_RX	-	
	PD1	-	-	-	-	-	-	-	-	-	CAN1_TX	-	
	PD2	TRACED2	-	TIM3_ETR	-	-	-	-	-	UART5_RX	-	-	
	PD3	-	-	-	-	-	SPI2_SCK/I2S2_CK	-	USART2_CTS	-	-	-	
	PD4	-	-	-	-	-	-	-	USART2_RTS	-	-	-	
	PD5	-	-	-	-	-	-	-	USART2_TX	-	-	-	
	PD6	-	-	-	-	-	SPI3_MOSI/I2S3_SD	SAI1_SDA	USART2_RX	-	-	-	-
	PD7	-	-	-	-	-	-	-	USART2_CK	SPDIFRX_IN0	-	-	-
	PD8	-	-	-	-	-	-	-	USART3_TX	SPDIFRX_IN1	-	-	-
	PD9	-	-	-	-	-	-	-	USART3_RX	-	-	-	-
	PD10	-	-	-	-	-	-	-	USART3_CK	-	-	-	-
	PD11	-	-	-	-	I2C4_SMBA	-	-	USART3_CTS	-	QUADSPI_BK1_IO0	SAI2_SDA	-
	PD12	-	-	TIM4_CH1	LPTIM1_IN1	I2C4_SCL	-	-	USART3_RTS	-	QUADSPI_BK1_IO1	SAI2_FSA	-
	PD13	-	-	TIM4_CH2	LPTIM1_OUT	I2C4_SDA	-	-	-	-	QUADSPI_BK1_IO3	SAI2_SCK_A	-

Table 12. STM32F750x8 alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/ 11/LPTIM 1/CEC	I2C1/2/3/ 4/CEC	SPI1/2/3/ 4/5/6	SPI3/ SAI1	SPI2/3/U SART1/2/ 3/UART5/ SPDIFRX	SAI2/US ART6/UA RT4/5/7/8 /SPDIFR X	CAN1/2/T IM12/13/ 14/QUAD SPI/LCD	SAI2/QU ADSPI/O TG2_HS/ OTG1_FS	ET OTG
Port D	PD14	-	-	TIM4_C H3	-	-	-	-	-	UART8_ CTS	-	-	-
	PD15	-	-	TIM4_C H4	-	-	-	-	-	UART8_ RTS	-	-	-
Port E	PE0	-	-	TIM4_ET R	LPTIM1_E TR	-	-	-	-	UART8_ Rx	-	SAI2_MC K_A	-
	PE1	-	-	-	LPTIM1_I N2	-	-	-	-	UART8_T x	-	-	-
	PE2	TRACE CLK	-	-	-	-	SPI4_SC K	SAI1_M CLK_A	-	-	QUADSP I_BK1_IO 2	-	ETH_ TX
	PE3	TRACE D0	-	-	-	-	-	SAI1_SD _B	-	-	-	-	-
	PE4	TRACE D1	-	-	-	-	SPI4_NS S	SAI1_FS _A	-	-	-	-	-
	PE5	TRACE D2	-	-	TIM9_CH 1	-	SPI4_MI SO	SAI1_SC K_A	-	-	-	-	-
	PE6	TRACE D3	TIM1_B KIN2	-	TIM9_CH 2	-	SPI4_M OSI	SAI1_SD _A	-	-	-	SAI2_MC K_B	-
	PE7	-	TIM1_ET R	-	-	-	-	-	-	UART7_ Rx	-	QUADSPI _BK2_IO0	-
	PE8	-	TIM1_C H1N	-	-	-	-	-	-	UART7_T x	-	QUADSPI _BK2_IO1	-
	PE9	-	TIM1_C H1	-	-	-	-	-	-	UART7_ RTS	-	QUADSPI _BK2_IO2	-
	PE10	-	TIM1_C H2N	-	-	-	-	-	-	UART7_ CTS	-	QUADSPI _BK2_IO3	-
	PE11	-	TIM1_C H2	-	-	-	SPI4_NS S	-	-	-	-	SAI2_SD_ B	-
	PE12	-	TIM1_C H3N	-	-	-	SPI4_SC K	-	-	-	-	SAI2_SC K_B	-
	PE13	-	TIM1_C H3	-	-	-	SPI4_MI SO	-	-	-	-	SAI2_FS_ B	-



**Table 12. STM32F750x8 alternate function mapping (continued)**

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/ 11/LPTIM 1/CEC	I2C1/2/3/ 4/CEC	SPI1/2/3/ 4/5/6	SPI3/ SAI1	SPI2/3/U SART1/2/ 3/UART5/ SPDIFRX	SAI2/US ART6/UA RT4/5/7/8 /SPDIFR X	CAN1/2/T IM12/13/ 14/QUAD SPI/LCD	SAI2/QU ADSPI/O TG2_HS/ OTG1_FS	ET OTG
Port E	PE14	-	TIM1_C H4	-	-	-	SPI4_M OSI	-	-	-	-	SAI2_MC K_B	-
	PE15	-	TIM1_B KIN	-	-	-	-	-	-	-	-	-	-
Port F	PF0	-	-	-	-	I2C2_SD A	-	-	-	-	-	-	-
	PF1	-	-	-	-	I2C2_SC L	-	-	-	-	-	-	-
	PF2	-	-	-	-	I2C2_SM BA	-	-	-	-	-	-	-
	PF3	-	-	-	-	-	-	-	-	-	-	-	-
	PF4	-	-	-	-	-	-	-	-	-	-	-	-
	PF5	-	-	-	-	-	-	-	-	-	-	-	-
	PF6	-	-	-	TIM10_C H1	-	SPI5_NS S	SAI1_SD _B	-	UART7_ Rx	QUADSP I_BK1_IO 3	-	-
	PF7	-	-	-	TIM11_CH 1	-	SPI5_SC K	SAI1_M CLK_B	-	UART7_T x	QUADSP I_BK1_IO 2	-	-
	PF8	-	-	-	-	-	SPI5_MI SO	SAI1_SC K_B	-	UART7_ RTS	TIM13_C H1	QUADSPI _BK1_IO0	-
	PF9	-	-	-	-	-	SPI5_M OSI	SAI1_FS _B	-	UART7_ CTS	TIM14_C H1	QUADSPI _BK1_IO1	-
	PF10	-	-	-	-	-	-	-	-	-	-	-	-
	PF11	-	-	-	-	-	SPI5_M OSI	-	-	-	-	-	SAI2_SD_ B
PF12	-	-	-	-	-	-	-	-	-	-	-	-	

Table 12. STM32F750x8 alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/ 11/LPTIM 1/CEC	I2C1/2/3/ 4/CEC	SPI1/2/3/ 4/5/6	SPI3/ SAI1	SPI2/3/U SART1/2/ 3/UART5/ SPDIFRX	SAI2/US ART6/UA RT4/5/7/8 /SPDIFR X	CAN1/2/T IM12/13/ 14/QUAD SPI/LCD	SAI2/QU ADSPI/O TG2_HS/ OTG1_FS	ET OTG	
Port F	PF13	-	-	-	-	I2C4_SM BA	-	-	-	-	-	-	-	
	PF14	-	-	-	-	I2C4_SC L	-	-	-	-	-	-	-	
	PF15	-	-	-	-	I2C4_SD A	-	-	-	-	-	-	-	
Port G	PG0	-	-	-	-	-	-	-	-	-	-	-	-	
	PG1	-	-	-	-	-	-	-	-	-	-	-	-	
	PG2	-	-	-	-	-	-	-	-	-	-	-	-	
	PG3	-	-	-	-	-	-	-	-	-	-	-	-	
	PG4	-	-	-	-	-	-	-	-	-	-	-	-	
	PG5	-	-	-	-	-	-	-	-	-	-	-	-	
	PG6	-	-	-	-	-	-	-	-	-	-	-	-	
	PG7	-	-	-	-	-	-	-	-	USART6 _CK	-	-	-	-
	PG8	-	-	-	-	-	SPI6_NS S	-	SPDIFRX _IN2	USART6 _RTS	-	-	-	ETH_ _O
	PG9	-	-	-	-	-	-	-	SPDIFRX _IN3	USART6 _RX	QUADSP I_BK2_IO 2	SAI2_FS_ B	-	-
	PG10	-	-	-	-	-	-	-	-	-	LCD_G3	SAI2_SD_ B	-	-



**Table 12. STM32F750x8 alternate function mapping (continued)**

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/11/LPTIM1/CEC	I2C1/2/3/4/CEC	SPI1/2/3/4/5/6	SPI3/SAI1	SPI2/3/USART1/2/3/UART5/SPDIFRX	SAI2/USART6/UART4/5/7/8/SPDIFRX	CAN1/2/TIM12/13/14/QUADSPI/LCD	SAI2/QUADSPI/OTG1_FS	ETH_OTG1_FS	
Port G	PG11	-	-	-	-	-	-	-	SPDIFRX_IN0	-	-	-	ETH_TX_ETH_TX_ETH_TX	
	PG12	-	-	-	LPTIM1_IN1	-	SPI6_MISO	-	SPDIFRX_IN1	USART6_RTS	LCD_B4	-	-	
	PG13	TRACE_D0	-	-	LPTIM1_OUT	-	SPI6_SCK	-	-	USART6_CTS	-	-	ETH_TXD_ETH_RXD_ETH_TXD	
	PG14	TRACE_D1	-	-	LPTIM1_ETR	-	SPI6_MOSI	-	-	USART6_TX	QUADSPI_BK2_IO3	-	ETH_TXD_ETH_RXD_ETH_TXD	
	PG15	-	-	-	-	-	-	-	-	USART6_CTS	-	-	-	
Port H	PH0	-	-	-	-	-	-	-	-	-	-	-	-	
	PH1	-	-	-	-	-	-	-	-	-	-	-	-	
	PH2	-	-	-	LPTIM1_IN2	-	-	-	-	-	QUADSPI_BK2_IO0	SAI2_SCK_B	ETH_CK_ETH_CK	
	PH3	-	-	-	-	-	-	-	-	-	QUADSPI_BK2_IO1	SAI2_MCK_B	ETH_CK_ETH_CK	
	PH4	-	-	-	-	I2C2_SCL	-	-	-	-	-	OTG_HS_ULPI_NXT	-	
	PH5	-	-	-	-	I2C2_SDA	SPI5_NSS	-	-	-	-	-	-	-
	PH6	-	-	-	-	I2C2_SMBAL	SPI5_SCK	-	-	-	-	TIM12_CH1	-	ETH_RX_ETH_RX
	PH7	-	-	-	-	I2C3_SCL	SPI5_MISO	-	-	-	-	-	-	ETH_RX_ETH_RX



Table 12. STM32F750x8 alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/ 11/LPTIM 1/CEC	I2C1/2/3/ 4/CEC	SPI1/2/3/ 4/5/6	SPI3/ SAI1	SPI2/3/U SART1/2/ 3/UART5/ SPDIFRX	SAI2/US ART6/UA RT4/5/7/8 /SPDIFR X	CAN1/2/T IM12/13/ 14/QUAD SPI/LCD	SAI2/QU ADSPI/O TG2_HS/ OTG1_FS	ET OTG
Port H	PH8	-	-	-	-	I2C3_SD A	-	-	-	-	-	-	-
	PH9	-	-	-	-	I2C3_SM BA	-	-	-	-	TIM12_C H2	-	-
	PH10	-	-	TIM5_C H1	-	I2C4_SM BA	-	-	-	-	-	-	-
	PH11	-	-	TIM5_C H2	-	I2C4_SC L	-	-	-	-	-	-	-
	PH12	-	-	TIM5_C H3	-	I2C4_SD A	-	-	-	-	-	-	-
	PH13	-	-	-	TIM8_CH 1N	-	-	-	-	-	-	CAN1_T X	-
	PH14	-	-	-	TIM8_CH 2N	-	-	-	-	-	-	-	-
PH15	-	-	-	TIM8_CH 3N	-	-	-	-	-	-	-	-	
Port I	PI0	-	-	TIM5_C H4	-	-	SPI2_NS S/I2S2_ WS	-	-	-	-	-	-
	PI1	-	-	-	TIM8_BKI N2	-	SPI2_SC K/I2S2_ CK	-	-	-	-	-	-
	PI2	-	-	-	TIM8_CH 4	-	SPI2_MI SO	-	-	-	-	-	-
	PI3	-	-	-	TIM8_ET R	-	SPI2_M OSI/I2S2_ _SD	-	-	-	-	-	-
	PI4	-	-	-	TIM8_BKI N	-	-	-	-	-	-	SAI2_MC K_A	-
	PI5	-	-	-	TIM8_CH 1	-	-	-	-	-	-	SAI2_SC K_A	-
	PI6	-	-	-	TIM8_CH 2	-	-	-	-	-	-	SAI2_SD_ A	-



**Table 12. STM32F750x8 alternate function mapping (continued)**

Port	AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11
	SYS	TIM1/2	TIM3/4/5	TIM8/9/10/ 11/LPTIM 1/CEC	I2C1/2/3/ 4/CEC	SPI1/2/3/ 4/5/6	SPI3/ SAI1	SPI2/3/U SART1/2/ 3/UART5/ SPDIFRX	SAI2/US ART6/UA RT4/5/7/8 /SPDIFR X	CAN1/2/T IM12/13/ 14/QUAD SPI/LCD	SAI2/QU ADSPI/O TG2_HS/ OTG1_FS	ETH OTG
Port I	PI7	-	-	-	TIM8_CH 3	-	-	-	-	-	-	SAI2_FS_ A
	PI8	-	-	-	-	-	-	-	-	-	-	-
	PI9	-	-	-	-	-	-	-	-	-	CAN1_R X	-
	PI10	-	-	-	-	-	-	-	-	-	-	ETH_ RX_
	PI11	-	-	-	-	-	-	-	-	-	-	OTG_HS_ ULPI_DIR
	PI12	-	-	-	-	-	-	-	-	-	-	-
	PI13	-	-	-	-	-	-	-	-	-	-	-
	PI14	-	-	-	-	-	-	-	-	-	-	-
	PI15	-	-	-	-	-	-	-	-	-	-	-
Port J	PJ0	-	-	-	-	-	-	-	-	-	-	-
	PJ1	-	-	-	-	-	-	-	-	-	-	-
	PJ2	-	-	-	-	-	-	-	-	-	-	-
	PJ3	-	-	-	-	-	-	-	-	-	-	-
	PJ4	-	-	-	-	-	-	-	-	-	-	-
	PJ5	-	-	-	-	-	-	-	-	-	-	-
	PJ6	-	-	-	-	-	-	-	-	-	-	-

Table 12. STM32F750x8 alternate function mapping (continued)

Port	AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11
	SYS	TIM1/2	TIM3/4/5	TIM8/9/10/ 11/LPTIM 1/CEC	I2C1/2/3/ 4/CEC	SPI1/2/3/ 4/5/6	SPI3/ SAI1	SPI2/3/U SART1/2/ 3/UART5/ SPDIFRX	SAI2/US ART6/UA RT4/5/7/8 /SPDIFR X	CAN1/2/T IM12/13/ 14/QUAD SPI/LCD	SAI2/QU ADSPI/O TG2_HS/ OTG1_FS	ET OTG
Port J	PJ7	-	-	-	-	-	-	-	-	-	-	-
	PJ8	-	-	-	-	-	-	-	-	-	-	-
	PJ9	-	-	-	-	-	-	-	-	-	-	-
	PJ10	-	-	-	-	-	-	-	-	-	-	-
	PJ11	-	-	-	-	-	-	-	-	-	-	-
	PJ12	-	-	-	-	-	-	-	-	-	-	-
	PJ13	-	-	-	-	-	-	-	-	-	-	-
	PJ14	-	-	-	-	-	-	-	-	-	-	-
PJ15	-	-	-	-	-	-	-	-	-	-	-	





**Table 12. STM32F750x8 alternate function mapping (continued)**

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/ 11/LPTIM 1/CEC	I2C1/2/3/ 4/CEC	SPI1/2/3/ 4/5/6	SPI3/ SAI1	SPI2/3/U SART1/2/ 3/UART5/ SPDIFRX	SAI2/US ART6/UA RT4/5/7/8 /SPDIFR X	CAN1/2/T IM12/13/ 14/QUAD SPI/LCD	SAI2/QU ADSPI/O TG2_HS/ OTG1_FS	ET OTG
Port K	PK0	-	-	-	-	-	-	-	-	-	-	-	-
	PK1	-	-	-	-	-	-	-	-	-	-	-	-
	PK2	-	-	-	-	-	-	-	-	-	-	-	-
	PK3	-	-	-	-	-	-	-	-	-	-	-	-
	PK4	-	-	-	-	-	-	-	-	-	-	-	-
	PK5	-	-	-	-	-	-	-	-	-	-	-	-
	PK6	-	-	-	-	-	-	-	-	-	-	-	-
	PK7	-	-	-	-	-	-	-	-	-	-	-	-

## 5 Memory mapping

Refer to the product line reference manual for details on the memory mapping as well as the boundary addresses for all peripherals.

## 6 Electrical characteristics

### 6.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to  $V_{SS}$ .

#### 6.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at  $T_A = 25\text{ }^\circ\text{C}$  and  $T_A = T_{Amax}$  (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation ( $\text{mean} \pm 3\sigma$ ).

#### 6.1.2 Typical values

Unless otherwise specified, typical data are based on  $T_A = 25\text{ }^\circ\text{C}$ ,  $V_{DD} = 3.3\text{ V}$  (for the  $1.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$  voltage range). They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated ( $\text{mean} \pm 2\sigma$ ).

#### 6.1.3 Typical curves

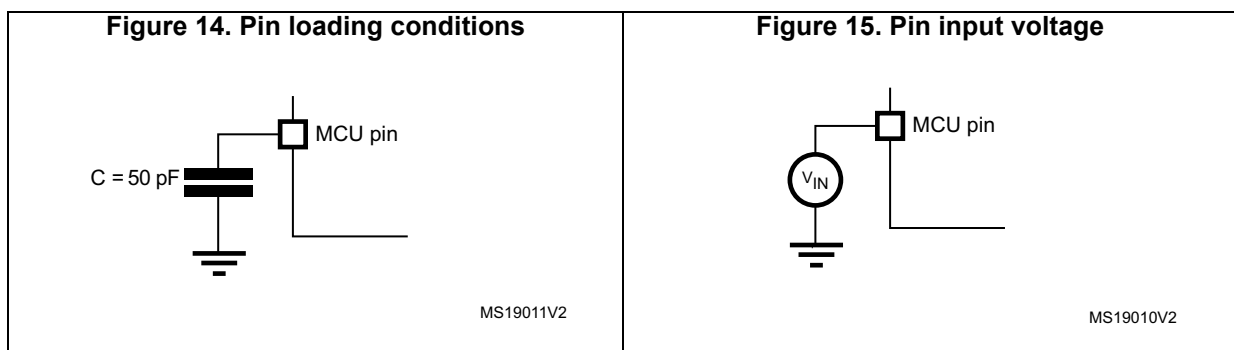
Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

#### 6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in [Figure 14](#).

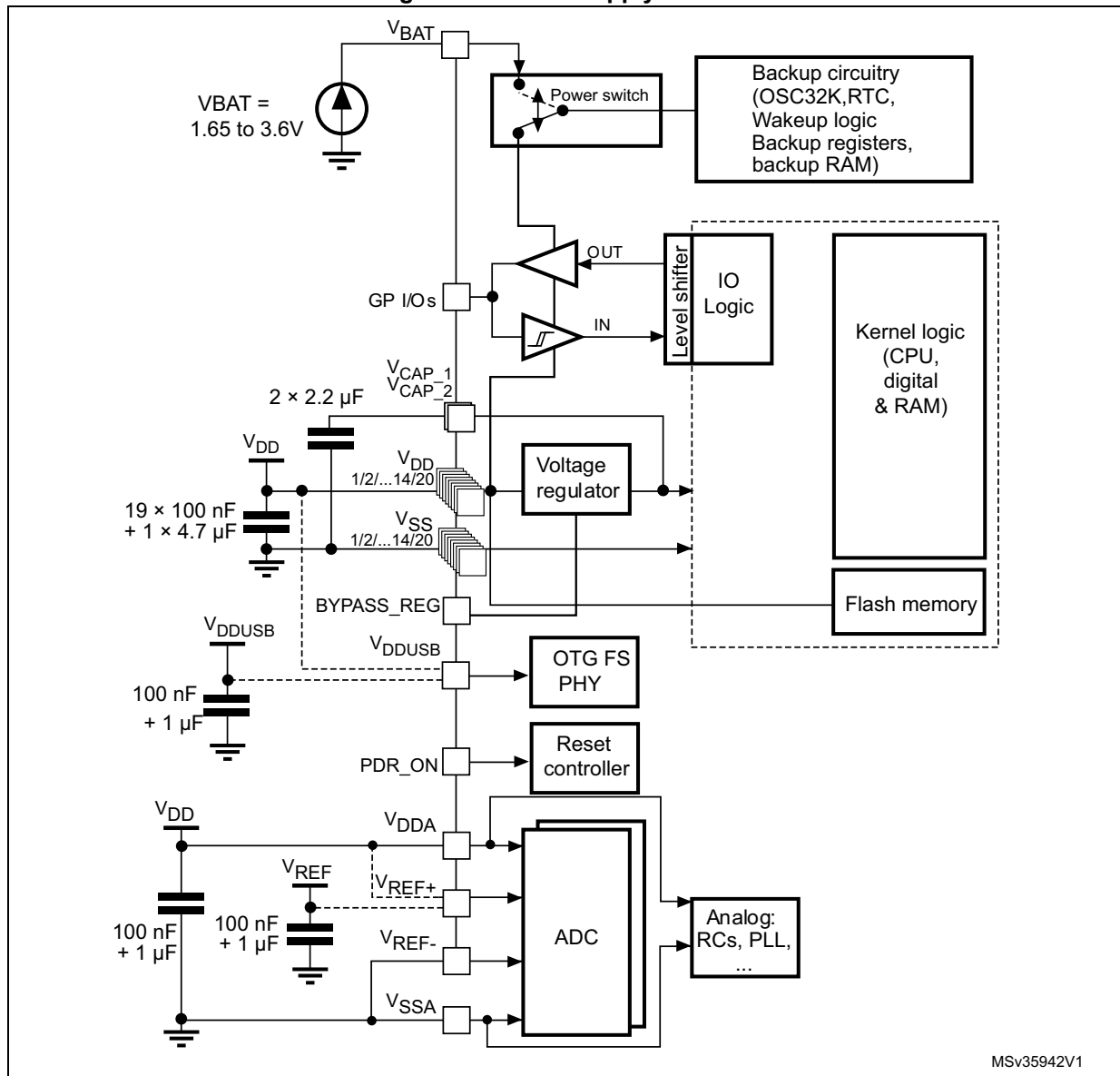
#### 6.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in [Figure 15](#).



6.1.6 Power supply scheme

Figure 16. Power supply scheme

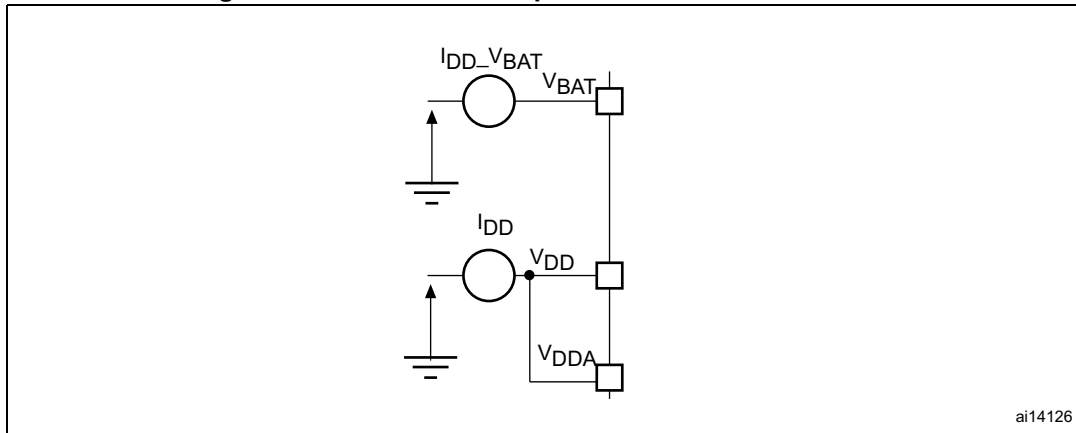


1. To connect BYPASS\_REG and PDR\_ON pins, refer to [Section 3.17: Power supply supervisor](#) and [Section 3.18: Voltage regulator](#)
2. The two 2.2 μF ceramic capacitors should be replaced by two 100 nF decoupling capacitors when the voltage regulator is OFF.
3. The 4.7 μF ceramic capacitor must be connected to one of the V<sub>DD</sub> pin.
4. V<sub>DDA</sub>=V<sub>DD</sub> and V<sub>SSA</sub>=V<sub>SS</sub>.

**Caution:** Each power supply pair (V<sub>DD</sub>/V<sub>SS</sub>, V<sub>DDA</sub>/V<sub>SSA</sub> ...) must be decoupled with filtering ceramic capacitors as shown above. These capacitors must be placed as close as possible to, or below, the appropriate pins on the underside of the PCB to ensure good operation of the device. It is not recommended to remove filtering capacitors to reduce PCB size or cost. This might cause incorrect operation of the device.

### 6.1.7 Current consumption measurement

Figure 17. Current consumption measurement scheme



## 6.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in [Table 13: Voltage characteristics](#), [Table 14: Current characteristics](#), and [Table 15: Thermal characteristics](#) may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Table 13. Voltage characteristics

Symbol	Ratings	Min	Max	Unit
$V_{DD-VSS}$	External main supply voltage (including $V_{DDA}$ , $V_{DD}$ , $V_{BAT}$ and $V_{DDUSB}$ ) <sup>(1)</sup>	- 0.3	4.0	V
$V_{IN}$	Input voltage on FT pins <sup>(2)</sup>	$V_{SS} - 0.3$	$V_{DD} + 4.0$	
	Input voltage on TTa pins	$V_{SS} - 0.3$	4.0	
	Input voltage on any other pin	$V_{SS} - 0.3$	4.0	
	Input voltage on BOOT pin	$V_{SS}$	9.0	
$ \Delta V_{DDx} $	Variations between different $V_{DD}$ power pins	-	50	mV
$ V_{SSx} - V_{SS} $	Variations between all the different ground pins <sup>(3)</sup>	-	50	
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	see <a href="#">Section 6.3.15: Absolute maximum ratings (electrical sensitivity)</a>		-

1. All main power ( $V_{DD}$ ,  $V_{DDA}$ ,  $V_{DDUSB}$ ) and ground ( $V_{SS}$ ,  $V_{SSA}$ ) pins must always be connected to the external power supply, in the permitted range.
2.  $V_{IN}$  maximum value must always be respected. Refer to [Table 14](#) for the values of the maximum allowed injected current.
3. Include VREF- pin.

**Table 14. Current characteristics**

Symbol	Ratings	Max.	Unit
$\Sigma I_{VDD}$	Total current into sum of all $V_{DD\_x}$ power lines (source) <sup>(1)</sup>	320	mA
$\Sigma I_{VSS}$	Total current out of sum of all $V_{SS\_x}$ ground lines (sink) <sup>(1)</sup>	- 320	
$\Sigma I_{VDDUSB}$	Total current into $V_{DDUSB}$ power line (source)	25	
$I_{VDD}$	Maximum current into each $V_{DD\_x}$ power line (source) <sup>(1)</sup>	100	
$I_{VSS}$	Maximum current out of each $V_{SS\_x}$ ground line (sink) <sup>(1)</sup>	- 100	
$I_{IO}$	Output current sunk by any I/O and control pin	25	
	Output current sourced by any I/Os and control pin	- 25	
$\Sigma I_{IO}$	Total output current sunk by sum of all I/O and control pins <sup>(2)</sup>	120	
	Total output current sunk by sum of all USB I/Os	25	
	Total output current sourced by sum of all I/Os and control pins <sup>(2)</sup>	- 120	
$I_{INJ(PIN)}$	Injected current on FT, FTf, RST and B pins <sup>(3)</sup>	- 5/+0	
	Injected current on TTA pins <sup>(4)</sup>	±5	
$\Sigma I_{INJ(PIN)}$ <sup>(4)</sup>	Total injected current (sum of all I/O and control pins) <sup>(5)</sup>	±25	

1. All main power ( $V_{DD}$ ,  $V_{DDA}$ ) and ground ( $V_{SS}$ ,  $V_{SSA}$ ) pins must always be connected to the external power supply, in the permitted range.
2. This current consumption must be correctly distributed over all I/Os and control pins. The total output current must not be sunk/sourced between two consecutive power supply pins referring to high pin count LQFP packages.
3. Positive injection is not possible on these I/Os and does not occur for input voltages lower than the specified maximum value.
4. A positive injection is induced by  $V_{IN} > V_{DDA}$  while a negative injection is induced by  $V_{IN} < V_{SS}$ .  $I_{INJ(PIN)}$  must never be exceeded. Refer to [Table 13: Voltage characteristics](#) for the values of the maximum allowed input voltage.
5. When several inputs are submitted to a current injection, the maximum  $\Sigma I_{INJ(PIN)}$  is the absolute sum of the positive and negative injected currents (instantaneous values).

**Table 15. Thermal characteristics**

Symbol	Ratings	Value	Unit
$T_{STG}$	Storage temperature range	- 65 to +150	°C
$T_J$	Maximum junction temperature	125	

## 6.3 Operating conditions

### 6.3.1 General operating conditions

Table 16. General operating conditions

Symbol	Parameter	Conditions <sup>(1)</sup>	Min	Typ	Max	Unit	
f <sub>HCLK</sub>	Internal AHB clock frequency	Power Scale 3 (VOS[1:0] bits in PWR_CR register = 0x01), Regulator ON, over-drive OFF	0	-	144	MHz	
		Power Scale 2 (VOS[1:0] bits in PWR_CR register = 0x10), Regulator ON	Over-drive OFF	0	-		168
			Over-drive ON	-	-		180
		Power Scale 1 (VOS[1:0] bits in PWR_CR register= 0x11), Regulator ON	Over-drive OFF	0	-		180
Over-drive ON	-		-	216 <sup>(2)</sup>			
f <sub>PCLK1</sub>	Internal APB1 clock frequency	Over-drive OFF	0	-	45		
		Over-drive ON	0	-	54		
f <sub>PCLK2</sub>	Internal APB2 clock frequency	Over-drive OFF	0	-	90		
		Over-drive ON	0	-	108		
V <sub>DD</sub>	Standard operating voltage	-	1.7 <sup>(3)</sup>	-	3.6	V	
V <sub>DDA</sub> <sup>(4)</sup> <sub>(5)</sub>	Analog operating voltage (ADC limited to 1.2 M samples)	Must be the same potential as V <sub>DD</sub> <sup>(6)</sup>	1.7 <sup>(3)</sup>	-	2.4		
	Analog operating voltage (ADC limited to 2.4 M samples)		2.4	-	3.6		
V <sub>DDUSB</sub>	USB supply voltage (supply voltage for PA11,PA12, PB14 and PB15 pins)	USB not used	1.7	3.3	3.6		
		USB used	3.0	-	3.6		
V <sub>BAT</sub>	Backup operating voltage	-	1.65	-	3.6		

Table 16. General operating conditions (continued)

Symbol	Parameter	Conditions <sup>(1)</sup>	Min	Typ	Max	Unit
V <sub>12</sub>	Regulator ON: 1.2 V internal voltage on V <sub>CAP_1</sub> /V <sub>CAP_2</sub> pins	Power Scale 3 ((VOS[1:0] bits in PWR_CR register = 0x01), 144 MHz HCLK max frequency)	1.08	1.14	1.20	V
		Power Scale 2 ((VOS[1:0] bits in PWR_CR register = 0x10), 168 MHz HCLK max frequency with over-drive OFF or 180 MHz with over-drive ON)	1.20	1.26	1.32	
		Power Scale 1 ((VOS[1:0] bits in PWR_CR register = 0x11), 180 MHz HCLK max frequency with over-drive OFF or 216 MHz with over-drive ON)	1.26	1.32	1.40	
	Regulator OFF: 1.2 V external voltage must be supplied from external regulator on V <sub>CAP_1</sub> /V <sub>CAP_2</sub> pins <sup>(7)</sup>	Max frequency 144 MHz	1.10	1.14	1.20	
		Max frequency 168MHz	1.20	1.26	1.32	
		Max frequency 180 MHz	1.26	1.32	1.38	
V <sub>IN</sub>	Input voltage on RST and FT pins <sup>(8)</sup>	2 V ≤ V <sub>DD</sub> ≤ 3.6 V	- 0.3	-	5.5	
		V <sub>DD</sub> ≤ 2 V	- 0.3	-	5.2	
	Input voltage on TTa pins	-	- 0.3	-	V <sub>DDA</sub> + 0.3	
	Input voltage on BOOT pin	-	0	-	9	
P <sub>D</sub>	Power dissipation at T <sub>A</sub> = 85 °C for suffix 6 or T <sub>A</sub> = 105 °C for suffix 7 <sup>(9)</sup>	LQFP100	-	-	465	mW
		LQFP144	-	-	500	
		TFBGA216	-	-	690	
T <sub>A</sub>	Ambient temperature for 6 suffix version	Maximum power dissipation	- 40	-	85	°C
		Low power dissipation <sup>(10)</sup>	- 40	-	105	
	Ambient temperature for 7 suffix version	Maximum power dissipation	- 40	-	105	°C
		Low power dissipation <sup>(10)</sup>	- 40	-	125	
T <sub>J</sub>	Junction temperature range	6 suffix version	- 40	-	105	°C
		7 suffix version	- 40	-	125	

1. The over-drive mode is not supported at the voltage ranges from 1.7 to 2.1 V.
2. 216 MHz maximum frequency for 6 suffix version (200 MHz maximum frequency for 7 suffix version).
3. V<sub>DD</sub>/V<sub>DDA</sub> minimum value of 1.7 V is obtained with the use of an external power supply supervisor (refer to [Section 3.17.2: Internal reset OFF](#)).
4. When the ADC is used, refer to [Table 61: ADC characteristics](#).
5. If V<sub>REF+</sub> pin is present, it must respect the following condition: V<sub>DDA</sub>-V<sub>REF+</sub> < 1.2 V.
6. It is recommended to power V<sub>DD</sub> and V<sub>DDA</sub> from the same source. A maximum difference of 300 mV between V<sub>DD</sub> and V<sub>DDA</sub> can be tolerated during power-up and power-down operation.
7. The over-drive mode is not supported when the internal regulator is OFF.
8. To sustain a voltage higher than VDD+0.3, the internal Pull-up and Pull-Down resistors must be disabled
9. If T<sub>A</sub> is lower, higher P<sub>D</sub> values are allowed as long as T<sub>J</sub> does not exceed T<sub>Jmax</sub>.
10. In low power dissipation state, T<sub>A</sub> can be extended to this range as long as T<sub>J</sub> does not exceed T<sub>Jmax</sub>.



**Table 17. Limitations depending on the operating power supply range**

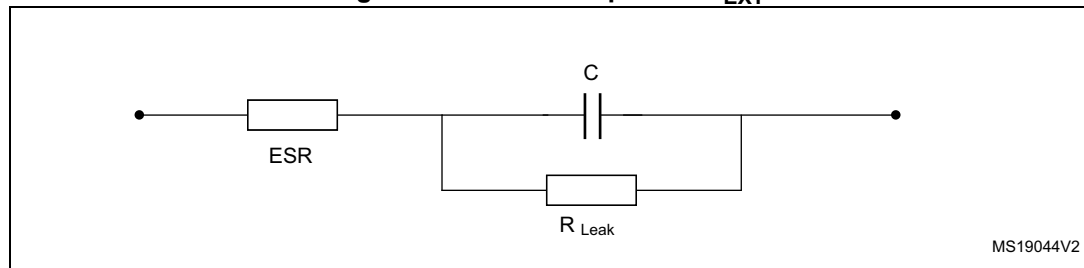
Operating power supply range	ADC operation	Maximum Flash memory access frequency with no wait states ( $f_{Flashmax}$ )	Maximum HCLK frequency vs Flash memory wait states <sup>(1)(2)</sup>	I/O operation	Possible Flash memory operations
$V_{DD} = 1.7$ to $2.1$ V <sup>(3)</sup>	Conversion time up to 1.2 Msps	20 MHz	180 MHz with 8 wait states and over-drive OFF	No I/O compensation	8-bit erase and program operations only
$V_{DD} = 2.1$ to $2.4$ V	Conversion time up to 1.2 Msps	22 MHz	216 MHz with 9 wait states and over-drive ON	No I/O compensation	16-bit erase and program operations
$V_{DD} = 2.4$ to $2.7$ V	Conversion time up to 2.4 Msps	24 MHz	216 MHz with 8 wait states and over-drive ON	I/O compensation works	16-bit erase and program operations
$V_{DD} = 2.7$ to $3.6$ V <sup>(4)</sup>	Conversion time up to 2.4 Msps	30 MHz	216 MHz with 7 wait states and over-drive ON	I/O compensation works	32-bit erase and program operations

1. Applicable only when the code is executed from Flash memory. When the code is executed from RAM, no wait state is required.
2. Thanks to the ART accelerator on ITCM interface and L1-cache on AXI interface, the number of wait states given here does not impact the execution speed from Flash memory since the ART accelerator or L1-cache allows to achieve a performance equivalent to 0-wait state program execution.
3.  $V_{DD}/V_{DDA}$  minimum value of 1.7 V is obtained with the use of an external power supply supervisor (refer to [Section 3.17.2: Internal reset OFF](#)).
4. The voltage range for USB full speed PHYs can drop down to 2.7 V. However the electrical characteristics of D- and D+ pins will be degraded between 2.7 and 3 V.

### 6.3.2 VCAP1/VCAP2 external capacitor

Stabilization for the main regulator is achieved by connecting an external capacitor  $C_{EXT}$  to the VCAP1/VCAP2 pins.  $C_{EXT}$  is specified in [Table 18](#).

**Figure 18. External capacitor  $C_{EXT}$**



1. Legend: ESR is the equivalent series resistance.

**Table 18. VCAP1/VCAP2 operating conditions<sup>(1)</sup>**

Symbol	Parameter	Conditions
C <sub>EXT</sub>	Capacitance of external capacitor	2.2 $\mu$ F
ESR	ESR of external capacitor	< 2 $\Omega$

1. When bypassing the voltage regulator, the two 2.2  $\mu$ F  $V_{CAP}$  capacitors are not required and should be replaced by two 100 nF decoupling capacitors.

### 6.3.3 Operating conditions at power-up / power-down (regulator ON)

Subject to general operating conditions for  $T_A$ .

**Table 19. Operating conditions at power-up / power-down (regulator ON)**

Symbol	Parameter	Min	Max	Unit
$t_{VDD}$	$V_{DD}$ rise time rate	20	$\infty$	$\mu\text{s/V}$
	$V_{DD}$ fall time rate	20	$\infty$	

### 6.3.4 Operating conditions at power-up / power-down (regulator OFF)

Subject to general operating conditions for  $T_A$ .

**Table 20. Operating conditions at power-up / power-down (regulator OFF)<sup>(1)</sup>**

Symbol	Parameter	Conditions	Min	Max	Unit
$t_{VDD}$	$V_{DD}$ rise time rate	Power-up	20	$\infty$	$\mu\text{s/V}$
	$V_{DD}$ fall time rate	Power-down	20	$\infty$	
$t_{VCAP}$	$V_{CAP\_1}$ and $V_{CAP\_2}$ rise time rate	Power-up	20	$\infty$	
	$V_{CAP\_1}$ and $V_{CAP\_2}$ fall time rate	Power-down	20	$\infty$	

1. To reset the internal logic at power-down, a reset must be applied on pin PA0 when  $V_{DD}$  reach below 1.08 V.

### 6.3.5 Reset and power control block characteristics

The parameters given in [Table 21](#) are derived from tests performed under ambient temperature and  $V_{DD}$  supply voltage conditions summarized in [Table 16](#).

Table 21. reset and power control block characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{PVD}$	Programmable voltage detector level selection	PLS[2:0]=000 (rising edge)	2.09	2.14	2.19	V
		PLS[2:0]=000 (falling edge)	1.98	2.04	2.08	V
		PLS[2:0]=001 (rising edge)	2.23	2.30	2.37	V
		PLS[2:0]=001 (falling edge)	2.13	2.19	2.25	V
		PLS[2:0]=010 (rising edge)	2.39	2.45	2.51	V
		PLS[2:0]=010 (falling edge)	2.29	2.35	2.39	V
		PLS[2:0]=011 (rising edge)	2.54	2.60	2.65	V
		PLS[2:0]=011 (falling edge)	2.44	2.51	2.56	V
		PLS[2:0]=100 (rising edge)	2.70	2.76	2.82	V
		PLS[2:0]=100 (falling edge)	2.59	2.66	2.71	V
		PLS[2:0]=101 (rising edge)	2.86	2.93	2.99	V
		PLS[2:0]=101 (falling edge)	2.65	2.84	2.92	V
		PLS[2:0]=110 (rising edge)	2.96	3.03	3.10	V
		PLS[2:0]=110 (falling edge)	2.85	2.93	2.99	V
		PLS[2:0]=111 (rising edge)	3.07	3.14	3.21	V
PLS[2:0]=111 (falling edge)	2.95	3.03	3.09	V		
$V_{PVDhyst}^{(1)}$	PVD hysteresis	-	-	100	-	mV
$V_{POR/PDR}$	Power-on/power-down reset threshold	Falling edge	1.60	1.68	1.76	V
		Rising edge	1.64	1.72	1.80	V
$V_{PDRhyst}^{(1)}$	PDR hysteresis	-	-	40	-	mV
$V_{BOR1}$	Brownout level 1 threshold	Falling edge	2.13	2.19	2.24	V
		Rising edge	2.23	2.29	2.33	V
$V_{BOR2}$	Brownout level 2 threshold	Falling edge	2.44	2.50	2.56	V
		Rising edge	2.53	2.59	2.63	V
$V_{BOR3}$	Brownout level 3 threshold	Falling edge	2.75	2.83	2.88	V
		Rising edge	2.85	2.92	2.97	V
$V_{BORhyst}^{(1)}$	BOR hysteresis	-	-	100	-	mV
$T_{RSTTEMPPO}^{(1)(2)}$	POR reset temporization	-	0.5	1.5	3.0	ms
$I_{RUSH}^{(1)}$	InRush current on voltage regulator power-on (POR or wakeup from Standby)	-	-	160	250	mA
$E_{RUSH}^{(1)}$	InRush energy on voltage regulator power-on (POR or wakeup from Standby)	$V_{DD} = 1.7\text{ V}$ , $T_A = 105\text{ °C}$ , $I_{RUSH} = 171\text{ mA}$ for $31\text{ }\mu\text{s}$	-	-	5.4	$\mu\text{C}$

1. Guaranteed by design.
2. The reset temporization is measured from the power-on (POR reset or wakeup from V<sub>BAT</sub>) to the instant when first instruction is read by the user application code.

### 6.3.6 Over-drive switching characteristics

When the over-drive mode switches from enabled to disabled or disabled to enabled, the system clock is stalled during the internal voltage set-up.

The over-drive switching characteristics are given in [Table 22](#). They are subject to general operating conditions for T<sub>A</sub>.

**Table 22. Over-drive switching characteristics<sup>(1)</sup>**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Tod_swen	Over_drive switch enable time	HSI	-	45	-	μs
		HSE max for 4 MHz and min for 26 MHz	45	-	100	
		External HSE 50 MHz	-	40	-	
Tod_swdis	Over_drive switch disable time	HSI	-	20	-	
		HSE max for 4 MHz and min for 26 MHz.	20	-	80	
		External HSE 50 MHz	-	15	-	

1. Guaranteed by design.

### 6.3.7 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code.

The current consumption is measured as described in [Figure 17: Current consumption measurement scheme](#).

All the run-mode current consumption measurements given in this section are performed with a reduced code that gives a consumption equivalent to CoreMark code.

**Typical and maximum current consumption**

The MCU is placed under the following conditions:

- All I/O pins are in input mode with a static value at V<sub>DD</sub> or V<sub>SS</sub> (no load).
- All peripherals are disabled except if it is explicitly mentioned.
- The Flash memory access time is adjusted both to f<sub>HCLK</sub> frequency and V<sub>DD</sub> range (see [Table 17: Limitations depending on the operating power supply range](#)).
- When the regulator is ON, the voltage scaling and over-drive mode are adjusted to f<sub>HCLK</sub> frequency as follows:
  - Scale 3 for f<sub>HCLK</sub> ≤ 144 MHz
  - Scale 2 for 144 MHz < f<sub>HCLK</sub> ≤ 168 MHz
  - Scale 1 for 168 MHz < f<sub>HCLK</sub> ≤ 216 MHz. The over-drive is only ON at 216 MHz.
- When the regulator is OFF, the V12 is provided externally as described in [Table 16: General operating conditions](#):
- The system clock is HCLK, f<sub>PCLK1</sub> = f<sub>HCLK</sub>/4, and f<sub>PCLK2</sub> = f<sub>HCLK</sub>/2.
- External clock frequency is 25 MHz and PLL is ON when f<sub>HCLK</sub> is higher than 25 MHz.
- The typical current consumption values are obtained for 1.7 V ≤ V<sub>DD</sub> ≤ 3.6 V voltage range and for T<sub>A</sub> = 25 °C unless otherwise specified.
- The maximum values are obtained for 1.7 V ≤ V<sub>DD</sub> ≤ 3.6 V voltage range and a maximum ambient temperature (T<sub>A</sub>) unless otherwise specified.
- For the voltage range 1.7 V ≤ V<sub>DD</sub> ≤ 3.6 V, the maximum frequency is 180 MHz.

**Table 23. Typical and maximum current consumption in Run mode, code with data processing running from ITCM RAM, regulator ON**

Symbol	Parameter	Conditions	f <sub>HCLK</sub> (MHz)	Typ	Max <sup>(1)</sup>			Unit
					T <sub>A</sub> = 25 °C	T <sub>A</sub> = 85 °C	T <sub>A</sub> = 105 °C	
I <sub>DD</sub>	Supply current in RUN mode	All peripherals enabled <sup>(2)(3)</sup>	216	178	208 <sup>(4)</sup>	230 <sup>(4)</sup>	-	mA
			200	165	193	212	230	
			180	147	171 <sup>(4)</sup>	185 <sup>(4)</sup>	198 <sup>(4)</sup>	
			168	130	152	164	177	
			144	100	116	127	137	
			60	44	52	63	73	
			25	21	25	36	46	
		All peripherals disabled <sup>(3)</sup>	216	102	120 <sup>(4)</sup>	141 <sup>(4)</sup>	-	
			200	95	111	131	149	
			180	84	98 <sup>(4)</sup>	112 <sup>(4)</sup>	125 <sup>(4)</sup>	
			168	75	87	100	112	
			144	58	67	77	88	
			60	25	30	41	51	
			25	12	15	25	36	

1. Guaranteed by characterization results.

2. When analog peripheral blocks such as ADCs, DACs, HSE, LSE, HSI, or LSI are ON, an additional power consumption should be considered.
3. When the ADC is ON (ADON bit set in the ADC\_CR2 register), add an additional power consumption of 1.73 mA per ADC for the analog part.
4. Guaranteed by test in production.

**Table 24. Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART ON except prefetch / L1-cache ON) or SRAM on AXI (L1-cache ON), regulator ON**

Symbol	Parameter	Conditions	f <sub>HCLK</sub> (MHz)	Typ	Max <sup>(1)</sup>			Unit
					T <sub>A</sub> = 25 °C	T <sub>A</sub> = 85 °C	T <sub>A</sub> = 105 °C	
I <sub>DD</sub>	Supply current in RUN mode	All peripherals enabled <sup>(2)(3)</sup>	216	186	213	234	-	mA
			200	172	197	217	235	
			180	152	175	189	202	
			168	135	155	168	180	
			144	104	119	130	140	
			60	46	53	64	74	
			25	22	25	36	47	
		All peripherals disabled <sup>(3)</sup>	216	108	124	146	-	
			200	100	115	135	154	
			180	89	102	116	129	
			168	79	90	103	115	
			144	61	69	80	90	
			60	27	31	42	52	
			25	12	15	26	36	

1. Guaranteed by characterization results.
2. When analog peripheral blocks such as ADCs, DACs, HSE, LSE, HSI, or LSI are ON, an additional power consumption should be considered.
3. When the ADC is ON (ADON bit set in the ADC\_CR2 register), add an additional power consumption of 1.73 mA per ADC for the analog part.

**Table 25. Typical and maximum current consumption in Run mode, code with data processing running from Flash memory or SRAM on AXI (L1-cache disabled), regulator ON**

Symbol	Parameter	Conditions	f <sub>HCLK</sub> (MHz)	Typ	Max <sup>(1)</sup>			Unit
					TA= 25 °C	TA=85 °C	TA=105 °C	
I <sub>DD</sub>	Supply current in RUN mode	All peripherals enabled <sup>(2)(3)</sup>	216	181	210	233	-	mA
			200	168	194	216	234	
			180	153	176	192	206	
			168	136	157	172	184	
			144	109	125	137	148	
			60	53	61	73	84	
			25	26	30	41	52	
		All peripherals disabled <sup>(3)</sup>	216	105	121	145	-	
			200	98	112	134	153	
			180	90	103	119	132	
			168	81	93	107	120	
			144	67	76	88	89	
			60	34	40	51	62	
			25	17	20	31	42	

1. Guaranteed by characterization results.
2. When analog peripheral blocks such as ADCs, DACs, HSE, LSE, HSI, or LSI are ON, an additional power consumption should be considered.
3. When the ADC is ON (ADON bit set in the ADC\_CR2 register), add an additional power consumption of 1.73 mA per ADC for the analog part.

**Table 26. Typical and maximum current consumption in Run mode, code with data processing running from Flash memory on ITCM interface (ART disabled), regulator ON**

Symbol	Parameter	Conditions	f <sub>HCLK</sub> (MHz)	Typ	Max <sup>(1)</sup>			Unit
					TA= 25 °C	TA=85 °C	TA=105 °C	
I <sub>DD</sub>	Supply current in RUN mode	All peripherals enabled <sup>(2)(3)</sup>	216	205	237	261	-	mA
			200	191	219	241	260	
			180	176	202	218	232	
			168	158	181	196	209	
			144	130	148	161	172	
			60	58	67	79	89	
			25	27	32	43	54	
		All peripherals disabled <sup>(3)</sup>	216	130	149	173	-	
			200	121	138	160	179	
			180	113	129	145	159	
			168	102	116	131	144	
			144	88	100	112	123	
			60	40	45	57	68	
			25	19	22	33	44	

1. Guaranteed by characterization results.
2. When analog peripheral blocks such as ADCs, DACs, HSE, LSE, HSI, or LSI are ON, an additional power consumption should be considered.
3. When the ADC is ON (ADON bit set in the ADC\_CR2 register), add an additional power consumption of 1.73 mA per ADC for the analog part.



**Table 27. Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART ON except prefetch / L1-cache ON) or SRAM on AXI (L1-cache ON), regulator OFF**

Symbol	Parameter	Conditions	f <sub>HCLK</sub> (MHz)	Typ		Max <sup>(1)</sup>						Unit
						TA= 25 °C		TA= 85 °C		TA= 105 °C		
				IDD12	IDD	IDD12	IDD	IDD12	IDD	IDD12	IDD	
IDD12/ IDD	Supply current in RUN mode from V12 and VDD supply	All Peripherals Enabled <sup>(2)(3)</sup>	180	151	1	174	2	190	2	204	2	mA
			168	135	1	156	2	170	2	182	2	
			144	108	1	124	2	136	2	146	2	
			60	52	1	60	2	71	2	82	2	
			25	25	1	29	2	40	2	50	2	
		All Peripherals Disabled <sup>(3)</sup>	180	89	1	102	2	117	2	130	2	
			168	80	1	91	2	105	2	118	2	
			144	66	1	75	2	86	2	97	2	
			60	33	1	38	2	49	2	60	2	
			25	16	1	18	2	29	2	40	2	

1. Guaranteed by characterization results.
2. When analog peripheral blocks such as ADCs, DACs, HSE, LSE, HSI, or LSI are ON, an additional power consumption should be considered.
3. When the ADC is ON (ADON bit set in the ADC\_CR2 register), add an additional power consumption of 1.73 mA per ADC for the analog part.

**Table 28. Typical and maximum current consumption in Sleep mode, regulator ON**

Symbol	Parameter	Conditions	f <sub>HCLK</sub> (MHz)	Typ	Max <sup>(1)</sup>			Unit
					T <sub>A</sub> = 25 °C	T <sub>A</sub> = 85 °C	T <sub>A</sub> = 105 °C	
I <sub>DD</sub>	Supply current in Sleep mode	All peripherals enabled <sup>(2)</sup>	216	116	137 <sup>(3)</sup>	159 <sup>(3)</sup>	-	mA
			200	108	127	147	166	
			180	95	112 <sup>(3)</sup>	126 <sup>(3)</sup>	140 <sup>(3)</sup>	
			168	85	99	112	125	
			144	65	76	87	98	
			60	30	35	46	57	
			25	15	18	29	39	
		All peripherals disabled	216	35	46 <sup>(3)</sup>	71 <sup>(3)</sup>	-	
			200	32	43	66	86	
			180	28	38 <sup>(3)</sup>	53 <sup>(3)</sup>	70 <sup>(3)</sup>	
			168	25	33	47	61	
			144	20	26	37	50	
			60	10	14	26	36	
			25	5	8	20	31	

1. Guaranteed by characterization results.
2. When analog peripheral blocks such as ADCs, DACs, HSE, LSE, HSI, or LSI are ON, an additional power consumption should be considered.
3. Guaranteed by test in production.

**Table 29. Typical and maximum current consumption in Sleep mode, regulator OFF**

Symbol	Parameter	Conditions	f <sub>HCLK</sub> (MHz)	Typ		Max <sup>(1)</sup>						Unit
						TA= 25 °C		TA= 85 °C		TA= 105 °C		
				IDD12	IDD	IDD12	IDD	IDD12	IDD	IDD12	IDD	
IDD12/ IDD	Supply current in RUN mode from V12 and V <sub>DD</sub> supply	All Peripherals Enabled <sup>(2)</sup>	180	94	1	110	2	125	2	138	2	mA
			168	83	1	96	2	111	2	123	2	
			144	64	1	74	2	85	2	96	2	
			60	29	1	34	2	44	2	55	2	
			25	14	1	16	2	27	2	37	2	
		All Peripherals Disabled	180	27	1	36	2	51	2	68	2	
			168	24	1	31	2	45	2	59	2	
			144	18	1	24	2	35	2	48	2	
			60	9	1	12	2	24	2	34	2	
			25	4	1	6	2	18	2	29	2	

1. Guaranteed by characterization results.

2. When analog peripheral blocks such as ADCs, DACs, HSE, LSE, HSI, or LSI are ON, an additional power consumption should be considered.

**Table 30. Typical and maximum current consumptions in Stop mode**

Symbol	Parameter	Conditions	Typ	Max <sup>(1)</sup>				Unit
				V <sub>DD</sub> = 3.6 V				
			T <sub>A</sub> = 25 °C	T <sub>A</sub> = 25 °C	T <sub>A</sub> = 85 °C	T <sub>A</sub> = 105 °C		
I <sub>DD_STOP_NM</sub> (normal mode)	Supply current in Stop mode, main regulator in Run mode	Flash memory in Stop mode, all oscillators OFF, no IWDG	0.45	2.00	14.00	22.00	mA	
		Flash memory in Deep power down mode, all oscillators OFF	0.40	2.00	14.00	22.00		
	Supply current in Stop mode, main regulator in Low-power mode	Flash memory in Stop mode, all oscillators OFF, no IWDG	0.32	1.50	10.00	18.00		
		Flash memory in Deep power down mode, all oscillators OFF, no IWDG	0.27	1.50	10.00	18.00		
I <sub>DD_STOP_UDM</sub> (under-drive mode)	Supply current in Stop mode, main regulator in Low voltage and under-drive modes	Regulator in Run mode, Flash memory in Deep power down mode, all oscillators OFF, no IWDG	0.15	0.80	4.00	7.00		
		Regulator in Low-power mode, Flash memory in Deep power down mode, all oscillators OFF, no IWDG	0.10	0.70	4.00	7.00		

1. Data based on characterization, tested in production.

**Table 31. Typical and maximum current consumptions in Standby mode**

Symbol	Parameter	Conditions	Typ <sup>(1)</sup>			Max <sup>(2)</sup>			Unit
			T <sub>A</sub> = 25 °C			T <sub>A</sub> = 25 °C	T <sub>A</sub> = 85 °C	T <sub>A</sub> = 105 °C	
			V <sub>DD</sub> = 1.7 V	V <sub>DD</sub> = 2.4 V	V <sub>DD</sub> = 3.3 V	V <sub>DD</sub> = 3.3 V			
I <sub>DD_STBY</sub>	Supply current in Standby mode	Backup SRAM OFF, RTC and LSE OFF	1.7	1.9	2.3	5 <sup>(3)</sup>	15 <sup>(3)</sup>	31 <sup>(3)</sup>	µA
		Backup SRAM ON, RTC and LSE OFF	2.4	2.6	3.0	6 <sup>(3)</sup>	20 <sup>(3)</sup>	40 <sup>(3)</sup>	
		Backup SRAM OFF, RTC ON and LSE in low drive mode	2.1	2.4	2.9	6	19	39	
		Backup SRAM OFF, RTC ON and LSE in medium low drive mode	2.1	2.4	2.9	6	19	39	
		Backup SRAM OFF, RTC ON and LSE in medium high drive mode	2.2	2.5	3.0	7	20	40	
		Backup SRAM OFF, RTC ON and LSE in high drive mode	2.3	2.6	3.1	7	20	42	
		Backup SRAM ON, RTC ON and LSE in low drive mode	2.7	3.0	3.6	8	23	49	
		Backup SRAM ON, RTC ON and LSE in Medium low drive mode	2.7	3.0	3.6	8	23	49	
		Backup SRAM ON, RTC ON and LSE in Medium high drive mode	2.8	3.1	3.7	8	24	50	
		Backup SRAM ON, RTC ON and LSE in High drive mode	2.9	3.2	3.8	8	25	51	

1. PDR is OFF for V<sub>DD</sub>=1.7V. When the PDR is OFF (internal reset OFF), the typical current consumption is reduced by additional 1.2 µA.
2. Guaranteed by characterization results.
3. Based on characterization, tested in production.

**Table 32. Typical and maximum current consumptions in V<sub>BAT</sub> mode**

Symbol	Parameter	Conditions <sup>(1)</sup>	Typ			Max <sup>(2)</sup>		Unit
			T <sub>A</sub> =25 °C			T <sub>A</sub> =85 °C	T <sub>A</sub> =105 °C	
			V <sub>BAT</sub> = 1.7 V	V <sub>BAT</sub> = 2.4 V	V <sub>BAT</sub> = 3.3 V	V <sub>BAT</sub> = 3.6 V		
I <sub>DD_VBAT</sub>	Supply current in V <sub>BAT</sub> mode	Backup SRAM OFF, RTC and LSE OFF	0.03	0.03	0.04	0.2	0.4	μA
		Backup SRAM ON, RTC and LSE OFF	0.74	0.75	0.78	3.0	7.0	
		Backup SRAM OFF, RTC ON and LSE in low drive mode	0.40	0.52	0.72	2.8	6.5	
		Backup SRAM OFF, RTC ON and LSE in medium low drive mode	0.40	0.52	0.72	2.8	6.5	
		Backup SRAM OFF, RTC ON and LSE in medium high drive mode	0.54	0.64	0.85	3.3	7.6	
		Backup SRAM OFF, RTC ON and LSE in high drive mode	0.62	0.73	0.94	3.6	8.4	
		Backup SRAM ON, RTC ON and LSE in low drive mode	1.06	1.18	1.41	5.4	12.7	
		Backup SRAM ON, RTC ON and LSE in Medium low drive mode	1.16	1.28	1.51	5.8	13.6	
		Backup SRAM ON, RTC ON and LSE in Medium high drive mode	1.18	1.3	1.54	5.9	13.8	
		Backup SRAM ON, RTC ON and LSE in High drive mode	1.36	1.48	1.73	6.7	15.5	

1. Crystal used: Abracon ABS07-120-32.768 kHz-T with a C<sub>L</sub> of 6 pF for typical values.

2. Guaranteed by characterization results.

Figure 19. Typical  $V_{BAT}$  current consumption (RTC ON/BKP SRAM OFF and LSE in low drive mode)

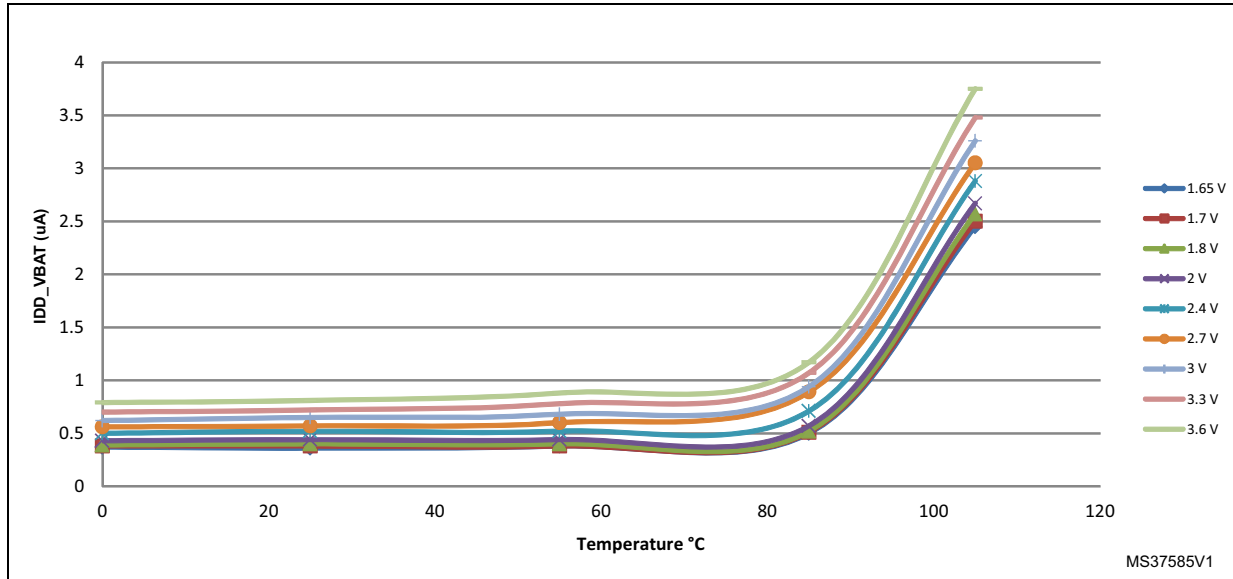


Figure 20. Typical  $V_{BAT}$  current consumption (RTC ON/BKP SRAM OFF and LSE in medium low drive mode)

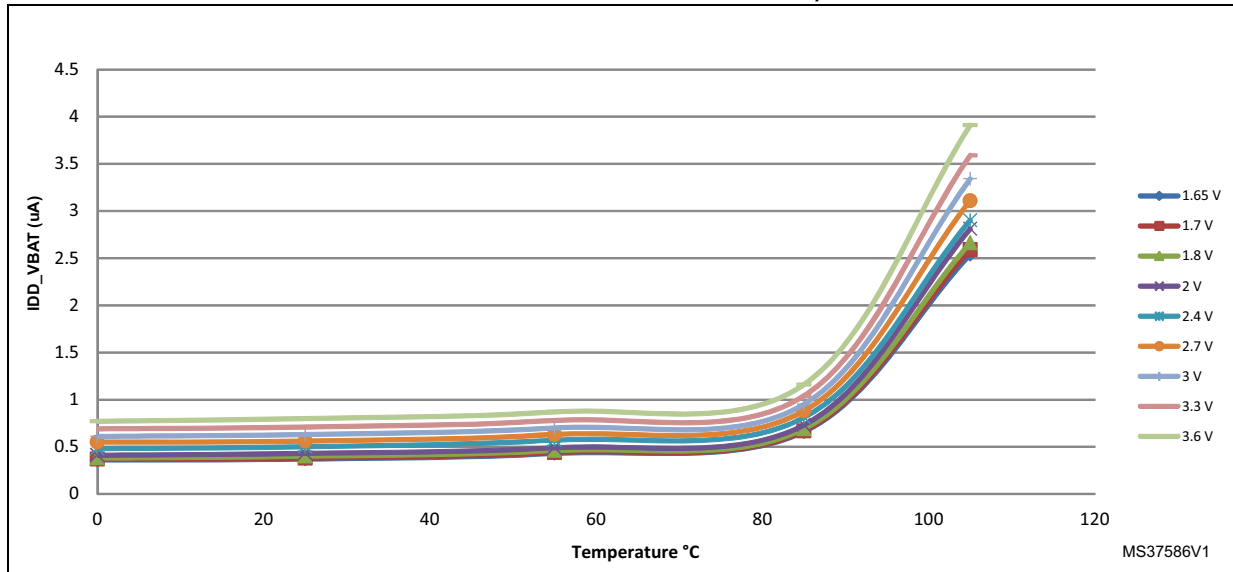


Figure 21. Typical  $V_{BAT}$  current consumption (RTC ON/BKP SRAM OFF and LSE in medium high drive mode)

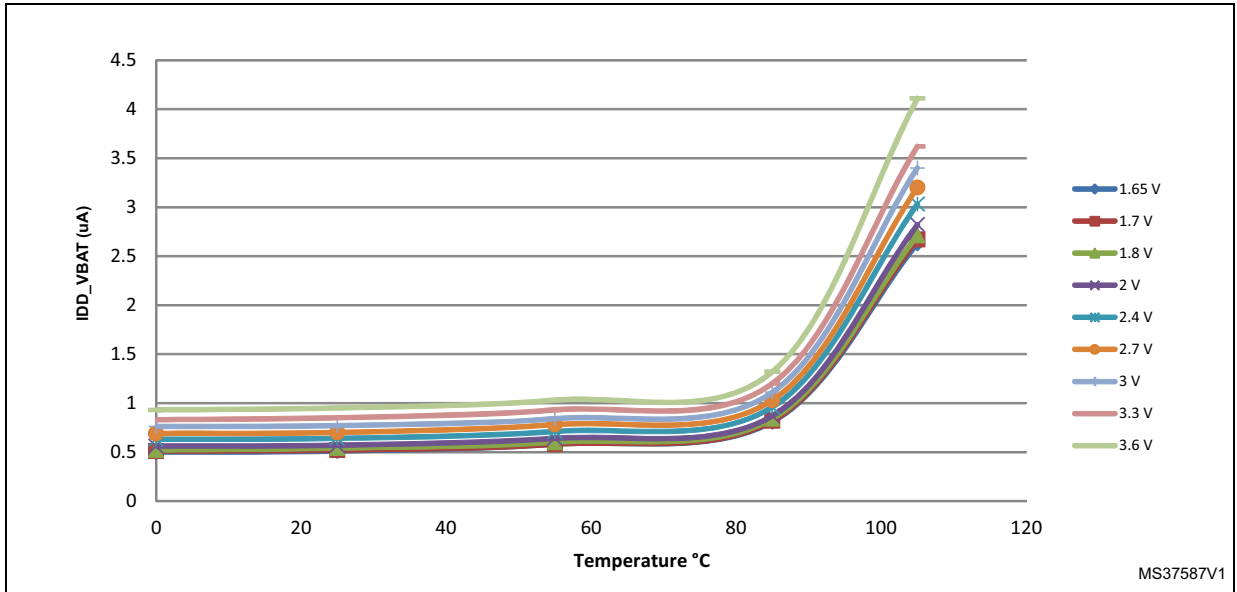


Figure 22. Typical  $V_{BAT}$  current consumption (RTC ON/BKP SRAM OFF and LSE in high drive mode)

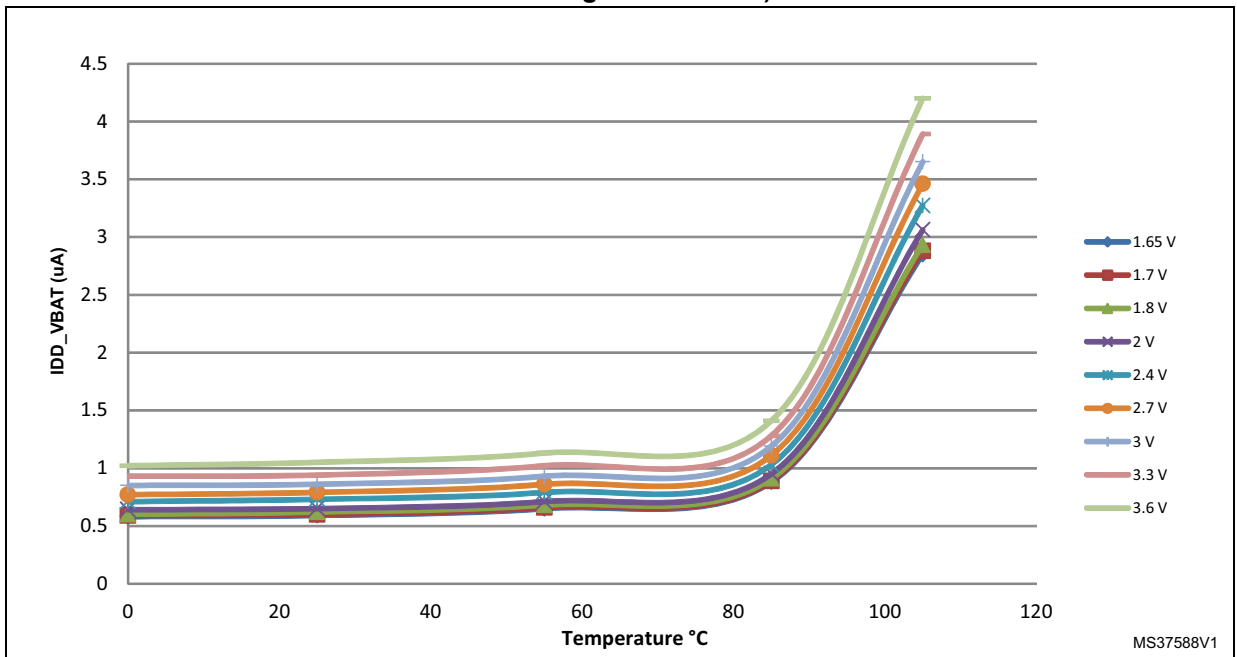
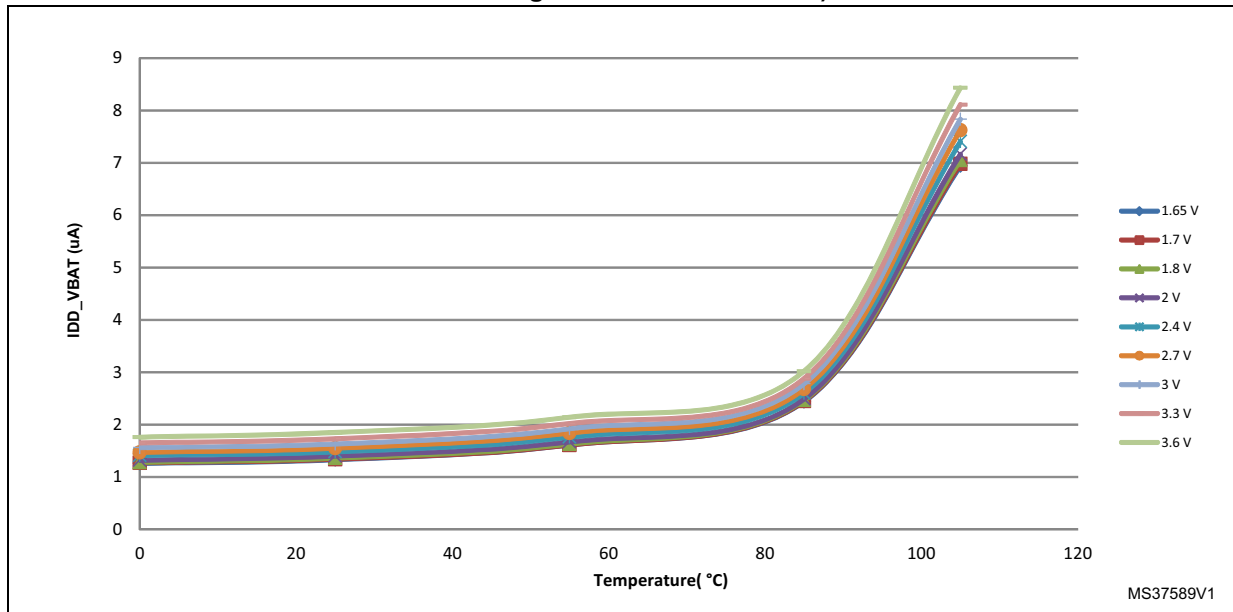


Figure 23. Typical  $V_{BAT}$  current consumption (RTC ON/BKP SRAM OFF and LSE in high medium drive mode)



### I/O system current consumption

The current consumption of the I/O system has two components: static and dynamic.

#### I/O static current consumption

All the I/Os used as inputs with pull-up generate current consumption when the pin is externally held low. The value of this current consumption can be simply computed by using the pull-up/pull-down resistors values given in [Table 55: I/O static characteristics](#).

For the output pins, any external pull-down or external load must also be considered to estimate the current consumption.

Additional I/O current consumption is due to I/Os configured as inputs if an intermediate voltage level is externally applied. This current consumption is caused by the input Schmitt trigger circuits used to discriminate the input value. Unless this specific configuration is required by the application, this supply current consumption can be avoided by configuring these I/Os in analog mode. This is notably the case of ADC input pins which should be configured as analog inputs.

**Caution:** Any floating input pin can also settle to an intermediate voltage level or switch inadvertently, as a result of external electromagnetic noise. To avoid current consumption related to floating pins, they must either be configured in analog mode, or forced internally to a definite digital value. This can be done either by using pull-up/down resistors or by configuring the pins in output mode.

#### I/O dynamic current consumption

In addition to the internal peripheral current consumption (see [Table 34: Peripheral current consumption](#)), the I/Os used by an application also contribute to the current consumption. When an I/O pin switches, it uses the current from the MCU supply voltage to supply the I/O



pin circuitry and to charge/discharge the capacitive load (internal or external) connected to the pin:

$$I_{SW} = V_{DD} \times f_{SW} \times C$$

where

$I_{SW}$  is the current sunk by a switching I/O to charge/discharge the capacitive load

$V_{DD}$  is the MCU supply voltage

$f_{SW}$  is the I/O switching frequency

$C$  is the total capacitance seen by the I/O pin:  $C = C_{INT} + C_{EXT}$

The test pin is configured in push-pull output mode and is toggled by software at a fixed frequency.

**Table 33. Switching output I/O current consumption<sup>(1)</sup>**

Symbol	Parameter	Conditions	I/O toggling frequency (fsw) MHz	Typ V <sub>DD</sub> = 3.3 V	Typ V <sub>DD</sub> = 1.8 V	Unit
I <sub>DDIO</sub>	I/O switching Current	C <sub>EXT</sub> = 0 pF C = C <sub>INT</sub> + C <sub>S</sub> + C <sub>EXT</sub>	2	0.1	0.1	mA
			8	0.4	0.2	
			25	1.1	0.7	
			50	2.4	1.3	
			60	3.1	1.6	
			84	4.3	2.4	
			90	4.9	2.6	
			100	5.4	2.8	
			108	5.6	-	
		C <sub>EXT</sub> = 10 pF C = C <sub>INT</sub> + C <sub>S</sub> + C <sub>EXT</sub>	2	0.2	0.1	
			8	0.6	0.3	
			25	1.8	1.1	
			50	3.1	2.3	
			60	4.6	3.4	
			84	9.7	3.6	
			90	10.12	5.2	
			100	14.92	5.4	
			108	18.11	-	

**Table 33. Switching output I/O current consumption<sup>(1)</sup> (continued)**

Symbol	Parameter	Conditions	I/O toggling frequency (fsw) MHz	Typ V <sub>DD</sub> = 3.3 V	Typ V <sub>DD</sub> = 1.8 V	Unit
I <sub>DDIO</sub>	I/O switching Current	C <sub>EXT</sub> = 22 pF C = C <sub>INT</sub> + C <sub>S</sub> + C <sub>EXT</sub>	2	0.3	0.1	mA
			8	1.0	0.5	
			25	3.5	1.6	
			50	5.9	4.2	
			60	10.0	4.4	
			84	19.12	5.8	
			90	19.6	-	
		C <sub>EXT</sub> = 33 pF C = C <sub>INT</sub> + C <sub>S</sub> + C <sub>EXT</sub>	2	0.3	0.2	
			8	1.3	0.7	
			25	3.5	2.3	
			50	10.26	5.19	
			60	16.53	-	

1. C<sub>INT</sub> + C<sub>S</sub>, PCB board capacitance including the pad pin is estimated to 15 pF.

**On-chip peripheral current consumption**

The MCU is placed under the following conditions:

- At startup, all I/O pins are in analog input configuration.
- All peripherals are disabled unless otherwise mentioned.
- I/O compensation cell enabled.
- The ART/L1-cache is ON.
- Scale 1 mode selected, internal digital voltage V<sub>I2</sub> = 1.32 V.
- HCLK is the system clock. f<sub>PCLK1</sub> = f<sub>HCLK</sub>/4, and f<sub>PCLK2</sub> = f<sub>HCLK</sub>/2.

The given value is calculated by measuring the difference of current consumption

- with all peripherals clocked off
- with only one peripheral clocked on
- f<sub>HCLK</sub> = 216 MHz (Scale 1 + over-drive ON), f<sub>HCLK</sub> = 168 MHz (Scale 2), f<sub>HCLK</sub> = 144 MHz (Scale 3)
- Ambient operating temperature is 25 °C and V<sub>DD</sub>=3.3 V.



Table 34. Peripheral current consumption

Peripheral		I <sub>DD</sub> (Typ) <sup>(1)</sup>			Unit
		Scale 1	Scale 2	Scale 3	
AHB1 (up to 216 MHz)	GPIOA	2.2	2.1	1.9	μA/MHz
	GPIOB	2.1	1.8	1.7	
	GPIOC	2.3	2.0	1.9	
	GPIOD	2.2	1.9	1.8	
	GPIOE	2.2	1.9	1.8	
	GPIOF	2.2	1.9	1.8	
	GPIOG	2.1	1.8	1.7	
	GPIOH	2.0	1.7	1.7	
	GPIOI	2.3	2.0	1.7	
	GPIOJ	2.2	1.9	1.7	
	GPIOK	2.0	1.7	1.7	
	CRC	1.0	0.9	0.8	
	BKPSRAM	0.8	0.7	0.6	
	DMA1	2.7 x N + 5.1	2.6 x N + 4.7	2.2 x N + 4	
	DMA2	2.2 x N + 4.9	2.6 x N + 4.4	2.2 x N + 4.1	
	DMA2D	87.1	82.5	69.6	
	ETH_MAC ETH_MAC_TX ETH_MAC_RX ETH_MAC_PTP	42.1	39.7	34.1	
OTG_HS	57.5	54.4	47.6		
OTG_HS+ULPI					
AHB2 (up to 216 MHz)	DCMI	5.1	4.7	4.0	μA/MHz
	CRYP	3.0	2.6	2.4	
	HASH	4.2	3.7	3.3	
	RNG	2.8	2.4	2.3	
	USB_OTG_FS	31.8	29.9	25.8	
AHB3 (up to 216 MHz)	FMC	18.9	17.7	15.2	μA/MHz
	QSPI	23.2	21.8	18.5	
Bus matrix <sup>(2)</sup>		21.06	20.3	17.2	μA/MHz

**Table 34. Peripheral current consumption (continued)**

Peripheral		I <sub>DD</sub> (Typ) <sup>(1)</sup>			Unit
		Scale 1	Scale 2	Scale 3	
APB1 (up to 54 MHz)	TIM2	19.8	18.7	16.1	μA/MHz
	TIM3	16.6	15.1	13.6	
	TIM4	16.2	15.1	13.3	
	TIM5	19	17.8	15.8	
	TIM6	3	2.7	2.5	
	TIM7	3	2.7	2.5	
	TIM12	12.4	11.3	10.3	
	TIM13	6	5.3	5	
	TIM14	6	5.3	5	
	LPTIM1	9.4	8.7	8.1	
	WWDG	1.8	1.6	1.4	
	SPI2/I2S2 <sup>(3)</sup>	3	2.9	2.8	
	SPI3/I2S3 <sup>(3)</sup>	3.2	2.9	2.8	
	SPDIFRX	2.2	2	1.7	
	USART2	12.8	12	10.8	
	USART3	15.6	14.2	13.1	
	UART4	11.8	10.7	9.7	
	UART5	11.2	10	9.2	
	I2C1	9.8	8.7	7.8	
	I2C2	8.6	7.8	7.2	
	I2C3	8.6	7.8	7.2	
	I2C4	12	10.9	9.7	
	CAN1	6.8	6	5.6	
	CAN2	6.8	6	5.8	
	CEC	1	0.7	0.8	
	PWR	1.2	0.9	0.8	
	DAC <sup>(4)</sup>	3	2.7	2.5	
	UART7	12.4	11.6	10	
UART8	10.4	9.3	8.6		

**Table 34. Peripheral current consumption (continued)**

Peripheral		I <sub>DD</sub> (Typ) <sup>(1)</sup>			Unit
		Scale 1	Scale 2	Scale 3	
APB2 (up to 108 MHz)	TIM1	25.2	23.9	20.4	μA/MHz
	TIM8	25.3	24	20.4	
	USART1	10.3	9.8	8.2	
	USART6	10.1	9.7	8.1	
	ADC1 <sup>(5)</sup>	4.5	4.4	3.5	
	ADC2 <sup>(5)</sup>	4.5	4.4	3.5	
	ADC3 <sup>(5)</sup>	4.5	4.4	3.3	
	SDMMC1	8.5	7.9	6.7	
	SPI1/I2S1 <sup>(3)</sup>	3.1	3	2.5	
	SPI4	3.1	3	2.5	
	SYSCFG	1.5	1.4	1	
	TIM9	8.8	8.4	6.9	
	TIM10	5.6	5.2	4.3	
	TIM11	5.4	5.2	4.3	
	SPI5	3	2.8	2.2	
	SPI6	3	2.8	2.2	
	SAI1	3.4	3.3	2.6	
	SAI2	3.3	3.2	2.5	
LTDC	56.7	53.8	45.7		

1. When the I/O compensation cell is ON, I<sub>DD</sub> typical value increases by 0.22 mA.
2. The BusMatrix is automatically active when at least one master is ON.
3. To enable an I2S peripheral, first set the I2SMOD bit and then the I2SE bit in the SPI\_I2SCFGR register.
4. When the DAC is ON and EN1/2 bits are set in DAC\_CR register, add an additional power consumption of 0.75 mA per DAC channel for the analog part.
5. When the ADC is ON (ADON bit set in the ADC\_CR2 register), add an additional power consumption of 1.73 mA per ADC for the analog part.

### 6.3.8 Wakeup time from low-power modes

The wakeup times given in [Table 35](#) are measured starting from the wakeup event trigger up to the first instruction executed by the CPU:

- For Stop or Sleep modes: the wakeup event is WFE.
- WKUP (PA0) pin is used to wakeup from Standby, Stop and Sleep modes.

All timings are derived from tests performed under ambient temperature and  $V_{DD}=3.3$  V.

**Table 35. Low-power mode wakeup timings**

Symbol	Parameter	Conditions	Typ <sup>(1)</sup>	Max <sup>(1)</sup>	Unit
$t_{WUSLEEP}^{(2)}$	Wakeup from Sleep	-	13	13	CPU clock cycles
$t_{WUSTOP}^{(2)}$	Wakeup from Stop mode with MR/LP regulator in normal mode	Main regulator is ON	14	14.9	μs
		Main regulator is ON and Flash memory in Deep power down mode	104.1	107.6	
		Low power regulator is ON	21.4	24.2	
		Low power regulator is ON and Flash memory in Deep power down mode	111.5	116.5	
$t_{WUSTOP}^{(2)}$	Wakeup from Stop mode with MR/LP regulator in Under-drive mode	Main regulator in under-drive mode (Flash memory in Deep power-down mode)	107.4	113.2	
		Low power regulator in under-drive mode (Flash memory in Deep power-down mode )	112.7	120	
$t_{WUSTDBY}^{(2)}$	Wakeup from Standby mode	Exit Standby mode on rising edge	308	313	
		Exit Standby mode on falling edge	307	313	

1. Guaranteed by characterization results.
2. The wakeup times are measured from the wakeup event to the point in which the application code reads the first

### 6.3.9 External clock source characteristics

#### High-speed external user clock generated from an external source

In bypass mode the HSE oscillator is switched off and the input pin is a standard I/O. The external clock signal has to respect the [Table 55: I/O static characteristics](#). However, the recommended clock input waveform is shown in [Figure 24](#).

The characteristics given in [Table 36](#) result from tests performed using an high-speed external clock source, and under ambient temperature and supply voltage conditions summarized in [Table 16](#).

**Table 36. High-speed external user clock characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$f_{HSE\_ext}$	External user clock source frequency <sup>(1)</sup>		1	-	50	MHz
$V_{HSEH}$	OSC_IN input pin high level voltage		$0.7V_{DD}$	-	$V_{DD}$	V
$V_{HSEL}$	OSC_IN input pin low level voltage		$V_{SS}$	-	$0.3V_{DD}$	
$t_{w(HSE)}$ $t_{w(HSE)}$	OSC_IN high or low time <sup>(1)</sup>		5	-	-	ns
$t_{r(HSE)}$ $t_{f(HSE)}$	OSC_IN rise or fall time <sup>(1)</sup>		-	-	10	
$C_{in(HSE)}$	OSC_IN input capacitance <sup>(1)</sup>	-	-	5	-	pF
$DuCy_{(HSE)}$	Duty cycle	-	45	-	55	%
$I_L$	OSC_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	$\pm 1$	$\mu A$

1. Guaranteed by design.

#### Low-speed external user clock generated from an external source

In bypass mode the LSE oscillator is switched off and the input pin is a standard I/O. The external clock signal has to respect the [Table 55: I/O static characteristics](#). However, the recommended clock input waveform is shown in [Figure 25](#).

The characteristics given in [Table 37](#) result from tests performed using an low-speed external clock source, and under ambient temperature and supply voltage conditions summarized in [Table 16](#).

Table 37. Low-speed external user clock characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$f_{LSE\_ext}$	User External clock source frequency <sup>(1)</sup>		-	32.768	1000	kHz
$V_{LSEH}$	OSC32_IN input pin high level voltage	-	$0.7V_{DD}$	-	$V_{DD}$	V
$V_{LSEL}$	OSC32_IN input pin low level voltage		$V_{SS}$	-	$0.3V_{DD}$	
$t_{w(LSE)}$ $t_{f(LSE)}$	OSC32_IN high or low time <sup>(1)</sup>	-	450	-	-	ns
$t_{r(LSE)}$ $t_{f(LSE)}$	OSC32_IN rise or fall time <sup>(1)</sup>		-	-	50	
$C_{in(LSE)}$	OSC32_IN input capacitance <sup>(1)</sup>	-	-	5	-	pF
DuCy(LSE)	Duty cycle	-	30	-	70	%
$I_L$	OSC32_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	$\pm 1$	$\mu A$

1. Guaranteed by design.

Figure 24. High-speed external clock source AC timing diagram

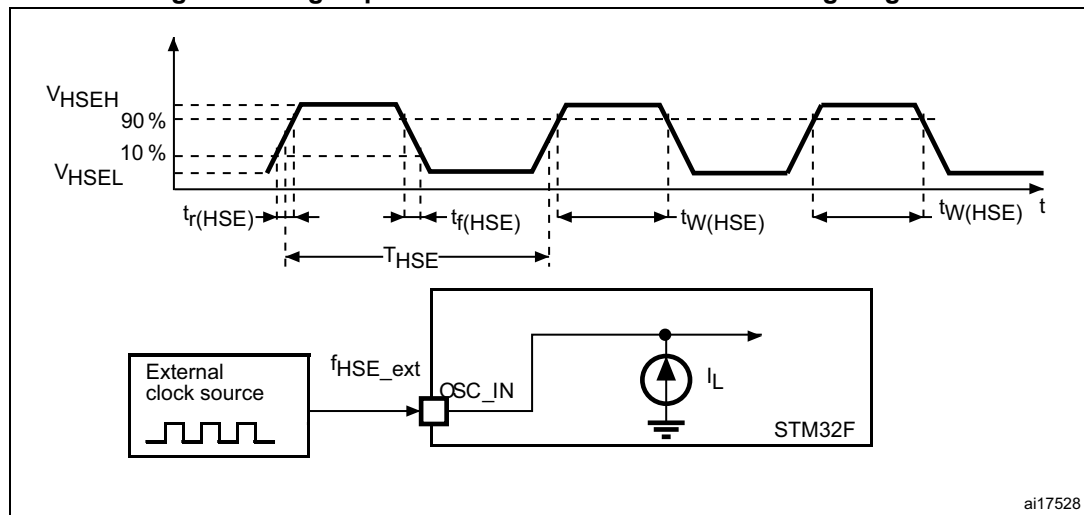
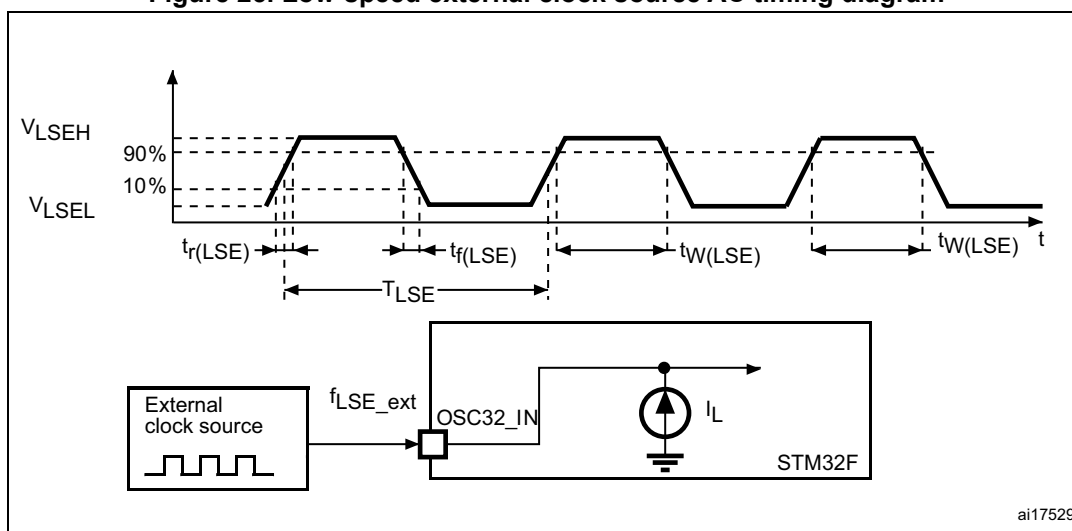




Figure 25. Low-speed external clock source AC timing diagram



### High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 4 to 26 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in [Table 38](#). In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 38. HSE 4-26 MHz oscillator characteristics<sup>(1)</sup>

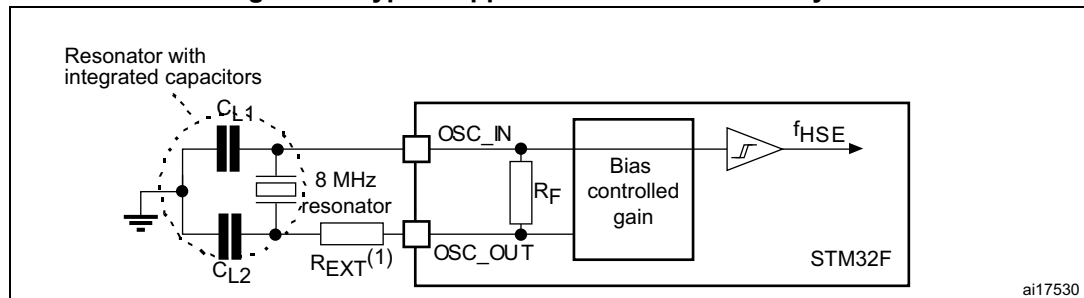
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f <sub>OSC_IN</sub>	Oscillator frequency	-	4	-	26	MHz
R <sub>F</sub>	Feedback resistor	-	-	200	-	kΩ
I <sub>DD</sub>	HSE current consumption	V <sub>DD</sub> =3.3 V, ESR= 30 Ω, C <sub>L</sub> =5 pF@25 MHz	-	450	-	μA
		V <sub>DD</sub> =3.3 V, ESR= 30 Ω, C <sub>L</sub> =10 pF@25 MHz	-	530	-	
ACC <sub>HSE</sub> <sup>(2)</sup>	HSE accuracy	-	- 500	-	500	ppm
G <sub>m_crit_max</sub>	Maximum critical crystal g <sub>m</sub>	Startup	-	-	1	mA/V
t <sub>SU(HSE)</sub> <sup>(3)</sup>	Startup time	V <sub>DD</sub> is stabilized	-	2	-	ms

1. Guaranteed by design.
2. This parameter depends on the crystal used in the application. The minimum and maximum values must be respected to comply with USB standard specifications.
3. t<sub>SU(HSE)</sub> is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is based on characterization results. It is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

For  $C_{L1}$  and  $C_{L2}$ , it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see [Figure 26](#)).  $C_{L1}$  and  $C_{L2}$  are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of  $C_{L1}$  and  $C_{L2}$ . PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing  $C_{L1}$  and  $C_{L2}$ .

*Note:* For information on selecting the crystal, refer to the application note AN2867 “Oscillator design guide for ST microcontrollers” available from the ST website [www.st.com](http://www.st.com).

**Figure 26. Typical application with an 8 MHz crystal**



1.  $R_{EXT}$  value depends on the crystal characteristics.

**Low-speed external clock generated from a crystal/ceramic resonator**

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in [Table 39](#). In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

**Table 39. LSE oscillator characteristics ( $f_{LSE} = 32.768$  kHz) <sup>(1)</sup>**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{DD}$	LSE current consumption	LSEDRV[1:0]=00 Low drive capability	-	250	-	nA
		LSEDRV[1:0]=10 Medium low drive capability	-	300	-	
		LSEDRV[1:0]=01 Medium high drive capability	-	370	-	
		LSEDRV[1:0]=11 High drive capability	-	480	-	

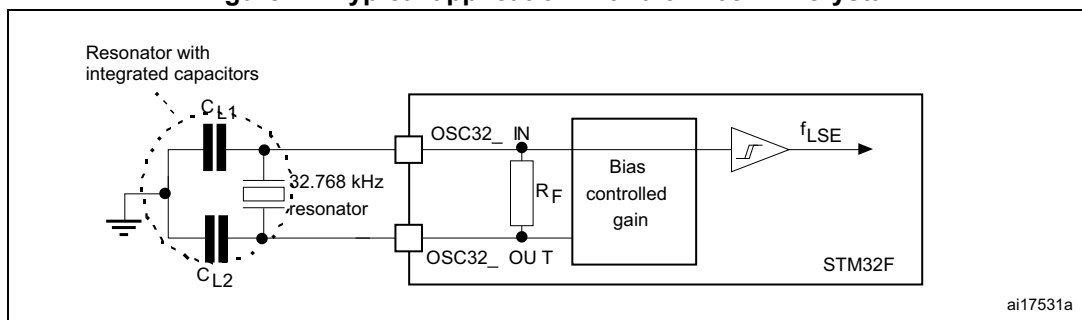
**Table 39. LSE oscillator characteristics ( $f_{LSE} = 32.768$  kHz) <sup>(1)</sup> (continued)**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$G_{m\_crit\_max}$	Maximum critical crystal $g_m$	LSEDRV[1:0]=00 Low drive capability	-	-	0.48	$\mu A/V$
		LSEDRV[1:0]=10 Medium low drive capability	-	-	0.75	
		LSEDRV[1:0]=01 Medium high drive capability	-	-	1.7	
		LSEDRV[1:0]=11 High drive capability	-	-	2.7	
$t_{SU}^{(2)}$	start-up time	$V_{DD}$ is stabilized	-	2	-	s

1. Guaranteed by design.
2. Guaranteed by characterization results.  $t_{SU}$  is the start-up time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

*Note:* For information on selecting the crystal, refer to the application note AN2867 “Oscillator design guide for ST microcontrollers” available from the ST website [www.st.com](http://www.st.com).

**Figure 27. Typical application with a 32.768 kHz crystal**



### 6.3.10 Internal clock source characteristics

The parameters given in [Table 40](#) and [Table 41](#) are derived from tests performed under ambient temperature and  $V_{DD}$  supply voltage conditions summarized in [Table 16](#).

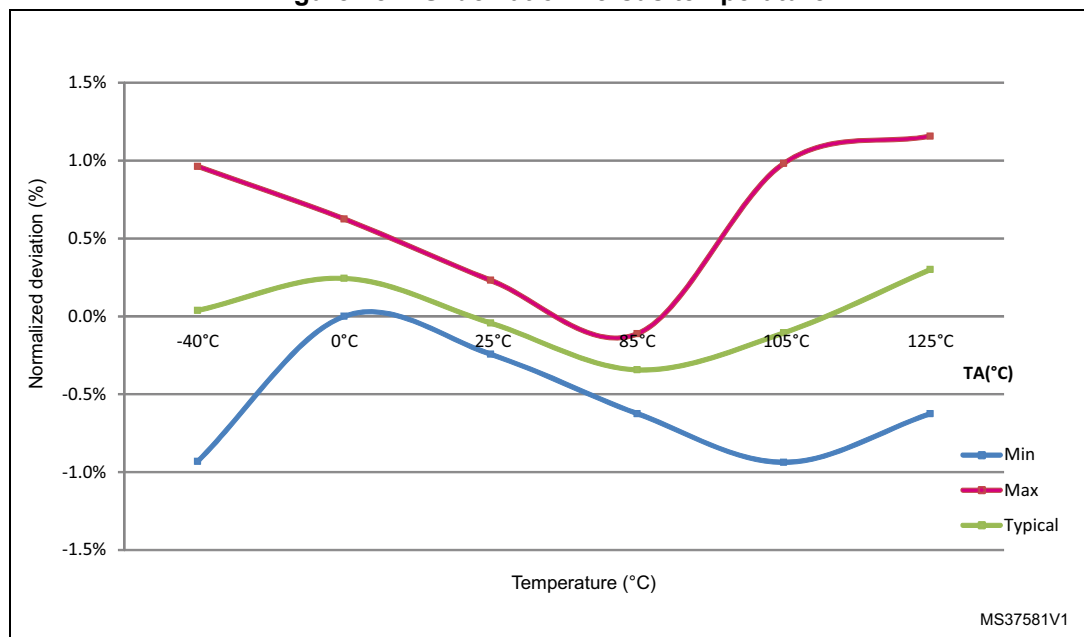
#### High-speed internal (HSI) RC oscillator

**Table 40. HSI oscillator characteristics <sup>(1)</sup>**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$f_{HSI}$	Frequency	-	-	16	-	MHz
$ACC_{HSI}$	HSI user trimming step <sup>(2)</sup>	-	-	-	1	%
	Accuracy of the HSI oscillator	$T_A = -40$ to $105$ °C <sup>(3)</sup>	- 8	-	4.5	%
		$T_A = -10$ to $85$ °C <sup>(3)</sup>	- 4	-	4	%
		$T_A = 25$ °C <sup>(4)</sup>	- 1	-	1	%
$t_{su(HSI)}$ <sup>(2)</sup>	HSI oscillator startup time	-	-	2.2	4	μs
$I_{DD(HSI)}$ <sup>(2)</sup>	HSI oscillator power consumption	-	-	60	80	μA

- $V_{DD} = 3.3$  V,  $T_A = -40$  to  $105$  °C unless otherwise specified.
- Guaranteed by design.
- Guaranteed by characterization results.
- Factory calibrated, parts not soldered.

**Figure 28. HSI deviation versus temperature**



- Guaranteed by characterization results.

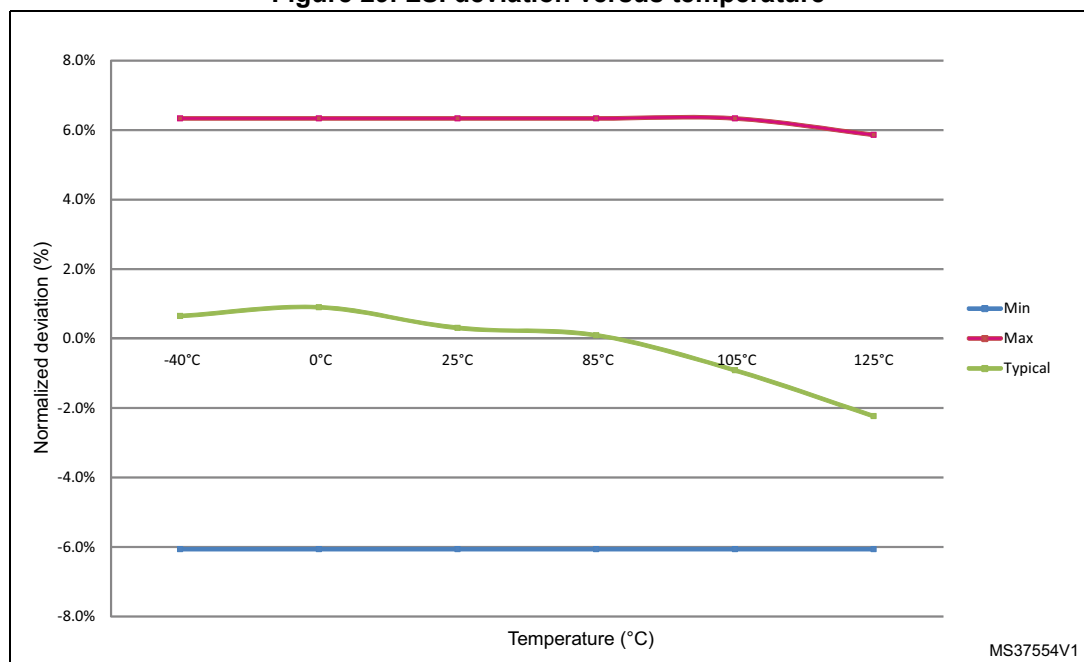
Low-speed internal (LSI) RC oscillator

Table 41. LSI oscillator characteristics <sup>(1)</sup>

Symbol	Parameter	Min	Typ	Max	Unit
$f_{LSI}^{(2)}$	Frequency	17	32	47	kHz
$t_{su(LSI)}^{(3)}$	LSI oscillator startup time	-	15	40	$\mu s$
$I_{DD(LSI)}^{(3)}$	LSI oscillator power consumption	-	0.4	0.6	$\mu A$

- $V_{DD} = 3 V, T_A = -40$  to  $105$  °C unless otherwise specified.
- Guaranteed by characterization results.
- Guaranteed by design.

Figure 29. LSI deviation versus temperature



6.3.11 PLL characteristics

The parameters given in [Table 42](#) and [Table 43](#) are derived from tests performed under temperature and  $V_{DD}$  supply voltage conditions summarized in [Table 16](#).

Table 42. Main PLL characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$f_{PLL\_IN}$	PLL input clock <sup>(1)</sup>	-	0.95 <sup>(2)</sup>	1	2.10	MHz
$f_{PLL\_OUT}$	PLL multiplier output clock	-	24	-	216	
$f_{PLL48\_OUT}$	48 MHz PLL multiplier output clock	-	-	48	75	
$f_{VCO\_OUT}$	PLL VCO output	-	100	-	432	

**Table 42. Main PLL characteristics (continued)**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
t <sub>LOCK</sub>	PLL lock time	VCO freq = 100 MHz	75	-	200	µs	
		VCO freq = 432 MHz	100	-	300		
Jitter <sup>(3)</sup>	Cycle-to-cycle jitter	System clock 216 MHz	RMS	-	25	-	ps
			peak to peak	-	±150	-	
	RMS		-	15	-		
	peak to peak		-	±200	-		
	Period Jitter						
	Main clock output (MCO) for RMI Ethernet	Cycle to cycle at 50 MHz on 1000 samples	-	32	-		
	Main clock output (MCO) for MII Ethernet	Cycle to cycle at 25 MHz on 1000 samples	-	40	-		
	Bit Time CAN jitter	Cycle to cycle at 1 MHz on 1000 samples	-	330	-		
I <sub>DD(PLL)</sub> <sup>(4)</sup>	PLL power consumption on V <sub>DD</sub>	VCO freq = 100 MHz	0.15	-	0.40	mA	
		VCO freq = 432 MHz	0.45	-	0.75		
I <sub>DDA(PLL)</sub> <sup>(4)</sup>	PLL power consumption on V <sub>DDA</sub>	VCO freq = 100 MHz	0.30	-	0.40	mA	
		VCO freq = 432 MHz	0.55	-	0.85		

1. Take care of using the appropriate division factor M to obtain the specified PLL input clock values. The M factor is shared between PLL and PLLI2S.
2. Guaranteed by design.
3. The use of 2 PLLs in parallel could degraded the Jitter up to +30%.
4. Guaranteed by characterization results.

**Table 43. PLLI2S characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f <sub>PLLI2S_IN</sub>	PLLI2S input clock <sup>(1)</sup>	-	0.95 <sup>(2)</sup>	1	2.10	MHz
f <sub>PLLI2SP_OUT</sub>	PLLI2S multiplier output clock for SPDIFRX	-	-	-	216	
f <sub>PLLI2SQ_OUT</sub>	PLLI2S multiplier output clock for SAI	-	-	-	216	
f <sub>PLLI2SR_OUT</sub>	PLLI2S multiplier output clock for I2S	-	-	-	216	
f <sub>VCO_OUT</sub>	PLLI2S VCO output	-	100	-	432	
t <sub>LOCK</sub>	PLLI2S lock time	VCO freq = 100 MHz	75	-	200	µs
		VCO freq = 432 MHz	100	-	300	

**Table 43. PLLI2S characteristics (continued)**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
Jitter <sup>(3)</sup>	Master I2S clock jitter	Cycle to cycle at 12.288 MHz on 48KHz period, N=432, R=5	RMS	-	90	-	ps
			peak to peak	-	±280	-	
	WS I2S clock jitter	Cycle to cycle at 48 KHz on 1000 samples	Average frequency of 12.288 MHz N = 432, R = 5 on 1000 samples	-	90	-	ps
			-	-	400	-	ps
I <sub>DD(PLLI2S)</sub> <sup>(4)</sup>	PLLI2S power consumption on V <sub>DD</sub>	VCO freq = 100 MHz VCO freq = 432 MHz	0.15 0.45	-	0.40 0.75	mA	
I <sub>DDA(PLLI2S)</sub> <sup>(4)</sup>	PLLI2S power consumption on V <sub>DDA</sub>	VCO freq = 100 MHz VCO freq = 432 MHz	0.30 0.55	-	0.40 0.85	mA	

1. Take care of using the appropriate division factor M to have the specified PLL input clock values.
2. Guaranteed by design.
3. Value given with main PLL running.
4. Guaranteed by characterization results.

**Table 44. PLLSAI characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f <sub>PLLSAI_IN</sub>	PLLSAI input clock <sup>(1)</sup>	-	0.95 <sup>(2)</sup>	1	2.10	MHz
f <sub>PLLSAIP_OUT</sub>	PLLSAI multiplier output clock for 48 MHz	-	-	48	75	
f <sub>PLLSAIQ_OUT</sub>	PLLSAI multiplier output clock for SAI	-	-	-	216	
f <sub>PLLSAIR_OUT</sub>	PLLSAI multiplier output clock for LCD-TFT	-	-	-	216	
f <sub>VCO_OUT</sub>	PLLSAI VCO output	-	100	-	432	
t <sub>LOCK</sub>	PLLSAI lock time	VCO freq = 100 MHz	75	-	200	µs
		VCO freq = 432 MHz	100	-	300	

**Table 44. PLLISAI characteristics (continued)**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
Jitter <sup>(3)</sup>	Master SAI clock jitter	Cycle to cycle at 12.288 MHz on 48KHz period, N=432, R=5	RMS	-	90	-	
			peak to peak	-	±280	-	ps
		Average frequency of 12.288 MHz N = 432, R = 5 on 1000 samples	-	90	-	ps	
	FS clock jitter	Cycle to cycle at 48 KHz on 1000 samples	-	400	-	ps	
I <sub>DD(PLLSAI)</sub> <sup>(4)</sup>	PLLSAI power consumption on V <sub>DD</sub>	VCO freq = 100 MHz VCO freq = 432 MHz	0.15 0.45	-	0.40 0.75	mA	
I <sub>DDA(PLLSAI)</sub> <sup>(4)</sup>	PLLSAI power consumption on V <sub>DDA</sub>	VCO freq = 100 MHz VCO freq = 432 MHz	0.30 0.55	-	0.40 0.85	mA	

1. Take care of using the appropriate division factor M to have the specified PLL input clock values.
2. Guaranteed by design.
3. Value given with main PLL running.
4. Guaranteed by characterization results.

### 6.3.12 PLL spread spectrum clock generation (SSCG) characteristics

The spread spectrum clock generation (SSCG) feature allows to reduce electromagnetic interferences (see [Table 51: EMI characteristics](#)). It is available only on the main PLL.

**Table 45. SSCG parameters constraint**

Symbol	Parameter	Min	Typ	Max <sup>(1)</sup>	Unit
f <sub>Mod</sub>	Modulation frequency	-	-	10	KHz
md	Peak modulation depth	0.25	-	2	%
MODEPER * INCSTEP	-	-	-	2 <sup>15</sup> - 1	-

1. Guaranteed by design.

Equation 1

The frequency modulation period (MODEPER) is given by the equation below:

$$\text{MODEPER} = \text{round}[\text{f}_{\text{PLL\_IN}} / (4 \times \text{f}_{\text{Mod}})]$$

f<sub>PLL\_IN</sub> and f<sub>Mod</sub> must be expressed in Hz.

As an example:

If f<sub>PLL\_IN</sub> = 1 MHz, and f<sub>MOD</sub> = 1 kHz, the modulation depth (MODEPER) is given by equation 1:

$$\text{MODEPER} = \text{round}[10^6 / (4 \times 10^3)] = 250$$



Equation 2

Equation 2 allows to calculate the increment step (INCSTEP):

$$\text{INCSTEP} = \text{round}[\frac{(2^{15} - 1) \times \text{md} \times \text{PLLN}}{(100 \times 5 \times \text{MODEPER})}]$$

$f_{\text{VCO\_OUT}}$  must be expressed in MHz.

With a modulation depth (md) = ±2 % (4 % peak to peak), and PLLN = 240 (in MHz):

$$\text{INCSTEP} = \text{round}[\frac{(2^{15} - 1) \times 2 \times 240}{(100 \times 5 \times 250)}] = 126\text{md}(\text{quantitized})\%$$

An amplitude quantization error may be generated because the linear modulation profile is obtained by taking the quantized values (rounded to the nearest integer) of MODPER and INCSTEP. As a result, the achieved modulation depth is quantized. The percentage quantized modulation depth is given by the following formula:

$$\text{md}_{\text{quantitized}}\% = \frac{(\text{MODEPER} \times \text{INCSTEP} \times 100 \times 5)}{(2^{15} - 1) \times \text{PLLN}}$$

As a result:

$$\text{md}_{\text{quantitized}}\% = \frac{(250 \times 126 \times 100 \times 5)}{(2^{15} - 1) \times 240} = 2.002\%(\text{peak})$$

Figure 30 and Figure 31 show the main PLL output clock waveforms in center spread and down spread modes, where:

F0 is  $f_{\text{PLL\_OUT}}$  nominal.

$T_{\text{mode}}$  is the modulation period.

md is the modulation depth.

**Figure 30. PLL output clock waveforms in center spread mode**

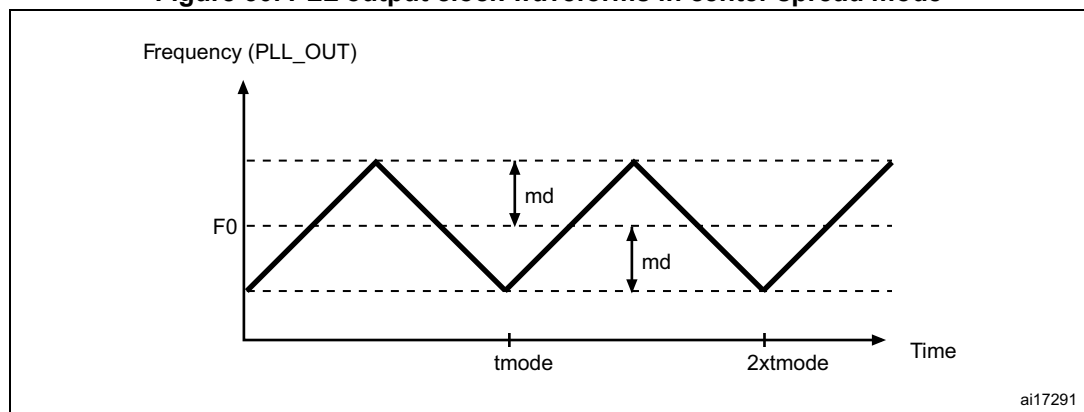
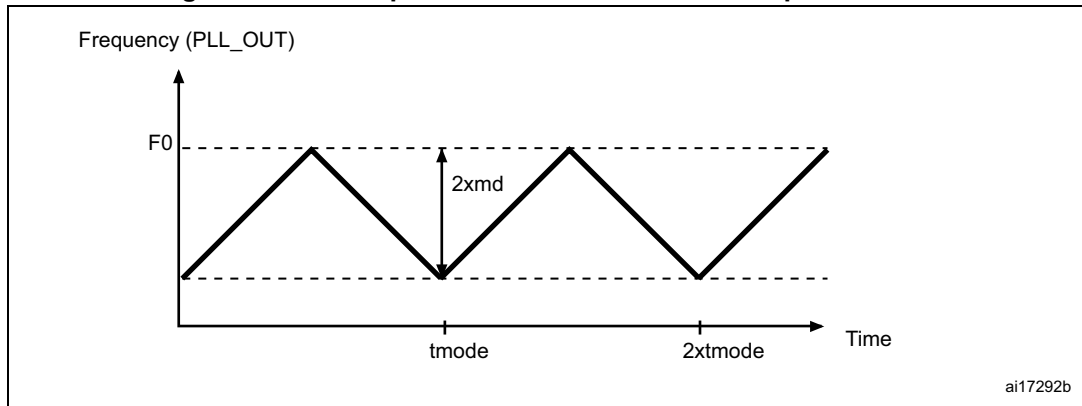


Figure 31. PLL output clock waveforms in down spread mode



### 6.3.13 Memory characteristics

#### Flash memory

The characteristics are given at TA = -40 to 105 °C unless otherwise specified.

The devices are shipped to customers with the Flash memory erased.

Table 46. Flash memory characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I <sub>DD</sub>	Supply current	Write / Erase 8-bit mode, V <sub>DD</sub> = 1.7 V	-	14	-	mA
		Write / Erase 16-bit mode, V <sub>DD</sub> = 2.1 V	-	17	-	
		Write / Erase 32-bit mode, V <sub>DD</sub> = 3.3 V	-	24	-	

Table 47. Flash memory programming

Symbol	Parameter	Conditions	Min <sup>(1)</sup>	Typ	Max <sup>(1)</sup>	Unit
t <sub>prog</sub>	Word programming time	Program/erase parallelism (PSIZE) = x 8/16/32	-	16	100 <sup>(2)</sup>	µs
t <sub>ERASE32KB</sub>	Sector (32 KB) erase time	Program/erase parallelism (PSIZE) = x 8	-	400	800	ms
		Program/erase parallelism (PSIZE) = x 16	-	250	600	
		Program/erase parallelism (PSIZE) = x 32	-	200	500	
t <sub>ERASE128KB</sub>	Sector (128 KB) erase time	Program/erase parallelism (PSIZE) = x 8	-	1100	2400	ms
		Program/erase parallelism (PSIZE) = x 16	-	800	1400	
		Program/erase parallelism (PSIZE) = x 32	-	500	1100	

**Table 47. Flash memory programming (continued)**

Symbol	Parameter	Conditions	Min <sup>(1)</sup>	Typ	Max <sup>(1)</sup>	Unit
t <sub>ERASE256KB</sub>	Sector (256 KB) erase time	Program/erase parallelism (PSIZE) = x 8	-	2.1	4	s
		Program/erase parallelism (PSIZE) = x 16	-	1.5	2.6	
		Program/erase parallelism (PSIZE) = x 32	-	1	2	
t <sub>ME</sub>	Mass erase time	Program/erase parallelism (PSIZE) = x 8	-	8	16	s
		Program/erase parallelism (PSIZE) = x 16	-	5.6	11.2	
		Program/erase parallelism (PSIZE) = x 32	-	4	8	
V <sub>prog</sub>	Programming voltage	32-bit program operation	2.7	-	3	V
		16-bit program operation	2.1	-	3.6	V
		8-bit program operation	1.7	-	3.6	V

1. Guaranteed by characterization results.
2. The maximum programming time is measured after 100K erase operations.

**Table 48. Flash memory programming with V<sub>PP</sub>**

Symbol	Parameter	Conditions	Min <sup>(1)</sup>	Typ	Max <sup>(1)</sup>	Unit
t <sub>prog</sub>	Double word programming	T <sub>A</sub> = 0 to +40 °C V <sub>DD</sub> = 3.3 V V <sub>PP</sub> = 8.5 V	-	16	100 <sup>(2)</sup>	µs
t <sub>ERASE32KB</sub>	Sector (32 KB) erase time		-	180	-	ms
t <sub>ERASE128KB</sub>	Sector (128 KB) erase time		-	450	-	
t <sub>ERASE256KB</sub>	Sector (256 KB) erase time		-	900	-	
t <sub>ME</sub>	Mass erase time	-	-	6.9	-	s
V <sub>prog</sub>	Programming voltage	-	2.7	-	3.6	V
V <sub>PP</sub>	V <sub>PP</sub> voltage range	-	7	-	9	V
I <sub>PP</sub>	Minimum current sunk on the V <sub>PP</sub> pin	-	10	-	-	mA
t <sub>VPP</sub> <sup>(3)</sup>	Cumulative time during which V <sub>PP</sub> is applied	-	-	-	1	hour

1. Guaranteed by design.
2. The maximum programming time is measured after 100K erase operations.
3. V<sub>PP</sub> should only be connected during programming/erasing.

**Table 49. Flash memory endurance and data retention**

Symbol	Parameter	Conditions	Value	Unit
			Min <sup>(1)</sup>	
N <sub>END</sub>	Endurance	T <sub>A</sub> = -40 to +85 °C (6 suffix versions) T <sub>A</sub> = -40 to +105 °C (7 suffix versions)	10	kcycles
t <sub>RET</sub>	Data retention	1 kcycle <sup>(2)</sup> at T <sub>A</sub> = 85 °C	30	Years
		1 kcycle <sup>(2)</sup> at T <sub>A</sub> = 105 °C	10	
		10 kcycles <sup>(2)</sup> at T <sub>A</sub> = 55 °C	20	

1. Guaranteed by characterization results.
2. Cycling performed over the whole temperature range.

### 6.3.14 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

#### Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports), the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB:** A burst of fast transient voltage (positive and negative) is applied to V<sub>DD</sub> and V<sub>SS</sub> through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in [Table 50](#). They are based on the EMS levels and classes defined in application note AN1709.

**Table 50. EMS characteristics**

Symbol	Parameter	Conditions	Level/Class
V <sub>FESD</sub>	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V <sub>DD</sub> = 3.3 V, T <sub>A</sub> = +25 °C, f <sub>HCLK</sub> = 216 MHz, conforms to IEC 61000-4-2	2B
V <sub>EFTB</sub>	Fast transient voltage burst limits to be applied through 100 pF on V <sub>DD</sub> and V <sub>SS</sub> pins to induce a functional disturbance	V <sub>DD</sub> = 3.3 V, TFBGA216, T <sub>A</sub> = +25 °C, f <sub>HCLK</sub> = 216 MHz, conforms to IEC 61000-4-2	4A

As a consequence, it is recommended to add a serial resistor (1 kΩ) located as close as possible to the MCU to the pins exposed to noise (connected to tracks longer than 50 mm on PCB).

### Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

#### Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)

#### Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

### Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application, executing EEMBC code, is running. This emission test is compliant with SAE IEC61967-2 standard which specifies the test board and the pin loading.

**Table 51. EMI characteristics**

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. [f <sub>HSE</sub> /f <sub>CPU</sub> ]	Unit
				25/200 MHz	
S <sub>EMI</sub>	Peak level	V <sub>DD</sub> = 3.6 V, T <sub>A</sub> = 25 °C, TFBGA216 package, conforming to IEC61967-2 ART/L1-cache OFF, over-drive ON, all peripheral clocks enabled, clock dithering disabled.	0.1 to 30 MHz	- 4	dBμV
			30 to 130 MHz	9	
			130 MHz to 1GHz	11	
			EMI Level	3	-
		V <sub>DD</sub> = 3.6 V, T <sub>A</sub> = 25 °C, TFBGA216 package, conforming to IEC61967-2 ART/L1-cache ON, over-drive ON, all peripheral clocks enabled, clock dithering disabled.	0.1 to 30 MHz	4	dBμV
			30 to 130 MHz	5	
			130 MHz to 1GHz	14	
			EMI level	3	-
		V <sub>DD</sub> = 3.6 V, T <sub>A</sub> = 25 °C, TFBGA216 package, conforming to IEC61967-2 ART/L1-cache ON, over-drive ON, all peripheral clocks enabled, clock dithering enabled.	0.1 to 30 MHz	- 9	dBμV
			30 to 130 MHz	-7	
			130 MHz to 1GHz	-5	
			EMI level	1.5	-

### 6.3.15 Absolute maximum ratings (electrical sensitivity)

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

#### Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the ANSI/ESDA/JEDEC JS-001-2012 and ANSI/ESD S5.3.1-2009 standards.

**Table 52. ESD absolute maximum ratings**

Symbol	Ratings	Conditions	Class	Maximum value <sup>(1)</sup>	Unit
V <sub>ESD(HBM)</sub>	Electrostatic discharge voltage (human body model)	T <sub>A</sub> = +25 °C conforming to ANSI/ESDA/JEDEC JS-001-2012	2	2000	V
V <sub>ESD(CDM)</sub>	Electrostatic discharge voltage (charge device model)	T <sub>A</sub> = +25 °C conforming to ANSI/ESD S5.3.1-2009, LQFP100, LQFP144 and TFBGA216 packages	C3	250	

1. Guaranteed by characterization results.

#### Static latchup

Two complementary static tests are required on six parts to assess the latchup performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD 78A IC latchup standard.

**Table 53. Electrical sensitivities**

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	T <sub>A</sub> = +105 °C conforming to JESD78A	II level A

### 6.3.16 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V<sub>SS</sub> or above V<sub>DD</sub> (for standard, 3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

#### Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (>5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of –

5  $\mu\text{A}/+0 \mu\text{A}$  range), or other functional failure (for example reset, oscillator frequency deviation).

Negative induced leakage current is caused by negative injection and positive induced leakage current by positive injection.

The test results are given in [Table 54](#).

**Table 54. I/O current injection susceptibility<sup>(1)</sup>**

Symbol	Description	Functional susceptibility		Unit
		Negative injection	Positive injection	
I <sub>INJ</sub>	Injected current on BOOT pin	- 0	NA	mA
	Injected current on NRST pin	- 0	NA	
	Injected current on PA0, PC0 pins	- 0	NA	
	Injected current on any other FT pin	- 5	NA	
	Injected current on any other pins	- 5	+5	

1. NA = not applicable.

*Note: It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.*

### 6.3.17 I/O port characteristics

#### General input/output characteristics

Unless otherwise specified, the parameters given in [Table 55: I/O static characteristics](#) are derived from tests performed under the conditions summarized in [Table 16](#). All I/Os are CMOS and TTL compliant.

**Table 55. I/O static characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>IL</sub>	FT, TTA and NRST I/O input low level voltage	1.7 V ≤ V <sub>DD</sub> ≤ 3.6 V	-	-	0.35V <sub>DD</sub> - 0.04 <sup>(1)</sup>	V
					0.3V <sub>DD</sub> <sup>(2)</sup>	
	BOOT I/O input low level voltage	1.75 V ≤ V <sub>DD</sub> ≤ 3.6 V, -40 °C ≤ T <sub>A</sub> ≤ 105 °C	-	-	0.1V <sub>DD</sub> + 0.1 <sup>(1)</sup>	
1.7 V ≤ V <sub>DD</sub> ≤ 3.6 V, 0 °C ≤ T <sub>A</sub> ≤ 105 °C						
V <sub>IH</sub>	FT, TTA and NRST I/O input high level voltage <sup>(5)</sup>	1.7 V ≤ V <sub>DD</sub> ≤ 3.6 V	0.45V <sub>DD</sub> + 0.3 <sup>(1)</sup>	-	-	V
			0.7V <sub>DD</sub> <sup>(2)</sup>			
	BOOT I/O input high level voltage	1.75 V ≤ V <sub>DD</sub> ≤ 3.6 V, -40 °C ≤ T <sub>A</sub> ≤ 105 °C	0.17V <sub>DD</sub> + 0.7 <sup>(1)</sup>	-	-	
1.7 V ≤ V <sub>DD</sub> ≤ 3.6 V, 0 °C ≤ T <sub>A</sub> ≤ 105 °C						

Table 55. I/O static characteristics (continued)

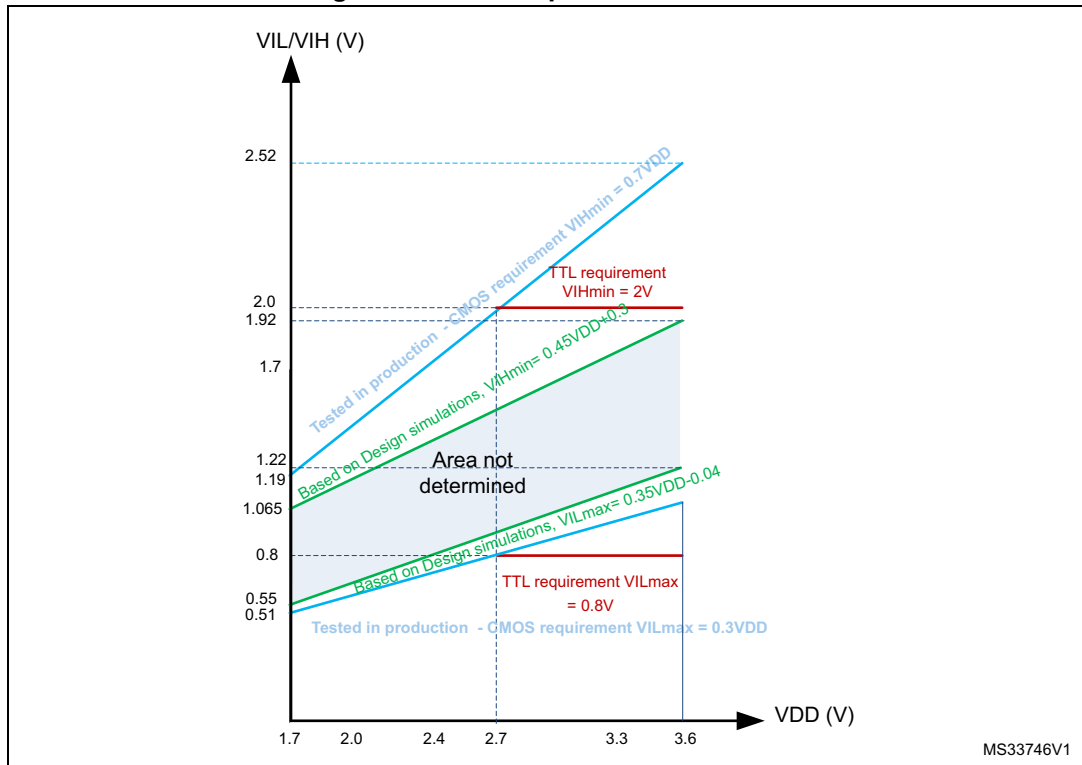
Symbol	Parameter		Conditions	Min	Typ	Max	Unit
V <sub>HYS</sub>	FT, TTA and NRST I/O input hysteresis		1.7 V ≤ V <sub>DD</sub> ≤ 3.6 V	10%V <sub>DD</sub> <sup>(3)</sup>	-	-	V
	BOOT I/O input hysteresis		1.75 V ≤ V <sub>DD</sub> ≤ 3.6 V, -40 °C ≤ T <sub>A</sub> ≤ 105 °C	0.1	-	-	
			1.7 V ≤ V <sub>DD</sub> ≤ 3.6 V, 0 °C ≤ T <sub>A</sub> ≤ 105 °C				
I <sub>lkg</sub>	I/O input leakage current <sup>(4)</sup>		V <sub>SS</sub> ≤ V <sub>IN</sub> ≤ V <sub>DD</sub>	-	-	±1	μA
	I/O FT input leakage current <sup>(5)</sup>		V <sub>IN</sub> = 5 V	-	-	3	
R <sub>PU</sub>	Weak pull-up equivalent resistor <sup>(6)</sup>	All pins except for PA10/PB12 (OTG_FS_ID, OTG_HS_ID)	V <sub>IN</sub> = V <sub>SS</sub>	30	40	50	kΩ
		PA10/PB12 (OTG_FS_ID, OTG_HS_ID)		7	10	14	
R <sub>PD</sub>	Weak pull-down equivalent resistor <sup>(7)</sup>	All pins except for PA10/PB12 (OTG_FS_ID, OTG_HS_ID)	V <sub>IN</sub> = V <sub>DD</sub>	30	40	50	
		PA10/PB12 (OTG_FS_ID, OTG_HS_ID)		7	10	14	
C <sub>IO</sub> <sup>(8)</sup>	I/O pin capacitance		-	-	5	-	pF

1. Guaranteed by design.
2. Tested in production.
3. With a minimum of 200 mV.
4. Leakage could be higher than the maximum value, if negative current is injected on adjacent pins, Refer to [Table 54: I/O current injection susceptibility](#)
5. To sustain a voltage higher than VDD +0.3 V, the internal pull-up/pull-down resistors must be disabled. Leakage could be higher than the maximum value, if negative current is injected on adjacent pins. Refer to [Table 54: I/O current injection susceptibility](#)
6. Pull-up resistors are designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is minimum (~10% order).
7. Pull-down resistors are designed with a true resistance in series with a switchable NMOS. This NMOS contribution to the series resistance is minimum (~10% order).
8. Hysteresis voltage between Schmitt trigger switching levels. Guaranteed by characterization results.

All I/Os are CMOS and TTL compliant (no software configuration required). Their characteristics cover more than the strict CMOS-technology or TTL parameters. The coverage of these requirements for FT I/Os is shown in [Figure 32](#).



Figure 32. FT I/O input characteristics



**Output driving current**

The GPIOs (general purpose input/outputs) can sink or source up to  $\pm 8$  mA, and sink or source up to  $\pm 20$  mA (with a relaxed  $V_{OL}/V_{OH}$ ) except PC13, PC14, PC15 and PI8 which can sink or source up to  $\pm 3$ mA. When using the PC13 to PC15 and PI8 GPIOs in output mode, the speed should not exceed 2 MHz with a maximum load of 30 pF.

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in Section 6.2. In particular:

- The sum of the currents sourced by all the I/Os on  $V_{DD}$ , plus the maximum Run consumption of the MCU sourced on  $V_{DD}$ , cannot exceed the absolute maximum rating  $\Sigma I_{VDD}$  (see Table 14).
- The sum of the currents sunk by all the I/Os on  $V_{SS}$  plus the maximum Run consumption of the MCU sunk on  $V_{SS}$  cannot exceed the absolute maximum rating  $\Sigma I_{VSS}$  (see Table 14).

**Output voltage levels**

Unless otherwise specified, the parameters given in Table 56 are derived from tests performed under ambient temperature and  $V_{DD}$  supply voltage conditions summarized in Table 16. All I/Os are CMOS and TTL compliant.

Table 56. Output voltage characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{OL}^{(1)}$	Output low level voltage for an I/O pin	CMOS port <sup>(2)</sup> $I_{IO} = +8 \text{ mA}$ $2.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$	-	0.4	V
$V_{OH}^{(3)}$	Output high level voltage for an I/O pin except PC14	CMOS port <sup>(2)</sup> $I_{IO} = -8 \text{ mA}$ $2.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$	$V_{DD} - 0.4$	-	
$V_{OH}^{(3)}$	Output high level voltage for PC14	CMOS port <sup>(2)</sup> $I_{IO} = -2 \text{ mA}$ $2.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$	$V_{DD} - 0.4$	-	
$V_{OL}^{(1)}$	Output low level voltage for an I/O pin	TTL port <sup>(2)</sup> $I_{IO} = +8 \text{ mA}$ $2.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$	-	0.4	V
$V_{OH}^{(3)}$	Output high level voltage for an I/O pin except PC14	TTL port <sup>(2)</sup> $I_{IO} = -8 \text{ mA}$ $2.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$	2.4	-	
$V_{OL}^{(1)}$	Output low level voltage for an I/O pin	$I_{IO} = +20 \text{ mA}$ $2.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$	-	1.3 <sup>(4)</sup>	V
$V_{OH}^{(3)}$	Output high level voltage for an I/O pin except PC14	$I_{IO} = -20 \text{ mA}$ $2.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$	$V_{DD} - 1.3^{(4)}$	-	
$V_{OL}^{(1)}$	Output low level voltage for an I/O pin	$I_{IO} = +6 \text{ mA}$ $1.8 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$	-	0.4 <sup>(4)</sup>	V
$V_{OH}^{(3)}$	Output high level voltage for an I/O pin except PC14	$I_{IO} = -6 \text{ mA}$ $1.8 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$	$V_{DD} - 0.4^{(4)}$	-	
$V_{OL}^{(1)}$	Output low level voltage for an I/O pin	$I_{IO} = +4 \text{ mA}$ $1.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$	-	0.4 <sup>(5)</sup>	V
$V_{OH}^{(3)}$	Output high level voltage for an I/O pin except PC14	$I_{IO} = -4 \text{ mA}$ $1.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$	$V_{DD} - 0.4^{(5)}$	-	
$V_{OH}^{(3)}$	Output high level voltage for PC14	$I_{IO} = -1 \text{ mA}$ $1.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$	$V_{DD} - 0.4^{(5)}$	-	

1. The  $I_{IO}$  current sunk by the device must always respect the absolute maximum rating specified in [Table 14](#). and the sum of  $I_{IO}$  (I/O ports and control pins) must not exceed  $I_{VSS}$ .
2. TTL and CMOS outputs are compatible with JEDEC standards JESD36 and JESD52.
3. The  $I_{IO}$  current sourced by the device must always respect the absolute maximum rating specified in [Table 14](#) and the sum of  $I_{IO}$  (I/O ports and control pins) must not exceed  $I_{VDD}$ .
4. Based on characterization data.
5. Guaranteed by design.

Input/output AC characteristics

The definition and values of input/output AC characteristics are given in [Figure 33](#) and [Table 57](#), respectively.

Unless otherwise specified, the parameters given in [Table 57](#) are derived from tests performed under the ambient temperature and  $V_{DD}$  supply voltage conditions summarized in [Table 16](#).

**Table 57. I/O AC characteristics<sup>(1)(2)</sup>**

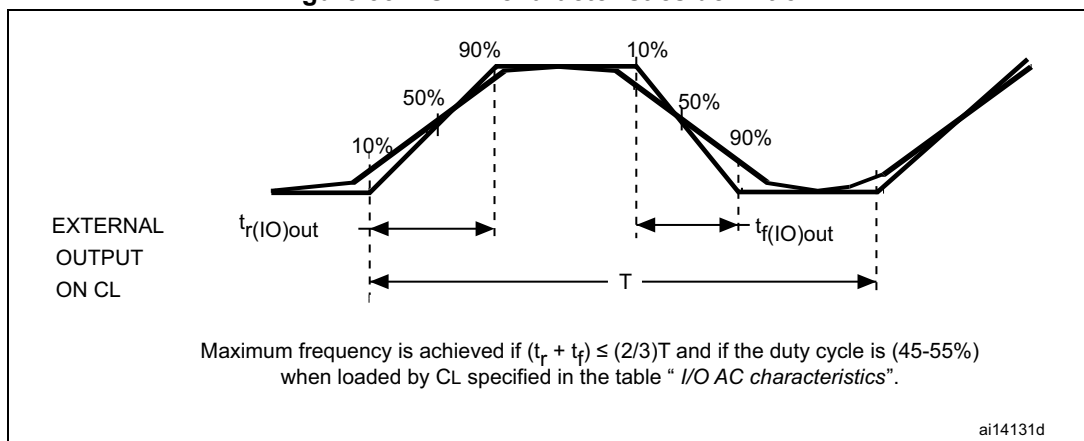
OSPEEDRy [1:0] bit value <sup>(1)</sup>	Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
00	$f_{\max(\text{IO})\text{out}}$	Maximum frequency <sup>(3)</sup>	$C_L = 50 \text{ pF}, V_{DD} \geq 2.7 \text{ V}$	-	-	4	MHz	
			$C_L = 50 \text{ pF}, V_{DD} \geq 1.7 \text{ V}$	-	-	2		
			$C_L = 10 \text{ pF}, V_{DD} \geq 2.7 \text{ V}$	-	-	8		
			$C_L = 10 \text{ pF}, V_{DD} \geq 1.8 \text{ V}$	-	-	4		
			$C_L = 10 \text{ pF}, V_{DD} \geq 1.7 \text{ V}$	-	-	3		
	$t_{f(\text{IO})\text{out}}/$ $t_{r(\text{IO})\text{out}}$	Output high to low level fall time and output low to high level rise time	$C_L = 50 \text{ pF}, V_{DD} = 1.7 \text{ V to } 3.6 \text{ V}$	-	-	100	ns	
01	$f_{\max(\text{IO})\text{out}}$	Maximum frequency <sup>(3)</sup>	$C_L = 50 \text{ pF}, V_{DD} \geq 2.7 \text{ V}$	-	-	25	MHz	
			$C_L = 50 \text{ pF}, V_{DD} \geq 1.8 \text{ V}$	-	-	12.5		
			$C_L = 50 \text{ pF}, V_{DD} \geq 1.7 \text{ V}$	-	-	10		
			$C_L = 10 \text{ pF}, V_{DD} \geq 2.7 \text{ V}$	-	-	50		
			$C_L = 10 \text{ pF}, V_{DD} \geq 1.8 \text{ V}$	-	-	20		
			$C_L = 10 \text{ pF}, V_{DD} \geq 1.7 \text{ V}$	-	-	12.5		
		$t_{f(\text{IO})\text{out}}/$ $t_{r(\text{IO})\text{out}}$	Output high to low level fall time and output low to high level rise time	$C_L = 50 \text{ pF}, V_{DD} \geq 2.7 \text{ V}$	-	-	10	ns
		$C_L = 10 \text{ pF}, V_{DD} \geq 2.7 \text{ V}$	-	-	6			
		$C_L = 50 \text{ pF}, V_{DD} \geq 1.7 \text{ V}$	-	-	20			
		$C_L = 10 \text{ pF}, V_{DD} \geq 1.7 \text{ V}$	-	-	10			
10	$f_{\max(\text{IO})\text{out}}$	Maximum frequency <sup>(3)</sup>	$C_L = 40 \text{ pF}, V_{DD} \geq 2.7 \text{ V}$	-	-	50 <sup>(4)</sup>	MHz	
			$C_L = 10 \text{ pF}, V_{DD} \geq 2.7 \text{ V}$	-	-	100 <sup>(4)</sup>		
			$C_L = 40 \text{ pF}, V_{DD} \geq 1.7 \text{ V}$	-	-	25		
			$C_L = 10 \text{ pF}, V_{DD} \geq 1.8 \text{ V}$	-	-	50		
			$C_L = 10 \text{ pF}, V_{DD} \geq 1.7 \text{ V}$	-	-	42.5		
		$t_{f(\text{IO})\text{out}}/$ $t_{r(\text{IO})\text{out}}$	Output high to low level fall time and output low to high level rise time	$C_L = 40 \text{ pF}, V_{DD} \geq 2.7 \text{ V}$	-	-	6	ns
			$C_L = 10 \text{ pF}, V_{DD} \geq 2.7 \text{ V}$	-	-	4		
			$C_L = 40 \text{ pF}, V_{DD} \geq 1.7 \text{ V}$	-	-	10		
		$C_L = 10 \text{ pF}, V_{DD} \geq 1.7 \text{ V}$	-	-	6			

Table 57. I/O AC characteristics<sup>(1)(2)</sup> (continued)

OSPEEDRy [1:0] bit value <sup>(1)</sup>	Symbol	Parameter	Conditions	Min	Typ	Max	Unit
11	$f_{\max(\text{IO})\text{out}}$	Maximum frequency <sup>(3)</sup>	$C_L = 30 \text{ pF}, V_{DD} \geq 2.7 \text{ V}$	-	-	100 <sup>(4)</sup>	MHz
			$C_L = 30 \text{ pF}, V_{DD} \geq 1.8 \text{ V}$	-	-	50	
			$C_L = 30 \text{ pF}, V_{DD} \geq 1.7 \text{ V}$	-	-	42.5	
			$C_L = 10 \text{ pF}, V_{DD} \geq 2.7 \text{ V}$	-	-	180 <sup>(4)</sup>	
			$C_L = 10 \text{ pF}, V_{DD} \geq 1.8 \text{ V}$	-	-	100	
			$C_L = 10 \text{ pF}, V_{DD} \geq 1.7 \text{ V}$	-	-	72.5	
	$t_{f(\text{IO})\text{out}}/ t_{r(\text{IO})\text{out}}$	Output high to low level fall time and output low to high level rise time	$C_L = 30 \text{ pF}, V_{DD} \geq 2.7 \text{ V}$	-	-	4	ns
			$C_L = 30 \text{ pF}, V_{DD} \geq 1.8 \text{ V}$	-	-	6	
			$C_L = 30 \text{ pF}, V_{DD} \geq 1.7 \text{ V}$	-	-	7	
			$C_L = 10 \text{ pF}, V_{DD} \geq 2.7 \text{ V}$	-	-	2.5	
			$C_L = 10 \text{ pF}, V_{DD} \geq 1.8 \text{ V}$	-	-	3.5	
			$C_L = 10 \text{ pF}, V_{DD} \geq 1.7 \text{ V}$	-	-	4	
-	$t_{\text{EXTI}pw}$	Pulse width of external signals detected by the EXTI controller	-	10	-	-	ns

1. Guaranteed by design.
2. The I/O speed is configured using the OSPEEDRy[1:0] bits. Refer to the STM32F75xxx and STM32F74xxx reference manual for a description of the GPIOx\_SPEEDR GPIO port output speed register.
3. The maximum frequency is defined in [Figure 33](#).
4. For maximum frequencies above 50 MHz and  $V_{DD} > 2.4 \text{ V}$ , the compensation cell should be used.

Figure 33. I/O AC characteristics definition



### 6.3.18 NRST pin characteristics

The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor,  $R_{PU}$  (see [Table 55: I/O static characteristics](#)).

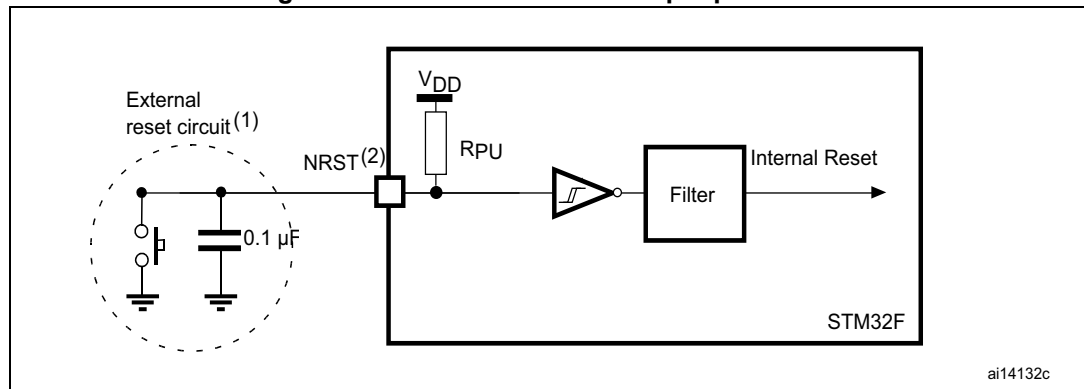
Unless otherwise specified, the parameters given in [Table 58](#) are derived from tests performed under the ambient temperature and  $V_{DD}$  supply voltage conditions summarized in [Table 16](#).

**Table 58. NRST pin characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{PU}$	Weak pull-up equivalent resistor <sup>(1)</sup>	$V_{IN} = V_{SS}$	30	40	50	k $\Omega$
$V_{F(NRST)}$ <sup>(2)</sup>	NRST Input filtered pulse	-	-	-	100	ns
$V_{NF(NRST)}$ <sup>(2)</sup>	NRST Input not filtered pulse	$V_{DD} > 2.7 V$	300	-	-	ns
$T_{NRST\_OUT}$	Generated reset pulse duration	Internal Reset source	20	-	-	$\mu s$

1. The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance must be minimum (~10% order).
2. Guaranteed by design.

**Figure 34. Recommended NRST pin protection**



1. The reset network protects the device against parasitic resets.
2. The user must ensure that the level on the NRST pin can go below the  $V_{IL(NRST)}$  max level specified in [Table 58](#). Otherwise the reset is not taken into account by the device.

### 6.3.19 TIM timer characteristics

The parameters given in [Table 59](#) are guaranteed by design.

Refer to [Section 6.3.17: I/O port characteristics](#) for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

**Table 59. TIMx characteristics<sup>(1)(2)</sup>**

Symbol	Parameter	Conditions <sup>(3)</sup>	Min	Max	Unit
t <sub>res(TIM)</sub>	Timer resolution time	AHB/APBx prescaler=1 or 2 or 4, f <sub>TIMxCLK</sub> = 216 MHz	1	-	t <sub>TIMxCLK</sub>
		AHB/APBx prescaler>4, f <sub>TIMxCLK</sub> = 108 MHz	1	-	t <sub>TIMxCLK</sub>
f <sub>EXT</sub>	Timer external clock frequency on CH1 to CH4	f <sub>TIMxCLK</sub> = 216 MHz	0	f <sub>TIMxCLK</sub> /2	MHz
Res <sub>TIM</sub>	Timer resolution		-	16/32	bit
t <sub>MAX_COUNT</sub>	Maximum possible count with 32-bit counter	-	-	65536 × 65536	t <sub>TIMxCLK</sub>

1. TIMx is used as a general term to refer to the TIM1 to TIM12 timers.
2. Guaranteed by design.
3. The maximum timer frequency on APB1 or APB2 is up to 216 MHz, by setting the TIMPRE bit in the RCC\_DCKCFGR register, if APBx prescaler is 1 or 2 or 4, then TIMxCLK = HCLK, otherwise TIMxCLK = 4x PCLKx.

### 6.3.20 RTC characteristics

**Table 60. RTC characteristics**

Symbol	Parameter	Conditions	Min	Max
-	f <sub>PCLK1</sub> /RTCCLK frequency ratio	Any read/write operation from/to an RTC register	4	-

### 6.3.21 12-bit ADC characteristics

Unless otherwise specified, the parameters given in [Table 61](#) are derived from tests performed under the ambient temperature, f<sub>PCLK2</sub> frequency and V<sub>DDA</sub> supply voltage conditions summarized in [Table 16](#).

**Table 61. ADC characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>DDA</sub>	Power supply	V <sub>DDA</sub> - V <sub>REF+</sub> < 1.2 V	1.7 <sup>(1)</sup>	-	3.6	V
V <sub>REF+</sub>	Positive reference voltage		1.7 <sup>(1)</sup>	-	V <sub>DDA</sub>	V
V <sub>REF-</sub>	Negative reference voltage	-	-	0	-	V

**Table 61. ADC characteristics (continued)**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f <sub>ADC</sub>	ADC clock frequency	V <sub>DDA</sub> = 1.7 <sup>(1)</sup> to 2.4 V	0.6	15	18	MHz
		V <sub>DDA</sub> = 2.4 to 3.6 V	0.6	30	36	MHz
f <sub>TRIG</sub> <sup>(2)</sup>	External trigger frequency	f <sub>ADC</sub> = 30 MHz, 12-bit resolution	-	-	1764	kHz
		-	-	-	17	1/f <sub>ADC</sub>
V <sub>AIN</sub>	Conversion voltage range <sup>(3)</sup>	-	0 (V <sub>SSA</sub> or V <sub>REF-</sub> tied to ground)	-	V <sub>REF+</sub>	V
R <sub>AIN</sub> <sup>(2)</sup>	External input impedance	See <a href="#">Equation 1</a> for details	-	-	50	kΩ
R <sub>ADC</sub> <sup>(2)(4)</sup>	Sampling switch resistance	-	-	-	6	kΩ
C <sub>ADC</sub> <sup>(2)</sup>	Internal sample and hold capacitor	-	-	4	7	pF
t <sub>lat</sub> <sup>(2)</sup>	Injection trigger conversion latency	f <sub>ADC</sub> = 30 MHz	-	-	0.100	μs
		-	-	-	3 <sup>(5)</sup>	1/f <sub>ADC</sub>
t <sub>latr</sub> <sup>(2)</sup>	Regular trigger conversion latency	f <sub>ADC</sub> = 30 MHz	-	-	0.067	μs
		-	-	-	2 <sup>(5)</sup>	1/f <sub>ADC</sub>
t <sub>S</sub> <sup>(2)</sup>	Sampling time	f <sub>ADC</sub> = 30 MHz	0.100	-	16	μs
		-	3	-	480	1/f <sub>ADC</sub>
t <sub>STAB</sub> <sup>(2)</sup>	Power-up time	-	-	2	3	μs
t <sub>CONV</sub> <sup>(2)</sup>	Total conversion time (including sampling time)	f <sub>ADC</sub> = 30 MHz 12-bit resolution	0.50	-	16.40	μs
		f <sub>ADC</sub> = 30 MHz 10-bit resolution	0.43	-	16.34	μs
		f <sub>ADC</sub> = 30 MHz 8-bit resolution	0.37	-	16.27	μs
		f <sub>ADC</sub> = 30 MHz 6-bit resolution	0.30	-	16.20	μs
		9 to 492 (t <sub>S</sub> for sampling +n-bit resolution for successive approximation)				
f <sub>S</sub> <sup>(2)</sup>	Sampling rate (f <sub>ADC</sub> = 30 MHz, and t <sub>S</sub> = 3 ADC cycles)	12-bit resolution Single ADC	-	-	2	Msp/s
		12-bit resolution Interleave Dual ADC mode	-	-	3.75	Msp/s
		12-bit resolution Interleave Triple ADC mode	-	-	6	Msp/s

Table 61. ADC characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{V_{REF+}}^{(2)}$	ADC $V_{REF}$ DC current consumption in conversion mode	-	-	300	500	$\mu A$
$I_{V_{DDA}}^{(2)}$	ADC $V_{DDA}$ DC current consumption in conversion mode	-	-	1.6	1.8	mA

- $V_{DDA}$  minimum value of 1.7 V is obtained with the use of an external power supply supervisor (refer to [Section 3.17.2: Internal reset OFF](#)).
- Guaranteed by characterization results.
- $V_{REF+}$  is internally connected to  $V_{DDA}$  and  $V_{REF-}$  is internally connected to  $V_{SSA}$ .
- $R_{ADC}$  maximum value is given for  $V_{DD}=1.7$  V, and minimum value for  $V_{DD}=3.3$  V.
- For external triggers, a delay of  $1/f_{PCLK2}$  must be added to the latency specified in [Table 61](#).

**Equation 1:  $R_{AIN}$  max formula**

$$R_{AIN} = \frac{(k - 0.5)}{f_{ADC} \times C_{ADC} \times \ln(2^{N+2})} - R_{ADC}$$

The formula above ([Equation 1](#)) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. N = 12 (from 12-bit resolution) and k is the number of sampling periods defined in the ADC\_SMPR1 register.

Table 62. ADC static accuracy at  $f_{ADC} = 18$  MHz

Symbol	Parameter	Test conditions	Typ	Max <sup>(1)</sup>	Unit
ET	Total unadjusted error	$f_{ADC} = 18$ MHz $V_{DDA} = 1.7$ to $3.6$ V $V_{REF} = 1.7$ to $3.6$ V $V_{DDA} - V_{REF} < 1.2$ V	$\pm 3$	$\pm 4$	LSB
EO	Offset error		$\pm 2$	$\pm 3$	
EG	Gain error		$\pm 1$	$\pm 3$	
ED	Differential linearity error		$\pm 1$	$\pm 2$	
EL	Integral linearity error		$\pm 2$	$\pm 3$	

- Guaranteed by characterization results.

Table 63. ADC static accuracy at  $f_{ADC} = 30$  MHz

Symbol	Parameter	Test conditions	Typ	Max <sup>(1)</sup>	Unit
ET	Total unadjusted error	$f_{ADC} = 30$ MHz, $R_{AIN} < 10$ k $\Omega$ , $V_{DDA} = 2.4$ to $3.6$ V, $V_{REF} = 1.7$ to $3.6$ V, $V_{DDA} - V_{REF} < 1.2$ V	$\pm 2$	$\pm 5$	LSB
EO	Offset error		$\pm 1.5$	$\pm 2.5$	
EG	Gain error		$\pm 1.5$	$\pm 4$	
ED	Differential linearity error		$\pm 1$	$\pm 2$	
EL	Integral linearity error		$\pm 1.5$	$\pm 3$	

- Guaranteed by characterization results.



**Table 64. ADC static accuracy at  $f_{ADC} = 36$  MHz**

Symbol	Parameter	Test conditions	Typ	Max <sup>(1)</sup>	Unit
ET	Total unadjusted error	$f_{ADC} = 36$ MHz, $V_{DDA} = 2.4$ to $3.6$ V, $V_{REF} = 1.7$ to $3.6$ V $V_{DDA} - V_{REF} < 1.2$ V	±4	±7	LSB
EO	Offset error		±2	±3	
EG	Gain error		±3	±6	
ED	Differential linearity error		±2	±3	
EL	Integral linearity error		±3	±6	

1. Guaranteed by characterization results.

**Table 65. ADC dynamic accuracy at  $f_{ADC} = 18$  MHz - limited test conditions<sup>(1)</sup>**

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
ENOB	Effective number of bits	$f_{ADC} = 18$ MHz $V_{DDA} = V_{REF+} = 1.7$ V Input Frequency = 20 KHz Temperature = 25 °C	10.3	10.4	-	bits
SINAD	Signal-to-noise and distortion ratio		64	64.2	-	dB
SNR	Signal-to-noise ratio		64	65	-	
THD	Total harmonic distortion		- 67	- 72	-	

1. Guaranteed by characterization results.

**Table 66. ADC dynamic accuracy at  $f_{ADC} = 36$  MHz - limited test conditions<sup>(1)</sup>**

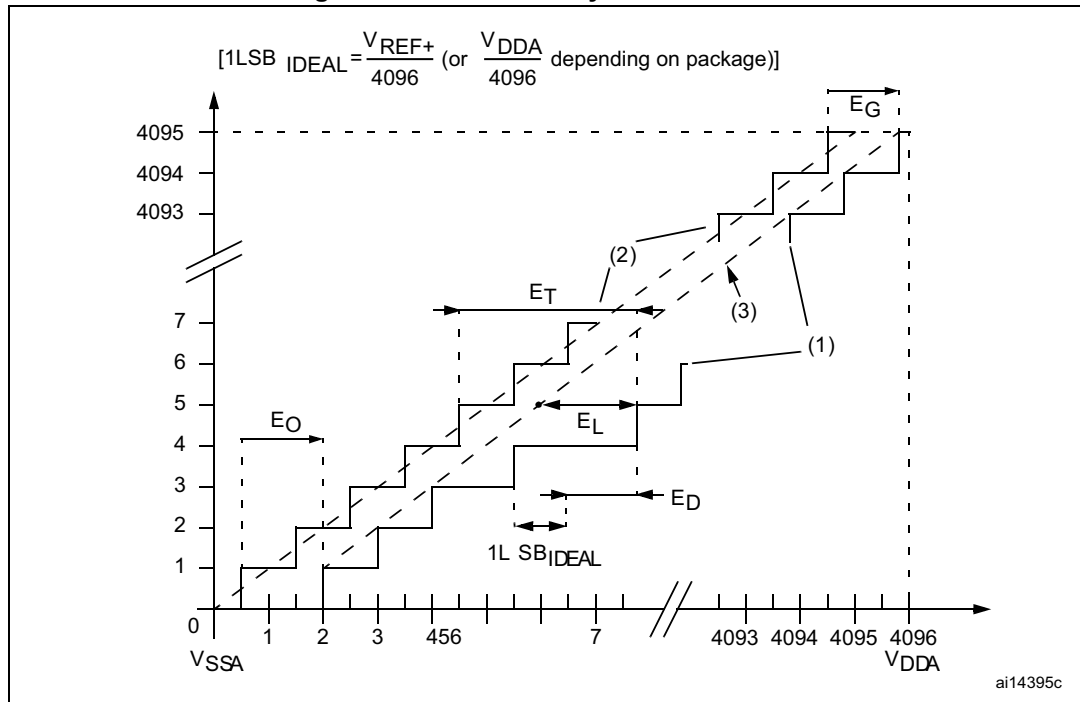
Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
ENOB	Effective number of bits	$f_{ADC} = 36$ MHz $V_{DDA} = V_{REF+} = 3.3$ V Input Frequency = 20 KHz Temperature = 25 °C	10.6	10.8	-	bits
SINAD	Signal-to noise and distortion ratio		66	67	-	dB
SNR	Signal-to noise ratio		64	68	-	
THD	Total harmonic distortion		- 70	- 72	-	

1. Guaranteed by characterization results.

Note: ADC accuracy vs. negative injection current: injecting a negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.

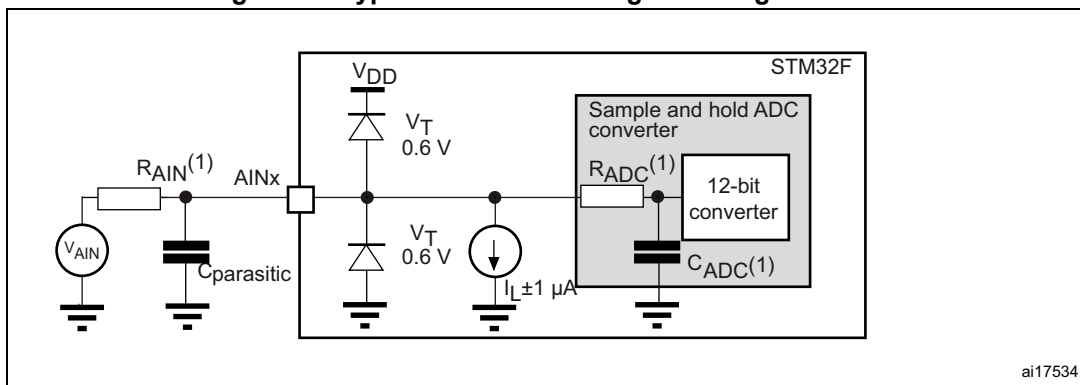
Any positive injection current within the limits specified for  $I_{INJ(PIN)}$  and  $\Sigma I_{INJ(PIN)}$  in [Section 6.3.17](#) does not affect the ADC accuracy.

Figure 35. ADC accuracy characteristics



1. See also [Table 63](#).
2. Example of an actual transfer curve.
3. Ideal transfer curve.
4. End point correlation line.
5.  $E_T$  = Total Unadjusted Error: maximum deviation between the actual and the ideal transfer curves.  
 $E_O$  = Offset Error: deviation between the first actual transition and the first ideal one.  
 $E_G$  = Gain Error: deviation between the last ideal transition and the last actual one.  
 $E_D$  = Differential Linearity Error: maximum deviation between actual steps and the ideal one.  
 $E_L$  = Integral Linearity Error: maximum deviation between any actual transition and the end point correlation line.

Figure 36. Typical connection diagram using the ADC

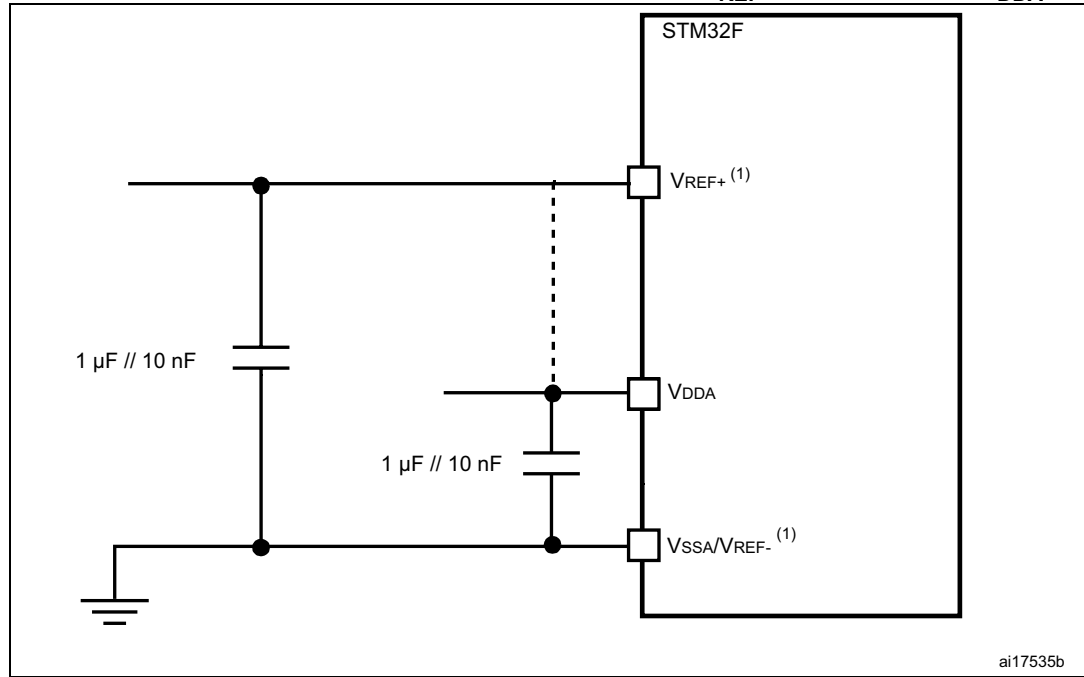


1. Refer to [Table 61](#) for the values of  $R_{AIN}$ ,  $R_{ADC}$  and  $C_{ADC}$ .
2.  $C_{parasitic}$  represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 5 pF). A high  $C_{parasitic}$  value downgrades conversion accuracy. To remedy this,  $f_{ADC}$  should be reduced.

**General PCB design guidelines**

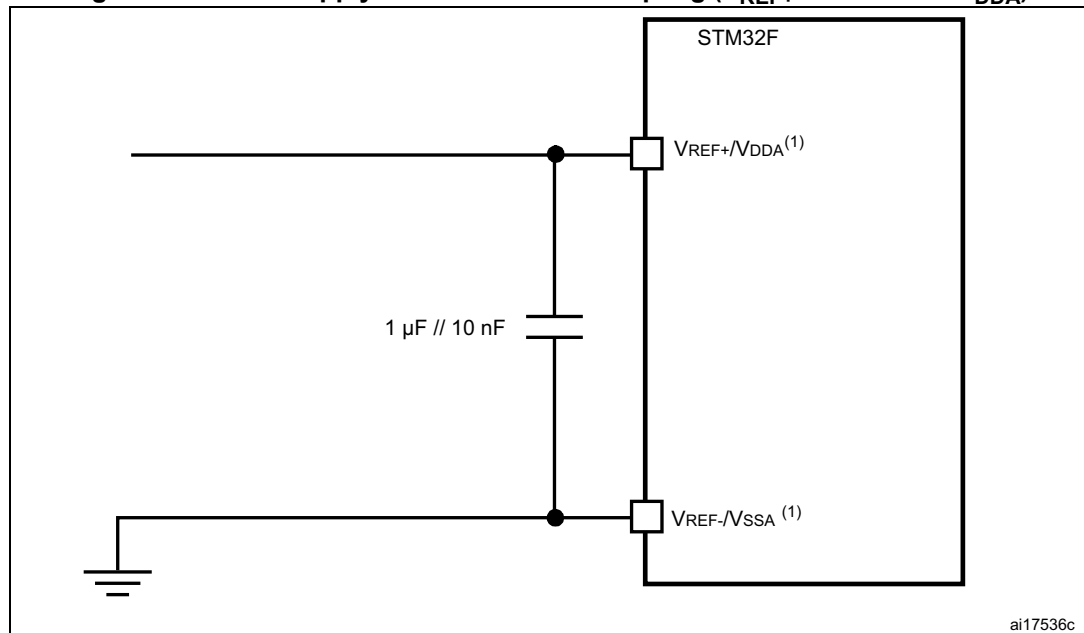
Power supply decoupling should be performed as shown in [Figure 37](#) or [Figure 38](#), depending on whether  $V_{REF+}$  is connected to  $V_{DDA}$  or not. The 10 nF capacitors should be ceramic (good quality). They should be placed them as close as possible to the chip.

**Figure 37. Power supply and reference decoupling ( $V_{REF+}$  not connected to  $V_{DDA}$ )**



1.  $V_{REF+}$  input is available on all the packages whereas the  $V_{REF-}$  is available only on TFBGA216. When  $V_{REF-}$  is not available, it is internally connected to  $V_{DDA}$  and  $V_{SSA}$ .

**Figure 38. Power supply and reference decoupling ( $V_{REF+}$  connected to  $V_{DDA}$ )**



1.  $V_{REF+}$  input is available on all the packages whereas the  $V_{REF-}$  is available only on TFBGA216. When  $V_{REF-}$  is not available, it is internally connected to  $V_{DDA}$  and  $V_{SSA}$ .

### 6.3.22 Temperature sensor characteristics

Table 67. Temperature sensor characteristics

Symbol	Parameter	Min	Typ	Max	Unit
$T_L^{(1)}$	$V_{SENSE}$ linearity with temperature	-	$\pm 1$	$\pm 2$	$^{\circ}\text{C}$
Avg_Slope <sup>(1)</sup>	Average slope	-	2.5	-	mV/ $^{\circ}\text{C}$
$V_{25}^{(1)}$	Voltage at 25 $^{\circ}\text{C}$	-	0.76	-	V
$t_{START}^{(2)}$	Startup time	-	6	10	$\mu\text{s}$
$T_{S\_temp}^{(2)}$	ADC sampling time when reading the temperature (1 $^{\circ}\text{C}$ accuracy)	10	-	-	$\mu\text{s}$

1. Guaranteed by characterization results.
2. Guaranteed by design.

Table 68. Temperature sensor calibration values

Symbol	Parameter	Memory address
TS_CAL1	TS ADC raw data acquired at temperature of 30 $^{\circ}\text{C}$ , $V_{DDA} = 3.3\text{ V}$	0x1FF0 F44C - 0x1FF0 F44D
TS_CAL2	TS ADC raw data acquired at temperature of 110 $^{\circ}\text{C}$ , $V_{DDA} = 3.3\text{ V}$	0x1FF0 F44E - 0x1FF0 F44F

### 6.3.23 $V_{BAT}$ monitoring characteristics

Table 69.  $V_{BAT}$  monitoring characteristics

Symbol	Parameter	Min	Typ	Max	Unit
R	Resistor bridge for $V_{BAT}$	-	50	-	K $\Omega$
Q	Ratio on $V_{BAT}$ measurement	-	4	-	-
$E_r^{(1)}$	Error on Q	-1	-	+1	%
$T_{S\_vbat}^{(2)(2)}$	ADC sampling time when reading the $V_{BAT}$ 1 mV accuracy	5	-	-	$\mu\text{s}$

1. Guaranteed by design.
2. Shortest sampling time can be determined in the application by multiple iterations.

### 6.3.24 Reference voltage

The parameters given in [Table 70](#) are derived from tests performed under ambient temperature and  $V_{DD}$  supply voltage conditions summarized in [Table 16](#).

Table 70. internal reference voltage

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{REFINT}$	Internal reference voltage	$-40\text{ }^{\circ}\text{C} < T_A < +105\text{ }^{\circ}\text{C}$	1.18	1.21	1.24	V
$T_{S\_vrefint}^{(1)}$	ADC sampling time when reading the internal reference voltage	-	10	-	-	$\mu\text{s}$
$V_{RERINT\_s}^{(2)}$	Internal reference voltage spread over the temperature range	$V_{DD} = 3\text{V} \pm 10\text{mV}$	-	3	5	mV

**Table 70. internal reference voltage (continued)**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$T_{\text{Coeff}}^{(2)}$	Temperature coefficient	-	-	30	50	ppm/°C
$t_{\text{START}}^{(2)}$	Startup time	-	-	6	10	µs

1. Shortest sampling time can be determined in the application by multiple iterations.
2. Guaranteed by design.

**Table 71. Internal reference voltage calibration values**

Symbol	Parameter	Memory address
$V_{\text{REFIN\_CAL}}$	Raw data acquired at temperature of 30 °C $V_{\text{DDA}} = 3.3 \text{ V}$	0x1FF0 F44A - 0x1FF0 F44B

### 6.3.25 DAC electrical characteristics

**Table 72. DAC characteristics**

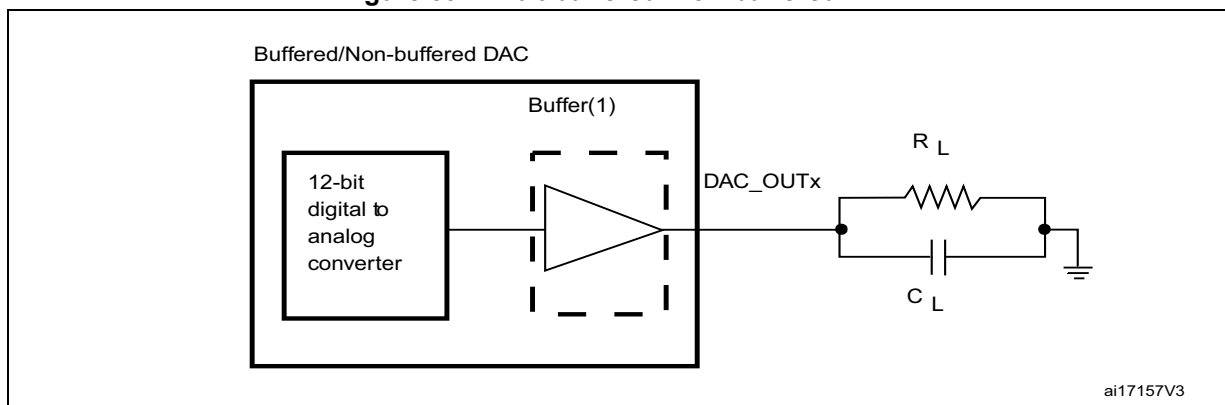
Symbol	Parameter	Min	Typ	Max	Unit	Comments
$V_{\text{DDA}}$	Analog supply voltage	1.7 <sup>(1)</sup>	-	3.6	V	-
$V_{\text{REF+}}$	Reference supply voltage	1.7 <sup>(1)</sup>	-	3.6	V	$V_{\text{REF+}} \leq V_{\text{DDA}}$
$V_{\text{SSA}}$	Ground	0	-	0	V	-
$R_{\text{LOAD}}^{(2)}$	Resistive load with buffer ON	5	-	-	kΩ	-
$R_{\text{O}}^{(2)}$	Impedance output with buffer OFF	-	-	15	kΩ	When the buffer is OFF, the Minimum resistive load between DAC_OUT and $V_{\text{SS}}$ to have a 1% accuracy is 1.5 MΩ
$C_{\text{LOAD}}^{(2)}$	Capacitive load	-	-	50	pF	Maximum capacitive load at DAC_OUT pin (when the buffer is ON).
$\text{DAC\_OUT}_{\text{min}}^{(2)}$	Lower DAC_OUT voltage with buffer ON	0.2	-	-	V	It gives the maximum output excursion of the DAC. It corresponds to 12-bit input code (0x0E0) to (0xF1C) at $V_{\text{REF+}} = 3.6 \text{ V}$ and (0x1C7) to (0xE38) at $V_{\text{REF+}} = 1.7 \text{ V}$
$\text{DAC\_OUT}_{\text{max}}^{(2)}$	Higher DAC_OUT voltage with buffer ON	-	-	$V_{\text{DDA}} - 0.2$	V	
$\text{DAC\_OUT}_{\text{min}}^{(2)}$	Lower DAC_OUT voltage with buffer OFF	-	0.5	-	mV	It gives the maximum output excursion of the DAC.
$\text{DAC\_OUT}_{\text{max}}^{(2)}$	Higher DAC_OUT voltage with buffer OFF	-	-	$V_{\text{REF+}} - 1\text{LSB}$	V	
$I_{\text{VREF+}}^{(4)}$	DAC DC $V_{\text{REF}}$ current consumption in quiescent mode (Standby mode)	-	170	240	µA	With no load, worst code (0x800) at $V_{\text{REF+}} = 3.6 \text{ V}$ in terms of DC consumption on the inputs
		-	50	75		With no load, worst code (0xF1C) at $V_{\text{REF+}} = 3.6 \text{ V}$ in terms of DC consumption on the inputs

Table 72. DAC characteristics (continued)

Symbol	Parameter	Min	Typ	Max	Unit	Comments
$I_{DDA}^{(4)}$	DAC DC $V_{DDA}$ current consumption in quiescent mode <sup>(3)</sup>	-	280	380	$\mu A$	With no load, middle code (0x800) on the inputs
		-	475	625	$\mu A$	With no load, worst code (0xF1C) at $V_{REF+} = 3.6 V$ in terms of DC consumption on the inputs
DNL <sup>(4)</sup>	Differential non linearity Difference between two consecutive code-1LSB)	-	-	$\pm 0.5$	LSB	Given for the DAC in 10-bit configuration.
		-	-	$\pm 2$	LSB	Given for the DAC in 12-bit configuration.
INL <sup>(4)</sup>	Integral non linearity (difference between measured value at Code i and the value at Code i on a line drawn between Code 0 and last Code 1023)	-	-	$\pm 1$	LSB	Given for the DAC in 10-bit configuration.
		-	-	$\pm 4$	LSB	Given for the DAC in 12-bit configuration.
Offset <sup>(4)</sup>	Offset error (difference between measured value at Code (0x800) and the ideal value = $V_{REF+}/2$ )	-	-	$\pm 10$	mV	Given for the DAC in 12-bit configuration
		-	-	$\pm 3$	LSB	Given for the DAC in 10-bit at $V_{REF+} = 3.6 V$
		-	-	$\pm 12$	LSB	Given for the DAC in 12-bit at $V_{REF+} = 3.6 V$
Gain error <sup>(4)</sup>	Gain error	-	-	$\pm 0.5$	%	Given for the DAC in 12-bit configuration
$t_{SETTLING}^{(4)}$	Settling time (full scale: for a 10-bit input code transition between the lowest and the highest input codes when DAC_OUT reaches final value $\pm 4LSB$ )	-	3	6	$\mu s$	$C_{LOAD} \leq 50 pF$ , $R_{LOAD} \geq 5 k\Omega$
THD <sup>(4)</sup>	Total Harmonic Distortion Buffer ON	-	-	-	dB	$C_{LOAD} \leq 50 pF$ , $R_{LOAD} \geq 5 k\Omega$
Update rate <sup>(2)</sup>	Max frequency for a correct DAC_OUT change when small variation in the input code (from code i to i+1LSB)	-	-	1	MS/s	$C_{LOAD} \leq 50 pF$ , $R_{LOAD} \geq 5 k\Omega$
$t_{WAKEUP}^{(4)}$	Wakeup time from off state (Setting the ENx bit in the DAC Control register)	-	6.5	10	$\mu s$	$C_{LOAD} \leq 50 pF$ , $R_{LOAD} \geq 5 k\Omega$ input code between lowest and highest possible ones.
PSRR <sup>+</sup> <sup>(2)</sup>	Power supply rejection ratio (to $V_{DDA}$ ) (static DC measurement)	-	-67	-40	dB	No $R_{LOAD}$ , $C_{LOAD} = 50 pF$

- $V_{DDA}$  minimum value of 1.7 V is obtained with the use of an external power supply supervisor (refer to [Section 3.17.2: Internal reset OFF](#)).
- Guaranteed by design.
- The quiescent mode corresponds to a state where the DAC maintains a stable output level to ensure that no dynamic consumption occurs.
- Guaranteed by characterization results.

Figure 39. 12-bit buffered /non-buffered DAC



1. The DAC integrates an output buffer that can be used to reduce the output impedance and to drive external loads directly without the use of an external operational amplifier. The buffer can be bypassed by configuring the BOFFx bit in the DAC\_CR register.

### 6.3.26 Communications interfaces

#### I<sup>2</sup>C interface characteristics

The I<sup>2</sup>C interface meets the timings requirements of the I<sup>2</sup>C-bus specification and user manual rev. 03 for:

- Standard-mode (Sm): with a bit rate up to 100 kbit/s
- Fast-mode (Fm): with a bit rate up to 400 kbit/s.
- Fast-mode Plus (Fm+): with a bit rate up to 1Mbit/s.

The I<sup>2</sup>C timings requirements are guaranteed by design when the I2C peripheral is properly configured (refer to RM0385 reference manual) and when the I2CCLK frequency is greater than the minimum shown in the table below:

Table 73. Minimum I2CCLK frequency in all I2C modes

Symbol	Parameter	Condition		Min	Unit
f(I2CCLK)	I2CCLK frequency	Standard-mode		2	MHz
		Fast-mode	Analog Filtre ON DNF=0	10	
			Analog Filtre OFF DNF=1	9	
		Fast-mode Plus	Analog Filtre ON DNF=0	22.5	
Analog Filtre OFF DNF=1	16				

The SDA and SCL I/O requirements are met with the following restrictions: the SDA and SCL I/O pins are not “true” open-drain. When configured as open-drain, the PMOS connected between the I/O pin and V<sub>DD</sub> is disabled, but is still present.

The 20mA output drive requirement in Fast-mode Plus is not supported. This limits the maximum load Cload supported in Fm+, which is given by these formulas:

- $T_r(SDA/SCL) = 0.8473 \times R_p \times C_{load}$
- $R_p(\min) = (V_{DD} - V_{OL}(\max)) / I_{OL}(\max)$

Where Rp is the I2C lines pull-up. Refer to [Section 6.3.17: I/O port characteristics](#) for the I2C I/Os characteristics.

All I<sup>2</sup>C SDA and SCL I/Os embed an analog filter. Refer to the table below for the analog filter characteristics:

**Table 74. I2C analog filter characteristics<sup>(1)</sup>**

Symbol	Parameter	Min	Max	Unit
t <sub>AF</sub>	Maximum pulse width of spikes that are suppressed by the analog filter	50 <sup>(2)</sup>	150 <sup>(3)</sup>	ns

1. Guaranteed by characterization results.
2. Spikes with widths below t<sub>AF(min)</sub> are filtered.
3. Spikes with widths above t<sub>AF(max)</sub> are not filtered



**SPI interface characteristics**

Unless otherwise specified, the parameters given in [Table 75](#) for the SPI interface are derived from tests performed under the ambient temperature,  $f_{PCLKX}$  frequency and  $V_{DD}$  supply voltage conditions summarized in [Table 16](#), with the following configuration:

- Output speed is set to  $OSPEEDRy[1:0] = 11$
- Capacitive load  $C = 30 \text{ pF}$
- Measurement points are done at CMOS levels:  $0.5V_{DD}$

Refer to [Section 6.3.17: I/O port characteristics](#) for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO for SPI).

**Table 75. SPI dynamic characteristics<sup>(1)</sup>**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$f_{SCK}$ $1/t_{c(SCK)}$	SPI clock frequency	Master mode SPI1,4,5,6 $2.7 \leq V_{DD} \leq 3.6$	-	-	54 <sup>(2)</sup>	MHz
		Master mode SPI1,4,5,6 $1.71 \leq V_{DD} \leq 3.6$			27	
		Master transmitter mode SPI1,4,5,6 $1.71 \leq V_{DD} \leq 3.6$			54	
		Slave receiver mode SPI1,4,5,6 $1.71 \leq V_{DD} \leq 3.6$			54	
		Slave mode transmitter/full duplex SPI1,4,5,6 $2.7 \leq V_{DD} \leq 3.6$			50 <sup>(3)</sup>	
		Slave mode transmitter/full duplex SPI1,4,5,6 $1.71 \leq V_{DD} \leq 3.6$			38 <sup>(3)</sup>	
		Master & Slave mode SPI2,3 $1.71 \leq V_{DD} \leq 3.6$			27	
$t_{su}(NSS)$	NSS setup time	Slave mode, SPI presc = 2	$4 \cdot T_{pclk}$	-	-	ns
$t_h(NSS)$	NSS hold time	Slave mode, SPI presc = 2	$2 \cdot T_{pclk}$	-	-	
$t_w(SCKH)$ $t_w(SCKL)$	SCK high and low time	Master mode	$T_{pclk} - 2$	$T_{pclk}$	$T_{pclk} + 2$	

Table 75. SPI dynamic characteristics<sup>(1)</sup> (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
tsu(MI)	Data input setup time	Master mode	5.5	-	-	ns
tsu(SI)		Slave mode	4	-	-	
th(MI)	Data input hold time	Master mode	4	-	-	
th(SI)		Slave mode	2	-	-	
ta(SO)	Data output access time	Slave mode	7	-	21	
tdis(SO)	Data output disable time	Slave mode	5	-	12	
tv(SO)	Data output valid time	Slave mode 2.7≤VDD≤3.6V	-	6.5	10	
		Slave mode 1.71≤VDD≤3.6V	-	6.5	13	
tv(MO)		Master mode	-	2	4	
th(SO)	Data output hold time	Slave mode 1.71≤VDD≤3.6V	5.5	-	-	
th(MO)		Master mode	0	-	-	

1. Guaranteed by characterization results.
2. Excepting SPI1 with SCK IO pin mapped on PA5. In this configuration, Maximum achievable frequency is 40MHz.
3. Maximum Frequency of Slave Transmitter is determined by sum of Tv(SO) and Tsu(MI) intervals which has to fit into SCK level phase preceding the SCK sampling edge. This value can be achieved when it communicates with a Master having Tsu(MI)=0 while signal Duty(SCK)=50%.

Figure 40. SPI timing diagram - slave mode and CPHA = 0

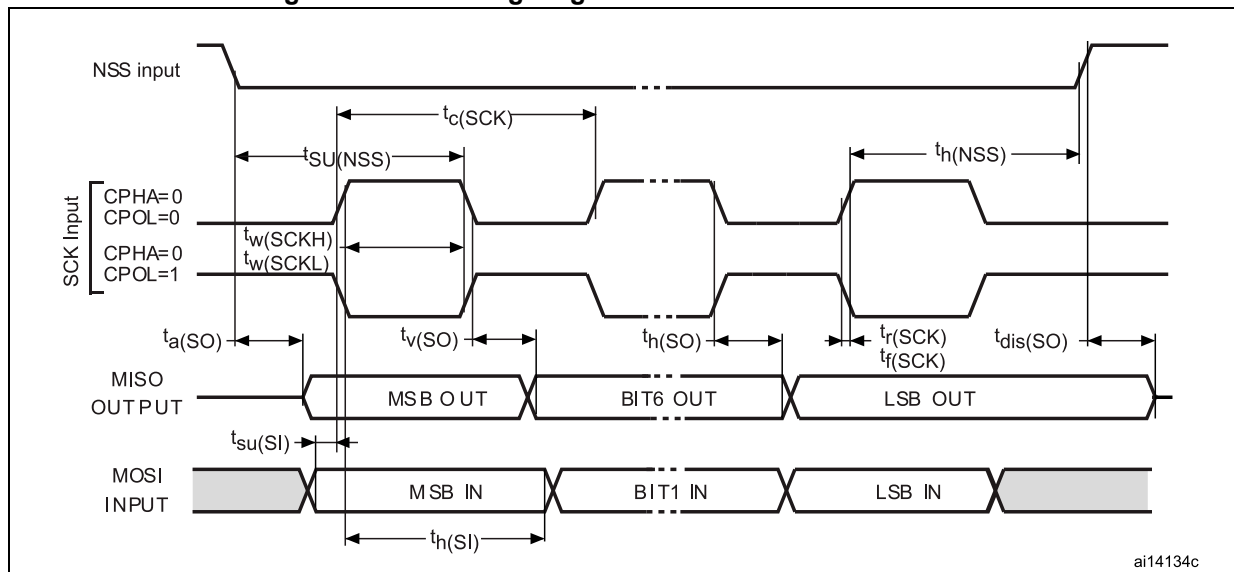


Figure 41. SPI timing diagram - slave mode and CPHA = 1

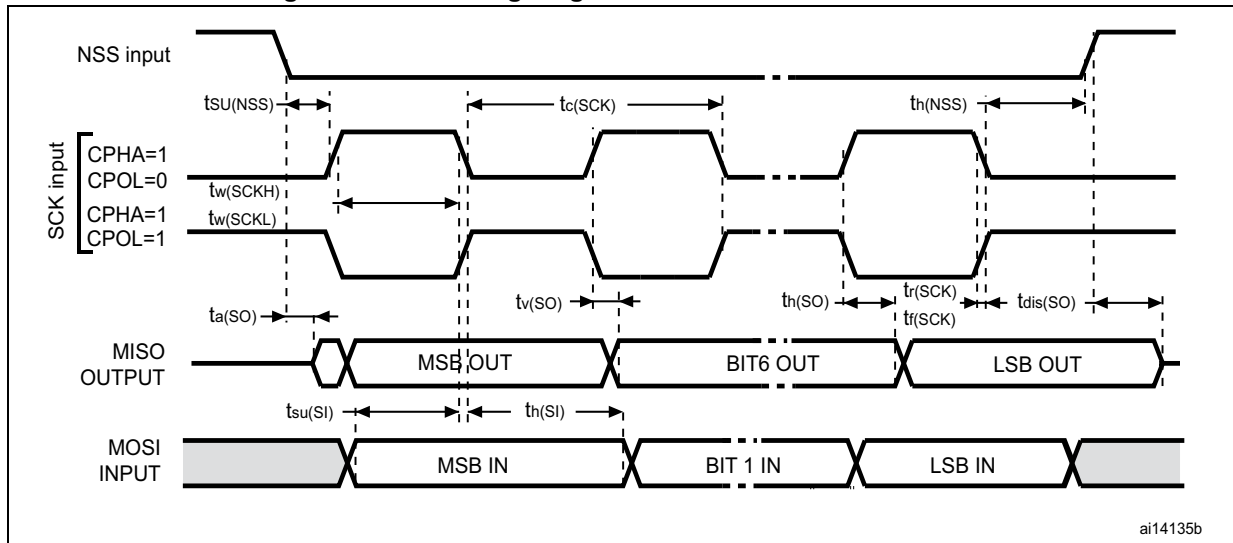
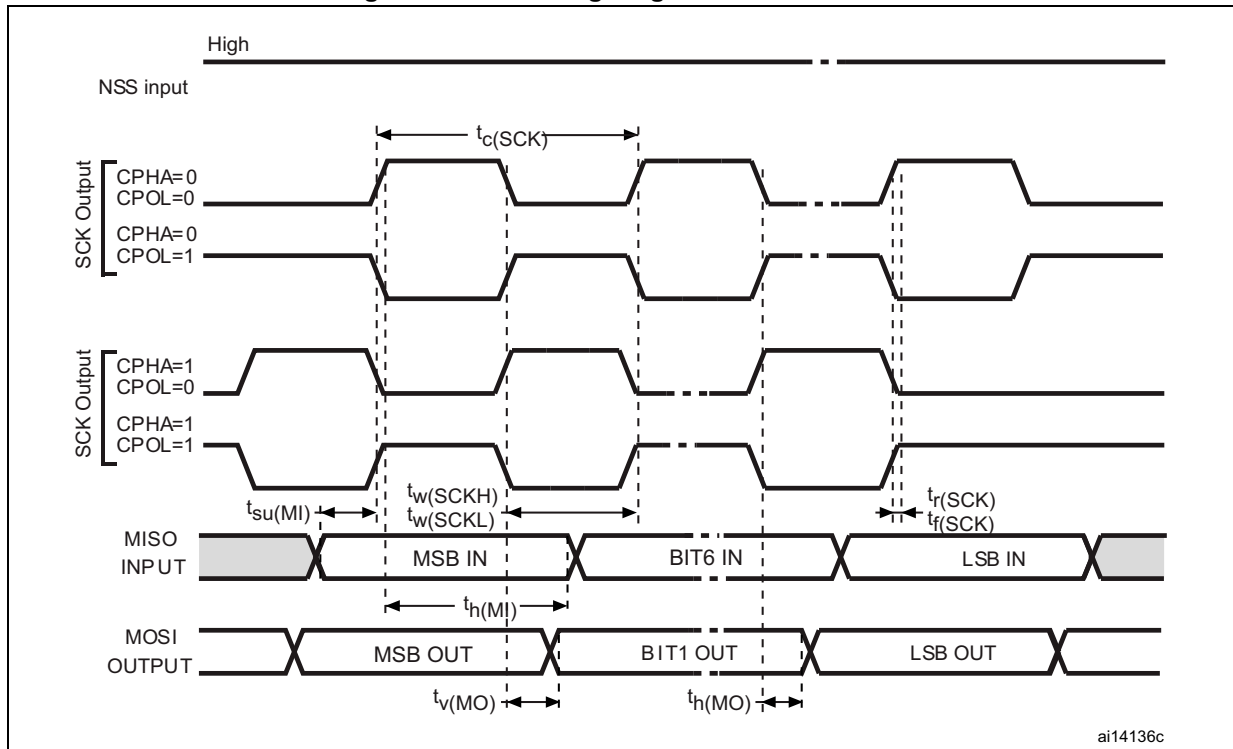


Figure 42. SPI timing diagram - master mode



### I<sup>2</sup>S interface characteristics

Unless otherwise specified, the parameters given in [Table 76](#) for the I<sup>2</sup>S interface are derived from tests performed under the ambient temperature,  $f_{PCLKx}$  frequency and  $V_{DD}$  supply voltage conditions summarized in [Table 16](#), with the following configuration:

- Output speed is set to  $OSPEEDRy[1:0] = 10$
- Capacitive load  $C = 30$  pF
- Measurement points are done at CMOS levels:  $0.5V_{DD}$

Refer to [Section 6.3.17: I/O port characteristics](#) for more details on the input/output alternate function characteristics (CK, SD, WS).

**Table 76. I<sup>2</sup>S dynamic characteristics<sup>(1)</sup>**

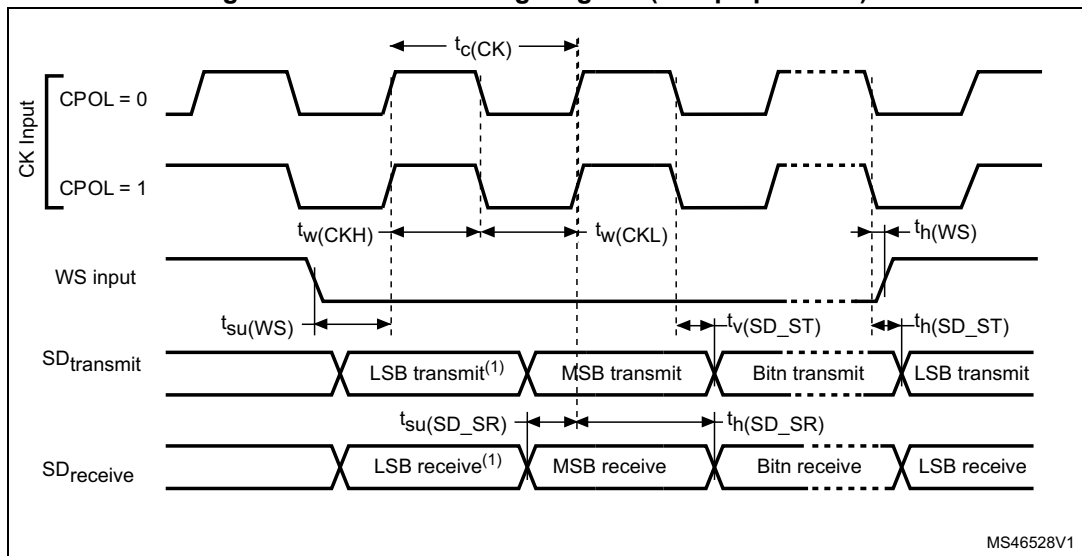
Symbol	Parameter	Conditions	Min	Max	Unit
f <sub>MCK</sub>	I2S Main clock output	-	256x8K	256xFs <sup>(2)</sup>	MHz
f <sub>CK</sub>	I2S clock frequency	Master data: 32 bits	-	64xFs	MHz
		Slave data: 32 bits	-	64xFs	
D <sub>CK</sub>	I2S clock frequency duty cycle	Slave receiver	30	70	%
t <sub>v(WS)</sub>	WS valid time	Master mode	-	5	ns
t <sub>h(WS)</sub>	WS hold time	Master mode	0	-	
t <sub>su(WS)</sub>	WS setup time	Slave mode	5	-	ns
		Slave mode PCM short pulse mode <sup>(3)</sup>	3	-	
t <sub>h(WS)</sub>	WS hold time	Slave mode	0	-	
		Slave mode PCM short pulse mode <sup>(3)</sup>	2	-	
t <sub>su(SD_MR)</sub>	Data input setup time	Master receiver	5	-	
t <sub>su(SD_SR)</sub>		Slave receiver	1	-	
t <sub>h(SD_MR)</sub>	Data input hold time	Master receiver	5	-	
t <sub>h(SD_SR)</sub>		Slave receiver	1.5	-	
t <sub>v(SD_ST)</sub>	Data output valid time	Slave transmitter (after enable edge)	-	16	
t <sub>v(SD_MT)</sub>		Master transmitter (after enable edge)	-	3.5	
t <sub>h(SD_ST)</sub>	Data output hold time	Slave transmitter (after enable edge)	5	-	
t <sub>h(SD_MT)</sub>		Master transmitter (after enable edge)	0	-	

1. Guaranteed by characterization results.
2. The maximum value of 256xFs is 45 MHz (APB1 maximum frequency).
3. Measurement done with respect to I2S\_CK rising edge.

**Note:** Refer to RM0385 reference manual I2S section for more details on the sampling frequency (F<sub>S</sub>).

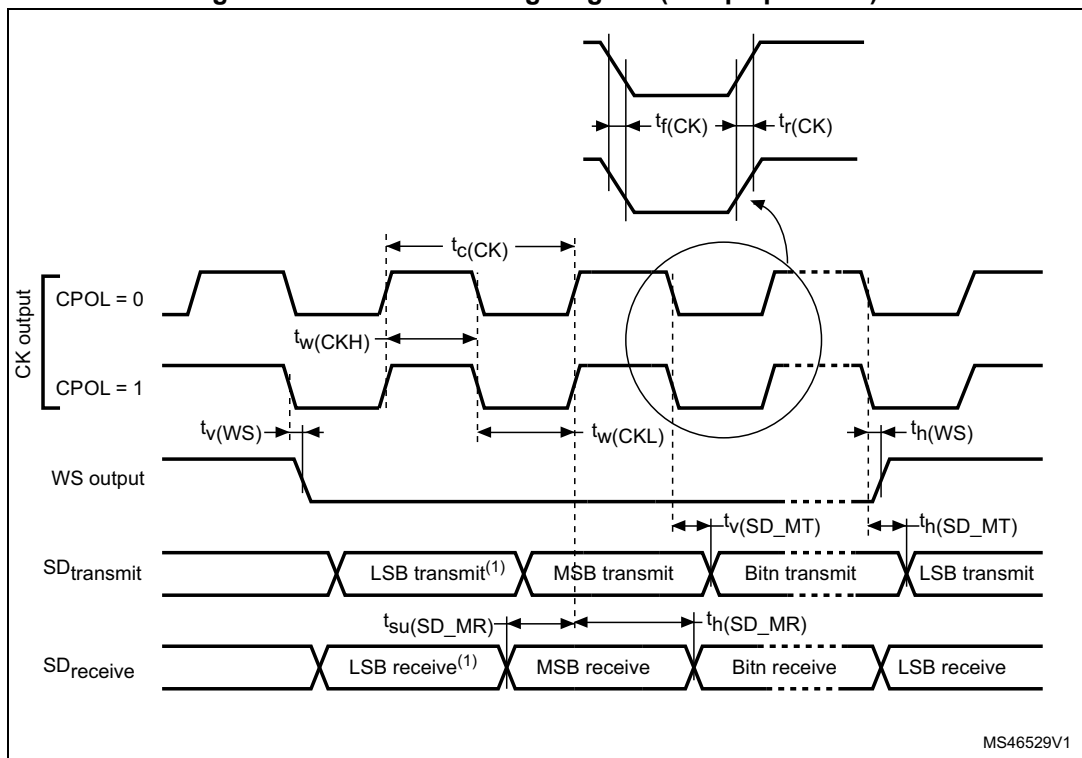
f<sub>MCK</sub>, f<sub>CK</sub>, and D<sub>CK</sub> values reflect only the digital peripheral behavior. The values of these parameters might be slightly impacted by the source clock precision. D<sub>CK</sub> depends mainly on the value of ODD bit. The digital contribution leads to a minimum value of (I2SDIV/(2\*I2SDIV+ODD)) and a maximum value of (I2SDIV+ODD)/(2\*I2SDIV+ODD). F<sub>S</sub> maximum value is supported for each mode/condition.

Figure 43. I<sup>2</sup>S slave timing diagram (Philips protocol)<sup>(1)</sup>



1. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

Figure 44. I<sup>2</sup>S master timing diagram (Philips protocol)<sup>(1)</sup>



1. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

**SAI characteristics**

Unless otherwise specified, the parameters given in [Table 77](#) for SAI are derived from tests performed under the ambient temperature,  $f_{PCLKx}$  frequency and VDD supply voltage conditions summarized in [Table 16](#), with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load C=30 pF
- Measurement points are performed at CMOS levels:  $0.5V_{DD}$

Refer to [Section 6.3.17: I/O port characteristics](#) for more details on the input/output alternate function characteristics (SCK,SD,WS).

**Table 77. SAI characteristics<sup>(1)</sup>**

Symbol	Parameter	Conditions	Min	Max	Unit
$f_{MCKL}$	SAI Main clock output	-	256 x 8K	256xFs <sup>(2)</sup>	MHz
$F_{SCK}$	SAI clock frequency	Master data: 32 bits	-	128xFs	MHz
		Slave data: 32 bits	-	128xFs	
$D_{SCK}$	SAI clock frequency duty cycle	Slave receiver	30	70	%
$t_{v(FS)}$	FS valid time	Master mode	8	22	ns
$t_{su(FS)}$	FS setup time	Slave mode	2	-	
$t_{h(FS)}$	FS hold time	Master mode	8	-	
		Slave mode	0	-	
$t_{su(SD\_MR)}$	Data input setup time	Master receiver	5	-	
$t_{su(SD\_SR)}$		Slave receiver	3	-	
$t_{h(SD\_MR)}$	Data input hold time	Master receiver	0	-	
$t_{h(SD\_SR)}$		Slave receiver	6	-	
$t_{v(SD\_ST)}$	Data output valid time	Slave transmitter (after enable edge)	-	15	
$t_{h(SD\_ST)}$		Master transmitter (after enable edge)	-	20	
$t_{v(SD\_MT)}$	Data output hold time	Master transmitter (after enable edge)	7	-	
$t_{h(SD\_MT)}$					

1. Guaranteed by characterization results.
2. 256xFs maximum corresponds to 45 MHz (APB2 maximum frequency)

Figure 45. SAI master timing waveforms

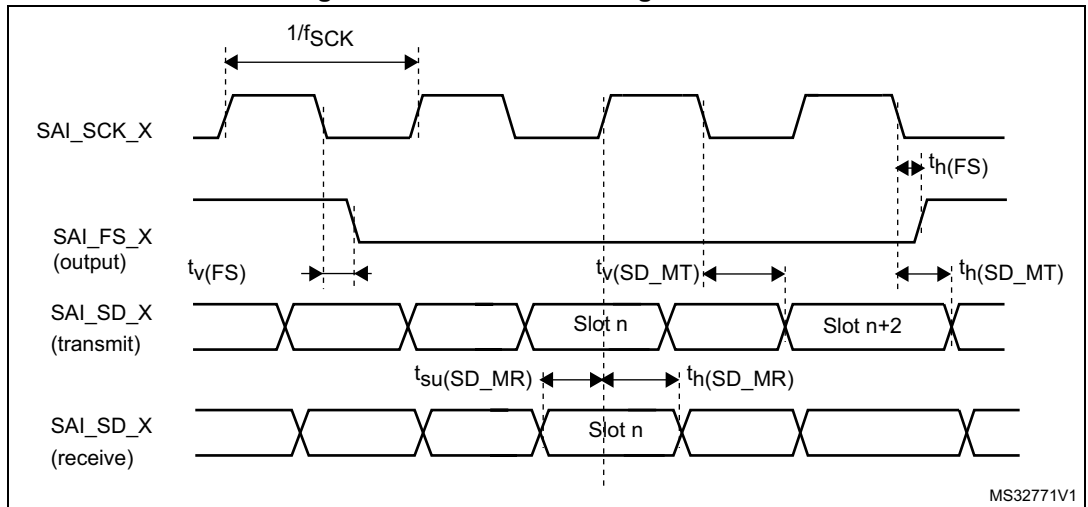
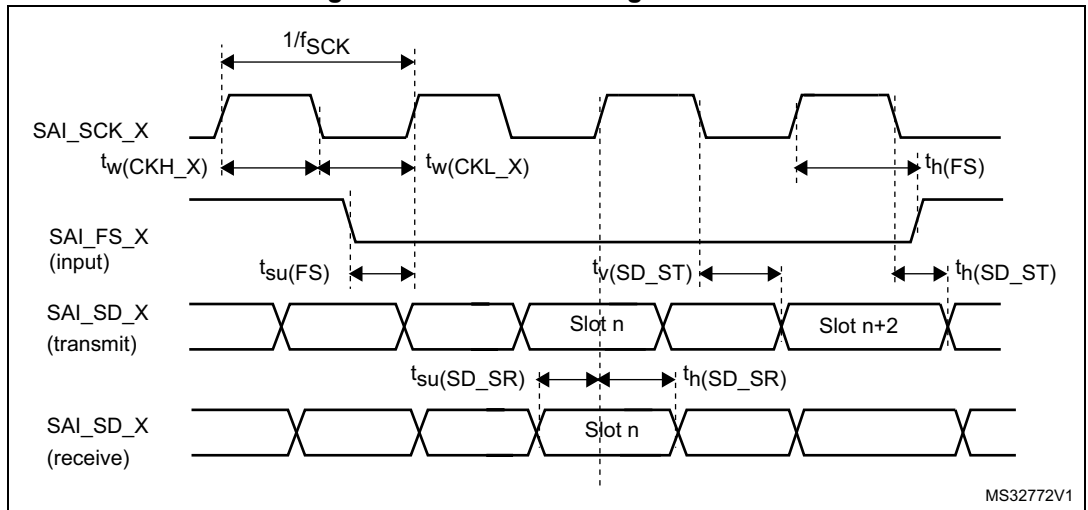


Figure 46. SAI slave timing waveforms



**USB OTG full speed (FS) characteristics**

This interface is present in both the USB OTG HS and USB OTG FS controllers.

**Table 78. USB OTG full speed startup time**

Symbol	Parameter	Max	Unit
$t_{STARTUP}^{(1)}$	USB OTG full speed transceiver startup time	1	$\mu s$

1. Guaranteed by design.

**Table 79. USB OTG full speed DC electrical characteristics**

Symbol	Parameter	Conditions	Min. (1)	Typ.	Max. (1)	Unit	
Input levels	$V_{DDUSB}$	USB OTG full speed transceiver operating voltage	-	3.0 <sup>(2)</sup>	-	3.6	V
	$V_{DI}^{(3)}$	Differential input sensitivity	I(USB_FS_DP/DM, USB_HS_DP/DM)	0.2	-	-	V
	$V_{CM}^{(3)}$	Differential common mode range	Includes $V_{DI}$ range	0.8	-	2.5	
	$V_{SE}^{(3)}$	Single ended receiver threshold	-	1.3	-	2.0	
Output levels	$V_{OL}$	Static output level low	$R_L$ of 1.5 k $\Omega$ to 3.6 V <sup>(4)</sup>	-	-	0.3	V
	$V_{OH}$	Static output level high	$R_L$ of 15 k $\Omega$ to $V_{SS}^{(4)}$	2.8	-	3.6	
$R_{PD}$	PA11, PA12, PB14, PB15 (USB_FS_DP/DM, USB_HS_DP/DM)	$V_{IN} = V_{DD}$	17	21	24	k $\Omega$	
	PA9, PB13 (OTG_FS_VBUS, OTG_HS_VBUS)		0.65	1.1	2.0		
$R_{PU}$	PA12, PB15 (USB_FS_DP, USB_HS_DP)	$V_{IN} = V_{SS}$	1.5	1.8	2.1		
	PA9, PB13 (OTG_FS_VBUS, OTG_HS_VBUS)	$V_{IN} = V_{SS}$	0.25	0.37	0.55		

1. All the voltages are measured from the local ground potential.
2. The USB OTG full speed transceiver functionality is ensured down to 2.7 V but not the full USB full speed electrical characteristics which are degraded in the 2.7-to-3.0 V  $V_{DDUSB}$  voltage range.
3. Guaranteed by design.
4.  $R_L$  is the load connected on the USB OTG full speed drivers.

**Note:** *When VBUS sensing feature is enabled, PA9 and PB13 should be left at their default state (floating input), not as alternate function. A typical 200  $\mu A$  current consumption of the sensing block (current to voltage conversion to determine the different sessions) can be observed on PA9 and PB13 when the feature is enabled.*



Figure 47. USB OTG full speed timings: definition of data signal rise and fall time

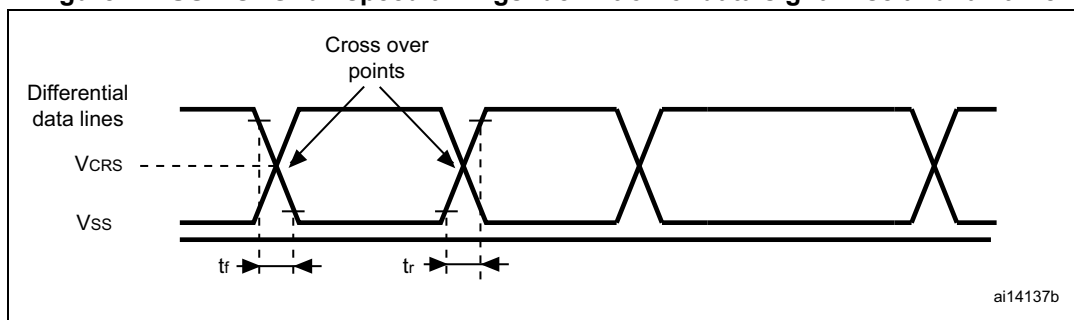


Table 80. USB OTG full speed electrical characteristics<sup>(1)</sup>

Driver characteristics					
Symbol	Parameter	Conditions	Min	Max	Unit
$t_r$	Rise time <sup>(2)</sup>	$C_L = 50 \text{ pF}$	4	20	ns
$t_f$	Fall time <sup>(2)</sup>	$C_L = 50 \text{ pF}$	4	20	ns
$t_{rfm}$	Rise/ fall time matching	$t_r/t_f$	90	110	%
$V_{CRS}$	Output signal crossover voltage	-	1.3	2.0	V
$Z_{DRV}$	Output driver impedance <sup>(3)</sup>	Driving high or low	28	44	$\Omega$

1. Guaranteed by design.
2. Measured from 10% to 90% of the data signal. For more detailed informations, please refer to USB Specification - Chapter 7 (version 2.0).
3. No external termination series resistors are required on DP (D+) and DM (D-) pins since the matching impedance is included in the embedded driver.

### USB high speed (HS) characteristics

Unless otherwise specified, the parameters given in [Table 83](#) for ULPI are derived from tests performed under the ambient temperature,  $f_{HCLK}$  frequency summarized in [Table 82](#) and  $V_{DD}$  supply voltage conditions summarized in [Table 81](#), with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 11, unless otherwise specified
- Capacitive load  $C = 20 \text{ pF}$ , unless otherwise specified
- Measurement points are done at CMOS levels:  $0.5V_{DD}$ .

Refer to [Section 6.3.17: I/O port characteristics](#) for more details on the input/output characteristics.

Table 81. USB HS DC electrical characteristics

Symbol	Parameter	Min. <sup>(1)</sup>	Max. <sup>(1)</sup>	Unit
Input level $V_{DD}$	USB OTG HS operating voltage	1.7	3.6	V

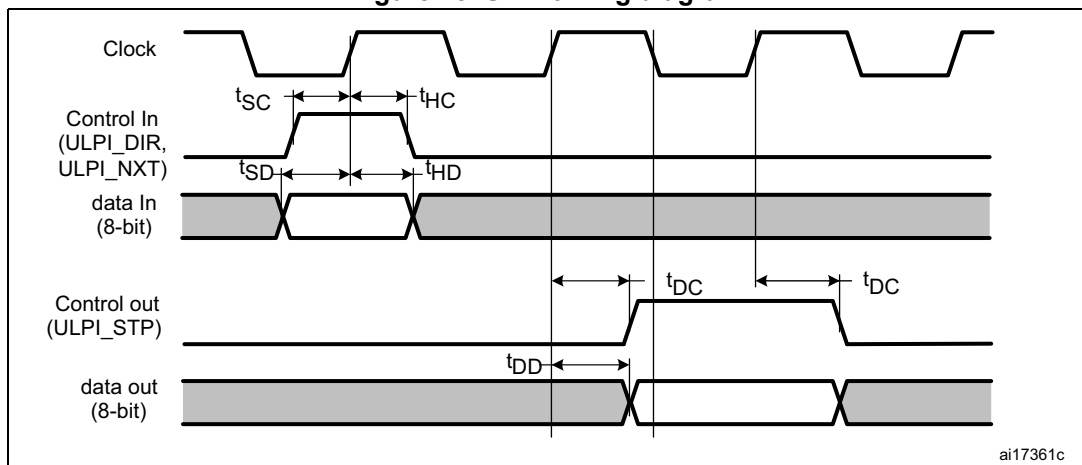
1. All the voltages are measured from the local ground potential.

Table 82. USB HS clock timing parameters<sup>(1)</sup>

Symbol	Parameter		Min	Typ	Max	Unit
-	f <sub>HCLK</sub> value to guarantee proper operation of USB HS interface		30	-	-	MHz
F <sub>START_8BIT</sub>	Frequency (first transition)	8-bit ±10%	54	60	66	MHz
F <sub>STEADY</sub>	Frequency (steady state) ±500 ppm		59.97	60	60.03	MHz
D <sub>START_8BIT</sub>	Duty cycle (first transition)	8-bit ±10%	40	50	60	%
D <sub>STEADY</sub>	Duty cycle (steady state) ±500 ppm		49.975	50	50.025	%
t <sub>STEADY</sub>	Time to reach the steady state frequency and duty cycle after the first transition		-	-	1.4	ms
t <sub>START_DEV</sub>	Clock startup time after the de-assertion of SuspendM	Peripheral	-	-	5.6	ms
t <sub>START_HOST</sub>		Host	-	-	-	
t <sub>PREP</sub>	PHY preparation time after the first transition of the input clock		-	-	-	µs

1. Guaranteed by design.

Figure 48. ULPI timing diagram



ai17361c

**Table 83. Dynamic characteristics: USB ULPI<sup>(1)</sup>**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
t <sub>SC</sub>	Control in (ULPI_DIR, ULPI_NXT) setup time	-	3	-	-	ns
t <sub>HC</sub>	Control in (ULPI_DIR, ULPI_NXT) hold time	-	1	-	-	
t <sub>SD</sub>	Data in setup time	-	1.5	-	-	
t <sub>HD</sub>	Data in hold time	-	0.5	-	-	
t <sub>DC</sub> /t <sub>DD</sub>	Data/control output delay	2.7 V < V <sub>DD</sub> < 3.6 V, C <sub>L</sub> = 20 pF and OSPEEDRy[1:0] = 11	-	5.5	9	
		1.7 V < V <sub>DD</sub> < 3.6 V, C <sub>L</sub> = 15 pF and OSPEEDRy[1:0] = 11	-	5.5	11.5	

1. Guaranteed by characterization results.

**Ethernet characteristics**

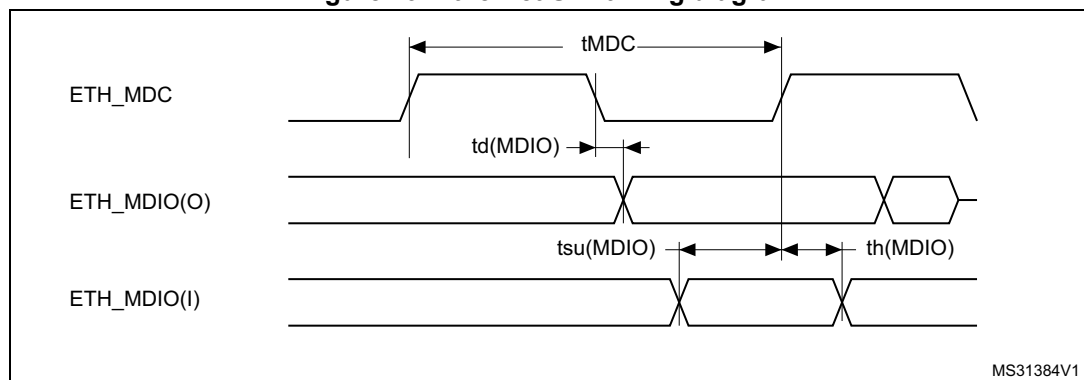
Unless otherwise specified, the parameters given in [Table 84](#), [Table 85](#) and [Table 86](#) for SMI, RMII and MII are derived from tests performed under the ambient temperature, f<sub>HCLK</sub> frequency summarized in [Table 16](#) and V<sub>DD</sub> supply voltage conditions summarized in [Table 84](#), with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load C = 20 pF
- Measurement points are done at CMOS levels: 0.5V<sub>DD</sub>.

Refer to [Section 6.3.17: I/O port characteristics](#) for more details on the input/output characteristics.

[Table 84](#) gives the list of Ethernet MAC signals for the SMI (station management interface) and [Figure 49](#) shows the corresponding timing diagram.

**Figure 49. Ethernet SMI timing diagram**



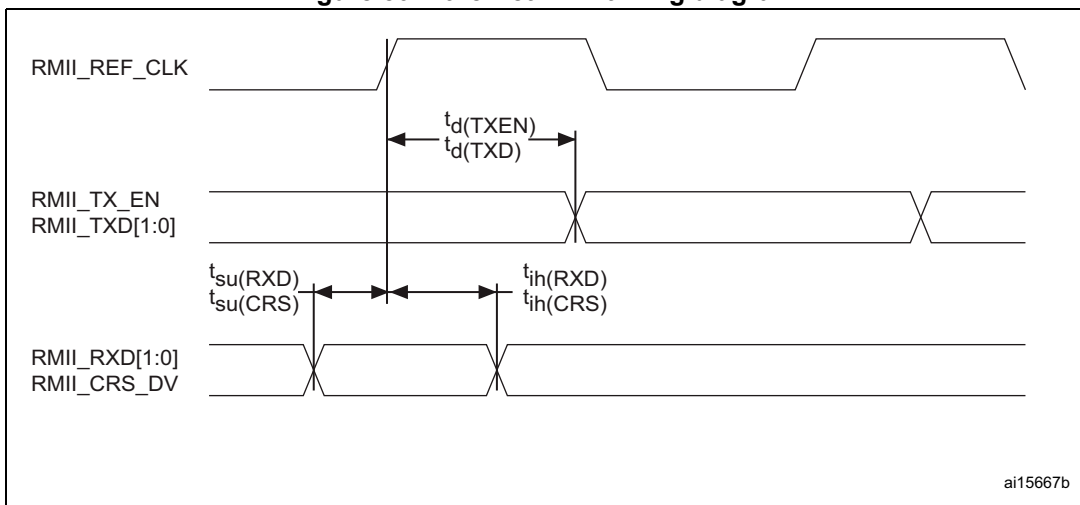
**Table 84. Dynamics characteristics: Ethernet MAC signals for SMI<sup>(1)</sup>**

Symbol	Parameter	Min	Typ	Max	Unit
$t_{MDC}$	MDC cycle time(2.38 MHz)	400	400	403	ns
$T_d(MDIO)$	Write data valid time	10	10.5	12.5	
$t_{su}(MDIO)$	Read data setup time	12.5	-	-	
$t_h(MDIO)$	Read data hold time	0	-	-	

1. Guaranteed by characterization results.

[Table 85](#) gives the list of Ethernet MAC signals for the RMIi and [Figure 50](#) shows the corresponding timing diagram.

**Figure 50. Ethernet RMIi timing diagram**



**Table 85. Dynamics characteristics: Ethernet MAC signals for RMIi<sup>(1)</sup>**

Symbol	Parameter	Min	Typ	Max	Unit
$t_{su}(RXD)$	Receive data setup time	1	-	-	ns
$t_h(RXD)$	Receive data hold time	1.5	-	-	
$t_{su}(CRS)$	Carrier sense setup time	1	-	-	
$t_h(CRS)$	Carrier sense hold time	1	-	-	
$t_d(TXEN)$	Transmit enable valid delay time	5	6	10.5	
$t_d(TXD)$	Transmit data valid delay time	5	6	12	

1. Guaranteed by characterization results.

Table 86 gives the list of Ethernet MAC signals for MII and Figure 50 shows the corresponding timing diagram.

Figure 51. Ethernet MII timing diagram

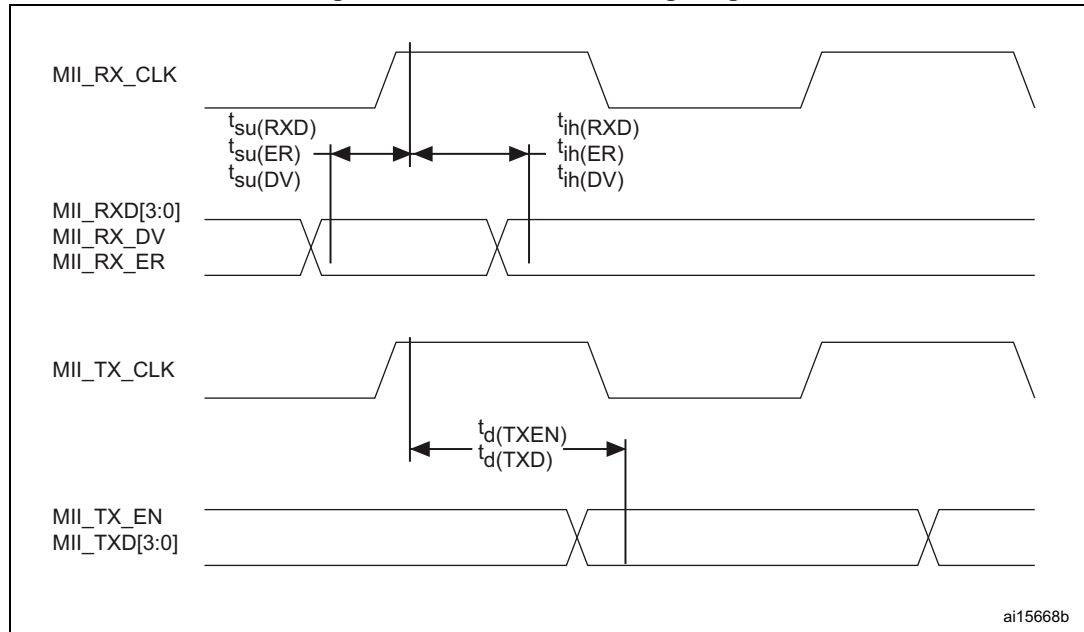


Table 86. Dynamics characteristics: Ethernet MAC signals for MII<sup>(1)</sup>

Symbol	Parameter	Min	Typ	Max	Unit
$t_{su}(RXD)$	Receive data setup time	3	-	-	ns
$t_{ih}(RXD)$	Receive data hold time	1.5	-	-	
$t_{su}(DV)$	Data valid setup time	0	-	-	
$t_{ih}(DV)$	Data valid hold time	1.5	-	-	
$t_{su}(ER)$	Error setup time	1.5	-	-	
$t_{ih}(ER)$	Error hold time	0.5	-	-	
$t_d(TXEN)$	Transmit enable valid delay time	6.5	7	13.5	
$t_d(TXD)$	Transmit data valid delay time	6.5	7	13.5	

1. Guaranteed by characterization results.

### CAN (controller area network) interface

Refer to [Section 6.3.17: I/O port characteristics](#) for more details on the input/output alternate function characteristics (CANx\_TX and CANx\_RX).

### 6.3.27 FMC characteristics

Unless otherwise specified, the parameters given in [Table 87](#) to [Table 100](#) for the FMC interface are derived from tests performed under the ambient temperature,  $f_{\text{HCLK}}$  frequency and  $V_{\text{DD}}$  supply voltage conditions summarized in [Table 16](#), with the following configuration:

- Output speed is set to  $\text{OSPEEDRy}[1:0] = 11$
- Measurement points are done at CMOS levels:  $0.5V_{\text{DD}}$

Refer to [Section 6.3.17: I/O port characteristics](#) for more details on the input/output characteristics.

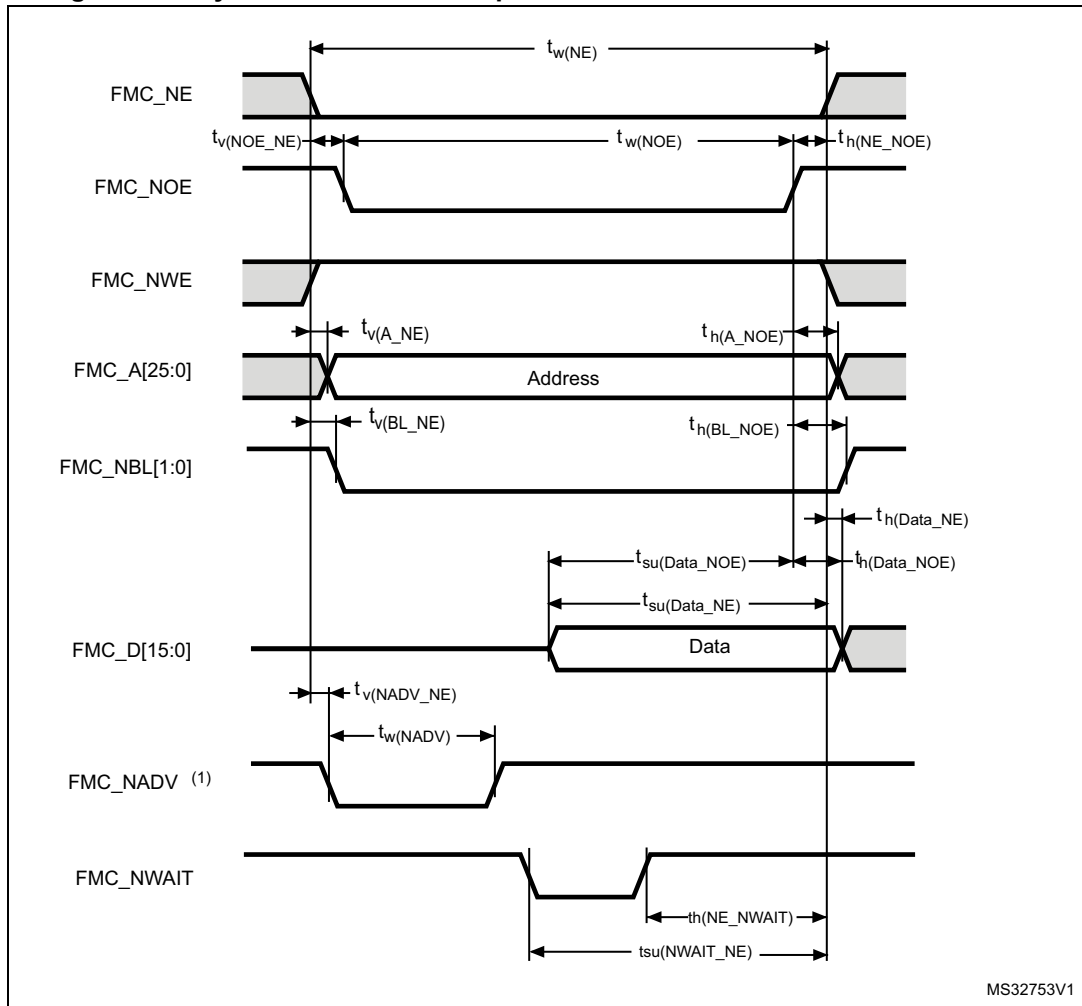
#### Asynchronous waveforms and timings

[Figure 52](#) through [Figure 55](#) represent asynchronous waveforms and [Table 87](#) through [Table 94](#) provide the corresponding timings. The results shown in these tables are obtained with the following FMC configuration:

- $\text{AddressSetupTime} = 0x1$
- $\text{AddressHoldTime} = 0x1$
- $\text{DataSetupTime} = 0x1$  (except for asynchronous NWAIT mode ,  $\text{DataSetupTime} = 0x5$ )
- $\text{BusTurnAroundDuration} = 0x0$
- Capacitive load  $\text{CL} = 30 \text{ pF}$

In all timing tables, the  $T_{\text{HCLK}}$  is the HCLK clock period

Figure 52. Asynchronous non-multiplexed SRAM/PSRAM/NOR read waveforms



1. Mode 2/B, C and D only. In Mode 1, FMC\_NADV is not used.

**Table 87. Asynchronous non-multiplexed SRAM/PSRAM/NOR read timings<sup>(1)</sup>**

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$2T_{HCLK} - 0.5$	$2T_{HCLK} + 1.5$	ns
$t_{v(NOE\_NE)}$	FMC_NEx low to FMC_NOE low	0	1	
$t_{w(NOE)}$	FMC_NOE low time	$2T_{HCLK} - 1$	$2T_{HCLK} + 1$	
$t_{h(NE\_NOE)}$	FMC_NOE high to FMC_NE high hold time	0	-	
$t_{v(A\_NE)}$	FMC_NEx low to FMC_A valid	-	0.5	
$t_{h(A\_NOE)}$	Address hold time after FMC_NOE high	0	-	
$t_{v(BL\_NE)}$	FMC_NEx low to FMC_BL valid	-	0.5	
$t_{h(BL\_NOE)}$	FMC_BL hold time after FMC_NOE high	0	-	
$t_{su(Data\_NE)}$	Data to FMC_NEx high setup time	$T_{HCLK} - 2$	-	
$t_{su(Data\_NOE)}$	Data to FMC_NOEx high setup time	$T_{HCLK} - 2$	-	
$t_{h(Data\_NOE)}$	Data hold time after FMC_NOE high	0	-	
$t_{h(Data\_NE)}$	Data hold time after FMC_NEx high	0	-	
$t_{v(NADV\_NE)}$	FMC_NEx low to FMC_NADV low	-	0	
$t_{w(NADV)}$	FMC_NADV low time	-	$T_{HCLK} + 1$	

1.  $C_L = 30$  pF.

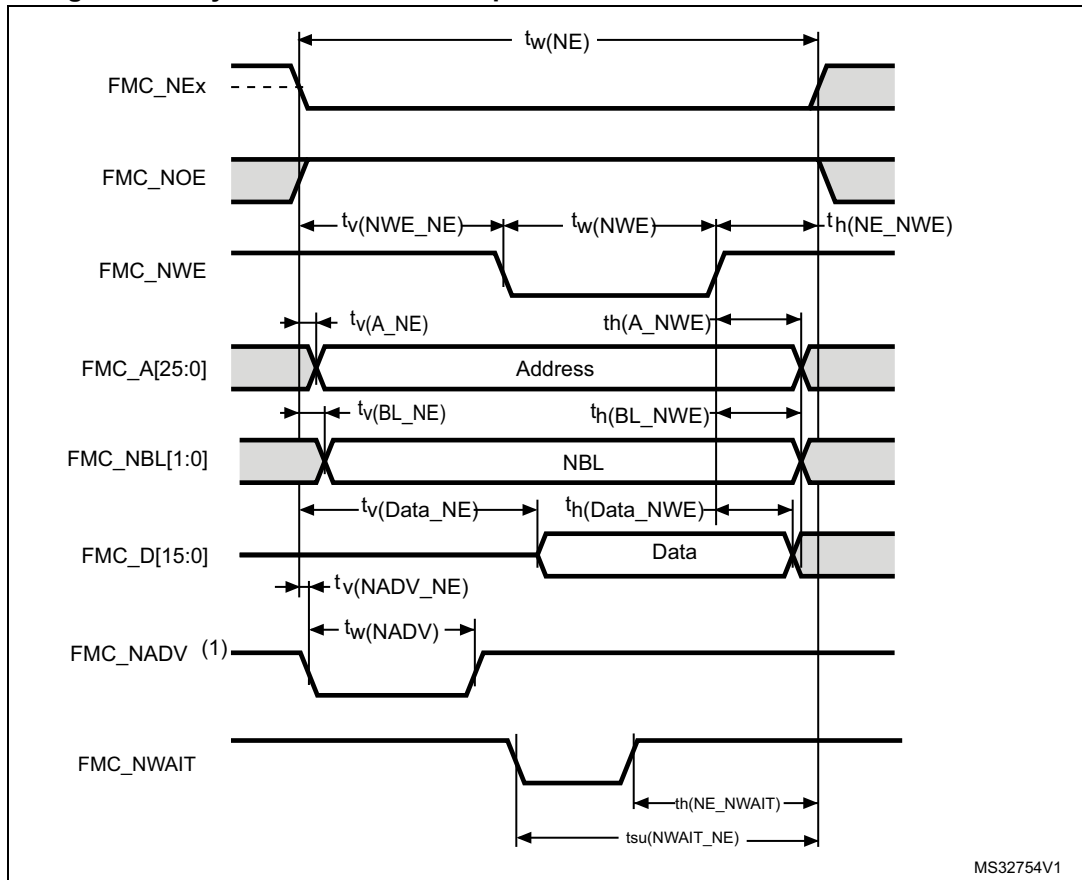
**Table 88. Asynchronous non-multiplexed SRAM/PSRAM/NOR read - NWAIT timings<sup>(1)</sup>**

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$7T_{HCLK} - 1$	$7T_{HCLK}$	ns
$t_{w(NOE)}$	FMC_NWE low time	$5T_{HCLK} - 1$	$5T_{HCLK} + 1$	
$t_{w(NWAIT)}$	FMC_NWAIT low time	$T_{HCLK} - 0.5$	-	
$t_{su(NWAIT\_NE)}$	FMC_NWAIT valid before FMC_NEx high	$5T_{HCLK} + 1.5$	-	
$t_{h(NE\_NWAIT)}$	FMC_NEx hold time after FMC_NWAIT invalid	$4T_{HCLK} + 1$	-	

1. Guaranteed by characterization results.



Figure 53. Asynchronous non-multiplexed SRAM/PSRAM/NOR write waveforms



MS32754V1

1. Mode 2/B, C and D only. In Mode 1, FMC\_NADV is not used.

Table 89. Asynchronous non-multiplexed SRAM/PSRAM/NOR write timings<sup>(1)</sup>

Symbol	Parameter	Min	Max	Unit
$t_w(NE)$	FMC_NE low time	$3T_{HCLK}-0.5$	$3T_{HCLK}+1.5$	ns
$t_v(NWE\_NE)$	FMC_NEx low to FMC_NWE low	$T_{HCLK}-0.5$	$T_{HCLK}+1$	
$t_w(NWE)$	FMC_NWE low time	$T_{HCLK}-0.5$	$T_{HCLK}+1$	
$t_h(NE\_NWE)$	FMC_NWE high to FMC_NE high hold time	$T_{HCLK}-0.5$	-	
$t_v(A\_NE)$	FMC_NEx low to FMC_A valid	-	0	
$t_h(A\_NWE)$	Address hold time after FMC_NWE high	$T_{HCLK}-0.5$	-	
$t_v(BL\_NE)$	FMC_NEx low to FMC_NBL valid	-	0	
$t_h(BL\_NWE)$	FMC_NBL hold time after FMC_NWE high	$T_{HCLK}-0.5$	-	
$t_v(Data\_NE)$	Data to FMC_NEx low to Data valid	-	$T_{HCLK}+3$	
$t_h(Data\_NWE)$	Data hold time after FMC_NWE high	$T_{HCLK}+0.5$	-	
$t_v(NADV\_NE)$	FMC_NEx low to FMC_NADV low	-	0	
$t_w(NADV)$	FMC_NADV low time	-	$T_{HCLK}+0.5$	

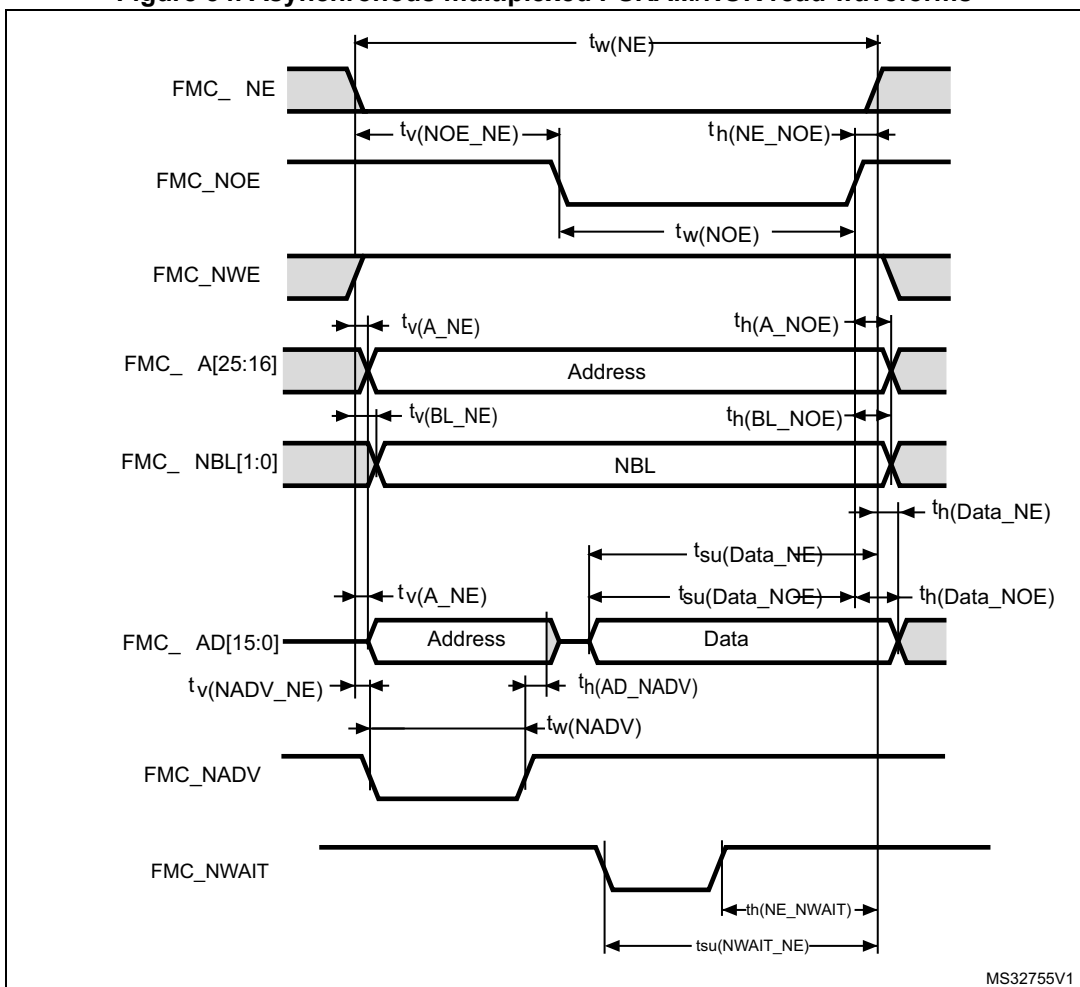
1. Guaranteed by characterization results.

**Table 90. Asynchronous non-multiplexed SRAM/PSRAM/NOR write - NWAIT timings<sup>(1)</sup>**

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$8T_{HCLK}-0.5$	$8T_{HCLK}+1.5$	ns
$t_{w(NWE)}$	FMC_NWE low time	$6T_{HCLK}-0.5$	$6T_{HCLK}+1$	
$t_{su(NWAIT\_NE)}$	FMC_NWAIT valid before FMC_NEx high	$6T_{HCLK}-1$	-	
$t_{h(NE\_NWAIT)}$	FMC_NEx hold time after FMC_NWAIT invalid	$4T_{HCLK}+2$	-	

1. Guaranteed by characterization results.

**Figure 54. Asynchronous multiplexed PSRAM/NOR read waveforms**



MS32755V1

**Table 91. Asynchronous multiplexed PSRAM/NOR read timings<sup>(1)</sup>**

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$3T_{HCLK}-0.5$	$3T_{HCLK}+1.5$	ns
$t_{v(NOE\_NE)}$	FMC_NEx low to FMC_NOE low	$2T_{HCLK}-1$	$2T_{HCLK}+0.5$	
$t_{tw(NOE)}$	FMC_NOE low time	$T_{HCLK}-0.5$	$T_{HCLK}+0.5$	
$t_{h(NE\_NOE)}$	FMC_NOE high to FMC_NE high hold time	0	-	
$t_{v(A\_NE)}$	FMC_NEx low to FMC_A valid	-	0.5	
$t_{v(NADV\_NE)}$	FMC_NEx low to FMC_NADV low	0	0.5	
$t_{w(NADV)}$	FMC_NADV low time	$T_{HCLK}-0.5$	$T_{HCLK}+1.5$	
$t_{h(AD\_NADV)}$	FMC_AD(address) valid hold time after FMC_NADV high)	0	-	
$t_{h(A\_NOE)}$	Address hold time after FMC_NOE high	$T_{HCLK}-0.5$	-	
$t_{h(BL\_NOE)}$	FMC_BL time after FMC_NOE high	0	-	
$t_{v(BL\_NE)}$	FMC_NEx low to FMC_BL valid	-	0.5	
$t_{su(Data\_NE)}$	Data to FMC_NEx high setup time	$T_{HCLK}-2$	-	
$t_{su(Data\_NOE)}$	Data to FMC_NOE high setup time	$T_{HCLK}-2$	-	
$t_{h(Data\_NE)}$	Data hold time after FMC_NEx high	0	-	
$t_{h(Data\_NOE)}$	Data hold time after FMC_NOE high	0	-	

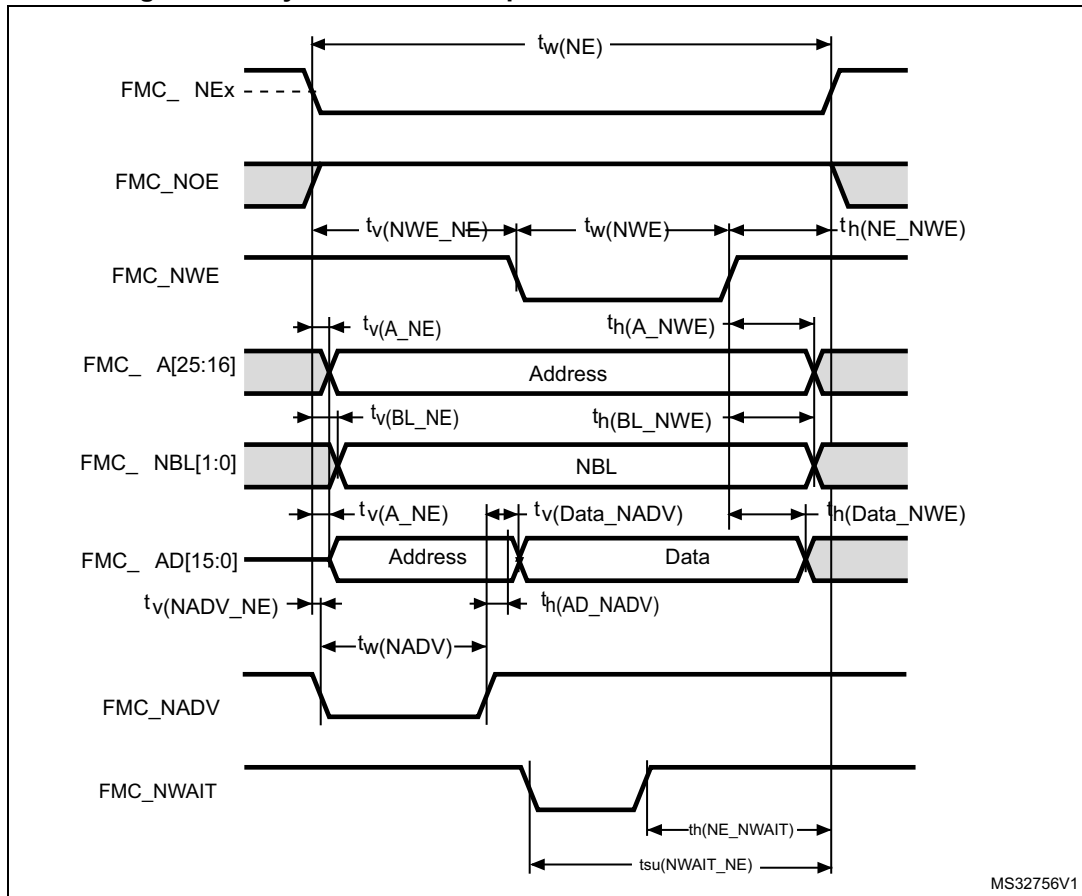
1. Guaranteed by characterization results.

**Table 92. Asynchronous multiplexed PSRAM/NOR read-NWAIT timings<sup>(1)</sup>**

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$8T_{HCLK}-1$	$8T_{HCLK}+2$	ns
$t_{w(NOE)}$	FMC_NWE low time	$5T_{HCLK}-1$	$5T_{HCLK}+1$	
$t_{su(NWAIT\_NE)}$	FMC_NWAIT valid before FMC_NEx high	$5T_{HCLK}+1.5$	-	
$t_{h(NE\_NWAIT)}$	FMC_NEx hold time after FMC_NWAIT invalid	$4T_{HCLK}+1$	-	

1. Guaranteed by characterization results.

Figure 55. Asynchronous multiplexed PSRAM/NOR write waveforms



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Table 93. Asynchronous multiplexed PSRAM/NOR write timings<sup>(1)</sup>

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$4T_{HCLK}-0.5$	$4T_{HCLK}+1.5$	ns
$t_{v(NWE\_NE)}$	FMC_NEx low to FMC_NWE low	$T_{HCLK}-1$	$T_{HCLK}+0.5$	
$t_{w(NWE)}$	FMC_NWE low time	$2T_{HCLK}-0.5$	$2T_{HCLK}+0.5$	
$t_{h(NE\_NWE)}$	FMC_NWE high to FMC_NE high hold time	$T_{HCLK}$	-	
$t_{v(A\_NE)}$	FMC_NEx low to FMC_A valid	-	0	
$t_{v(NADV\_NE)}$	FMC_NEx low to FMC_NADV low	0	0.5	
$t_{w(NADV)}$	FMC_NADV low time	$T_{HCLK}-0.5$	$T_{HCLK}+1.5$	
$t_{h(AD\_NADV)}$	FMC_AD(address) valid hold time after FMC_NADV high	$T_{HCLK}-2$	-	
$t_{h(A\_NWE)}$	Address hold time after FMC_NWE high	$T_{HCLK}$	-	
$t_{h(BL\_NWE)}$	FMC_BL hold time after FMC_NWE high	$T_{HCLK}-2$	-	
$t_{v(BL\_NE)}$	FMC_NEx low to FMC_BL valid	-	0	
$t_{v(Data\_NADV)}$	FMC_NADV high to Data valid	-	$T_{HCLK}+2$	
$t_{h(Data\_NWE)}$	Data hold time after FMC_NWE high	$T_{HCLK}+0.5$	-	

1. Guaranteed by characterization results.

**Table 94. Asynchronous multiplexed PSRAM/NOR write-NWAIT timings<sup>(1)</sup>**

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$9T_{HCLK}$	$9T_{HCLK}+1.5$	ns
$t_{w(NWE)}$	FMC_NWE low time	$7T_{HCLK}-0.5$	$7T_{HCLK}+0.5$	
$t_{su(NWAIT\_NE)}$	FMC_NWAIT valid before FMC_NEx high	$6T_{HCLK}+2$	-	
$t_{h(NE\_NWAIT)}$	FMC_NEx hold time after FMC_NWAIT invalid	$4T_{HCLK}-1$	-	

1. Guaranteed by characterization results.

### Synchronous waveforms and timings

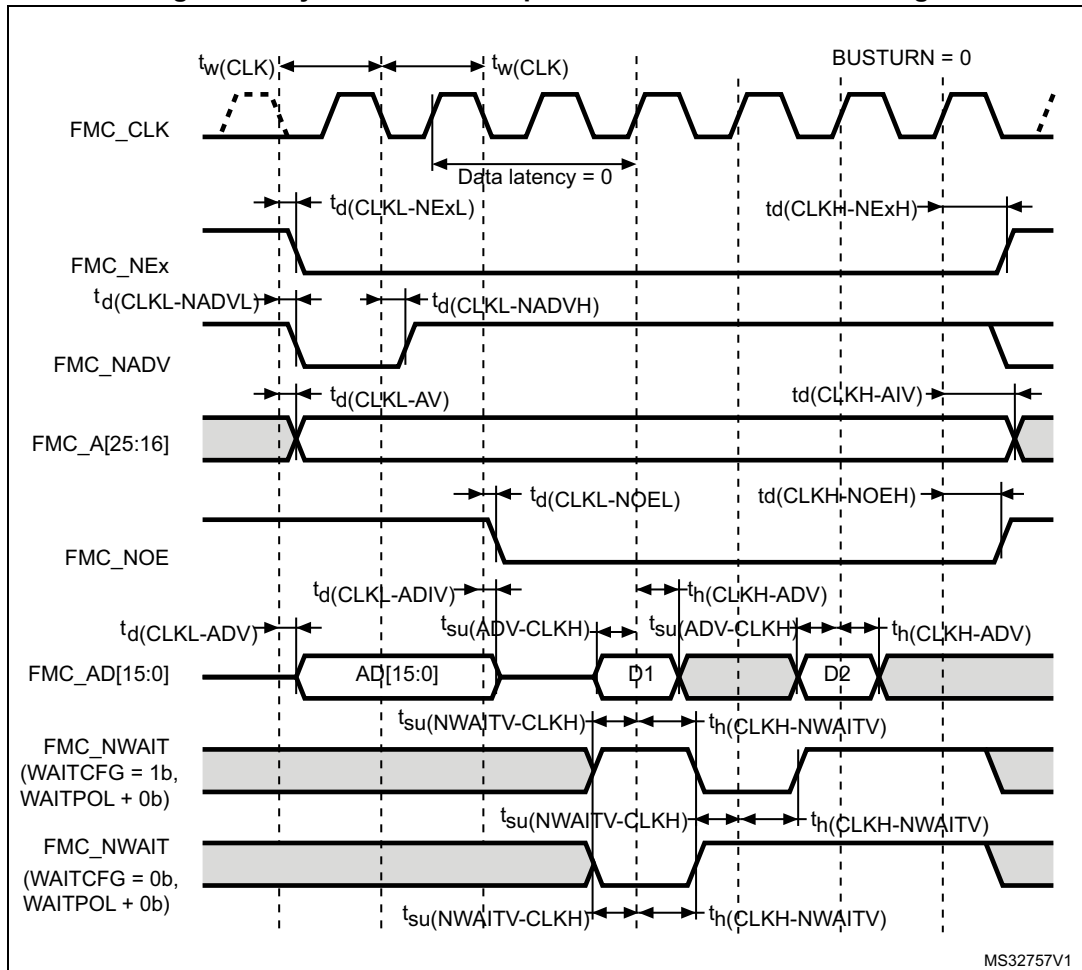
Figure 56 through Figure 59 represent synchronous waveforms and Table 95 through Table 98 provide the corresponding timings. The results shown in these tables are obtained with the following FMC configuration:

- BurstAccessMode = FMC\_BurstAccessMode\_Enable;
- MemoryType = FMC\_MemoryType\_CRAM;
- WriteBurst = FMC\_WriteBurst\_Enable;
- CLKDivision = 1;
- DataLatency = 1 for NOR Flash; DataLatency = 0 for PSRAM
- CL = 30 pF on data and address lines. CL = 10 pF on FMC\_CLK unless otherwise specified.

In all timing tables, the  $T_{HCLK}$  is the HCLK clock period.

- For  $2.7 V \leq V_{DD} \leq 3.6 V$ , maximum FMC\_CLK = 108 MHz at CL=20 pF or 90 MHz at CL=30 pF (on FMC\_CLK).
- For  $1.71 V \leq V_{DD} < 2.7 V$ , maximum FMC\_CLK = 70 MHz at CL=10 pF (on FMC\_CLK).

Figure 56. Synchronous multiplexed NOR/PSRAM read timings

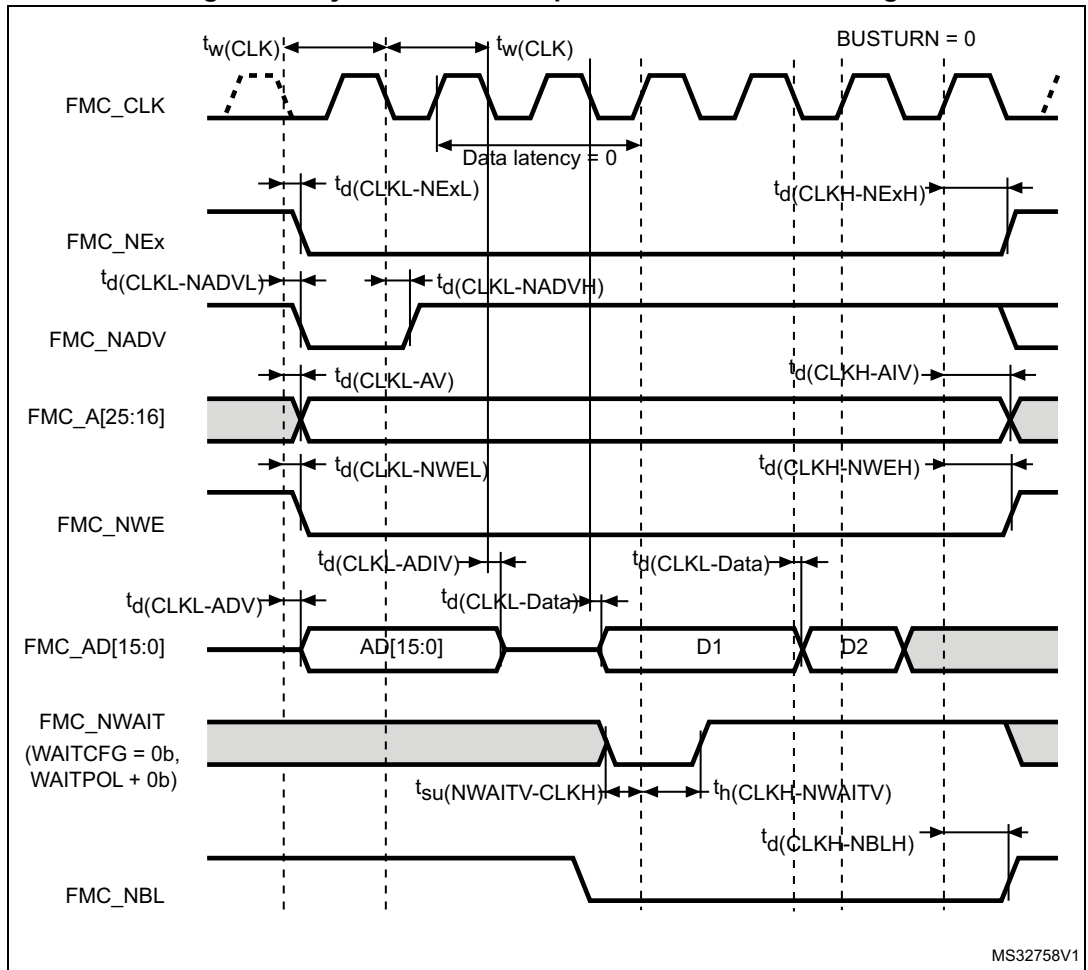


**Table 95. Synchronous multiplexed NOR/PSRAM read timings<sup>(1)</sup>**

Symbol	Parameter	Min	Max	Unit
$t_{w(CLK)}$	FMC_CLK period	$2T_{HCLK}-0.5$	-	ns
$t_{d(CLKL-NEXL)}$	FMC_CLK low to FMC_NEx low (x=0..2)	-	2	
$t_{d(CLKH-NEXH)}$	FMC_CLK high to FMC_NEx high (x= 0...2)	$T_{HCLK}+0.5$	-	
$t_{d(CLKL-NADV L)}$	FMC_CLK low to FMC_NADV low	-	1.5	
$t_{d(CLKL-NADV H)}$	FMC_CLK low to FMC_NADV high	0	-	
$t_{d(CLKL-AV)}$	FMC_CLK low to FMC_Ax valid (x=16...25)	-	2	
$t_{d(CLKH-AIV)}$	FMC_CLK high to FMC_Ax invalid (x=16...25)	$T_{HCLK}$	-	
$t_{d(CLKL-NOEL)}$	FMC_CLK low to FMC_NOE low	-	2	
$t_{d(CLKH-NOEH)}$	FMC_CLK high to FMC_NOE high	$T_{HCLK}-0.5$	-	
$t_{d(CLKL-ADV)}$	FMC_CLK low to FMC_AD[15:0] valid	-	3	
$t_{d(CLKL-ADIV)}$	FMC_CLK low to FMC_AD[15:0] invalid	0	-	
$t_{su(ADV-CLKH)}$	FMC_A/D[15:0] valid data before FMC_CLK high	1.5	-	
$t_h(CLKH-ADV)$	FMC_A/D[15:0] valid data after FMC_CLK high	1	-	
$t_{su(NWAIT-CLKH)}$	FMC_NWAIT valid before FMC_CLK high	2	-	
$t_h(CLKH-NWAIT)$	FMC_NWAIT valid after FMC_CLK high	3.5	-	

1. Guaranteed by characterization results.

Figure 57. Synchronous multiplexed PSRAM write timings





**Table 96. Synchronous multiplexed PSRAM write timings<sup>(1)</sup>**

Symbol	Parameter	Min	Max	Unit
$t_{w(CLK)}$	FMC_CLK period	$2T_{HCLK}-0.5$	-	ns
$t_{d(CLKL-NExL)}$	FMC_CLK low to FMC_NEx low (x=0..2)	-	1.5	
$t_{d(CLKH-NExH)}$	FMC_CLK high to FMC_NEx high (x= 0...2)	$T_{HCLK}+0.5$	-	
$t_{d(CLKL-NADVl)}$	FMC_CLK low to FMC_NADV low	-	1.5	
$t_{d(CLKL-NADVh)}$	FMC_CLK low to FMC_NADV high	0	-	
$t_{d(CLKL-AV)}$	FMC_CLK low to FMC_Ax valid (x=16...25)	-	2	
$t_{d(CLKH-AIV)}$	FMC_CLK high to FMC_Ax invalid (x=16...25)	$T_{HCLK}$	-	
$t_{d(CLKL-NWEL)}$	FMC_CLK low to FMC_NWE low	-	1.5	
$t_{d(CLKH-NWEH)}$	FMC_CLK high to FMC_NWE high	$T_{HCLK}-0.5$	-	
$t_{d(CLKL-ADV)}$	FMC_CLK low to FMC_AD[15:0] valid	-	3	
$t_{d(CLKL-ADIV)}$	FMC_CLK low to FMC_AD[15:0] invalid	0	-	
$t_{d(CLKL-DATA)}$	FMC_A/D[15:0] valid data after FMC_CLK low	-	3.5	
$t_{d(CLKL-NBLl)}$	FMC_CLK low to FMC_NBL low	1	-	
$t_{d(CLKH-NBLH)}$	FMC_CLK high to FMC_NBL high	$T_{HCLK}+0.5$	-	
$t_{su(NWAIT-CLKH)}$	FMC_NWAIT valid before FMC_CLK high	2	-	
$t_h(CLKH-NWAIT)$	FMC_NWAIT valid after FMC_CLK high	3.5	-	

1. Guaranteed by characterization results.

Figure 58. Synchronous non-multiplexed NOR/PSRAM read timings

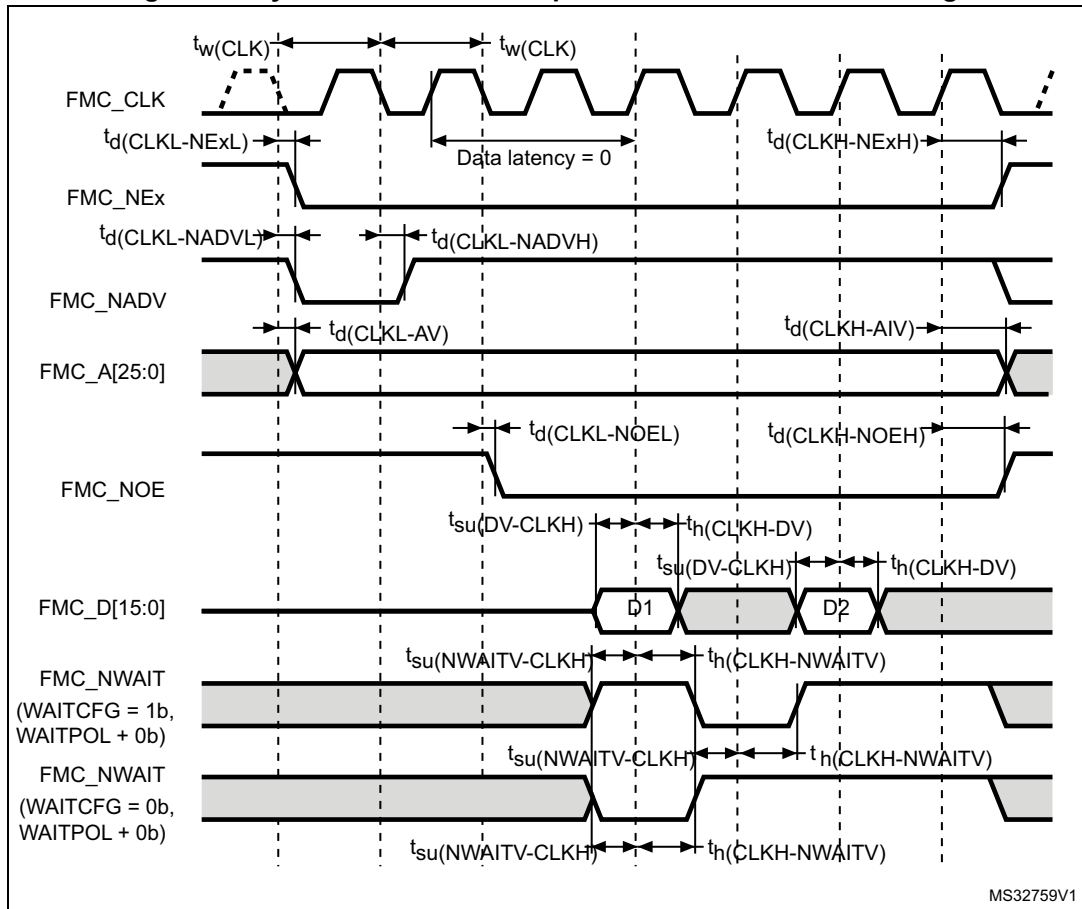


Table 97. Synchronous non-multiplexed NOR/PSRAM read timings<sup>(1)</sup>

Symbol	Parameter	Min	Max	Unit
$t_w(\text{CLK})$	FMC_CLK period	$2T_{\text{HCLK}}-1$	-	ns
$t_{\text{d}}(\text{CLKL-NExL})$	FMC_CLK low to FMC_NEx low (x=0..2)	-	2.5	
$t_{\text{d}}(\text{CLKH-NExH})$	FMC_CLK high to FMC_NEx high (x=0...2)	$T_{\text{HCLK}}+0.5$	-	
$t_{\text{d}}(\text{CLKL-NADVl})$	FMC_CLK low to FMC_NADV low	-	0	
$t_{\text{d}}(\text{CLKL-NADVh})$	FMC_CLK low to FMC_NADV high	0	-	
$t_{\text{d}}(\text{CLKL-AV})$	FMC_CLK low to FMC_Ax valid (x=16...25)	-	2.5	
$t_{\text{d}}(\text{CLKH-AIV})$	FMC_CLK high to FMC_Ax invalid (x=16...25)	$T_{\text{HCLK}}$	-	
$t_{\text{d}}(\text{CLKL-NOEL})$	FMC_CLK low to FMC_NOE low	-	2	
$t_{\text{d}}(\text{CLKH-NOEH})$	FMC_CLK high to FMC_NOE high	$T_{\text{HCLK}}+0.5$	-	
$t_{\text{su}}(\text{DV-CLKH})$	FMC_D[15:0] valid data before FMC_CLK high	1.5	-	
$t_{\text{h}}(\text{CLKH-DV})$	FMC_D[15:0] valid data after FMC_CLK high	1	-	
$t_{\text{su}}(\text{NWAITV-CLKH})$	FMC_NWAIT valid before FMC_CLK high	2	-	
$t_{\text{h}}(\text{CLKH-NWAITV})$	FMC_NWAIT valid after FMC_CLK high	3.5	-	

1. Guaranteed by characterization results.

**Figure 59. Synchronous non-multiplexed PSRAM write timings**

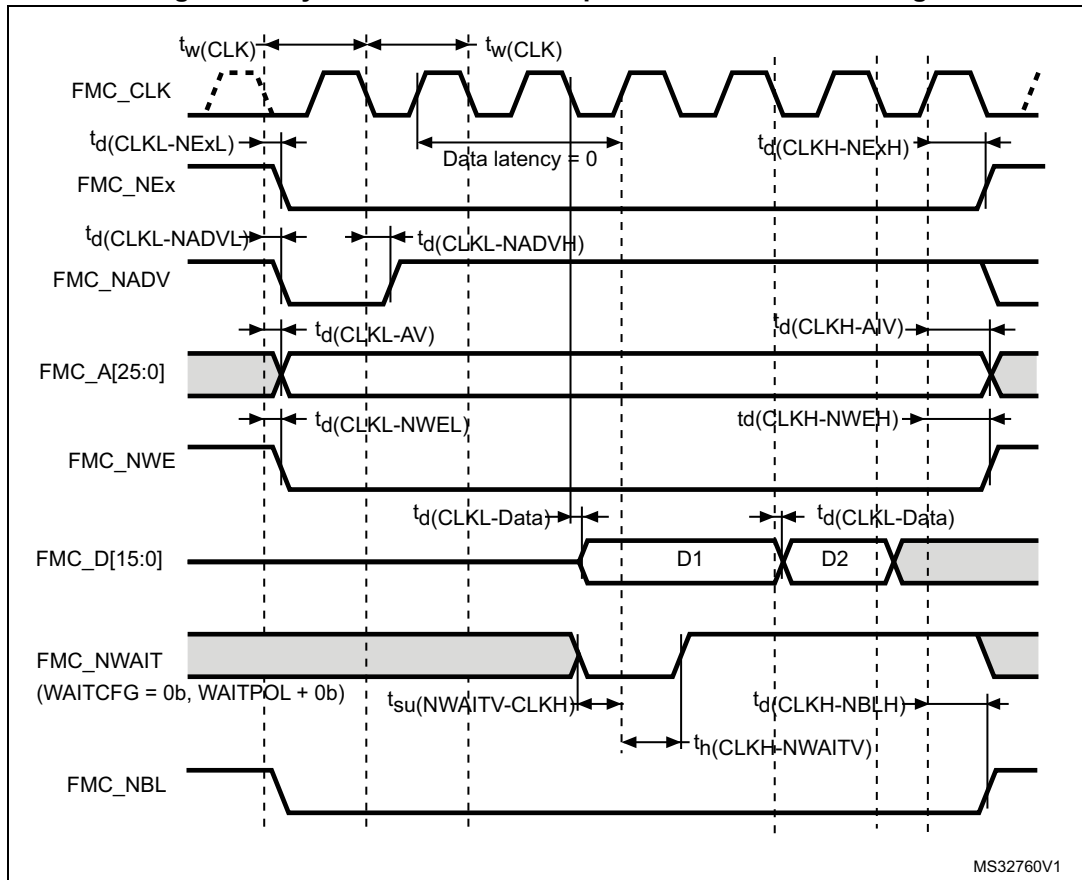


Table 98. Synchronous non-multiplexed PSRAM write timings<sup>(1)</sup>

Symbol	Parameter	Min	Max	Unit
$t_{(CLK)}$	FMC_CLK period	$2T_{HCLK}-1$	-	ns
$t_{d(CLKL-NExL)}$	FMC_CLK low to FMC_NEx low (x=0..2)	-	2.5	
$t_{(CLKH-NExH)}$	FMC_CLK high to FMC_NEx high (x= 0...2)	$T_{HCLK}+0.5$	-	
$t_{d(CLKL-NADV L)}$	FMC_CLK low to FMC_NADV low	-	1.5	
$t_{d(CLKL-NADV H)}$	FMC_CLK low to FMC_NADV high	0	-	
$t_{d(CLKL-AV)}$	FMC_CLK low to FMC_Ax valid (x=16...25)	-	2.5	
$t_{d(CLKH-AIV)}$	FMC_CLK high to FMC_Ax invalid (x=16...25)	0	-	
$t_{d(CLKL-NWEL)}$	FMC_CLK low to FMC_NWE low	-	1.5	
$t_{d(CLKH-NWEH)}$	FMC_CLK high to FMC_NWE high	$T_{HCLK}+1$	-	
$t_{d(CLKL-Data)}$	FMC_D[15:0] valid data after FMC_CLK low	-	3	
$t_{d(CLKL-NBLL)}$	FMC_CLK low to FMC_NBL low	1.5	-	
$t_{d(CLKH-NBLH)}$	FMC_CLK high to FMC_NBL high	$T_{HCLK}+0.5$	-	
$t_{su(NWAIT-CLKH)}$	FMC_NWAIT valid before FMC_CLK high	2	-	
$t_{h(CLKH-NWAIT)}$	FMC_NWAIT valid after FMC_CLK high	3.5	-	

1. Guaranteed by characterization results.

### NAND controller waveforms and timings

Figure 60 through Figure 63 represent synchronous waveforms, and Table 99 and Table 100 provide the corresponding timings. The results shown in this table are obtained with the following FMC configuration:

- COM.FMC\_SetupTime = 0x01;
- COM.FMC\_WaitSetupTime = 0x03;
- COM.FMC\_HoldSetupTime = 0x02;
- COM.FMC\_HiZSetupTime = 0x01;
- ATT.FMC\_SetupTime = 0x01;
- ATT.FMC\_WaitSetupTime = 0x03;
- ATT.FMC\_HoldSetupTime = 0x02;
- ATT.FMC\_HiZSetupTime = 0x01;
- Bank = FMC\_Bank\_NAND;
- MemoryDataWidth = FMC\_MemoryDataWidth\_16b;
- ECC = FMC\_ECC\_Enable;
- ECCPageSize = FMC\_ECCPageSize\_512Bytes;
- TCLRSetupTime = 0;
- TARSetupTime = 0.

In all timing tables, the  $T_{HCLK}$  is the HCLK clock period.

Figure 60. NAND controller waveforms for read access

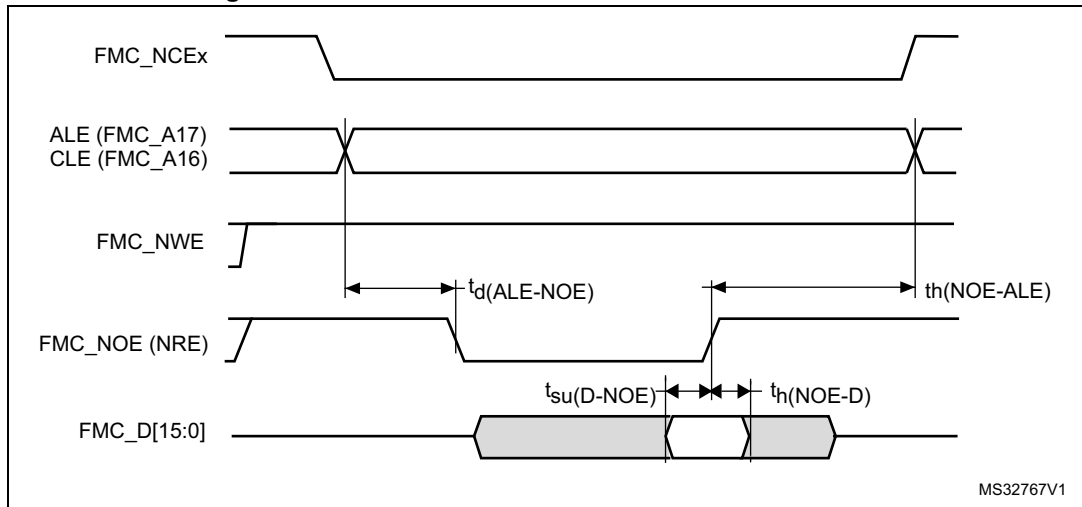


Figure 61. NAND controller waveforms for write access

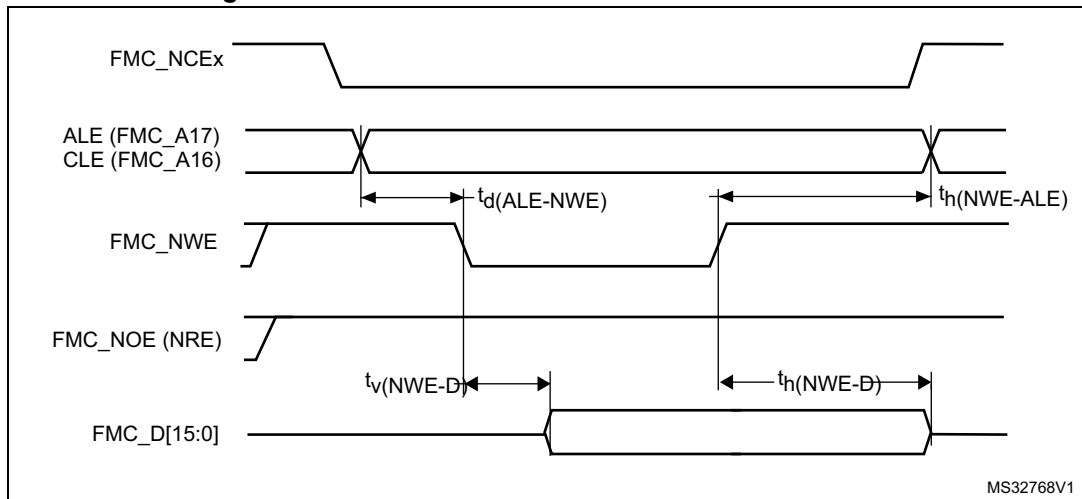


Figure 62. NAND controller waveforms for common memory read access

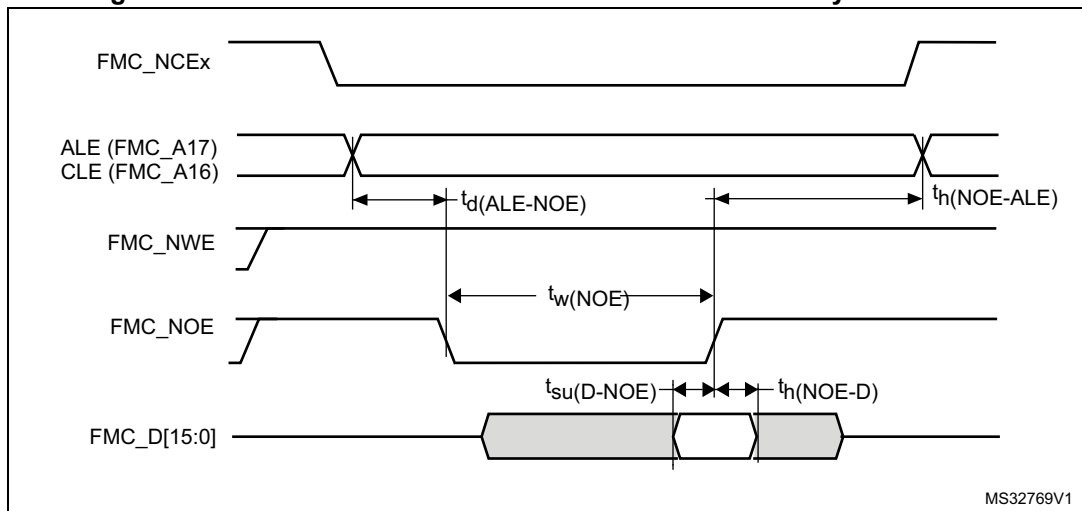


Figure 63. NAND controller waveforms for common memory write access

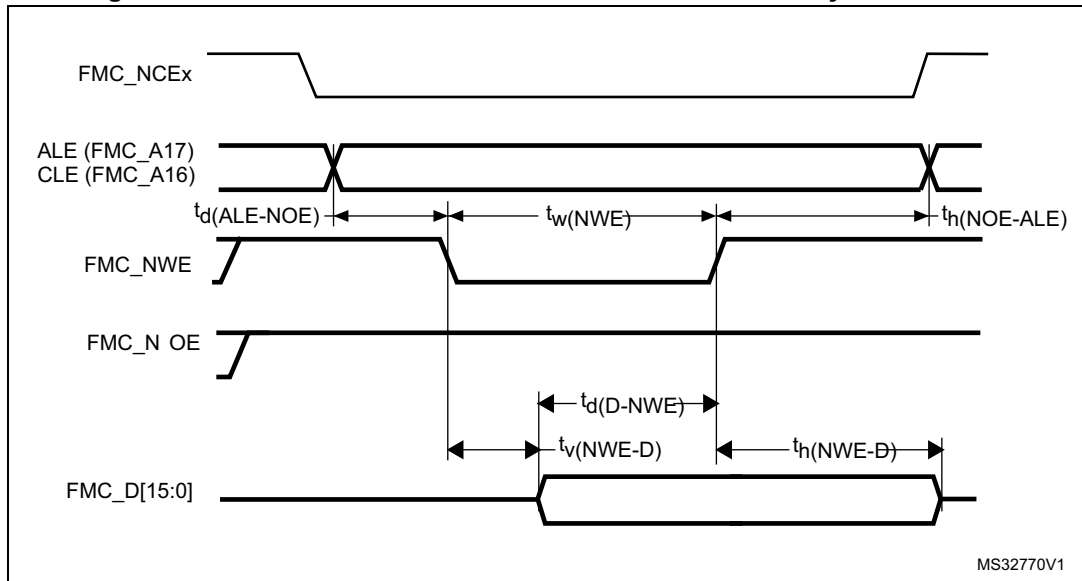


Table 99. Switching characteristics for NAND Flash read cycles<sup>(1)</sup>

Symbol	Parameter	Min	Max	Unit
$t_{w(\text{NOE})}$	FMC_NOE low width	$4T_{\text{HCLK}}-0.5$	$4T_{\text{HCLK}}$	ns
$t_{\text{su}(\text{D-NOE})}$	FMC_D[15-0] valid data before FMC_NOE high	13	-	
$t_{\text{h}(\text{NOE-D})}$	FMC_D[15-0] valid data after FMC_NOE high	3	-	
$t_{\text{d}(\text{ALE-NOE})}$	FMC_ALE valid before FMC_NOE low	-	$3T_{\text{HCLK}}-0.5$	
$t_{\text{h}(\text{NOE-ALE})}$	FMC_NWE high to FMC_ALE invalid	$3T_{\text{HCLK}}-2$	-	

1. Guaranteed by characterization results.

Table 100. Switching characteristics for NAND Flash write cycles<sup>(1)</sup>

Symbol	Parameter	Min	Max	Unit
$t_{w(\text{NWE})}$	FMC_NWE low width	$4T_{\text{HCLK}}-0.5$	$4T_{\text{HCLK}}$	ns
$t_{\text{v}(\text{NWE-D})}$	FMC_NWE low to FMC_D[15-0] valid	0	-	
$t_{\text{h}(\text{NWE-D})}$	FMC_NWE high to FMC_D[15-0] invalid	$3T_{\text{HCLK}}-1$	-	
$t_{\text{d}(\text{D-NWE})}$	FMC_D[15-0] valid before FMC_NWE high	$5T_{\text{HCLK}}-3$	-	
$t_{\text{d}(\text{ALE-NWE})}$	FMC_ALE valid before FMC_NWE low	-	$3T_{\text{HCLK}}-0.5$	
$t_{\text{h}(\text{NWE-ALE})}$	FMC_NWE high to FMC_ALE invalid	$3T_{\text{HCLK}}-2$	-	

1. Guaranteed by characterization results.

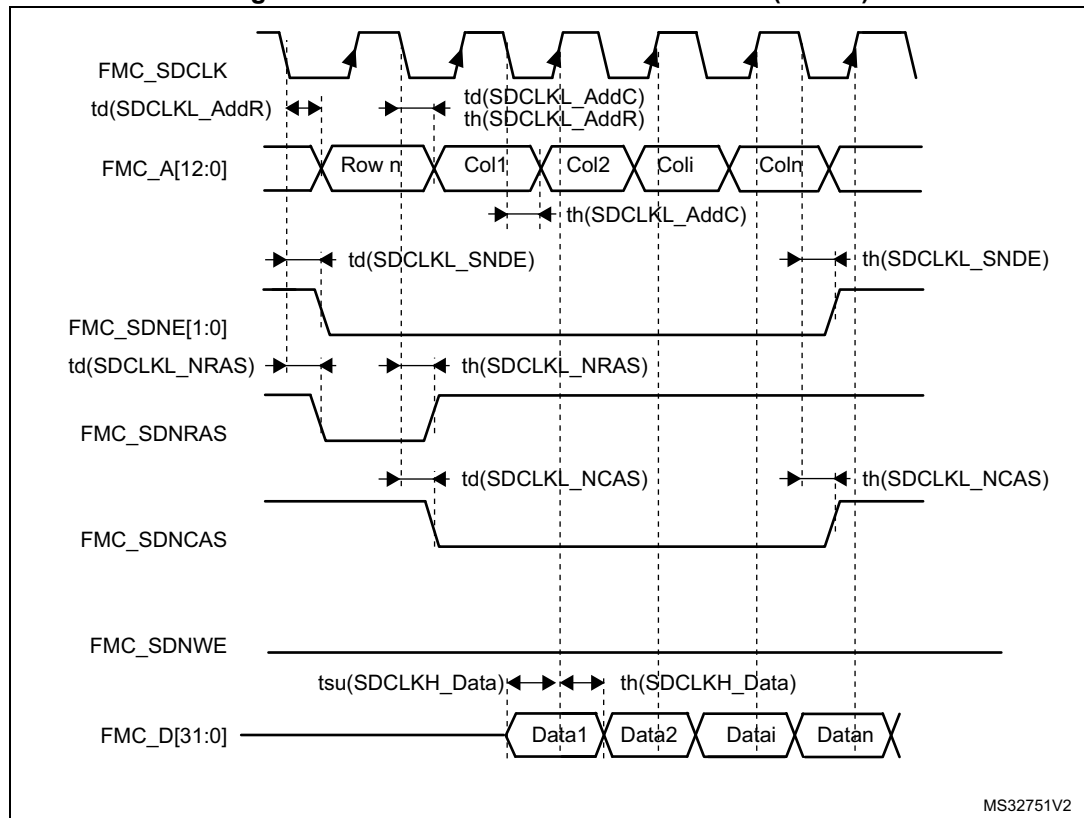
**SDRAM waveforms and timings**

- CL = 30 pF on data and address lines. CL = 10 pF on FMC\_SDCLK unless otherwise specified.

In all timing tables, the  $T_{HCLK}$  is the HCLK clock period.

- For  $3.0 V \leq V_{DD} \leq 3.6 V$ , maximum FMC\_SDCLK = 100 MHz at CL=20 pF (on FMC\_SDCLK).
- For  $2.7 V \leq V_{DD} \leq 3.6 V$ , maximum FMC\_SDCLK = 90 MHz at CL=30 pF (on FMC\_SDCLK).
- For  $1.71 V \leq V_{DD} < 1.9 V$ , maximum FMC\_SDCLK = 70 MHz at CL=10 pF (on FMC\_SDCLK).

**Figure 64. SDRAM read access waveforms (CL = 1)**



**Table 101. SDRAM read timings<sup>(1)</sup>**

Symbol	Parameter	Min	Max	Unit
$t_{w(SDCLK)}$	FMC_SDCLK period	$2T_{HCLK}-0.5$	$2T_{HCLK}+0.5$	ns
$t_{su(SDCLKH\_Data)}$	Data input setup time	3.5	-	
$t_{h(SDCLKH\_Data)}$	Data input hold time	1.5	-	
$t_{d(SDCLKL\_Add)}$	Address valid time	-	4	
$t_{d(SDCLKL\_SDNE)}$	Chip select valid time	-	0.5	
$t_{h(SDCLKL\_SDNE)}$	Chip select hold time	0	-	
$t_{d(SDCLKL\_SDNRAS)}$	SDNRAS valid time	-	0.5	
$t_{h(SDCLKL\_SDNRAS)}$	SDNRAS hold time	0	-	
$t_{d(SDCLKL\_SDNCAS)}$	SDNCAS valid time	-	0.5	
$t_{h(SDCLKL\_SDNCAS)}$	SDNCAS hold time	0	-	

1. Guaranteed by characterization results.

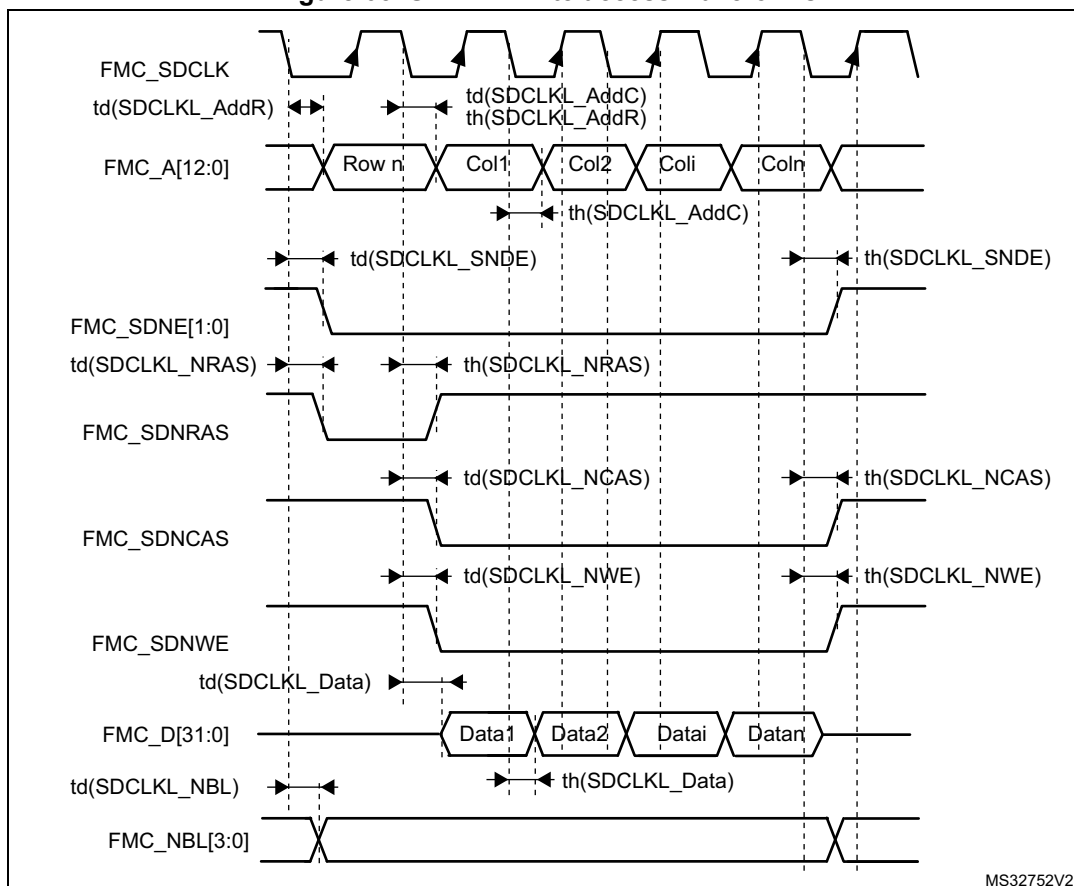
**Table 102. LPSPDR SDRAM read timings<sup>(1)</sup>**

Symbol	Parameter	Min	Max	Unit
$t_{w(SDCLK)}$	FMC_SDCLK period	$2T_{HCLK}-0.5$	$2T_{HCLK}+0.5$	ns
$t_{su(SDCLKH\_Data)}$	Data input setup time	3	-	
$t_{h(SDCLKH\_Data)}$	Data input hold time	1.5	-	
$t_{d(SDCLKL\_Add)}$	Address valid time	-	3.5	
$t_{d(SDCLKL\_SDNE)}$	Chip select valid time	-	0.5	
$t_{h(SDCLKL\_SDNE)}$	Chip select hold time	0	-	
$t_{d(SDCLKL\_SDNRAS)}$	SDNRAS valid time	-	0.5	
$t_{h(SDCLKL\_SDNRAS)}$	SDNRAS hold time	0	-	
$t_{d(SDCLKL\_SDNCAS)}$	SDNCAS valid time	-	0.5	
$t_{h(SDCLKL\_SDNCAS)}$	SDNCAS hold time	0	-	

1. Guaranteed by characterization results.



Figure 65. SDRAM write access waveforms



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Table 103. SDRAM write timings<sup>(1)</sup>

Symbol	Parameter	Min	Max	Unit
$t_w(\text{SDCLK})$	FMC_SDCLK period	$2T_{\text{HCLK}}-0.5$	$2T_{\text{HCLK}}+0.5$	ns
$t_d(\text{SDCLKL\_Data})$	Data output valid time	-	2	
$t_h(\text{SDCLKL\_Data})$	Data output hold time	0.5	-	
$t_d(\text{SDCLKL\_Add})$	Address valid time	-	4	
$t_d(\text{SDCLKL\_SDNWE})$	SDNWE valid time	-	0.5	
$t_h(\text{SDCLKL\_SDNWE})$	SDNWE hold time	0	-	
$t_d(\text{SDCLKL\_SDNE})$	Chip select valid time	-	0.5	
$t_h(\text{SDCLKL\_SDNE})$	Chip select hold time	0	-	
$t_d(\text{SDCLKL\_SDNRAS})$	SDNRAS valid time	-	0.5	
$t_h(\text{SDCLKL\_SDNRAS})$	SDNRAS hold time	0	-	
$t_d(\text{SDCLKL\_SDNCAS})$	SDNCAS valid time	-	0.5	
$t_h(\text{SDCLKL\_SDNCAS})$	SDNCAS hold time	0	-	

1. Guaranteed by characterization results.

**Table 104. LPDDR SDRAM write timings<sup>(1)</sup>**

Symbol	Parameter	Min	Max	Unit
$t_w(\text{SDCLK})$	FMC_SDCLK period	$2T_{\text{HCLK}}-0.5$	$2T_{\text{HCLK}}+0.5$	ns
$t_d(\text{SDCLKL\_Data})$	Data output valid time	-	4	
$t_h(\text{SDCLKL\_Data})$	Data output hold time	0	-	
$t_d(\text{SDCLKL\_Add})$	Address valid time	-	3.5	
$t_d(\text{SDCLKL-SDNWE})$	SDNWE valid time	-	0.5	
$t_h(\text{SDCLKL-SDNWE})$	SDNWE hold time	0	-	
$t_d(\text{SDCLKL-SDNE})$	Chip select valid time	-	0.5	
$t_h(\text{SDCLKL-SDNE})$	Chip select hold time	0	-	
$t_d(\text{SDCLKL-SDNRAS})$	SDNRAS valid time	-	0.5	
$t_h(\text{SDCLKL-SDNRAS})$	SDNRAS hold time	0	-	
$t_d(\text{SDCLKL-SDNCAS})$	SDNCAS valid time	-	0.5	
$t_d(\text{SDCLKL-SDNCAS})$	SDNCAS hold time	0	-	

1. Guaranteed by characterization results.

### 6.3.28 Quad-SPI interface characteristics

Unless otherwise specified, the parameters given in [Table 105](#) and [Table 106](#) for Quad-SPI are derived from tests performed under the ambient temperature,  $f_{\text{AHB}}$  frequency and  $V_{\text{DD}}$  supply voltage conditions summarized in [Table 16: General operating conditions](#), with the following configuration:

- Output speed is set to  $\text{OSPEEDRy}[1:0] = 11$
- Capacitive load  $C = 20 \text{ pF}$
- Measurement points are done at CMOS levels:  $0.5 \times V_{\text{DD}}$

Refer to [Section 6.3.17: I/O port characteristics](#) for more details on the input/output alternate function characteristics.

**Table 105. Quad-SPI characteristics in SDR mode<sup>(1)</sup>**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$F_{\text{ck1}}/t(\text{CK})$	Quad-SPI clock frequency	$2.7 \text{ V} \leq V_{\text{DD}} < 3.6 \text{ V}$ $CL=20 \text{ pF}$	-	-	108	MHz
		$1.71 \text{ V} < V_{\text{DD}} \leq 3.6 \text{ V}$ $CL=15 \text{ pF}$	-	-	100	

**Table 105. Quad-SPI characteristics (continued)in SDR mode<sup>(1)</sup> (continued)**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
tw(CKH)	Quad-SPI clock high and low time	-	$t(CK)/2 - 1$	-	$t(CK)/2$	ns
tw(CKL)			$t(CK)/2$	-	$t(CK)/2 + 1$	
ts(IN)	Data input setup time	-	1	-	-	
th(IN)	Data input hold time		3	-	-	
tv(OUT)	Data output valid time	$2.7 V < V_{DD} < 3.6 V$	-	1.5	3	
		$1.71 V < V_{DD} < 3.6 V$	-	1.5	4	
th(OUT)	Data output hold time	-	0	-	-	

1. Guaranteed by characterization results.

**Table 106. Quad-SPI characteristics in DDR mode<sup>(1)</sup>**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Fck1/t(CK)	Quad-SPI clock frequency	$2.7 V < V_{DD} < 3.6 V$ CL=20 pF	-	-	80	MHz
		$1.8 V < V_{DD} < 3.6 V$ CL=15 pF	-	-	80	
		$1.71 V < V_{DD} < 3.6 V$ CL=10 pF	-	-	80	
tw(CKH)	Quad-SPI clock high and low time	-	$t(CK)/2 - 1$	-	$t(CK)/2$	ns
tw(CKL)			$t(CK)/2$	-	$t(CK)/2 + 1$	
ts(IN), tsf(IN)	Data input setup time	$2.7 V < V_{DD} < 3.6 V$	1.5	-	-	
		$1.71 V < V_{DD} < 2 V$	0.75	-	-	
thr(IN), thf(IN)	Data input hold time	$2.7 V < V_{DD} < 3.6 V$	3.5	-	-	
		$1.71 V < V_{DD} < 2 V$	4.5	-	-	
tvr(OUT), tvf(OUT)	Data output valid time	$2.7 V < V_{DD} < 3.6 V$	-	8	10.5	
		$1.71 V < V_{DD} < 3.6 V$ DHHC=0	-	8	14.5	
		DHHC=1 Pres=1, 2...	-	Thclk/2 + 1.75	Thclk/2 + 2.25	
thr(OUT), thf(OUT)	Data output hold time	DHHC=0	7.5	-	-	
		DHHC=1 Pres=1, 2...	Thclk/2 + 1.5	-	-	

1. Guaranteed by characterization results.

Figure 66. Quad-SPI timing diagram - SDR mode

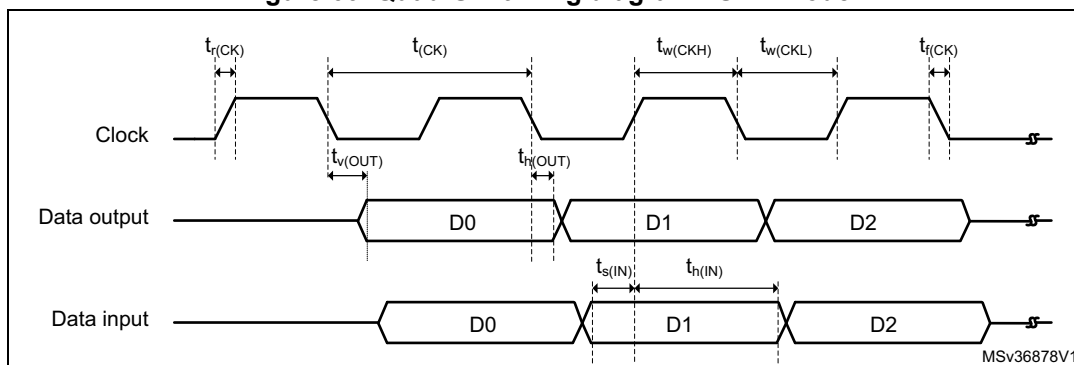
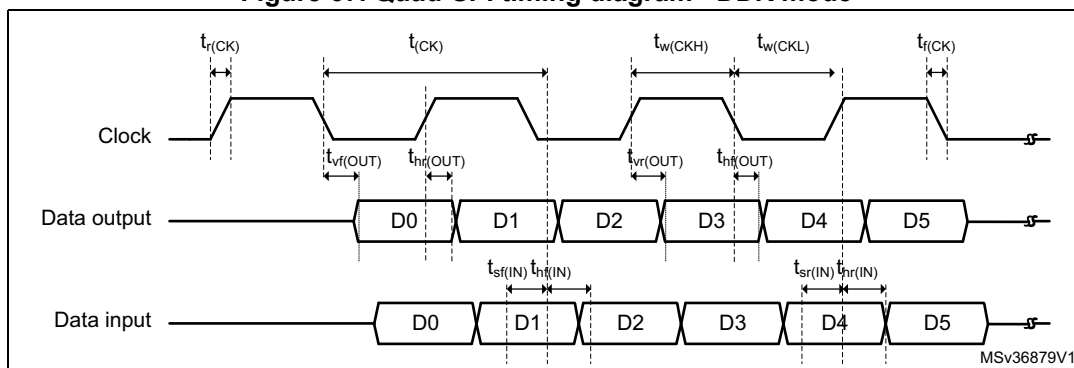


Figure 67. Quad-SPI timing diagram - DDR mode



### 6.3.29 Camera interface (DCMI) timing specifications

Unless otherwise specified, the parameters given in [Table 107](#) for DCMI are derived from tests performed under the ambient temperature,  $f_{HCLK}$  frequency and  $V_{DD}$  supply voltage summarized in [Table 16](#), with the following configuration:

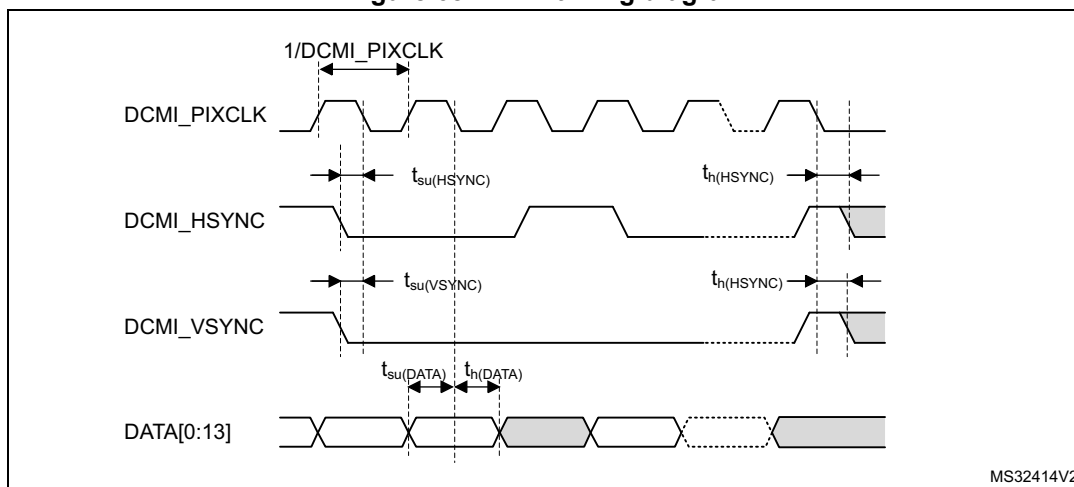
- DCMI\_PIXCLK polarity: falling
- DCMI\_VSYNC and DCMI\_HSYNC polarity: high
- Data formats: 14 bits

Table 107. DCMI characteristics<sup>(1)</sup>

Symbol	Parameter	Min	Max	Unit
-	Frequency ratio DCMI_PIXCLK/ $f_{HCLK}$	-	0.4	
DCMI_PIXCLK	Pixel clock input	-	54	MHz
$D_{Pixel}$	Pixel clock input duty cycle	30	70	%
$t_{su(DATA)}$	Data input setup time	3.5	-	ns
$t_{h(DATA)}$	Data input hold time	0	-	
$t_{su(HSYNC)}$ $t_{su(VSYNC)}$	DCMI_HSYNC/DCMI_VSYNC input setup time	2.5	-	
$t_{h(HSYNC)}$ $t_{h(VSYNC)}$	DCMI_HSYNC/DCMI_VSYNC input hold time	0	-	

1. Guaranteed by characterization results.

Figure 68. DCMI timing diagram



MS32414V2

### 6.3.30 LCD-TFT controller (LTDC) characteristics

Unless otherwise specified, the parameters given in [Table 108](#) for LCD-TFT are derived from tests performed under the ambient temperature, f<sub>HCLK</sub> frequency and V<sub>DD</sub> supply voltage summarized in [Table 16](#), with the following configuration:

- LCD\_CLK polarity: high
- LCD\_DE polarity : low
- LCD\_VSYNC and LCD\_HSYNC polarity: high
- Pixel formats: 24 bits

Table 108. LTDC characteristics <sup>(1)</sup>

Symbol	Parameter	Min	Max	Unit
f <sub>CLK</sub>	LTDC clock output frequency	-	45	MHz
D <sub>CLK</sub>	LTDC clock output duty cycle	45	55	%
t <sub>w</sub> (CLKH) t <sub>w</sub> (CLKL)	Clock High time, low time	tw(CLK)/2 - 0.5	tw(CLK)/2+0.5	ns
t <sub>v</sub> (DATA)	Data output valid time	-	6	
t <sub>h</sub> (DATA)	Data output hold time	2	-	
t <sub>v</sub> (HSYNC)	HSYNC/VSYNC/DE output valid time	-	3	
t <sub>v</sub> (VSYNC)				
t <sub>v</sub> (DE)				
t <sub>h</sub> (HSYNC)	HSYNC/VSYNC/DE output hold time	0.5	-	
t <sub>h</sub> (VSYNC)				
t <sub>h</sub> (DE)				

1. Guaranteed by characterization results.

Figure 69. LCD-TFT horizontal timing diagram

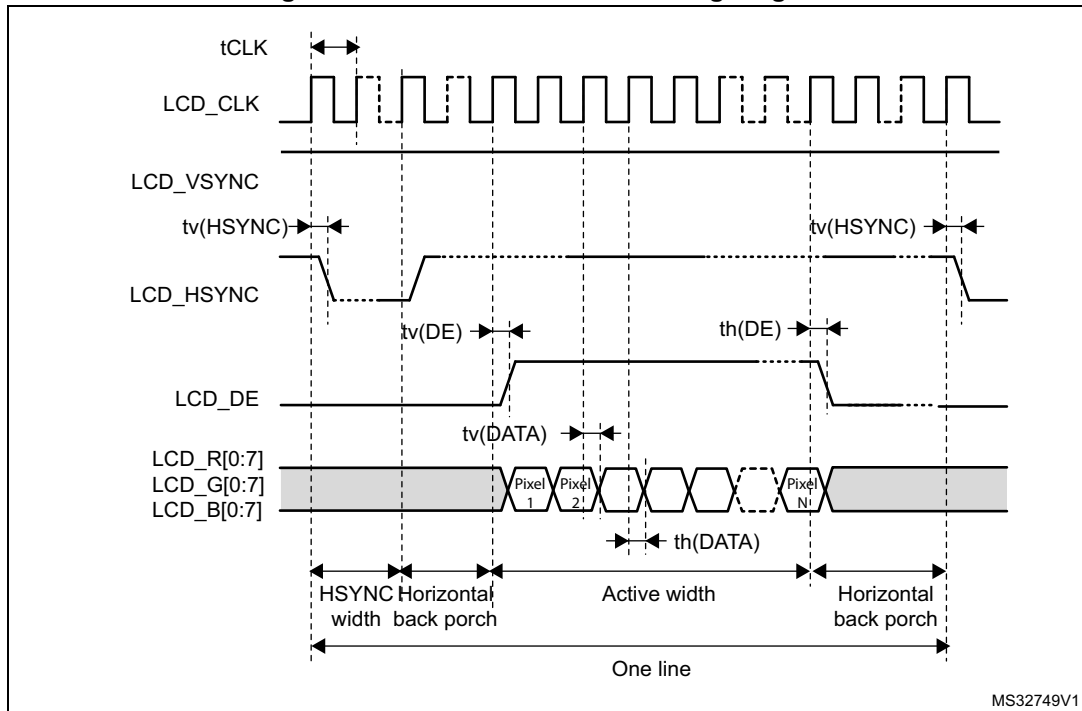
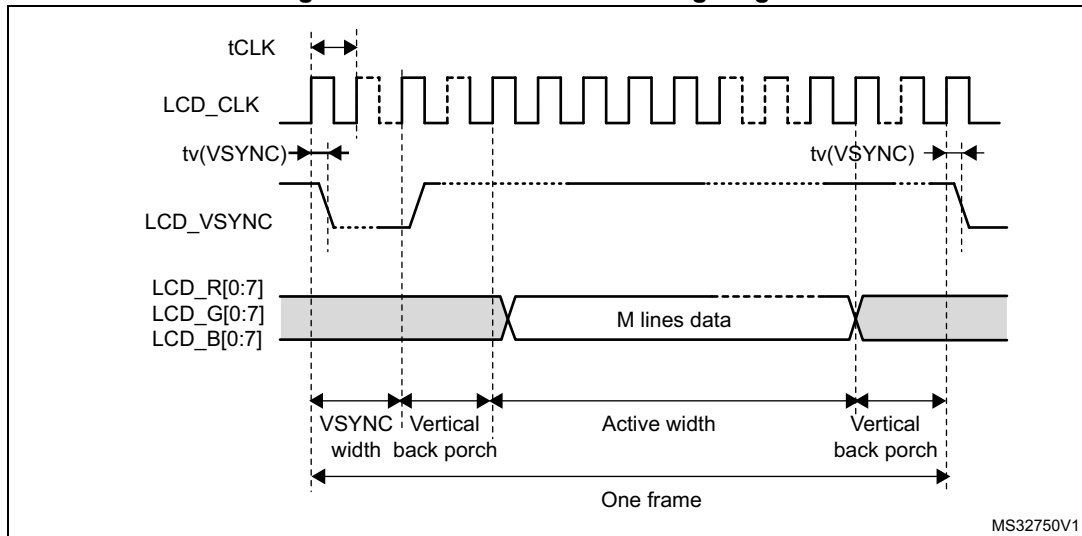


Figure 70. LCD-TFT vertical timing diagram



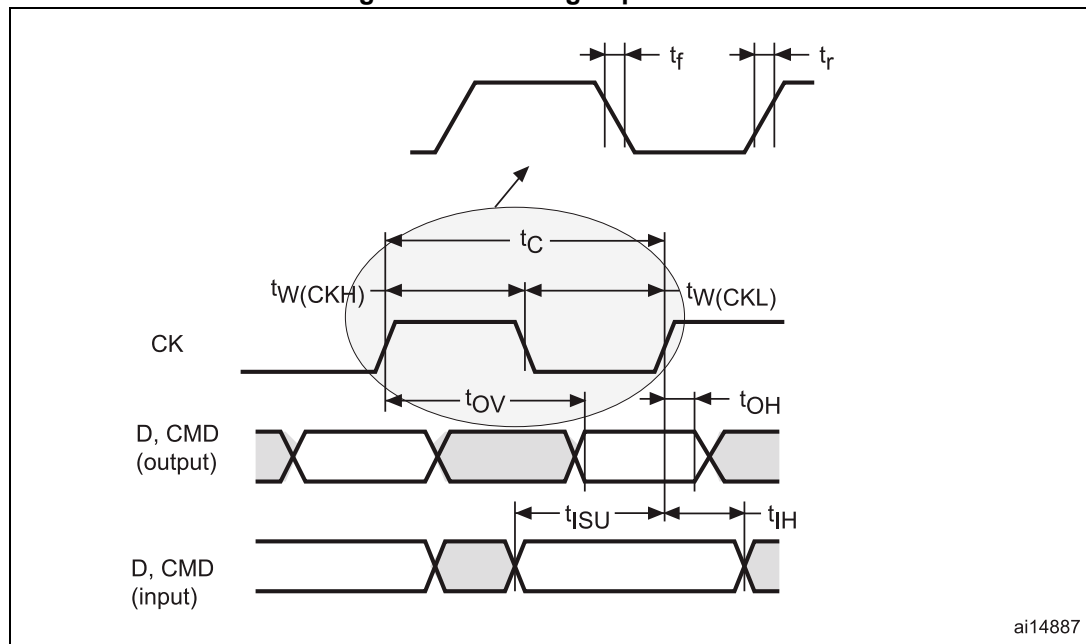
### 6.3.31 SD/SDIO MMC card host interface (SDMMC) characteristics

Unless otherwise specified, the parameters given in [Table 109](#) for the SDIO/MMC interface are derived from tests performed under the ambient temperature,  $f_{PCLK2}$  frequency and  $V_{DD}$  supply voltage conditions summarized in [Table 16](#), with the following configuration:

- Output speed is set to  $OSPEEDRy[1:0] = 11$
- Capacitive load  $C = 30\text{ pF}$
- Measurement points are done at CMOS levels:  $0.5V_{DD}$

Refer to [Section 6.3.17: I/O port characteristics](#) for more details on the input/output characteristics.

**Figure 71. SDIO high-speed mode**



**Figure 72. SD default mode**

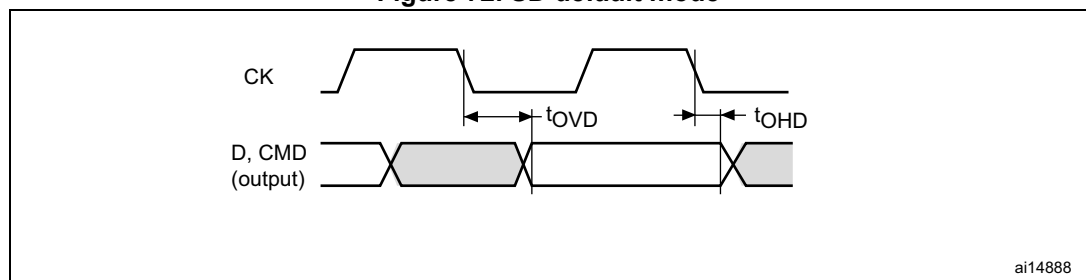


Table 109. Dynamic characteristics: SD / MMC characteristics,  $V_{DD}=2.7V$  to  $3.6V^{(1)}$ 

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$f_{PP}$	Clock frequency in data transfer mode	-	0	-	50	MHz
-	SDMMC_CK/fPCLK2 frequency ratio	-	-	-	8/3	-
$t_{W(CKL)}$	Clock low time	fpp =50 MHz	9.5	10.5	-	ns
$t_{W(CKH)}$	Clock high time	fpp =50 MHz	8.5	9.5	-	
<b>CMD, D inputs (referenced to CK) in MMC and SD HS mode</b>						
$t_{ISU}$	Input setup time HS	fpp =50 MHz	2.5	-	-	ns
$t_{IH}$	Input hold time HS	fpp =50 MHz	3	-	-	
<b>CMD, D outputs (referenced to CK) in MMC and SD HS mode</b>						
$t_{OV}$	Output valid time HS	fpp =50 MHz	-	11.5	12	ns
$t_{OH}$	Output hold time HS	fpp =50 MHz	10.5	-	-	
<b>CMD, D inputs (referenced to CK) in SD default mode</b>						
$t_{ISUD}$	Input setup time SD	fpp =25 MHz	2	-	-	ns
$t_{IHD}$	Input hold time SD	fpp =25 MHz	4	-	-	
<b>CMD, D outputs (referenced to CK) in SD default mode</b>						
$t_{OVD}$	Output valid default time SD	fpp =25 MHz	-	1.5	2	ns
$t_{OHD}$	Output hold default time SD	fpp =25 MHz	0.5	-	-	

1. Guaranteed by characterization results,.

Table 110. Dynamic characteristics: eMMC characteristics,  $V_{DD}=1.71V$  to  $1.9V^{(1)(2)}$ 

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$f_{PP}$	Clock frequency in data transfer mode	-	0	-	50	MHz
-	SDMMC_CK/fPCLK2 frequency ratio	-	-	-	8/3	-
$t_{W(CKL)}$	Clock low time	fpp =50 MHz	9.5	10.5	-	ns
$t_{W(CKH)}$	Clock high time	fpp =50 MHz	8.5	9.5	-	
<b>CMD, D inputs (referenced to CK) in eMMC mode</b>						
$t_{ISU}$	Input setup time HS	fpp =50 MHz	0.5	-	-	ns
$t_{IH}$	Input hold time HS	fpp =50 MHz	3.5	-	-	
<b>CMD, D outputs (referenced to CK) in eMMC mode</b>						
$t_{OV}$	Output valid time HS	fpp =50 MHz	-	12	12.5	ns
$t_{OH}$	Output hold time HS	fpp =50 MHz	11	-	-	

1. Guaranteed by characterization results.

2. Cload = 20 pF.

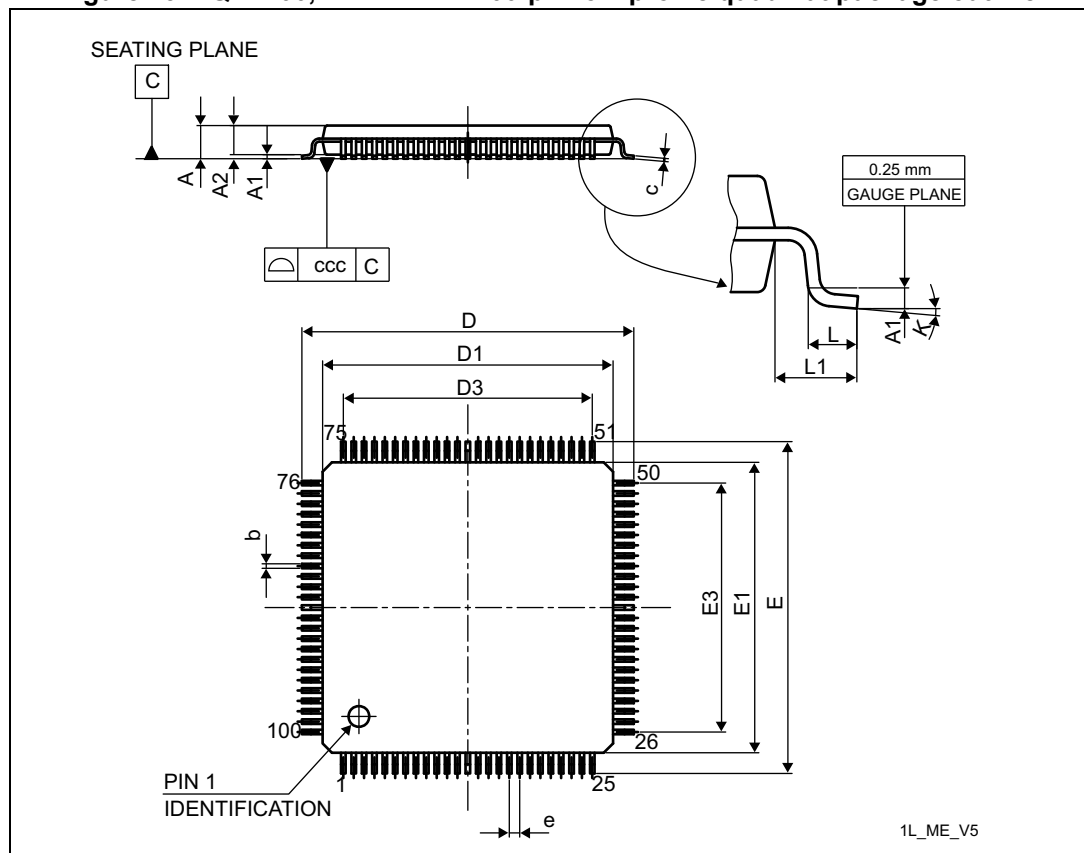


## 7 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

### 7.1 LQFP100, 14 x 14 mm low-profile quad flat package information

Figure 73. LQFP100, 14 x 14 mm 100-pin low-profile quad flat package outline



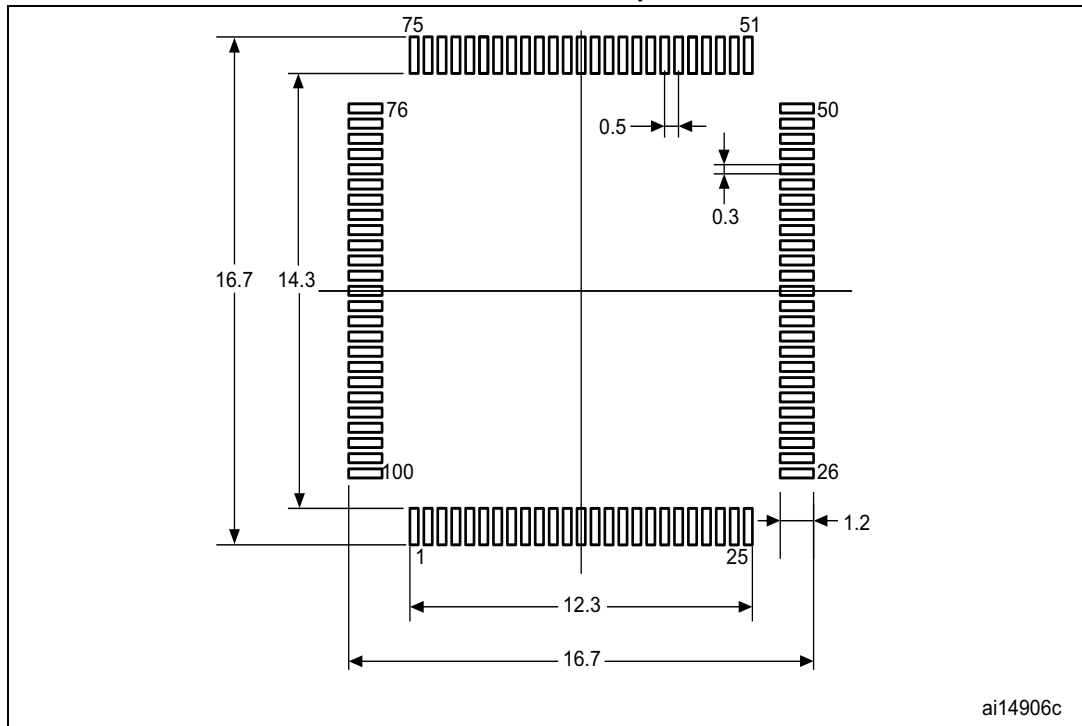
1. Drawing is not to scale.

Table 111. LQPF100, 14 x 14 mm 100-pin low-profile quad flat package mechanical data

Symbol	millimeters			inches <sup>(1)</sup>		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	15.800	16.000	16.200	0.6220	0.6299	0.6378
D1	13.800	14.000	14.200	0.5433	0.5512	0.5591
D3	-	12.000	-	-	0.4724	-
E	15.800	16.000	16.200	0.6220	0.6299	0.6378
E1	13.800	14.000	14.200	0.5433	0.5512	0.5591
E3	-	12.000	-	-	0.4724	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	3.5°	7°	0°	3.5°	7°
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

**Figure 74. LQFP100, 14 x 14 mm, 100-pin low-profile quad flat package recommended footprint**



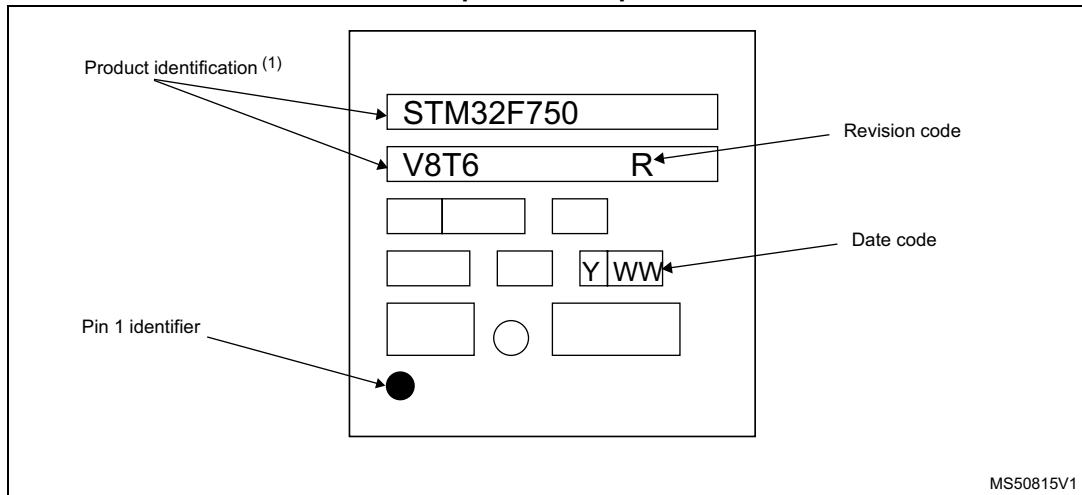
1. Dimensions are expressed in millimeters.

**LQFP100 device marking**

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

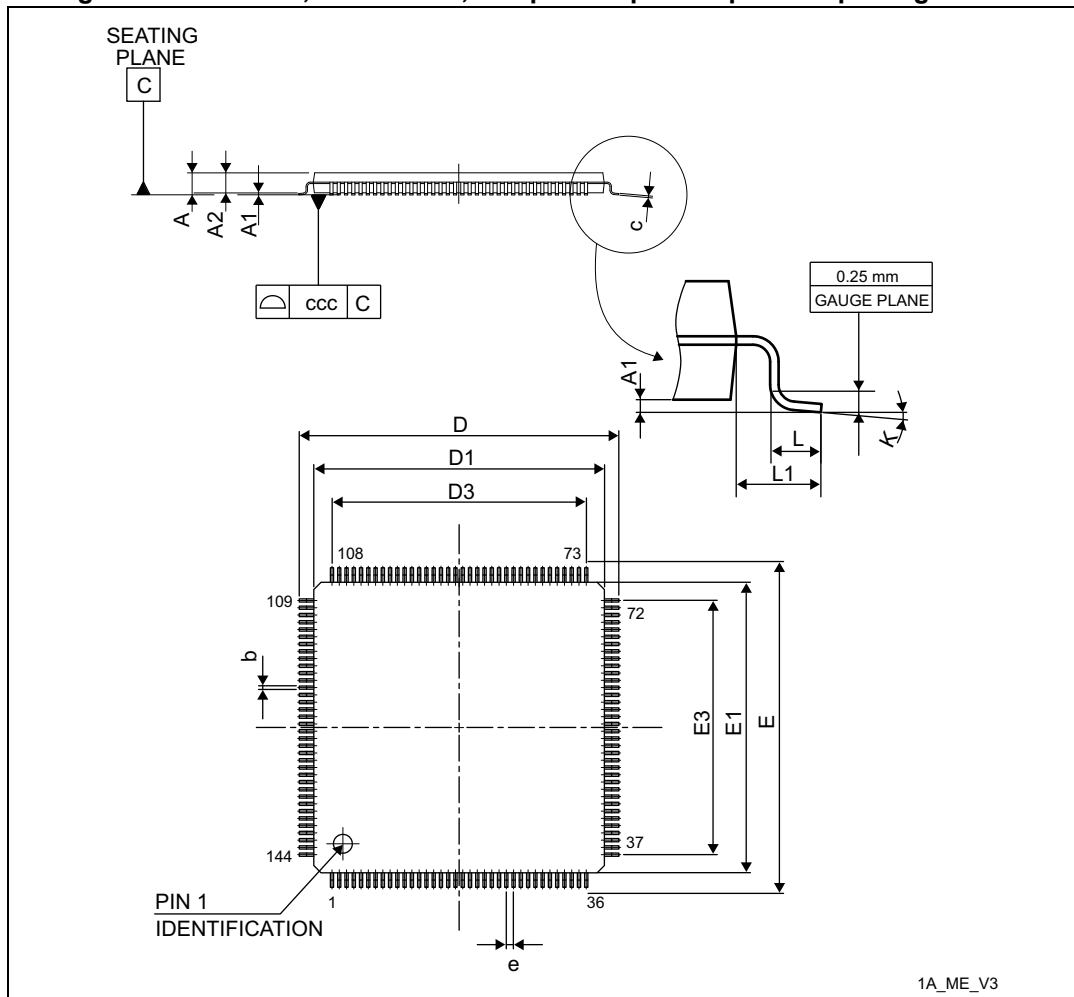
**Figure 75. LQFP100, 14 x 14 mm, 100-pin low-profile quad flat package top view example**



1. Parts marked as ES or E or accompanied by an engineering sample notification letter are not yet qualified and therefore not approved for use in production. ST is not responsible for any consequences resulting from such use. In no event will ST be liable for the customer using any of these engineering samples in production. ST's Quality department must be contacted prior to any decision to use these engineering samples to run a qualification activity.

## 7.2 LQFP144, 20 x 20 mm low-profile quad flat package information

Figure 76. LQFP144, 20 x 20 mm, 144-pin low-profile quad flat package outline



1. Drawing is not to scale.

Table 112. LQFP144, 20 x 20 mm, 144-pin low-profile quad flat package mechanical data

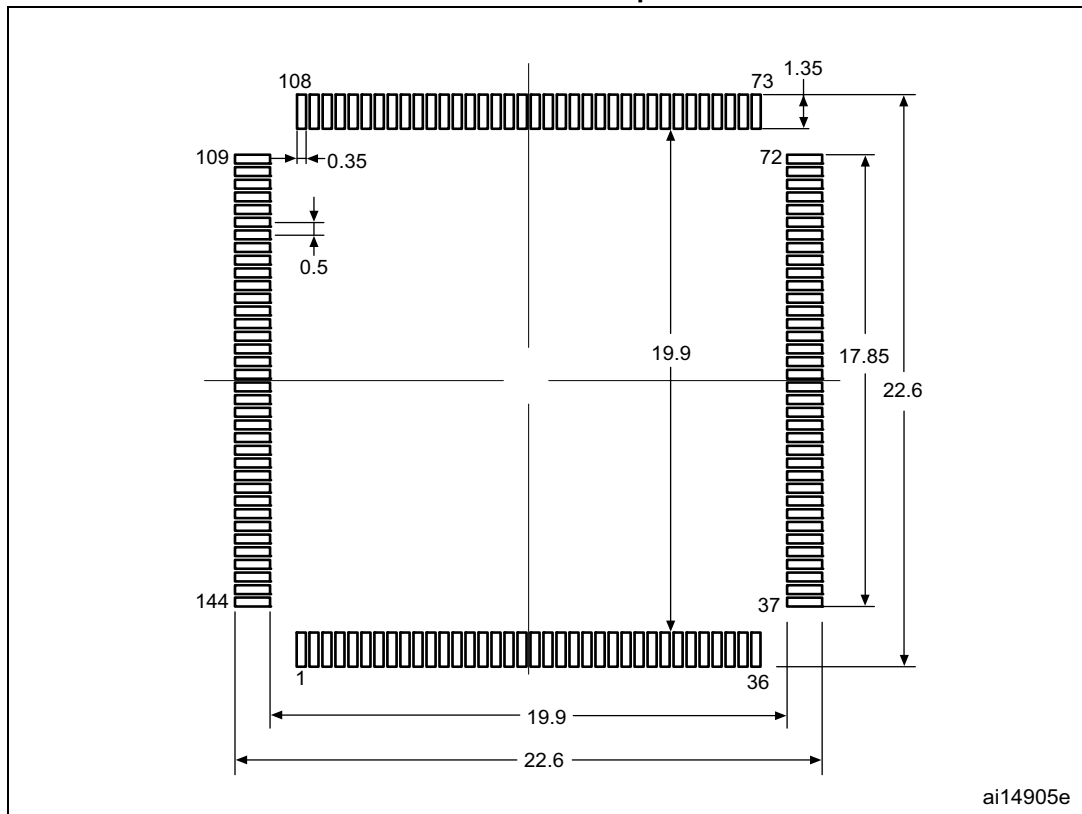
Symbol	millimeters			inches <sup>(1)</sup>		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	21.800	22.000	22.200	0.8583	0.8661	0.874

**Table 112. LQFP144, 20 x 20 mm, 144-pin low-profile quad flat package mechanical data (continued)**

Symbol	millimeters			inches <sup>(1)</sup>		
	Min	Typ	Max	Min	Typ	Max
D1	19.800	20.000	20.200	0.7795	0.7874	0.7953
D3	-	17.500	-	-	0.689	-
E	21.800	22.000	22.200	0.8583	0.8661	0.8740
E1	19.800	20.000	20.200	0.7795	0.7874	0.7953
E3	-	17.500	-	-	0.6890	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	3.5°	7°	0°	3.5°	7°
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

**Figure 77. LQFP144, 20 x 20 mm, 144-pin low-profile quad flat package recommended footprint**



ai14905e

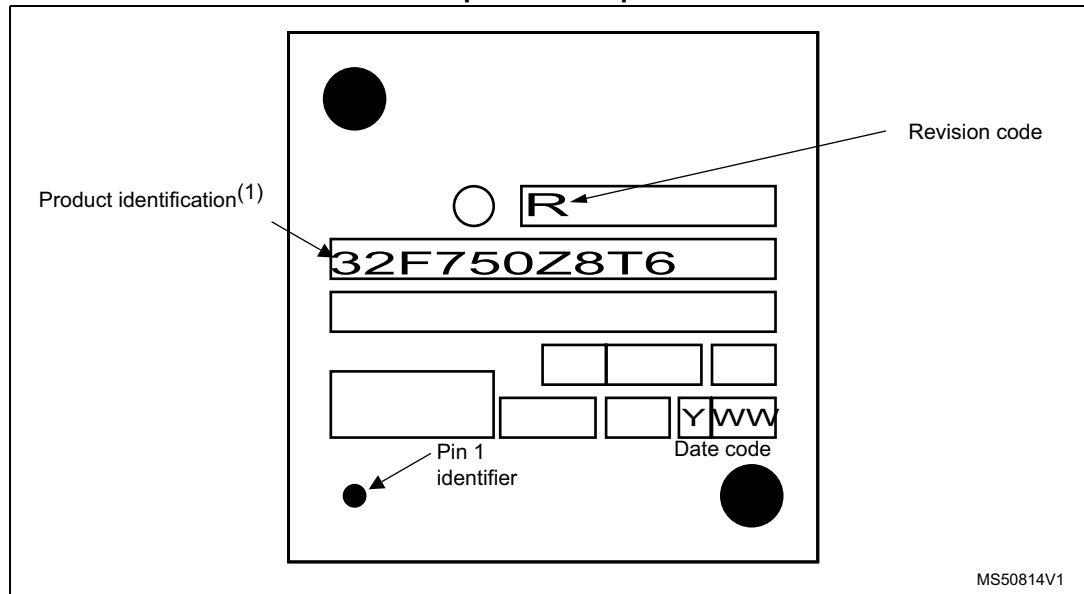
1. Dimensions are expressed in millimeters.

**LQFP144 device marking**

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

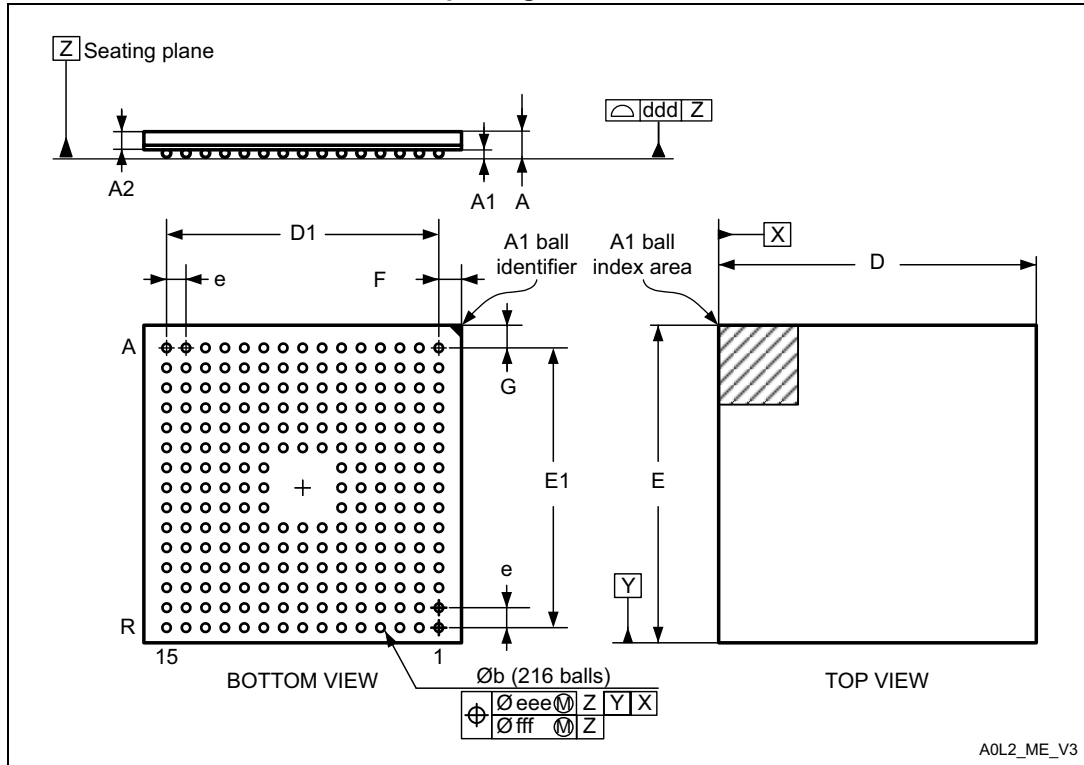
**Figure 78. LQFP144, 20 x 20mm, 144-pin low-profile quad flat package top view example**



1. Parts marked as ES or E or accompanied by an engineering sample notification letter are not yet qualified and therefore not approved for use in production. ST is not responsible for any consequences resulting from such use. In no event will ST be liable for the customer using any of these engineering samples in production. ST's Quality department must be contacted prior to any decision to use these engineering samples to run a qualification activity.

### 7.3 TFBGA216, 13 × 13 × 0.8 mm thin fine-pitch ball grid array package information

Figure 79. TFBGA216, 13 × 13 × 0.8 mm thin fine-pitch ball grid array package outline



1. Drawing is not to scale.

Table 113. TFBGA216, 13 × 13 × 0.8 mm thin fine-pitch ball grid array package mechanical data

Symbol	millimeters			inches <sup>(1)</sup>		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.100	-	-	0.0433
A1	0.150	-	-	0.0059	-	-
A2	-	0.760	-	-	0.0299	-
b	0.350	0.400	0.450	0.0138	0.0157	0.0177
D	12.850	13.000	13.150	0.5118	0.5118	0.5177
D1	-	11.200	-	-	0.4409	-
E	12.850	13.000	13.150	0.5118	0.5118	0.5177
E1	-	11.200	-	-	0.4409	-
e	-	0.800	-	-	0.0315	-
F	-	0.900	-	-	0.0354	-

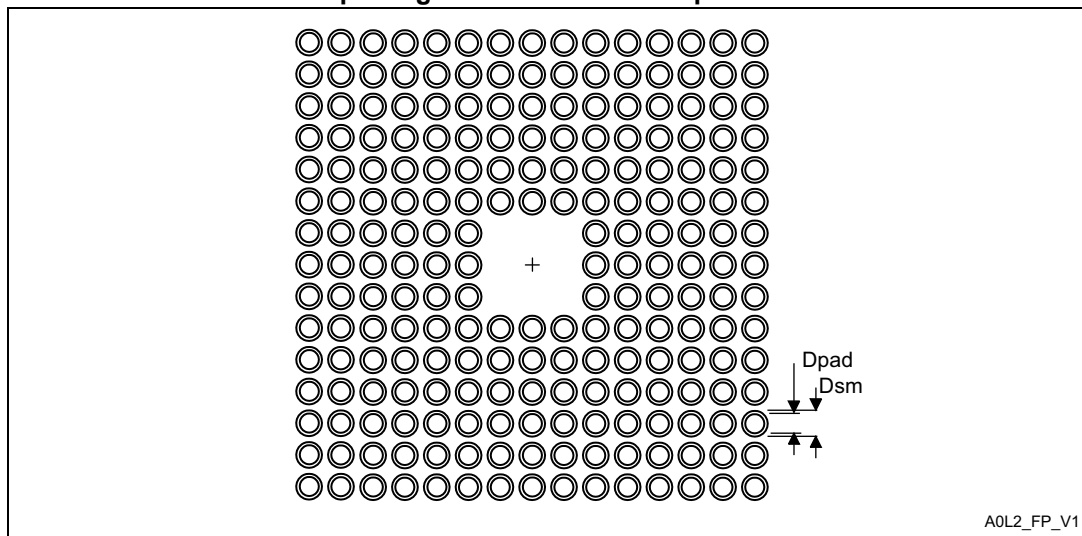


**Table 113. TFBGA216, 13 × 13 × 0.8 mm thin fine-pitch ball grid array package mechanical data (continued)**

Symbol	millimeters			inches <sup>(1)</sup>		
	Min	Typ	Max	Min	Typ	Max
G	-	0.900	-	-	0.0354	-
ddd	-	-	0.100	-	-	0.0039
eee	-	-	0.150	-	-	0.0059
fff	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

**Figure 80. TFBGA216, 13 x 13 x 0.8 mm thin fine-pitch ball grid array package recommended footprint**



**Table 114. TFBGA216 recommended PCB design rules (0.8 mm pitch BGA)**

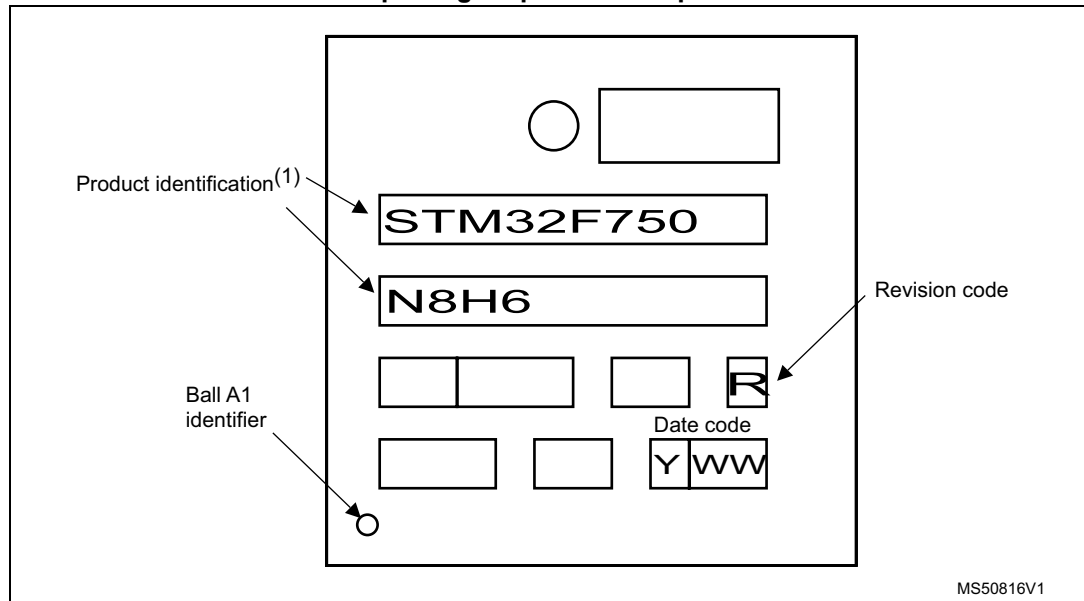
Dimension	Recommended values
Pitch	0.8
Dpad	0.400 mm
Dsm	0.470 mm typ. (depends on the soldermask registration tolerance)
Stencil opening	0.400 mm
Stencil thickness	Between 0.100 mm and 0.125 mm
Pad trace width	0.120 mm

### TFBGA216 device marking

The following figure gives an example of topside marking orientation versus ball A1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

**Figure 81. TFBGA216, 13 × 13 × 0.8 mm thin fine-pitch ball grid array package top view example**



1. Parts marked as ES or E or accompanied by an engineering sample notification letter are not yet qualified and therefore not approved for use in production. ST is not responsible for any consequences resulting from such use. In no event will ST be liable for the customer using any of these engineering samples in production. ST's Quality department must be contacted prior to any decision to use these engineering samples to run a qualification activity.

## 7.4 Thermal characteristics

The maximum chip-junction temperature,  $T_J \text{ max}$ , in degrees Celsius, may be calculated using the following equation:

$$T_J \text{ max} = T_A \text{ max} + (P_D \text{ max} \times \Theta_{JA})$$

Where:

- $T_A \text{ max}$  is the maximum ambient temperature in °C,
- $\Theta_{JA}$  is the package junction-to-ambient thermal resistance, in °C/W,
- $P_D \text{ max}$  is the sum of  $P_{INT} \text{ max}$  and  $P_{IO} \text{ max}$  ( $P_D \text{ max} = P_{INT} \text{ max} + P_{IO} \text{ max}$ ),
- $P_{INT} \text{ max}$  is the product of  $I_{DD}$  and  $V_{DD}$ , expressed in Watts. This is the maximum chip internal power.

$P_{IO} \text{ max}$  represents the maximum power dissipation on output pins where:

$$P_{IO} \text{ max} = \Sigma (V_{OL} \times I_{OL}) + \Sigma ((V_{DD} - V_{OH}) \times I_{OH}),$$

taking into account the actual  $V_{OL} / I_{OL}$  and  $V_{OH} / I_{OH}$  of the I/Os at low and high level in the application.

**Table 115. Package thermal characteristics**

Symbol	Parameter	Value	Unit
$\Theta_{JA}$	Thermal resistance junction-ambient LQFP100 - 14 × 14 mm / 0.5 mm pitch	43	°C/W
	Thermal resistance junction-ambient LQFP144 - 20 × 20 mm / 0.5 mm pitch	40	
	Thermal resistance junction-ambient TFBGA216 - 13 × 13 mm / 0.8 mm pitch	29	

### Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from [www.jedec.org](http://www.jedec.org).

# 8 Ordering information

**Table 116. Ordering information scheme**

Example:	STM32	F	750	V	8	T	6	xxx
<b>Device family</b>								
STM32 = Arm-based 32-bit microcontroller								
<b>Product type</b>								
F = general-purpose								
<b>Device subfamily</b>								
750= STM32F750x8, USB OTG FS/HS, camera interface, Ethernet, LCD-TFT, cryptographic acceleration								
<b>Pin count</b>								
V = 100 pins								
Z = 144 pins								
N = 216 pins								
<b>Flash memory size</b>								
8 = 64 Kbytes of Flash memory								
<b>Package</b>								
T = LQFP								
H = TFBGA								
<b>Temperature range</b>								
6 = Industrial temperature range, -40 to 85 °C.								
7 = Industrial temperature range, -40 to 105 °C.								
<b>Options</b>								
xxx = programmed parts								
TR = tape and reel								

For a list of available options (speed, package, etc.) or for further information on any aspect of this device, please contact your nearest ST sales office.

## Appendix A Recommendations when using internal reset OFF

When the internal reset is OFF, the following integrated features are no longer supported:

- The integrated power-on reset (POR) / power-down reset (PDR) circuitry is disabled.
- The brownout reset (BOR) circuitry must be disabled.
- The embedded programmable voltage detector (PVD) is disabled.
- V<sub>BAT</sub> functionality is no more available and VBAT pin should be connected to V<sub>DD</sub>.
- The over-drive mode is not supported.

### A.1 Operating conditions

Table 117. Limitations depending on the operating power supply range

Operating power supply range	ADC operation	Maximum Flash memory access frequency with no wait states (f <sub>Flashmax</sub> )	Maximum Flash memory access frequency with wait states <sup>(1)(2)</sup>	I/O operation	Possible Flash memory operations
V <sub>DD</sub> = 1.7 to 2.1 V <sup>(3)</sup>	Conversion time up to 1.2 Msps	20 MHz	180 MHz with 8 wait states and over-drive OFF	– No I/O compensation	8-bit erase and program operations only

1. Applicable only when the code is executed from Flash memory. When the code is executed from RAM, no wait state is required.
2. Thanks to the ART accelerator on ITCM interface and L1-cache on AXI interface, the number of wait states given here does not impact the execution speed from the Flash memory since the ART accelerator or L1-cache allows to achieve a performance equivalent to 0-wait state program execution.
3. V<sub>DD</sub>/V<sub>DDA</sub> minimum value of 1.7 V, with the use of an external power supply supervisor (refer to [Section 3.17.1: Internal reset ON](#)).

## Revision history

**Table 118. Document revision history**

Date	Revision	Changes
27-Jun-2018	1	Initial release.

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[CY9AF156NPMC-G-JNE2](#) [MB9BF104NAPMC-G-JNE1](#) [CY8C4724FNI-S402T](#) [ADUCM410BCBZ-RL7](#) [ADUCM410BBCZ-RL7](#)

[GD32f303RGT6](#) [NHS3152UK/A1Z](#) [MK26FN2M0CAC18R](#) [EFM32TG230F32-D-QFN64](#) [EFM32TG232F32-D-QFP64](#) [EFM32TG825F32-D-](#)

[BGA48](#) [MB9AFB44NBBGL-GE1](#) [MB9BF304RBPMC-G-JNE2](#) [MB9BF416RPMC-G-JNE2](#) [MB9AF155MABGL-GE1](#) [MB9BF306RBPMC-](#)

[G-JNE2](#) [MB9BF618TBGL-GE1](#) [MK20DX64VFT5](#) [MK50DX128CMC7](#) [MK51DN256CMD10](#) [MK51DX128CMC7](#) [MK53DX256CMD10](#)

[MKL25Z32VFT4](#) [MKL25Z64VFT4](#) [LPC1754FBD80](#) [STM32F030K6T6TR](#) [STM32L073VBT6](#) [XMC4108Q48K64BAXUMA1](#)

[AT91M42800A-33AU](#) [AT91SAM7L64-CU](#) [ATSAM3N0AA-MU](#) [ATSAM3N0CA-CU](#) [ATSAM3SD8BA-MU](#) [ATSAM4LC4BA-MU](#)

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